# life.augmented

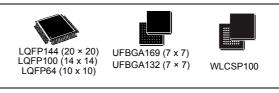
### STM32L4A6xG

# Ultra-low-power Arm<sup>®</sup> Cortex<sup>®</sup>-M4 32-bit MCU+FPU, 100DMIPS, 1MB Flash, 320KB SRAM, USB OTG FS, audio, AES+HASH, ext. SMPS

Datasheet - production data

### **Features**

- Ultra-low-power with FlexPowerControl
  - 1.71 V to 3.6 V power supply
  - -40 °C to 85/125 °C temperature range
  - 320 nA in V<sub>BAT</sub> mode: supply for RTC and 32x32-bit backup registers
  - 25 nA Shutdown mode (5 wakeup pins)
  - 108 nA Standby mode (5 wakeup pins)
  - 426 nA Standby mode with RTC
  - 2.57  $\mu A$  Stop 2 mode, 2.86  $\mu A$  Stop 2 with RTC
  - 91 μA/MHz run mode (LDO Mode)
  - 37 μA/MHz run mode (@3.3 V SMPS Mode)
  - Batch acquisition mode (BAM)
  - 5 µs wakeup from Stop mode
  - Brown out reset (BOR) in all modes except shutdown
  - Interconnect matrix
- Core: Arm<sup>®</sup> 32-bit Cortex<sup>®</sup>-M4 CPU with FPU, Adaptive real-time accelerator (ART Accelerator<sup>™</sup>) allowing 0-wait-state execution from Flash memory, frequency up to 80 MHz, MPU, 100 DMIPS and DSP instructions
- · Performance benchmark
  - 1.25 DMIPS/MHz (Drystone 2.1)
  - 273.55 Coremark<sup>®</sup> (3.42 Coremark/MHz @ 80 MHz)
- · Energy benchmark
  - 279 ULPMark™ CP score
  - 80.2 ULPMark™ PP score
- 16 x timers: 2 x 16-bit advanced motor-control, 2 x 32-bit and 5 x 16-bit general purpose, 2 x 16-bit basic, 2 x low-power 16-bit timers (available in Stop mode), 2 x watchdogs, SysTick timer
- RTC with HW calendar, alarms and calibration



- Up to 136 fast I/Os, most 5 V-tolerant, up to 14 I/Os with independent supply down to 1.08 V
- Dedicated Chrom-ART Accelerator™ for enhanced graphic content creation (DMA2D)
- 8- to 14-bit camera interface up to 32 MHz (black&white) or 10 MHz (color)
- Encryption hardware accelerator: AES (128/256-bit key), HASH (SHA-256)
- Memories
  - 1 MB Flash, 2 banks read-while-write, proprietary code readout protection
  - 320 KB of SRAM including 64 KB with hardware parity check
  - External memory interface for static memories supporting SRAM, PSRAM, NOR and NAND memories
  - Dual-flash Quad SPI memory interface
- Clock Sources
  - 4 to 48 MHz crystal oscillator
  - 32 kHz crystal oscillator for RTC (LSE)
  - Internal 16 MHz factory-trimmed RC (±1%)
  - Internal low-power 32 kHz RC (±5%)
  - Internal multispeed 100 kHz to 48 MHz oscillator, auto-trimmed by LSE (better than ±0.25% accuracy)
  - Internal 48 MHz with clock recovery
  - 3 PLLs for system clock, USB, audio, ADC
- LCD 8 × 40 or 4 × 44 with step-up converter
- Up to 24 capacitive sensing channels: support touchkey, linear and rotary touch sensors
- · 4 x digital filters for sigma delta modulator

- Rich analog peripherals (independent supply)
  - 3 × 12-bit ADC 5 Msps, up to 16-bit with hardware oversampling, 200 μA/Msps
  - 2 x 12-bit DAC output channels, low-power sample and hold
  - 2 x operational amplifiers with built-in PGA
  - 2 x ultra-low-power comparators
- 20 x communication interfaces
  - USB OTG 2.0 full-speed, LPM and BCD
  - 2 x SAIs (serial audio interface)
  - 4 x I2C FM+(1 Mbit/s), SMBus/PMBus
  - 5 x U(S)ARTs (ISO 7816, LIN, IrDA, modem)

- 1 x LPUART
- 3 x SPIs (4 x SPIs with the Quad SPI)
- 2 x CAN (2.0B Active) and SDMMC
- SWPMI single wire protocol master I/F
- IRTIM (Infrared interface)
- 14-channel DMA controller
- True random number generator
- CRC calculation unit, 96-bit unique ID
- Development support: serial wire debug (SWD), JTAG, Embedded Trace Macrocell™

Table 1. Device summary

Reference	Part numbers
STM32L4A6xG	STM32L4A6AG, STM32L4A6QG, STM32L4A6RG, STM32L4A6VG, STM32L4A6ZG

STM32L4A6xG Contents

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STM32L4A6xG Introduction

### 1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L4A6xG microcontrollers.

This document should be read in conjunction with the STM32L4x6 reference manual (RM0351). The reference manual is available from the STMicroelectronics website <a href="https://www.st.com">www.st.com</a>.

For information on the Arm<sup>®(a)</sup> Cortex<sup>®</sup>-M4 core, please refer to the Cortex<sup>®</sup>-M4 Technical Reference Manual, available from the www.arm.com website.





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Description STM32L4A6xG

### 2 Description

The STM32L4A6xG devices are the ultra-low-power microcontrollers based on the high-performance Arm<sup>®</sup> Cortex<sup>®</sup>-M4 32-bit RISC core operating at a frequency of up to 80 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all Arm<sup>®</sup> single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32L4A6xG devices embed high-speed memories (1 Mbyte of Flash memory, 320 Kbyte of SRAM), a flexible external memory controller (FSMC) for static memories (for devices with packages of 100 pins and more), a Quad SPI flash memories interface (available on all packages) and an extensive range of enhanced I/Os and peripherals connected to two APB buses, two AHB buses and a 32-bit multi-AHB bus matrix.

The STM32L4A6xG devices embed several protection mechanisms for embedded Flash memory and SRAM: readout protection, write protection, proprietary code readout protection and Firewall.

The devices offer up to three fast 12-bit ADCs (5 Msps), two comparators, two operational amplifiers, two DAC channels, an internal voltage reference buffer, a low-power RTC, two general-purpose 32-bit timer, two 16-bit PWM timers dedicated to motor control, seven general-purpose 16-bit timers, and two 16-bit low-power timers. The devices support four digital filters for external sigma delta modulators (DFSDM).

In addition, up to 24 capacitive sensing channels are available. The devices also embed an integrated LCD driver 8x40 or 4x44, with internal step-up converter.

They also feature standard and advanced communication interfaces.

- Four I2Cs
- Three SPIs
- Three USARTs, two UARTs and one Low-Power UART.
- Two SAIs (Serial Audio Interfaces)
- One SDMMC
- Two CAN
- One USB OTG full-speed
- One SWPMI (Single Wire Protocol Master Interface)
- Camera interface
- DMA2D controller

The STM32L4A6xG devices embed AES and HASH hardware accelerator.

The STM32L4A6xG operates in the -40 to +85 °C (+105 °C junction), -40 to +125 °C (+130 °C junction) temperature ranges from a 1.71 to 3.6 V  $V_{DD}$  power supply when using internal LDO regulator and a 1.05 to 1.32V  $V_{DD12}$  power supply when using external SMPS supply. A comprehensive set of power-saving modes allows the design of low-power applications.

Some independent power supplies are supported: analog independent supply input for ADC, DAC, OPAMPs and comparators, 3.3 V dedicated supply input for USB and up to 14 I/Os can be supplied independently down to 1.08V. A VBAT input allows to backup the RTC



STM32L4A6xG Description

and backup registers. Dedicated  $V_{\text{DD12}}$  power supplies can be used to bypass the internal LDO regulator when connected to an external SMPS.

The STM32L4A6xG family offers six packages from 64-pin to 169-pin packages.

Table 2. STM32L4A6xG family device features and peripheral counts

Peripheral		STM32L4A6AG				STM32L4A6RG			
Flash memory				1 MB					
SRAM				320 KB					
External memory controller for static memories		Yes	Yes	Yes	Yes <sup>(1)</sup>	No			
Quad SPI				Yes					
	Advanced control		2 (16-bit)						
	General purpose			5 (16-bit) 2 (32-bit)					
	Basic		2 (16-bit)						
Timers	Low power			2 (16-bit)					
	SysTick timer			1					
	Watchdog timers (independent window)			2					
	SPI			3					
	I <sup>2</sup> C			4					
	USART UART LPUART			3 2 1					
Comm. interfaces	SAI			2					
	CAN			2					
	USB OTG FS			Yes					
	SDMMC			Yes					
	SWPMI	Yes							
Digital filters for sigma- delta modulators		Yes (4 filters)							
Number of	channels	8							
RTC		Yes							
Tamper pir	าร	3							
Camera in	terface		Y	es		Yes <sup>(2)</sup>			
Chrom-ART Accelerator™				Yes					

Description STM32L4A6xG

Table 2. STM32L4A6xG family device features and peripheral counts (continued)

Peripheral	STM32L4A6AG	STM32L4A6ZG	STM32L4A6QG	STM32L4A6VG	STM32L4A6RG
LCD			Yes		
COM x SEG			8x40 or 4x44		
Random generator			Yes		
AES + HASH			Yes		
GPIOs <sup>(3)</sup>	136	115	110	83	52
Wakeup pins	5	5	5	5	4
Nb of I/Os down to 1.08 V	14	14	14	0	0
Capacitive sensing Number of channels	24	24	24	21	21
12-bit ADCs	3	3	3	3	3
Number of channels	24	24	19	16	16
12-bit DAC channels			2		
Internal voltage reference buffer			Yes		
Analog comparator			2		
Operational amplifiers			2		
Max. CPU frequency			80 MHz		
Operating voltage (V <sub>DD</sub> )			1.71 to 3.6 V		
Operating voltage (V <sub>DD12</sub> )			1.05 to 1.32 V		
Operating temperature	Am	. •	emperature: -40 to ature: -40 to 105 °	85 °C / -40 to 125 C / -40 to 130 °C	s °C
Packages	UFBGA169	LQFP144	UFBGA132	LQFP100 WLCSP100	LQFP64

For the LQFP100 and WLCSP100 packages, only FMC Bank1 is available. Bank1 can only support a multiplexed NOR/PSRAM memory using the NE1 Chip Select.

<sup>2.</sup> Only up to 13 data bits.

<sup>3.</sup> In case external SMPS package type is used, 2 GPIO's are replaced by VDD12 pins to connect the SMPS power supplies hence reducing the number of available GPIO's by 2.

STM32L4A6xG Description

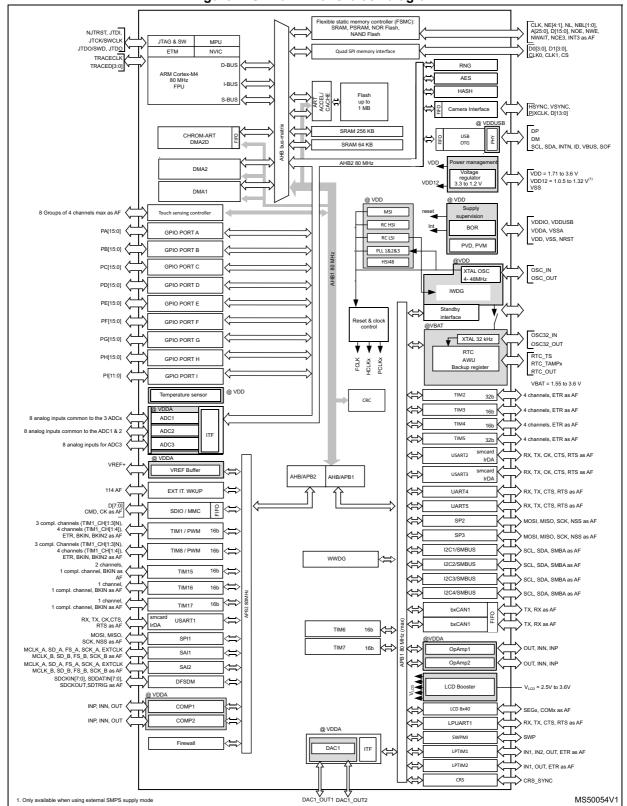


Figure 1. STM32L4A6xG block diagram

Note: AF: alternate function on I/O pins.



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### 3 Functional overview

### 3.1 Arm<sup>®</sup> Cortex<sup>®</sup>-M4 core with FPU

The Arm<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU processor is the latest generation of Arm<sup>®</sup> processors for embedded systems. It was developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced response to interrupts.

The Arm<sup>®</sup> Cortex<sup>®</sup>-M4 with FPU 32-bit RISC processor features exceptional codeefficiency, delivering the high-performance expected from an Arm<sup>®</sup> core in the memory size usually associated with 8- and 16-bit devices.

The processor supports a set of DSP instructions which allow efficient signal processing and complex algorithm execution.

Its single precision FPU speeds up software development by using metalanguage development tools, while avoiding saturation.

With its embedded Arm<sup>®</sup> core, the STM32L4A6xG family is compatible with all Arm<sup>®</sup> tools and software.

Figure 1 shows the general block diagram of the STM32L4A6xG family devices.

### 3.2 Adaptive real-time memory accelerator (ART Accelerator™)

The ART Accelerator $^{\rm TM}$  is a memory accelerator which is optimized for STM32 industry-standard Arm $^{\rm R}$  Cortex $^{\rm R}$ -M4 processors. It balances the inherent performance advantage of the Arm $^{\rm R}$  Cortex $^{\rm R}$ -M4 over Flash memory technologies, which normally requires the processor to wait for the Flash memory at higher frequencies.

To release the processor near 100 DMIPS performance at 80MHz, the accelerator implements an instruction prefetch queue and branch cache, which increases program execution speed from the 64-bit Flash memory. Based on CoreMark benchmark, the performance achieved thanks to the ART accelerator is equivalent to 0 wait state program execution from Flash memory at a CPU frequency up to 80 MHz.

### 3.3 Memory protection unit

The memory protection unit (MPU) is used to manage the CPU accesses to memory to prevent one task to accidentally corrupt the memory or resources used by any other active task. This memory area is organized into up to 8 protected areas that can in turn be divided up into 8 subareas. The protection area sizes are between 32 bytes and the whole 4 gigabytes of addressable memory.

The MPU is especially helpful for applications where some critical or certified code has to be protected against the misbehavior of other tasks. It is usually managed by an RTOS (real-time operating system). If a program accesses a memory location that is prohibited by the MPU, the RTOS can detect it and take action. In an RTOS environment, the kernel can dynamically update the MPU area setting, based on the process to be executed.

The MPU is optional and can be bypassed for applications that do not need it.

### 3.4 Embedded Flash memory

STM32L4A6xG devices feature 1 Mbyte of embedded Flash memory available for storing programs and data. The Flash memory is divided into two banks allowing read-while-write operations. This feature allows to perform a read operation from one bank while an erase or program operation is performed to the other bank. The dual bank boot is also supported. Each bank contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  - Level 0: no readout protection
  - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Area	Protection	U	ser executi	on	Debug, boot from RAM or boot from system memory (loader)					
	level	Read	Write	Erase	Read	Write	Erase			
Main	1	Yes	Yes	Yes	No	No	No			
memory	2	Yes	Yes	Yes	N/A	N/A	N/A			
System	1	Yes	No	No	Yes	No	No			
memory	2	Yes	No	No	N/A	N/A	N/A			
Option	1	Yes	Yes	Yes	Yes	Yes	Yes			
bytes	2	Yes	No	No	N/A	N/A	N/A			
Backup	1	Yes	Yes	N/A <sup>(1)</sup>	No	No	N/A <sup>(1)</sup>			
registers	2	Yes	Yes	N/A	N/A	N/A	N/A			
ODAMO	1	Yes	Yes	Yes <sup>(1)</sup>	No	No	No <sup>(1)</sup>			
SRAM2	2	Yes	Yes	Yes	N/A	N/A	N/A			

Table 3. Access status versus readout protection level and execution modes

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. One area per bank can be selected, with 64-bit granularity. An additional option bit (PCROP\_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.



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<sup>1.</sup> Erased when RDP change from Level 1 to Level 0.

The whole non-volatile memory embeds the error correction code (ECC) feature supporting:

- single error detection and correction
- double error detection.
- The address of the ECC fail can be read in the ECC register

### 3.5 Embedded SRAM

STM32L4A6xG devices feature 320 Kbyte of embedded SRAM. This SRAM is split into two blocks:

- 256 Kbyte mapped at address 0x2000 0000 (SRAM1)
- 64 Kbyte located at address 0x1000 0000 with hardware parity check (SRAM2).

This memory is also mapped at address 0x2004 0000, offering a contiguous address space with the SRAM1.

This block is accessed through the ICode/DCode buses for maximum performance.

These 64 Kbyte SRAM can also be retained in Standby mode.

The SRAM2 can be write-protected with 1 Kbyte granularity.

The memory can be accessed in read/write at CPU clock speed with 0 wait states.

### 3.6 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs and the DMA2D) and the slaves (Flash memory, RAM, FMC, QUADSPI, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high speed peripherals work simultaneously.

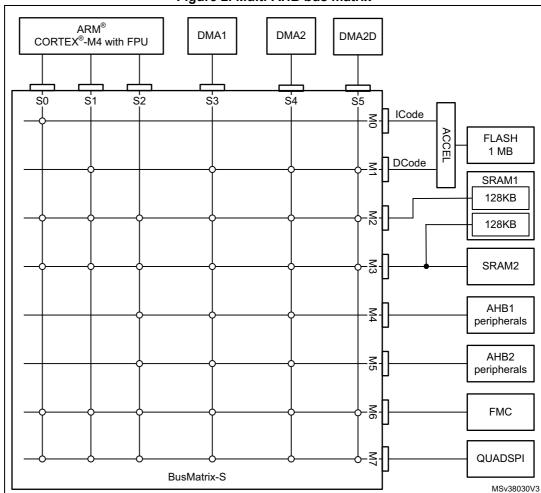


Figure 2. Multi-AHB bus matrix

### 3.7 Firewall

The device embeds a Firewall which protects code sensitive and secure data from any access performed by a code executed outside of the protected areas.

Each illegal access generates a reset which kills immediately the detected intrusion.

The Firewall main features are the following:

Three segments can be protected and defined thanks to the Firewall registers:

- Code segment (located in Flash or SRAM1 if defined as executable protected area)
- Non-volatile data segment (located in Flash)
- Volatile data segment (located in SRAM1)
- The start address and the length of each segments are configurable:
  - Code segment: up to 1024 Kbyte with granularity of 256 bytes
  - Non-volatile data segment: up to 1024 Kbyte with granularity of 256 bytes
  - Volatile data segment: up to 256 Kbyte of SRAM1 with a granularity of 64 bytes
- Specific mechanism implemented to open the Firewall to get access to the protected areas (call gate entry sequence)
- Volatile data segment can be shared or not with the non-protected code
- Volatile data segment can be executed or not depending on the Firewall configuration

The Flash readout protection must be set to level 2 in order to reach the expected level of protection.

### 3.8 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

BOOT0 value may come from the PH3-BOOT0 pin or from an option bit depending on the value of a user option bit to free the GPIO pad if needed.

A Flash empty check mechanism is implemented to force the boot from system flash if the first flash memory location is not programmed and if the boot selection is configured to boot from main flash.

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART, I2C, SPI, CAN or USB OTG FS in Device mode through DFU (device firmware upgrade).

### 3.9 Cyclic redundancy check calculation unit (CRC)

The CRC (cyclic redundancy check) calculation unit is used to get a CRC code using a configurable generator polynomial value and size.

Among other applications, CRC-based techniques are used to verify data transmission or storage integrity. In the scope of the EN/IEC 60335-1 standard, they offer a means of verifying the Flash memory integrity. The CRC calculation unit helps compute a signature of the software during runtime, to be compared with a reference signature generated at link-time and stored at a given memory location.

### 3.10 Power supply management

### 3.10.1 Power supply schemes

 V<sub>DD</sub> = 1.71 to 3.6 V: external power supply for I/Os (V<sub>DDIO1</sub>), the internal regulator and the system analog such as reset, power management and internal clocks. It is provided externally through VDD pins.

- V<sub>DD12</sub> = 1.05 to 1.32 V: external power supply bypassing internal regulator when connected to an external SMPS. It is provided externally through VDD12 pins and only available on packages with the external SMPS supply option. VDD12 does not require any external decoupling capacitance and cannot support any external load.
- V<sub>DDA</sub> = 1.62 V (ADCs/COMPs) / 1.8 (DAC/OPAMPs) to 3.6 V: external analog power supply for ADCs, DAC, OPAMPs, Comparators and Voltage reference buffer. The V<sub>DDA</sub> voltage level is independent from the V<sub>DD</sub> voltage.
- $V_{DDUSB}$  = 3.0 to 3.6 V: external independent power supply for USB transceivers. The  $V_{DDUSB}$  voltage level is independent from the  $V_{DD}$  voltage.
- V<sub>DDIO2</sub> = 1.08 to 3.6 V: external power supply for 14 I/Os (PG[15:2]). The V<sub>DDIO2</sub> voltage level is independent from the V<sub>DD</sub> voltage.
- V<sub>LCD</sub> = 2.5 to 3.6 V: the LCD controller can be powered either externally through VLCD pin, or internally from an internal voltage generated by the embedded step-up converter.
- V<sub>BAT</sub> = 1.55 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V<sub>DD</sub> is not present.

Note: When the functions supplied by  $V_{DDA}$ ,  $V_{DDUSB}$  or  $V_{DDIO2}$  are not used, these supplies should preferably be shorted to  $V_{DD}$ .

Note: If these supplies are tied to ground, the I/Os supplied by these power supplies are not 5 V tolerant (refer to Table 19: Voltage characteristics).

Note:  $V_{DDIOx}$  is the I/Os general purpose digital functions supply.  $V_{DDIOx}$  represents  $V_{DDIO1}$  or  $V_{DDIO2}$ , with  $V_{DDIO1} = V_{DD}$ .  $V_{DDIO2}$  supply voltage level is independent from  $V_{DDIO1}$ .

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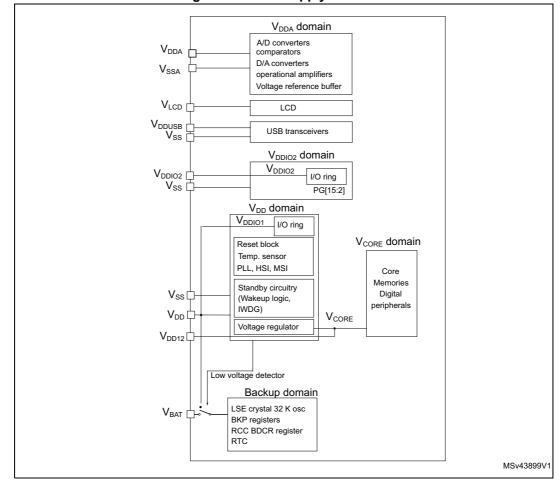


Figure 3. Power supply overview

During power-up and power-down phases, the following power sequence requirements must be respected:

- When  $V_{DD}$  is below 1 V, other power supplies ( $V_{DDA}$ ,  $V_{DDUSB}$ ,  $V_{DDIO2}$ ,  $V_{LCD}$  must remain below  $V_{DD}$  + 300 mV.
- When V<sub>DD</sub> is above 1 V, all power supplies are independent.

During the power-down phase,  $V_{DD}$  can temporarily become lower than other supplies only if the energy provided to the MCU remains below 1 mJ; this allows external decoupling capacitors to be discharged with different time constants during the power-down transient phase.

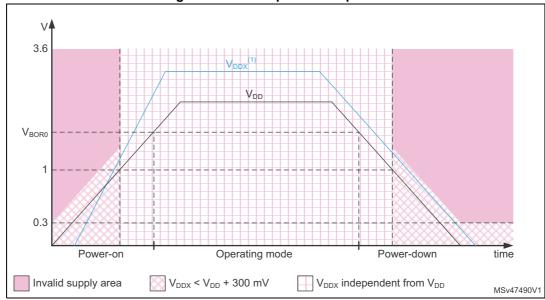


Figure 4. Power-up/down sequence

1.  $V_{DDX}$  refers to any power supply among  $V_{DDA}$ ,  $V_{DDUSB}$ ,  $V_{DDIO2}$ ,  $V_{LCD}$ .

### 3.10.2 Power supply supervisor

The device has an integrated ultra-low-power brown-out reset (BOR) active in all modes except Shutdown and ensuring proper operation after power-on and during power down. The device remains in reset mode when the monitored supply voltage  $V_{DD}$  is below a specified threshold, without the need for an external reset circuit.

The lowest BOR level is 1.71V at power on, and other higher thresholds can be selected through option bytes. The device features an embedded programmable voltage detector (PVD) that monitors the  $V_{DD}$  power supply and compares it to the VPVD threshold. An interrupt can be generated when  $V_{DD}$  drops below the VPVD threshold and/or when  $V_{DD}$  is higher than the VPVD threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

In addition, the device embeds a Peripheral Voltage Monitor which compares the independent supply voltages  $V_{DDA}$ ,  $V_{DDUSB}$ ,  $V_{DDIO2}$  with a fixed threshold in order to ensure that the peripheral is in its functional supply range.

### 3.10.3 Voltage regulator

Two embedded linear voltage regulators supply most of the digital circuitries: the main regulator (MR) and the low-power regulator (LPR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-Power Run, Low-Power Sleep, Stop 1 and Stop 2 modes. It is also used to supply the 64 Kbyte SRAM2 in Standby with SRAM2 retention.
- Both regulators are in power-down in Standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The ultralow-power STM32L4A6xG supports dynamic voltage scaling to optimize its power consumption in run mode. The voltage from the Main Regulator that supplies the logic (V<sub>CORF</sub>) can be adjusted according to the system's maximum operating frequency.

There are two power consumption ranges:

- Range 1 with the CPU running at up to 80 MHz.
- Range 2 with a maximum CPU frequency of 26 MHz. All peripheral clocks are also limited to 26 MHz.

The V<sub>CORE</sub> can be supplied by the low-power regulator, the main regulator being switched off. The system is then in Low-power run mode.

 Low-power run mode with the CPU running at up to 2 MHz. Peripherals with independent clock can be clocked by HSI16.

When the MR is in use, the STM32L4A6xG with the external SMPS option allows to force an external  $V_{CORE}$  supply on the VDD12 supply pins.

When V<sub>DD12</sub> is forced by an external source and is higher than the output of the internal LDO, the current is taken from this external supply and the overall power efficiency is significantly improved if using an external step down DC/DC converter.

### 3.10.4 Low-power modes

The ultra-low-power STM32L4A6xG supports seven low-power modes to achieve the best compromise between low-power consumption, short startup time, available peripherals and available wakeup sources.



Table 4. STM32L4A6xG modes overview

Mode	Regulator <sup>(1)</sup>	CPU	Flash	SRAM	Clocks	DMA & Peripherals <sup>(2)</sup>	Wakeup source	Consumption <sup>(3)</sup>	Wakeup time
	MR range 1					All		108 μA/MHz	
Run	SMPS range 2 High	Yes	ON <sup>(4)</sup>	ON	Anu	All	N/A	40 μA/MHz <sup>(5)</sup>	N/A
Rull	MR range2	res	ON	ON	Any	All except OTG_FS, RNG	IN/A	93 μA/MHz	IN/A
	SMPS range 2 Low					All except OTG_F3, KING		39 μA/MHz <sup>(6)</sup>	
LPRun	LPR	Yes	ON <sup>(4)</sup>	ON	Any except PLL	All except OTG_FS, RNG	N/A	129 μA/MHz	to Range 1: 4 μs to Range 2: 64 μs
	MR range 1					All		32 µA/MHz	
Clean	SMPS range 2 High	No	ON(4)	ON <sup>(7)</sup>	A	All	Any interrupt or	11.5 µA/MHz <sup>(5)</sup>	Cavalas
Sieep	Sleep MR range2		ON <sup>(4)</sup>	ON(')	Any	All except OTG FS, RNG	event	30 μA/MHz	6 cycles
	SMPS range 2 Low					All except OTG_F5, RNG		13 μA/MHz <sup>(6)</sup>	
LPSleep	LPR	No	ON <sup>(4)</sup>	ON <sup>(7)</sup>	Any except PLL	All except OTG_FS, RNG	Any interrupt or event	51 μA/MHz	6 cycles
Stop 0	MR Range 1 <sup>(8)</sup>	BOR, PVD, PVM RTC,LCD, IWDG COMPx (x=1,2) BOR, PVD, PVM DAC1 OPAMPx (x=1,2) COMPx (x=1,2) COMPx (x=1.2) USARTx (x=1,5)(9) USARTx (x=1,5)(9)		No	TBD	2.7 μs in SRAM			
Stop 0 -	MR Range 2 <sup>(8)</sup>	INO	OFF	ON	LSI	LPUART1 <sup>(9)</sup> I2Cx (x=14) <sup>(10)</sup> LPTIMx (x=1,2)  ***  All other peripherals are frozen.	LPUART1 <sup>(9)</sup> I2Cx (x=14) <sup>(10)</sup> LPTIMx (x=1,2) OTG_FS <sup>(11)</sup> SWPMI1 <sup>(12)</sup>	127 μΑ	6.2 μs in Flash

**Functional overview** 

		1	1		· · · · · ·	HAUXO IIIOGES OVEIVIEW	T	<del></del>			
Mode	Regulator <sup>(1)</sup>	CPU	Flash	SRAM	Clocks	DMA & Peripherals <sup>(2)</sup>	Wakeup source	Consumption <sup>(3)</sup>	Wakeup time		
Stop 1	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=1,2) DAC1 OPAMPx (x=1,2) USARTx (x=15) <sup>(9)</sup> LPUART1 <sup>(9)</sup> I2Cx (x=14) <sup>(10)</sup> LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=12) USARTx (x=15) <sup>(9)</sup> LPUART1 <sup>(9)</sup> I2Cx (x=14) <sup>(10)</sup> LPTIMx (x=1,2) OTG_FS <sup>(11)</sup> SWPMI1 <sup>(12)</sup>	11.2 μA w/o RTC 11.8 μA w RTC	6.6 μs in SRAM 7.8 μs in Flash		
Stop 2	LPR	No	Off	ON	LSE LSI	BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=12) I2C3 <sup>(10)</sup> LPUART1 <sup>(9)</sup> LPTIM1 ***  All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, LCD, IWDG COMPx (x=12) I2C3 <sup>(10)</sup> LPUART1 <sup>(9)</sup> LPTIM1	2.57 μA w/o RTC 2.86 μA w/RTC	6.8 μs in SRAM 8.2 μs in Flash		



#### Table 4. STM32L4A6xG modes overview (continued)

	(4)					(2)	,	,			
Mode	Regulator <sup>(1)</sup>	CPU	Flash	SRAM	Clocks	DMA & Peripherals <sup>(2)</sup>	Wakeup source	Consumption <sup>(3)</sup>	Wakeup time		
Standby	LPR			SRAM 2 ON		BOR, RTC, IWDG  ***	D i . i	0.48 μA w/o RTC 0.78 μA w/ RTC			
	OFF	Power ed Off	Off	Power ed Off	LSE LSI	All other peripherals are powered off.  ***  I/O configuration can be floating, pull-up or pull-down	Reset pin 5 I/Os (WKUPx) <sup>(13)</sup> BOR, RTC, IWDG	0.11 μA w/o RTC 0.42 μA w/ RTC	15.3 μs		
Shutdown	OFF	Power ed Off	Off	Power ed Off	LSE	RTC ***  All other peripherals are powered off.  ***  I/O configuration can be floating, pull-up or pull-down <sup>(14)</sup>	Reset pin 5 I/Os (WKUPx) <sup>(14)</sup> RTC	0.03 μA w/o RTC 0.23 μA w/ RTC	306 µs		

- 1. LPR means Main regulator is OFF and Low-power regulator is ON.
- 2. All peripherals can be active or clock gated to save power consumption.
- 3. Typical current at V<sub>DD</sub> = 1.8 V, 25°C. Consumptions values provided running from SRAM, Flash memory Off, 80 MHz in Range 1, 26 MHz in Range 2, 2 MHz in LPRun/LPSleep.
- 4. The Flash memory can be put in power-down and its clock can be gated off when executing from SRAM.
- Theoretical value based on V<sub>DD</sub> = 3.3 V, DC/DC Efficiency of 85%, V<sub>CORE</sub> = 1.10 V
- 6. Theoretical value based on  $V_{DD}$  = 3.3 V, DC/DC Efficiency of 85%,  $V_{CORE}$  = 1.05 V
- 7. The SRAM1 and SRAM2 clocks can be gated on or off independently.
- 8. SMPS mode can be used in STOP0 Mode, but no significant power gain can be expected.
- 9. U(S)ART and LPUART reception is functional in Stop mode, and generates a wakeup interrupt on Start, address match or received frame event.
- 10. I2C address detection is functional in Stop mode, and generates a wakeup interrupt in case of address match.
- 11. OTG FS wakeup by resume from suspend and attach detection protocol event.
- 12. SWPMI1 wakeup by resume from suspend.
- 13. The I/Os with wakeup from Standby/Shutdown capability are: PA0, PC13, PE6, PA2, PC5.
- 14. I/Os can be configured with internal pull-up, pull-down or floating in Shutdown mode but the configuration is lost when exiting the Shutdown mode.

By default, the microcontroller is in Run mode after a system or a power Reset. It is up to the user to select one of the low-power modes described below:

#### Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

#### Low-power run mode

This mode is achieved with  $V_{CORE}$  supplied by the low-power regulator to minimize the regulator's operating current. The code can be executed from SRAM or from Flash, and the CPU frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16.

#### Low-power sleep mode

This mode is entered from the low-power run mode. Only the CPU clock is stopped. When wakeup is triggered by an event or an interrupt, the system reverts to the low-power run mode.

#### Stop 0, Stop 1 and Stop 2 modes

Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the  $V_{CORE}$  domain are stopped, the PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are disabled. The LSE or LSI is still running.

The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

Some peripherals with wakeup capability can enable the HSI16 RC during Stop mode to detect their wakeup condition.

Three Stop modes are available: Stop 0, Stop 1 and Stop 2 modes. In Stop 2 mode, most of the  $V_{CORE}$  domain is put in a lower leakage mode.

Stop 1 offers the largest number of active peripherals and wakeup sources, a smaller wakeup time but a higher consumption than Stop 2. In Stop 0 mode, the main regulator remains ON, allowing a very fast wakeup time but with much higher consumption.

The system clock when exiting from Stop 0, Stop 1 or Stop 2 modes can be either MSI up to 48 MHz or HSI16, depending on software configuration.

### Standby mode

The Standby mode is used to achieve the lowest power consumption with BOR. The internal regulator is switched off so that the  $V_{CORE}$  domain is powered off. The PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are also switched off.

The RTC can remain active (Standby mode with RTC, Standby mode without RTC).

The brown-out reset (BOR) always remains active in Standby mode.

The state of each I/O during standby mode can be selected by software: I/O with internal pull-up, internal pull-down or floating.

After entering Standby mode, SRAM1 and register contents are lost except for registers in the Backup domain and Standby circuitry. Optionally, SRAM2 can be retained in Standby mode, supplied by the low-power Regulator (Standby with SRAM2 retention mode).

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

The system clock after wakeup is MSI up to 8 MHz.

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#### • Shutdown mode

The Shutdown mode allows to achieve the lowest power consumption. The internal regulator is switched off so that the  $V_{CORE}$  domain is powered off. The PLL, the HSI16, the MSI, the LSI and the HSE oscillators are also switched off.

The RTC can remain active (Shutdown mode with RTC, Shutdown mode without RTC).

The BOR is not available in Shutdown mode. No power voltage monitoring is possible in this mode, therefore the switch to Backup domain is not supported.

SRAM1, SRAM2 and register contents are lost except for registers in the Backup domain.

The device exits Shutdown mode when an external reset (NRST pin), a WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper).

The system clock after wakeup is MSI at 4 MHz.



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Table 5. Functionalities depending on the working  $\mathsf{mode}^{(1)}$ 

		5. Funct		•		0/1	1	p 2		dby	Shute	down	
Peripheral	Run	Sleep	Low- power run	Low- power sleep	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	-	Wakeup capability	VBAT
CPU	Υ	-	Υ	-	-	-	-	-	-	-	-	-	-
Flash memory (1 MB)	O <sup>(2)</sup>	O <sup>(2)</sup>	O <sup>(2)</sup>	O <sup>(2)</sup>	-	-	-	-	-	-	-	1	-
SRAM1 (256 KB)	Υ	Y <sup>(3)</sup>	Υ	Y <sup>(3)</sup>	Υ	-	Υ	-	-	-	-	-	-
SRAM2 (64 KB)	Υ	Y <sup>(3)</sup>	Υ	Y <sup>(3)</sup>	Υ	-	Υ	-	O <sup>(4)</sup>	-	-	-	-
FSMC	0	0	0	0	-	-	-	-	-	-	-	-	-
Quad SPI	0	0	0	0	-	-	-	-	-	-	-	-	-
Backup Registers	Υ	Y	Y	Y	Y	-	Υ	-	Υ	-	Υ	-	Υ
Brown-out reset (BOR)	Υ	Y	Y	Y	Y	Y	Y	Y	Y	Y	-	1	-
Programmable Voltage Detector (PVD)	0	0	0	0	0	0	0	0	-	-	-	-	-
Peripheral Voltage Monitor (PVMx; x=1,2,3,4)	0	0	0	0	0	0	0	0	-	-	-	-	-
DMA	0	0	0	0	-	-	-	-	-	-	-	-	
DMA2D	0	0	0	0	-	-	-	-	-	-	-	-	-
High Speed Internal (HSI16)	0	0	0	0	(5)	-	(5)	-	-	-	-	-	-
Oscillator HSI48	0	0	-	-	1	-	-	-	-	-	-	-	-
High Speed External (HSE)	0	0	0	0	ı	-	-	-	-	-	-	1	-
Low Speed Internal (LSI)	0	0	0	0	0	-	0	-	0	-	-	-	-
Low Speed External (LSE)	0	0	0	0	0	-	0	-	0	-	0	-	0
Multi-Speed Internal (MSI)	0	0	0	0	-	-	-	-	-	-	-	-	-
Clock Security System (CSS)	0	0	0	0	-	-	-	-	-	-	-	-	-
Clock Security System on LSE	0	0	0	0	0	0	0	0	0	0	-	-	-
RTC / Auto wakeup	0	0	0	0	0	0	0	0	0	0	0	0	0

Table 5. Functionalities depending on the working mode<sup>(1)</sup> (continued)

		ctionalii			Stop		Sto			ndby	Shute	down	
Peripheral	Run	Sleep	Low- power run	Low- power sleep	-	Wakeup capability	1	Wakeup capability	-	Wakeup capability	-	Wakeup capability	VBAT
Number of RTC Tamper pins	3	3	3	3	3	0	3	0	3	0	3	0	3
Camera interface	0	0	0	0	-	-	-	-	-	-	-	-	-
LCD	0	0	0	0	0	0	0	0	-	-	-	-	-
USB OTG FS	O <sup>(8)</sup>	O <sup>(8)</sup>	-	-	-	0	-		-	-	-		-
USARTx (x=1,2,3,4,5)	0	0	0	0	O <sup>(6)</sup>	O <sup>(6)</sup>	ı	-	-	-	-	-	-
Low-power UART (LPUART)	0	0	0	0	O <sup>(6)</sup>	O <sup>(6)</sup>	O <sup>(6)</sup>	O <sup>(6)</sup>	-	-	-	-	-
I2Cx (x=1,2,4)	0	0	0	0	O <sup>(7)</sup>	O <sup>(7)</sup>	-		-	-	-	1	-
I2C3	0	0	0	0	O <sup>(7)</sup>	O <sup>(7)</sup>	O <sup>(7)</sup>	O <sup>(7)</sup>	-	-	-	-	-
SPIx (x=1,2,3)	0	0	0	0	-	-	-	-	-	-	-	-	-
CAN(x=1,2)	0	0	0	0	-	-	-	-	-	-	-	-	-
SDMMC1	0	0	0	0	-	-	-	-	-	-	-	-	-
SWPMI1	0	0	0	0	-	0	-	-	-	-	-	-	-
SAIx (x=1,2)	0	0	0	0	-	-	-	-	-	-	-	-	-
DFSDM1	0	0	0	0	-	-	-	-	-	-	-	-	-
ADCx (x=1,2,3)	0	0	0	0	-	-	-	-	-	-	-	-	-
DAC1	0	0	0	0	0	-	-	-	-	-	-	-	-
VREFBUF	0	0	0	0	0	-	-		-	-	-	-	-
OPAMPx (x=1,2)	0	0	0	0	0	-	-	-	-	-	-	-	-
COMPx (x=1,2)	0	0	0	0	0	0	0	0	-	-	-	-	-
Temperature sensor	0	0	0	0	-	-	-	-	-	-	-	-	-
Timers (TIMx)	0	0	0	0	-	-	-	-	-	-	-	-	-
Low-power timer 1 (LPTIM1)	0	0	0	0	0	0	0	0	-	-	-	-	-
Low-power timer 2 (LPTIM2)	0	0	0	0	0	0	ı	-	-	-	-	ı	-
Independent watchdog (IWDG)	0	0	0	0	0	0	0	0	0	0	-	-	-
Window watchdog (WWDG)	0	0	0	0	-	-	-	-	-	-	-	-	-



**Stop 0/1** Stop 2 Standby Shutdown capability capability capability capability Low-Low-**VBAT Peripheral** Run Sleep power power run sleep Wakeup Wakeup Wakeup Wakeup SysTick timer 0 0 0 0 Touch sensing 0 0 0 0 controller (TSC) Random number  $O^{(8)}$  $O^{(8)}$ generator (RNG) AES hardware  $\cap$  $\cap$ 0  $\cap$ accelerator HASH hardware 0 0 0 0 accelerator CRC calculation unit 0 0 0 0 \_ 5 5 (9)(11)pins **GPIOs** 0 0 O O 0 0 00 pins

Table 5. Functionalities depending on the working mode<sup>(1)</sup> (continued)

- 1. Legend: Y = Yes (Enable). O = Optional (Disable by default. Can be enabled by software). = Not available.
- 2. The Flash can be configured in power-down mode. By default, it is not in power-down mode.
- 3. The SRAM clock can be gated on or off.
- 4. SRAM2 content is preserved when the bit RRS is set in PWR\_CR3 register.
- Some peripherals with wakeup from Stop capability can request HSI16 to be enabled. In this case, HSI16 is woken up by the peripheral, and only feeds the peripheral which requested it. HSI16 is automatically put off when the peripheral does not need it anymore.
- 6. UART and LPUART reception is functional in Stop mode, and generates a wakeup interrupt on Start, address match or received frame event.
- 7. I2C address detection is functional in Stop mode, and generates a wakeup interrupt in case of address match.
- 8. Voltage scaling Range 1 only.
- 9. I/Os can be configured with internal pull-up, pull-down or floating in Standby mode.
- 10. The I/Os with wakeup from Standby/Shutdown capability are: PA0, PC13, PE6, PA2, PC5.
- 11. I/Os can be configured with internal pull-up, pull-down or floating in Shutdown mode but the configuration is lost when exiting the Shutdown mode.

#### 3.10.5 Reset mode

In order to improve the consumption under reset, the I/Os state under and after reset is "analog state" (the I/O schmitt trigger is disable). In addition, the internal reset pull-up is deactivated when the reset source is internal.

#### 3.10.6 **VBAT** operation

The VBAT pin allows to power the device VBAT domain from an external battery, an external supercapacitor, or from V<sub>DD</sub> when no external battery and an external supercapacitor are

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(10)

(10)

present. The VBAT pin supplies the RTC with LSE and the backup registers. Three antitamper detection pins are available in VBAT mode.

VBAT operation is automatically activated when V<sub>DD</sub> is not present.

An internal VBAT battery charging circuit is embedded and can be activated when  $V_{\text{DD}}$  is present.

Note:

When the microcontroller is supplied from VBAT, external interrupts and RTC alarm/events do not exit it from VBAT operation.

### 3.11 Interconnect matrix

Several peripherals have direct connections between them. This allows autonomous communication between peripherals, saving CPU resources thus power supply consumption. In addition, these hardware connections allow fast and predictable latency.

Depending on peripherals, these interconnections can operate in Run, Sleep, low-power run and sleep, Stop 0, Stop 1 and Stop 2 modes.

Table 6. STM32L4A6xG peripherals interconnect matrix

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
	TIMx	Timers synchronization or chaining	Υ	Υ	Υ	Υ	-	-
TIMx	ADCx DAC1 DFSDM1	Conversion triggers	Y	Y	Υ	Y	1	-
	DMA	Memory to memory transfer trigger	Υ	Υ	Υ	Υ	-	-
	COMPx	Comparator output blanking	Υ	Υ	Υ	Υ	-	-
TIM16/TIM17	IRTIM	Infrared interface output generation	Υ	Υ	Υ	Υ	-	-
COMPx	TIM1, 8 TIM2, 3	Timer input channel, trigger, break from analog signals comparison	Υ	Υ	Υ	Υ	-	-
COMPX	LPTIMERx	Low-power timer triggered by analog signals comparison	Υ	Υ	Υ	Υ	Υ	Y (1)
ADCx	TIM1, 8	Timer triggered by analog watchdog	Υ	Υ	Υ	Υ	-	-
	TIM16	Timer input channel from RTC events	Υ	Υ	Υ	Υ	-	-
RTC	LPTIMERx	Low-power timer triggered by RTC alarms or tampers	Υ	Υ	Υ	Υ	Υ	Y (1)
All clocks sources (internal and external)	TIM2 TIM15, 16, 17	Clock source used as input channel for RC measurement and trimming	Y	Y	Υ	Υ	1	-
USB	TIM2	Timer triggered by USB SOF	Υ	Υ	-	-	-	-

Table 6. STM32L4A6xG peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
CSS CPU (hard fault) RAM (parity error) Flash memory (ECC error) COMPx PVD DFSDM1 (analog watchdog, short circuit detection)	TIM1,8 TIM15,16,17	Timer break	Y	Y	<b>Y</b>	Y	-	-
	TIMx	External trigger	Υ	Υ	Υ	Υ	-	-
GPIO	LPTIMERx	External trigger	Υ	Υ	Υ	Υ	Υ	Y (1)
	ADCx DAC1 DFSDM1	Conversion external trigger	Υ	Υ	Υ	Υ	-	-

<sup>1.</sup> LPTIM1 only.

#### 3.12 Clocks and startup

The clock controller (see *Figure 5*) distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- Clock prescaler: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler
- **Safe clock switching:** clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management:** to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- System clock source: four different clock sources can be used to drive the master clock SYSCLK:
  - 4-48 MHz high-speed external crystal or ceramic resonator (HSE), that can supply a PLL. The HSE can also be configured in bypass mode for an external clock.
  - 16 MHz high-speed internal RC oscillator (HSI16), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 12 frequencies from 100 kHz to 48 MHz. When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be automatically trimmed by hardware to reach better than ±0.25% accuracy. In this mode the MSI can feed the USB device, saving the need of an external high-speed crystal (HSE). The MSI can supply a PLL.
  - System PLL which can be fed by HSE, HSI16 or MSI, with a maximum frequency at 80 MHz.
- RC48 with clock recovery system (HSI48): internal 48 MHz clock source (HSI48)can be used to drive the USB, the SDMMC or the RNG peripherals. This clock can be output on the MCO.
- Auxiliary clock source: two ultralow-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE), supporting four drive capability modes. The LSE can also be configured in bypass mode for an external clock.
  - 32 kHz low-speed internal RC (LSI), also used to drive the independent watchdog.
     The LSI clock accuracy is ±5% accuracy.
- Peripheral clock sources: Several peripherals (USB, SDMMC, RNG, SAI, USARTs, I2Cs, LPTimers, ADC, SWPMI) have their own independent clock whatever the system clock. Three PLLs, each having three independent outputs allowing the highest flexibility, can generate independent clocks for the ADC, the USB/SDMMC/RNG and the two SAIs.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 4 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- Clock security system (CSS): this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI16 and a software

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interrupt is generated if enabled. LSE failure can also be detected and generated an interrupt.

- Clock-out capability:
  - MCO: microcontroller clock output: it outputs one of the internal clocks for external use by the application. Low frequency clocks (LSI, LSE) are available down to Stop 1 low power state.
  - LSCO: low speed clock output: it outputs LSI or LSE in all low-power modes down to Standby mode. LSE can also be output on LSCO in Shutdown mode. LSCO is not available in VBAT mode.

Several prescalers allow to configure the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 80 MHz.

to IWDG LSI RC 32 kHz LSCO to RTC and LCD OSC32\_OUT LSE OSC 32.768 kHz /32 OSC32\_IN to PWR LSI MSI to AHB bus, core, memory and DMA HSI16 мсо / 1→16 HSE HCLK FCLK Cortex free running clock AHB PRESC SYSCLK / 1,2,..512 PLLCLK to Cortex system timer HSI48 Clock PCLK1 source APB1 PRESC / 1,2,4,8,16 control OSC\_OUT to APB1 peripherals HSE OSC 4-48 MHz HSE x1 or x2 to TIMx OSC\_IN MSI Clock x=2..7 SYSCLK HSI16 LSE-HSI16-SYSCLKto USARTx x=2..5 to LPUART1 HSI RC HSI16 SYSCLK to I2Cx 16 MHz x=1,2,3,4 to LPTIMx MSI RC HSI16 100 kHz – 48 MHz HSI16 to SWPMI MSI HSI16 / M PLL APB2 PRESC HSE to APB2 peripherals PLLSAI3CLK / 1,2,4,8,16 vco Fvco / P PLL48M1CLK x1 or x2 to TIMx x=1,8,15,16,17 /Q PLLCLK / R to USART1 PLLSAI1 PLLSAI1CLK vco Fvc / P PLL48M2CLK /Q MSI 48 MHz clock to USB, RNG, SDMMC PLLADC1CLK / R SYSCLK to ADC HSI48 HSI RC 48MHz SYSCLK CRS to DFSDM1 PLLSA12 PLLSAI2CLK vco Fvc ) / P /Q to SAI1 PLLADC2CLK / R SAI1\_EXTCLK to SAI2 SAI2\_EXTCLK

Figure 5. Clock tree

MS50063V1

#### 3.13 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. Fast I/O toggling can be achieved thanks to their mapping on the AHB2 bus.

The I/Os alternate function configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

## 3.14 Direct memory access controller (DMA)

The device embeds 2 DMAs. Refer to *Table 7: DMA implementation* for the features implementation.

Direct memory access (DMA) is used in order to provide high-speed data transfer between peripherals and memory as well as memory to memory. Data can be quickly moved by DMA without any CPU actions. This keeps CPU resources free for other operations.

The two DMA controllers have 14 channels in total, each dedicated to managing memory access requests from one or more peripherals. Each has an arbiter for handling the priority between DMA requests.

#### The DMA supports:

- 14 independently configurable channels (requests)
- Each channel is connected to dedicated hardware DMA requests, software trigger is also supported on each channel. This configuration is done by software.
- Priorities between requests from channels of one DMA are software programmable (4 levels consisting of very high, high, medium, low) or hardware in case of equality (request 1 has priority over request 2, etc.)
- Independent source and destination transfer size (byte, half word, word), emulating packing and unpacking. Source/destination addresses must be aligned on the data size.
- Support for circular buffer management
- 3 event flags (DMA Half Transfer, DMA Transfer complete and DMA Transfer Error) logically ORed together in a single interrupt request for each channel
- Memory-to-memory transfer
- Peripheral-to-memory and memory-to-peripheral, and peripheral-to-peripheral transfers
- Access to Flash, SRAM, APB and AHB peripherals as source and destination
- Programmable number of data to be transferred: up to 65536.

**Table 7. DMA implementation** 

DMA features	DMA1	DMA2
Number of regular channels	7	7

## 3.15 Chrom-ART Accelerator™ (DMA2D)

The Chrom-Art Accelerator™ (DMA2D) is a graphic accelerator which offers advanced bit blitting, row data copy and pixel format conversion. It supports the following functions:

- Rectangle filling with a fixed color
- Rectangle copy
- Rectangle copy with pixel format conversion
- Rectangle composition with blending and pixel format conversion.

Various image format coding are supported, from indirect 4bpp color mode up to 32bpp direct color. It embeds dedicated memory to store color lookup tables.

An interrupt can be generated when an operation is complete or at a programmed watermark.

All the operations are fully automatized and are running independently from the CPU or the DMAs.

#### 3.16 Interrupts and events

#### 3.16.1 Nested vectored interrupt controller (NVIC)

The devices embed a nested vectored interrupt controller able to manage 16 priority levels, and handle up to 90 maskable interrupt channels plus the 16 interrupt lines of the Cortex<sup>®</sup>-M4.

The NVIC benefits are the following:

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail chaining
- Processor state automatically saved on interrupt entry, and restored on interrupt exit, with no instruction overhead

The NVIC hardware block provides flexible interrupt management features with minimal interrupt latency.

#### 3.16.2 Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 41 edge detector lines used to generate interrupt/event requests and wake-up the system from Stop mode. Each external line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The internal lines are connected to peripherals with wakeup from Stop mode capability. The EXTI can detect an external line with a pulse width shorter than the internal clock period. Up to 136 GPIOs can be connected to the 16 external interrupt lines.



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#### 3.17 Analog to digital converter (ADC)

The device embeds 3 successive approximation analog-to-digital converters with the following features:

- 12-bit native resolution, with built-in calibration
- 5.33 Msps maximum conversion rate with full resolution
  - Down to 18.75 ns sampling time
  - Increased conversion rate for lower resolution (up to 8.88 Msps for 6-bit resolution)
- Up to 24 external channels, some of them shared between ADC1 and ADC2, or ADC1, ADC2 and ADC3.
- 5 internal channels: internal reference voltage, temperature sensor, VBAT/3, DAC1\_OUT1 and DAC1\_OUT2.
- One external reference pin is available on some package, allowing the input voltage range to be independent from the power supply
- · Single-ended and differential mode inputs
- Low-power design
  - Capable of low-current operation at low conversion rate (consumption decreases linearly with speed)
  - Dual clock domain architecture: ADC speed independent from CPU frequency
- Highly versatile digital interface
  - Single-shot or continuous/discontinuous sequencer-based scan mode: 2 groups of analog signals conversions can be programmed to differentiate background and high-priority real-time conversions
  - Handles two ADC converters for dual mode operation (simultaneous or interleaved sampling modes)
  - Each ADC support multiple trigger inputs for synchronization with on-chip timers and external signals
  - Results stored into 3 data register or in RAM with DMA controller support
  - Data pre-processing: left/right alignment and per channel offset compensation
  - Built-in oversampling unit for enhanced SNR
  - Channel-wise programmable sampling time
  - Three analog watchdog for automatic voltage monitoring, generating interrupts and trigger for selected timers
  - Hardware assistant to prepare the context of the injected channels to allow fast context switching

#### 3.17.1 Temperature sensor

The temperature sensor (TS) generates a voltage V<sub>TS</sub> that varies linearly with temperature.

The temperature sensor is internally connected to the ADC1\_IN17 and ADC3\_IN17 input channels which is used to convert the sensor output voltage into a digital value.

The sensor provides good linearity but it has to be calibrated to obtain good overall accuracy of the temperature measurement. As the offset of the temperature sensor varies from chip to chip due to process variation, the uncalibrated internal temperature sensor is suitable for applications that detect temperature changes only.



To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at a temperature of 30 °C (± 5 °C), V <sub>DDA</sub> = V <sub>REF+</sub> = 3.0 V (± 10 mV)	0x1FFF 75A8 - 0x1FFF 75A9
TS_CAL2	TS ADC raw data acquired at a temperature of 130 °C (± 5 °C), V <sub>DDA</sub> = V <sub>REF+</sub> = 3.0 V (± 10 mV)	0x1FFF 75CA - 0x1FFF 75CB

Table 8. Temperature sensor calibration values

#### 3.17.2 Internal voltage reference (V<sub>REFINT</sub>)

The internal voltage reference (VREFINT) provides a stable (bandgap) voltage output for the ADC and Comparators. VREFINT is internally connected to the ADC1\_IN0 input channel. The precise voltage of VREFINT is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

	<u> </u>	
Calibration value name	Description	Memory address
VREFINT	Raw data acquired at a temperature of 30 °C (± 5 °C),	0x1FFF 75AA - 0x1FFF 75AB

Table 9. Internal voltage reference calibration values

#### 3.17.3 V<sub>BAT</sub> battery voltage monitoring

This embedded hardware feature allows the application to measure the  $V_{BAT}$  battery voltage using the internal ADC channel ADC1\_IN18 or ADC3\_IN18. As the  $V_{BAT}$  voltage may be higher than  $V_{DDA}$ , and thus outside the ADC input range, the VBAT pin is internally connected to a bridge divider by 3. As a consequence, the converted digital value is one third the  $V_{BAT}$  voltage.

## 3.18 Digital to analog converter (DAC)

Two 12-bit buffered DAC channels can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital interface supports the following features:

- Up to two DAC output channels
- 8-bit or 12-bit output mode
- Buffer offset calibration (factory and user trimming)
- Left or right data alignment in 12-bit mode
- Synchronized update capability
- Noise-wave generation
- Triangular-wave generation
- Dual DAC channel independent or simultaneous conversions
- DMA capability for each channel
- External triggers for conversion
- Sample and hold low-power mode, with internal or external capacitor

The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

## 3.19 Voltage reference buffer (VREFBUF)

The STM32L4A6xG devices embed an voltage reference buffer which can be used as voltage reference for ADCs, DAC and also as voltage reference for external components through the VREF+ pin.

The internal voltage reference buffer supports two voltages:

- 2.048 V
- 2.5 V

An external voltage reference can be provided through the VREF+ pin when the internal voltage reference buffer is off.

The VREF+ pin is double-bonded with VDDA on some packages. In these packages the internal voltage reference buffer is not available.

VREFBUF
VDDA DAC, ADC
Bandgap
Low frequency cut-off capacitor

MSv40197V1

Figure 6. Voltage reference buffer

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#### 3.20 Comparators (COMP)

The STM32L4A6xG devices embed two rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low-power) and with selectable output polarity.

The reference voltage can be one of the following:

- External I/O
- DAC output channels
- Internal reference voltage or submultiple (1/4, 1/2, 3/4).

All comparators can wake up from Stop mode, generate interrupts and breaks for the timers and can be also combined into a window comparator.

## 3.21 Operational amplifier (OPAMP)

The STM32L4A6xG embeds two operational amplifiers with external or internal follower routing and PGA capability.

The operational amplifier features:

- Low input bias current
- Low offset voltage
- Low-power mode
- Rail-to-rail input

## 3.22 Touch sensing controller (TSC)

The touch sensing controller provides a simple solution for adding capacitive sensing functionality to any application. Capacitive sensing technology is able to detect finger presence near an electrode which is protected from direct touch by a dielectric (glass, plastic, ...). The capacitive variation introduced by the finger (or any conductive object) is measured using a proven implementation based on a surface charge transfer acquisition principle.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

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The main features of the touch sensing controller are the following:

- Proven and robust surface charge transfer acquisition principle
- Supports up to 24 capacitive sensing channels
- Up to 3 capacitive sensing channels can be acquired in parallel offering a very good response time
- Spread spectrum feature to improve system robustness in noisy environments
- Full hardware management of the charge transfer acquisition sequence
- Programmable charge transfer frequency
- Programmable sampling capacitor I/O pin
- Programmable channel I/O pin
- Programmable max count value to avoid long acquisition when a channel is faulty
- Dedicated end of acquisition and max count error flags with interrupt capability
- One sampling capacitor for up to 3 capacitive sensing channels to reduce the system components
- Compatible with proximity, touchkey, linear and rotary touch sensor implementation
- Designed to operate with STMTouch touch sensing firmware library

Note:

The number of capacitive sensing channels is dependent on the size of the packages and subject to I/O availability.

#### 3.23 Liquid crystal display controller (LCD)

The LCD drives up to 8 common terminals and 44 segment terminals to drive up to 320 pixels.

- Internal step-up converter to guarantee functionality and contrast control irrespective of V<sub>DD</sub>. This converter can be deactivated, in which case the VLCD pin is used to provide the voltage to the LCD
- Supports static, 1/2, 1/3, 1/4 and 1/8 duty
- Supports static, 1/2, 1/3 and 1/4 bias
- Phase inversion to reduce power consumption and EMI
- Integrated voltage output buffers for higher LCD driving capability
- Up to 8 pixels can be programmed to blink
- Unneeded segments and common pins can be used as general I/O pins
- LCD RAM can be updated at any time owing to a double-buffer
- The LCD controller can operate in Stop mode

## 3.24 Digital filter for Sigma-Delta Modulators (DFSDM)

The device embeds one DFSDM with 4 digital filters modules and 8 external input serial channels (transceivers) or alternately 8 internal parallel inputs support.

The DFSDM peripheral is dedicated to interface the external  $\Sigma\Delta$  modulators to microcontroller and then to perform digital filtering of the received data streams (which represent analog value on  $\Sigma\Delta$  modulators inputs). DFSDM can also interface PDM (Pulse Density Modulation) microphones and perform PDM to PCM conversion and filtering in



hardware. DFSDM features optional parallel data stream inputs from microcontrollers memory (through DMA/CPU transfers into DFSDM or from internal ADCs).

DFSDM transceivers support several serial interface formats (to support various  $\Sigma\Delta$  modulators). DFSDM digital filter modules perform digital processing according user selected filter parameters with up to 24-bit final ADC resolution.

#### The DFSDM peripheral supports:

- 8 multiplexed input digital serial channels:
  - configurable SPI interface to connect various SD modulator(s)
  - configurable Manchester coded 1 wire interface support
  - PDM (Pulse Density Modulation) microphone input support
  - maximum input clock frequency up to 20 MHz (10 MHz for Manchester coding)
  - clock output for SD modulator(s): 0..20 MHz
- alternative inputs from 8 internal digital parallel channels (up to 16 bit input resolution):
  - internal sources: ADCs data or device memory data streams (DMA)
- 4 digital filter modules with adjustable digital signal processing:
  - Sinc<sup>x</sup> filter: filter order/type (1..5), oversampling ratio (up to 1..1024)
  - integrator: oversampling ratio (1..256)
- up to 24-bit output data resolution, signed output data format
- automatic data offset correction (offset stored in register by user)
- continuous or single conversion
- start-of-conversion triggered by:
  - software trigger
  - internal timers
  - external events
  - start-of-conversion synchronously with first digital filter module (DFSDM1\_FLT0)
- analog watchdog feature:
  - low value and high value data threshold registers
  - dedicated configurable Sincx digital filter (order = 1..3, oversampling ratio = 1..32)
  - input from final output data or from selected input digital serial channels
  - continuous monitoring independently from standard conversion
- short circuit detector to detect saturated analog input values (bottom and top range):
  - up to 8-bit counter to detect 1..256 consecutive 0's or 1's on serial data stream
  - monitoring continuously each input serial channel
- break signal generation on analog watchdog event or on short circuit detector event
- extremes detector:
  - storage of minimum and maximum values of final conversion data
  - refreshed by software
- DMA capability to read the final conversion data
- interrupts: end of conversion, overrun, analog watchdog, short circuit, input serial channel clock absence
- "regular" or "injected" conversions:
  - "regular" conversions can be requested at any time or even in continuous mode



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without having any impact on the timing of "injected" conversions

"injected" conversions for precise timing and with high conversion priority

#### 3.25 Random number generator (RNG)

All devices embed an RNG that delivers 32-bit random numbers generated by an integrated analog circuit.

#### 3.26 Digital camera interface (DCMI)

The devices embed a camera interface that can connect with camera modules and CMOS sensors through an 8-bit to 14-bit parallel interface, to receive video data. The camera interface can sustain a data transfer rate up to 54 Mbyte/s at 54 MHz. It features:

- Programmable polarity for the input pixel clock and synchronization signals
- Parallel data communication can be 8-, 10-, 12- or 14-bit
- Supports 8-bit progressive video monochrome or raw bayer format, YCbCr 4:2:2 progressive video, RGB 565 progressive video or compressed data (like JPEG)
- Supports continuous mode or snapshot (a single frame) mode
- Capability to automatically crop the image

## 3.27 Advanced encryption standard hardware accelerator (AES)

The devices embed an AES hardware accelerator can be used to both encipher and decipher data using AES algorithm.

The AES peripheral supports:

- Encryption/Decryption using AES Rijndael Block Cipher algorithm
- NIST FIPS 197 compliant implementation of AES encryption/decryption algorithm
- 128-bit and 256-bit register for storing the encryption, decryption or derivation key (4x 32-bit registers)
- Electronic codebook (ECB), Cipher block chaining (CBC), Counter mode (CTR), Galois Counter Mode (GCM), Galois Message Authentication Code mode (GMAC) and Cipher Message Authentication Code mode (CMAC) supported.
- Key scheduler
- Key derivation for decryption
- 128-bit data block processing
- 128-bit, 256-bit key length
- 1x32-bit INPUT buffer and 1x32-bit OUTPUT buffer.
- Register access supporting 32-bit data width only.
- One 128-bit Register for the initialization vector when AES is configured in CBC mode or for the 32-bit counter initialization when CTR mode is selected, GCM mode or CMAC mode.
- Automatic data flow control with support of direct memory access (DMA) using 2 channels, one for incoming data, and one for outcoming data.
- Suspend a message if another message with a higher priority needs to be processed



### 3.28 HASH hardware accelerator (HASH)

The hash processor is a fully compliant implementation of the secure hash algorithm (SHA-1, SHA-224, SHA-256), the MD5 (message-digest algorithm 5) hash algorithm and the HMAC (keyed-hash message authentication code) algorithm suitable for a variety of applications.

It computes a message digest (160 bits for the SHA-1 algorithm, 256 bits for the SHA-256 algorithm and 224 bits for the SHA-224 algorithm, 128 bits for the MD5 algorithm) for messages of up to (264 - 1) bits, while HMAC algorithms provide a way of authenticating messages by means of hash functions. HMAC algorithms consist in calling the SHA-1, SHA-224, SHA-256 or MD5 hash function twice.

## 3.29 Timers and watchdogs

The STM32L4A6xG includes two advanced control timers, up to nine general-purpose timers, two basic timers, two low-power timers, two watchdog timers and a SysTick timer. The table below compares the features of the advanced control, general purpose and basic timers.

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complementary outputs
Advanced control	TIM1, TIM8	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	3
General- purpose	TIM2, TIM5	32-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General- purpose	TIM3, TIM4	16-bit	Up, down, Up/down	Any integer between 1 and 65536	Yes	4	No
General- purpose	TIM15	16-bit	Up	Any integer between 1 and 65536	Yes	2	1
General- purpose	TIM16, TIM17	16-bit	Up	Any integer between 1 and 65536	Yes	1	1
Basic	TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Table 10. Timer feature comparison

#### 3.29.1 Advanced-control timer (TIM1, TIM8)

The advanced-control timer can each be seen as a three-phase PWM multiplexed on 6 channels. They have complementary PWM outputs with programmable inserted dead-

times. They can also be seen as complete general-purpose timers. The 4 independent channels can be used for:

- Input capture
- Output compare
- PWM generation (edge or center-aligned modes) with full modulation capability (0-100%)
- One-pulse mode output

In debug mode, the advanced-control timer counter can be frozen and the PWM outputs disabled to turn off any power switches driven by these outputs.

Many features are shared with those of the general-purpose TIMx timers (described in Section 3.29.2) using the same architecture, so the advanced-control timers can work together with the TIMx timers via the Timer Link feature for synchronization or event chaining.

# 3.29.2 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM15, TIM16, TIM17)

There are up to seven synchronizable general-purpose timers embedded in the STM32L4A6xG (see *Table 10* for differences). Each general-purpose timer can be used to generate PWM outputs, or act as a simple time base.

TIM2, TIM3, TIM4 and TIM5

They are full-featured general-purpose timers:

- TIM2 and TIM5 have a 32-bit auto-reload up/downcounter and 32-bit prescaler
- TIM3 and TIM4 have 16-bit auto-reload up/downcounter and 16-bit prescaler.

These timers feature 4 independent channels for input capture/output compare, PWM or one-pulse mode output. They can work together, or with the other general-purpose timers via the Timer Link feature for synchronization or event chaining.

The counters can be frozen in debug mode.

All have independent DMA request generation and support quadrature encoders.

TIM15, 16 and 17

They are general-purpose timers with mid-range features:

They have 16-bit auto-reload upcounters and 16-bit prescalers.

- TIM15 has 2 channels and 1 complementary channel
- TIM16 and TIM17 have 1 channel and 1 complementary channel

All channels can be used for input capture/output compare, PWM or one-pulse mode output.

The timers can work together via the Timer Link feature for synchronization or event chaining. The timers have independent DMA request generation.

The counters can be frozen in debug mode.

#### 3.29.3 Basic timers (TIM6 and TIM7)

The basic timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit timebases.



#### 3.29.4 Low-power timer (LPTIM1 and LPTIM2)

The devices embed two low-power timers. These timers have an independent clock and are running in Stop mode if they are clocked by LSE, LSI or an external clock. They are able to wakeup the system from Stop mode.

LPTIM1 is active in Stop 0, Stop 1 and Stop 2 modes.

LPTIM2 is active in Stop 0 and Stop 1 mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous/ one shot mode
- Selectable software/hardware input trigger
- Selectable clock source
  - Internal clock sources: LSE, LSI, HSI16 or APB clock
  - External clock source over LPTIM input (working even with no internal clock source running, used by pulse counter application).
- Programmable digital glitch filter
- Encoder mode (LPTIM1 only)

#### 3.29.5 Infrared interface (IRTIM)

The STM32L4A6xG includes one infrared interface (IRTIM). It can be used with an infrared LED to perform remote control functions. It uses TIM16 and TIM17 output channels to generate output signal waveforms on IR\_OUT pin.

#### 3.29.6 Independent watchdog (IWDG)

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC (LSI) and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

#### 3.29.7 System window watchdog (WWDG)

The window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.



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#### 3.29.8 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- A 24-bit down counter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0.
- Programmable clock source

#### 3.30 Real-time clock (RTC) and backup registers

The RTC is an independent BCD timer/counter. It supports the following features:

- Calendar with subsecond, seconds, minutes, hours (12 or 24 format), week day, date, month, year, in BCD (binary-coded decimal) format.
- Automatic correction for 28, 29 (leap year), 30, and 31 days of the month.
- Two programmable alarms.
- On-the-fly correction from 1 to 32767 RTC clock pulses. This can be used to synchronize it with a master clock.
- Reference clock detection: a more precise second source clock (50 or 60 Hz) can be used to enhance the calendar precision.
- Digital calibration circuit with 0.95 ppm resolution, to compensate for quartz crystal inaccuracy.
- Three anti-tamper detection pins with programmable filter.
- Timestamp feature which can be used to save the calendar content. This function can
  be triggered by an event on the timestamp pin, or by a tamper event, or by a switch to
  VBAT mode.
- 17-bit auto-reload wakeup timer (WUT) for periodic events with programmable resolution and period.

The RTC and the 32 backup registers are supplied through a switch that takes power either from the  $V_{DD}$  supply when present or from the VBAT pin.

The backup registers are 32-bit registers used to store 128 bytes of user application data when  $V_{DD}$  power is not present. They are not reset by a system or power reset, or when the device wakes up from Standby or Shutdown mode.

The RTC clock sources can be:

- A 32.768 kHz external crystal (LSE)
- An external resonator or oscillator (LSE)
- The internal low power RC oscillator (LSI, with typical frequency of 32 kHz)
- The high-speed external clock (HSE) divided by 32.

The RTC is functional in VBAT mode and in all low-power modes when it is clocked by the LSE. When clocked by the LSI, the RTC is not functional in VBAT mode, but is functional in all low-power modes except Shutdown mode.

All RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.



## 3.31 Inter-integrated circuit interface (I<sup>2</sup>C)

The device embeds four I2C. Refer to *Table 11: I2C implementation* for the features implementation.

The I<sup>2</sup>C bus interface handles communications between the microcontroller and the serial I<sup>2</sup>C bus. It controls all I<sup>2</sup>C bus-specific sequencing, protocol, arbitration and timing.

#### The I2C peripheral supports:

- I<sup>2</sup>C-bus specification and user manual rev. 5 compatibility:
  - Slave and master modes, multimaster capability
  - Standard-mode (Sm), with a bitrate up to 100 kbit/s
  - Fast-mode (Fm), with a bitrate up to 400 kbit/s
  - Fast-mode Plus (Fm+), with a bitrate up to 1 Mbit/s and 20 mA output drive I/Os
  - 7-bit and 10-bit addressing mode, multiple 7-bit slave addresses
  - Programmable setup and hold times
  - Optional clock stretching
- System Management Bus (SMBus) specification rev 2.0 compatibility:
  - Hardware PEC (Packet Error Checking) generation and verification with ACK control
  - Address resolution protocol (ARP) support
  - SMBus alert
- Power System Management Protocol (PMBus<sup>TM</sup>) specification rev 1.1 compatibility
- Independent clock: a choice of independent clock sources allowing the I2C communication speed to be independent from the PCLK reprogramming. Refer to Figure 5: Clock tree.
- Wakeup from Stop mode on address match
- Programmable analog and digital noise filters
- 1-byte buffer with DMA capability

Table 11. I2C implementation

I2C features <sup>(1)</sup>	I2C1	I2C2	I2C3	I2C4
Standard-mode (up to 100 kbit/s)	Χ	X	Х	X
Fast-mode (up to 400 kbit/s)	Х	Х	Х	Х
Fast-mode Plus with 20mA output drive I/Os (up to 1 Mbit/s)	Х	Х	Х	Х
Programmable analog and digital noise filters	Х	Х	Х	Х
SMBus/PMBus hardware support	Х	Х	Х	Х
Independent clock	Х	Х	Х	Х
Wakeup from Stop0, Stop 1 mode on address match	Х	Х	Х	Х
Wakeup from Stop 2 mode on address match	-	-	Х	-

1. X: supported



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# 3.32 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32L4A6xG devices have three embedded universal synchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4, UART5).

These interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. They provide hardware management of the CTS and RTS signals, and RS485 Driver Enable. They are able to communicate at speeds of up to 10Mbit/s.

USART1, USART2 and USART3 also provide Smart Card mode (ISO 7816 compliant) and SPI-like communication capability.

All USART have a clock domain independent from the CPU clock, allowing the USARTx (x=1,2,3,4,5) to wake up the MCU from Stop mode using baudrates up to 204 Kbaud. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- · Any received data frame
- A specific programmed data frame

All USART interfaces can be served by the DMA controller.

Table 12. STM32L4A6xG USART/UART/LPUART features

USART modes/features <sup>(1)</sup>	USART1	USART2	USART3	UART4	UART5	LPUART1
Hardware flow control for modem	Х	Х	Х	Х	Х	Х
Continuous communication using DMA	Х	Х	Х	Х	Х	Х
Multiprocessor communication	Х	Х	Х	Х	Х	Х
Synchronous mode	Х	Х	Х	-	-	-
Smartcard mode	Х	Х	Х	-	-	-
Single-wire half-duplex communication	Х	Х	Х	Х	Х	Х
IrDA SIR ENDEC block	Х	Х	Х	Х	Х	-
LIN mode	Х	Х	Х	Х	Х	-
Dual clock domain	Х	Х	Х	Х	Х	Х
Wakeup from Stop 0 / Stop 1 modes	Х	Х	Х	Х	Х	Х
Wakeup from Stop 2 mode	-	-	-	-	-	Х
Receiver timeout interrupt	Х	Х	Х	Х	Х	-
Modbus communication	Х	Х	Х	Х	Х	-
Auto baud rate detection		)	X (4 modes	)		-
Driver Enable	Х	Х	Х	Х	Х	Х
LPUART/USART data length			7, 8 ar	nd 9 bits		

<sup>1.</sup> X = supported.

# 3.33 Low-power universal asynchronous receiver transmitter (LPUART)

The device embeds one Low-Power UART. The LPUART supports asynchronous serial communication with minimum power consumption. It supports half duplex single wire communication and modem operations (CTS/RTS). It allows multiprocessor communication.

The LPUART has a clock domain independent from the CPU clock, and can wakeup the system from Stop mode using baudrates up to 220 Kbaud. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- Any received data frame
- A specific programmed data frame

Only a 32.768 kHz clock (LSE) is needed to allow LPUART communication up to 9600 baud. Therefore, even in Stop mode, the LPUART can wait for an incoming frame while having an extremely low energy consumption. Higher speed clock can be used to reach higher baudrates.

LPUART interface can be served by the DMA controller.



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#### 3.34 Serial peripheral interface (SPI)

Three SPI interfaces allow communication up to 40 Mbits/s in master and up to 24 Mbits/s slave modes, in half-duplex, full-duplex and simplex modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits. The SPI interfaces support NSS pulse mode, TI mode and Hardware CRC calculation.

All SPI interfaces can be served by the DMA controller.

#### 3.35 Serial audio interfaces (SAI)

The device embeds 2 SAI. Refer to *Table 13: SAI implementation* for the features implementation. The SAI bus interface handles communications between the microcontroller and the serial audio protocol.

The SAI peripheral supports:

- Two independent audio sub-blocks which can be transmitters or receivers with their respective FIFO.
- 8-word integrated FIFOs for each audio sub-block.
- Synchronous or asynchronous mode between the audio sub-blocks.
- Master or slave configuration independent for both audio sub-blocks.
- Clock generator for each audio block to target independent audio frequency sampling when both audio sub-blocks are configured in master mode.
- Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit.
- Peripheral with large configurability and flexibility allowing to target as example the following audio protocol: I2S, LSB or MSB-justified, PCM/DSP, TDM, AC'97 and SPDIF out.
- Up to 16 slots available with configurable size and with the possibility to select which
  ones are active in the audio frame.
- Number of bits by frame may be configurable.
- Frame synchronization active level configurable (offset, bit length, level).
- First active bit position in the slot is configurable.
- LSB first or MSB first for data transfer.
- Mute mode.
- Stereo/Mono audio frame capability.
- Communication clock strobing edge configurable (SCK).
- Error flags with associated interrupts if enabled respectively.
  - Overrun and underrun detection.
  - Anticipated frame synchronization signal detection in slave mode.
  - Late frame synchronization signal detection in slave mode.
  - Codec not ready for the AC'97 mode in reception.
- Interruption sources when enabled:
  - Errors.
  - FIFO requests.
- DMA interface with 2 dedicated channels to handle access to the dedicated integrated FIFO of each SAI audio sub-block.



SAI features <sup>(1)</sup>	SAI1	SAI2
I2S, LSB or MSB-justified, PCM/DSP, TDM, AC'97	X	X
Mute mode	Х	Х
Stereo/Mono audio frame capability.	X	Х
16 slots	Х	Х
Data size configurable: 8-, 10-, 16-, 20-, 24-, 32-bit	Х	Х
FIFO Size	X (8 Word)	X (8 Word)
SPDIF	Х	Х

Table 13. SAI implementation

## 3.36 Single wire protocol master interface (SWPMI)

The Single wire protocol master interface (SWPMI) is the master interface corresponding to the Contactless Frontend (CLF) defined in the ETSI TS 102 613 technical specification. The main features are:

- full-duplex communication mode
- automatic SWP bus state management (active, suspend, resume)
- configurable bitrate up to 2 Mbit/s
- automatic SOF, EOF and CRC handling

SWPMI can be served by the DMA controller.

## 3.37 Controller area network (CAN)

The two CANs are compliant with the 2.0A and B (active) specifications with a bit rate up to 1Mbit/s. They can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Each CAN has three transmit mailboxes, two receive FIFOS with 3 stages and 28 shared scalable filter banks (all of them can be used even if one CAN is used). 256 bytes of SRAM are allocated for each CAN.

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<sup>1.</sup> X: supported

Dual CAN peripheral configuration is available. The CAN peripheral supports:

- Supports CAN protocol version 2.0 A, B Active
- Bit rates up to 1 Mbit/s
- Transmission
  - Three transmit mailboxes
  - Configurable transmit priority
- Reception
  - Two receive FIFOs with three stages
  - Scalable filter banks: 28 filter banks shared between CAN1 and CAN2
  - Identifier list feature
  - Configurable FIFO overrun
- Time-triggered communication option
  - Disable automatic retransmission mode
  - 16-bit free running timer
  - Time Stamp sent in last two data bytes
- Management
  - Maskable interrupts
  - Software-efficient mailbox mapping at a unique address space

# 3.38 Secure digital input/output and MultiMediaCards Interface (SDMMC)

The card host interface (SDMMC) provides an interface between the APB peripheral bus and MultiMediaCards (MMCs), SD memory cards and SDIO cards.

The SDMMC features include the following:

- Full compliance with MultiMediaCard System Specification Version 4.2. Card support for three different databus modes: 1-bit (default), 4-bit and 8-bit
- Full compatibility with previous versions of MultiMediaCards (forward compatibility)
- Full compliance with SD Memory Card Specifications Version 2.0
- Full compliance with SD I/O Card Specification Version 2.0: card support for two different databus modes: 1-bit (default) and 4-bit
- Data transfer up to 48 MHz for the 8 bit mode
- Data write and read with DMA capability

## 3.39 Universal serial bus on-the-go full-speed (OTG\_FS)

The devices embed an USB OTG full-speed device/host/OTG peripheral with integrated transceivers. The USB OTG FS peripheral is compliant with the USB 2.0 specification and with the OTG 2.0 specification. It has software-configurable endpoint setting and supports suspend/resume. The USB OTG controller requires a dedicated 48 MHz clock that can be provided by the internal multispeed oscillator (MSI) automatically trimmed by 32.768 kHz external oscillator (LSE). This allows to use the USB device without external high speed crystal (HSE).



The synchronization for this oscillator can also be taken from the USB data stream itself (SOF signalization) which allows crystal less operation.

The major features are:

- Combined Rx and Tx FIFO size of 1.25 KB with dynamic FIFO sizing
- Supports the session request protocol (SRP) and host negotiation protocol (HNP)
- 1 bidirectional control endpoint + 5 IN endpoints + 5 OUT endpoints
- 12 host channels with periodic OUT support
- HNP/SNP/IP inside (no need for any external resistor)
- USB 2.0 LPM (Link Power Management) support
- Battery Charging Specification Revision 1.2 support
- Internal FS OTG PHY support

For OTG/Host modes, a power switch is needed in case bus-powered devices are connected.

## 3.40 Clock recovery system (CRS)

The STM32L4A6xG devices embed a special block which allows automatic trimming of the internal 48 MHz oscillator to guarantee its optimal accuracy over the whole device operational range. This automatic trimming is based on the external synchronization signal, which could be either derived from USB SOF signalization, from LSE oscillator, from an external signal on CRS\_SYNC pin or generated by user software. For faster lock-in during startup it is also possible to combine automatic trimming with manual trimming action.

## 3.41 Flexible static memory controller (FSMC)

The Flexible static memory controller (FSMC) includes two memory controllers:

- The NOR/PSRAM memory controller
- The NAND/memory controller

This memory controller is also named Flexible memory controller (FMC).

The main features of the FMC controller are the following:

- Interface with static-memory mapped devices including:
  - Static random access memory (SRAM)
  - NOR Flash memory/OneNAND Flash memory
  - PSRAM (4 memory banks)
  - NAND Flash memory with ECC hardware to check up to 8 Kbyte of data
- 8-.16- bit data bus width
- Independent Chip Select control for each memory bank
- Independent configuration for each memory bank
- Write FIFO
- The Maximum FMC\_CLK frequency for synchronous accesses is HCLK/2.



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#### LCD parallel interface

The FMC can be configured to interface seamlessly with most graphic LCD controllers. It supports the Intel 8080 and Motorola 6800 modes, and is flexible enough to adapt to specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost effective graphic applications using LCD modules with embedded controllers or high performance solutions using external controllers with dedicated acceleration.

For WLCSP100 package, address lines [A18:A16] are missing versus other 100 pin packages, thus FMC provides only 2MB of addressable space, split into 64K blocks. The main usage of the FMC in this case is to drive external LCD interface.

## 3.42 Dual-flash Quad SPI memory interface (QUADSPI)

The Dual-flash Quad SPI is a specialized communication interface targeting single, dual or quad SPI flash memories. It can operate in any of the three following modes:

- Indirect mode: all the operations are performed using the QUADSPI registers
- Status polling mode: the external flash status register is periodically read and an interrupt can be generated in case of flag setting
- Memory-mapped mode: the external Flash is memory mapped and is seen by the system as if it were an internal memory

Both throughput and capacity can be increased two-fold using dual-flash mode, where two Quad SPI flash memories are accessed simultaneously.

The Dual-flash Quad SPI interface supports:

- Three functional modes: indirect, status-polling, and memory-mapped
- Dual-flash mode, where 8 bits can be sent/received simultaneously by accessing two flash memories in parallel.
- SDR and DDR support
- Fully programmable opcode for both indirect and memory mapped mode
- Fully programmable frame format for both indirect and memory mapped mode
- Each of the 5 following phases can be configured independently (enable, length, single/dual/quad communication)
  - Instruction phase
  - Address phase
  - Alternate bytes phase
  - Dummy cycles phase
  - Data phase
- Integrated FIFO for reception and transmission
- 8, 16, and 32-bit data accesses are allowed
- DMA channel for indirect mode operations
- Programmable masking for external flash flag management
- Timeout management
- Interrupt generation on FIFO threshold, timeout, status match, operation complete, and access error



#### 3.43 Development support

#### 3.43.1 Serial wire JTAG debug port (SWJ-DP)

The Arm<sup>®</sup> SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

#### 3.43.2 Embedded Trace Macrocell™

The Arm<sup>®</sup> Embedded Trace Macrocell™ provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32L4A6xG through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. Real-time instruction and data flow activity be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell™ operates with third party debugger software tools.

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## 4 Pinouts and pin description

Figure 7. STM32L4A6Ax UFBGA169 pinout<sup>(1)</sup>

				9	. •			0, .	. СС р.				
	1	2	3	4	5	6	7	8	9	10	11	12	13
A	PI10	PH2	VDD	PE0	PB4	PB3	vss	VDD	PA15	PA14	PA13	P10	PH14
В	PI9	PI7	vss	PE1	PB5	VDDIO2	PG9	PD0	P16	PI2	PI1	PH15	PH12
С	VDD	vss	PI11	PB8	PB6	PG15	PD4	PD1	PH13	PI3	PI8	vss	VDD
D	PE4	PE3	PE2	PB9	PB7	PG10	PD5	PD2	PC10	PI4	PH9	PH7	PA12
E	PC13	VBAT	PE6	PE5	РН3-ВООТ0	PG11	PD6	PD3	PC11	PI5	PH6	VDDUSB	PA11
F	PC14- OSC32_IN	vss	PF2	PF1	PF0	PG12	PD7	PC12	PA10	PA9	PC6	VDDIO2	vss
G	PC15- OSC32_OUT	VDD	PF3	PF4	PF5	PG14	PG13	PA8	PC9	PC8	PG6	PC7	VDD
н	PH0-OSC_IN	vss	NRST	PF10	PC4	PG1	PE10	PB11	PG8	PG7	PD15	vss	VDD
J	PH1- OSC_OUT	PC0	PC1	PC2	PC5	PG0	PE9	PE15	PG5	PG4	PG3	PG2	PD10
к	PC3	VSSA/VREF-	PA0	PA5	PB0	PF15	PE8	PE14	PH4	PD14	PD12	PD11	PD13
L	VREF+	VDDA	PA4	PA7	PB1	PF14	PE7	PE13	PH5	PD9	PD8	VDD	vss
М	OPAMP1_VI NM	PA3	vss	PA6	PF11	PF13	vss	PE12	PH10	PH11	vss	PB15	PB14
N	PA2	PA1	VDD	OPAMP2_VI NM	PB2	PF12	VDD	PE11	PB10	PH8	VDD	PB12	PB13
				•			•					•	MSv38036

1. The above figure shows the package top view.

Figure 8. STM32L4A6Ax, external SMPS device, UFBGA169 pinout<sup>(1)</sup>

	1	2	3	4	5	6	7	8	9	10	11	12	13
A	PI10	PH2	VDD	PE0	PB4	PB3	vss	VDD	PA15	PA14	PA13	PI0	PH14
В	PI9	PI7	vss	PE1	PB5	VDDIO2	PG9	PD0	PI6	PI2	PI1	PH15	PH12
С	VDD	vss	PI11	PB8	PB6	VDD12	PD4	PD1	PH13	PI3	PI8	vss	VDD
D	PE4	PE3	PE2	PB9	PB7	PG10	PD5	PD2	PC10	PI4	PH9	PH7	PA12
E	PC13	VBAT	PE6	PE5	РН3-ВООТ0	PG11	PD6	PD3	PC11	PI5	PH6	VDDUSB	PA11
F	PC14- OSC32_IN	vss	PF2	PF1	PF0	PG12	PD7	PC12	PA10	PA9	PC6	VDDIO2	vss
G	PC15- OSC32_OUT	VDD	PF3	PF4	PF5	PG14	PG13	PA8	PC9	PC8	PG6	PC7	VDD
н	PH0-OSC_IN	vss	NRST	PF10	PC4	PG1	PE10	PB11	PG8	PG7	PD15	vss	VDD
J	PH1- OSC_OUT	PC0	PC1	PC2	PC5	PG0	PE9	PE15	PG5	PG4	PG3	PG2	PD10
к	PC3	VSSA/VREF-	PA0	PA5	PB0	PF15	PE8	PE14	PH4	PD14	PD12	PD11	PD13
L	VREF+	VDDA	PA4	PA7	PB1	PF14	PE7	PE13	PH5	PD9	PD8	VDD	vss
м	OPAMP1_VI NM	PA3	vss	PA6	PF11	PF13	vss	PE12	PH10	VDD12	vss	PB15	PB14
N	PA2	PA1	VDD	OPAMP2_VI	PB2	PF12	VDD	PE11	PB10	PH8	VDD	PB12	PB13

1. The above figure shows the package top view.



PE2 🗖 1 108 🗖 VDD PE3 🗌 2 107 🗖 VSS PE4 🖂 3 106 VDDUSB PE5 🗌 4 105 🗖 PA13 PE6 🗖 5 104 PA12 103 PA11 VBAT ☐ 6 PC13 🗖 7 102 PA10 101 PA9 100 PA8 PC15-OSC32\_OUT 9 99 🗖 PC9 98 PC8 97 PC7 PF2 🔲 12 PF3 🗖 13 96 🗖 PC6 95 VDDIO2 94 VSS PF4 🗖 14 PF5 🗖 15 VSS 🗖 16 93 🗖 PG8 92 PG7 91 PG6 VDD 🗖 17 PF6 🖂 18 LQFP144 PF7 🗖 19 90 🗖 PG5 89 PG4 88 PG3 PF8 🗖 20 PF9 🗖 21 PF10 🗖 22 87 PG2 PH0-OSC\_IN 23 86 PD15 PH1-OSC\_OUT 24 85 🗖 PD14 84 🗖 VDD NRST 🗌 25 PC0 🗆 26 83 VSS 82 PD13 PC1 🔀 27 PC2 🗖 28 81 PD12 80 🏻 PD11 PC3 🗆 29 VSSA 🖂 30 79 🗖 PD10 VREF- 🖂 31 78 PD9 VREF+ ☐ 32 77 🏻 PD8 VDDA 🖂 33 76 ☐ PB15 PA0 34 75 🗖 PB14 74 🏻 PB13 PA2 🖂 36 73 PB12 PA3 (VSS C) 38 (VVD C) 39 (VVD C) 44 (VVD C) MSv38033V4

Figure 9. STM32L4A6Zx LQFP144 pinout<sup>(1)</sup>



108 🗖 VDD PE2 🔲 1 PE3 🗌 2 107 🗀 VSS 106 VDDUSB 105 PA13 PF4 □ 3 PE5 🗌 4 PE6 🗆 5 104 🗖 PA12 VBAT ☐ 6 103 PA11 102 PA10 PC13 🔲 7 PC14-OSC32\_IN 8 101 🗀 PA9 PC15-OSC32\_OUT 🗍 9 100 PA8 99 PC9 100 PF0 🛮 10 PF1 🗖 11 98 🗖 PC8 PF2 🔲 12 97 PC7 PF3 🗖 13 96 PC6 95 🗖 VDDIO2 PF4 🔲 14 PF5 🗖 15 94 VSS VSS | 16 93 PG8 92 🏻 PG7 VDD 🔲 17 PF6 🗖 18 91 \_ PG6 LQFP144 PF7 🗍 19 90 🔓 PG5 PF8 🗌 20 89 🗖 PG4 88 PG3 87 PG2 PF9 🗖 21 PF10 🔲 22 PH0-OSC\_IN 23 86 🗖 PD15 85 PD14 84 VDD PH1-OSC OUT 24 NRST 🔲 25 PC0 🗖 26 83 🗖 VSS PC1 27 82 PD13 81 PD12 PC3 🗆 29 80 D PD11 79 🏻 PD10 VSSA ☐ 30 DPD9 VREF- 🔲 31 78 VREF+ ☐ 32 77 PD8 76 🏻 PB15 VDDA 🖂 33 PA0 🛮 34 75 PB14 74 PB13 PA1 🖂 35 PA2 🖂 36 73 PB12 

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Figure 10. STM32L4A6Zx, external SMPS device, LQFP144 pinout<sup>(1)</sup>

Figure 11. STM32L4A6Qx UFBGA132 ballout<sup>(1)</sup>

			iguic	11. 31	WIOZE	7/10/0/	COLD	3A 132	Dano	at.			
	1	2	3	4	5	6	7	8	9	10	11	12	
A	PE3	PE1	PB8	РН3-ВООТ0	PD7	PD5	PB4	PB3	PA15	PA14	PA13	PA12	
В	PE4	PE2	PB9	PB7	PB6	PD6	PD4	PD3	PD1	PC12	PC10	PA11	
С	PC13	PE5	PE0	VDD	PB5	PG14	PG13	PD2	PD0	PC11	VDDUSB	PA10	
D	PC14- OSC32_IN	PE6	vss	PF2	PF1	PF0	PG12	PG10	PG9	PA9	PA8	PC9	
E	PC15- OSC32_OUT	VBAT	vss	PF3					PG5	PC8	PC7	PC6	
F	PH0-OSC_IN	vss	PF4	PF5		vss	vss		PG3	PG4	vss	vss	
G	PH1- OSC_OUT	VDD	PG11	PG6		VDD	VDDIO2		PG1	PG2	VDD	VDD	
н	PC0	NRST	VDD	PG7					PG0	PD15	PD14	PD13	
J	VSSA/VREF-	PC1	PC2	PA4	PA7	PG8	PF12	PF14	PF15	PD12	PD11	PD10	
К	PG15	PC3	PA2	PA5	PC4	PF11	PF13	PD9	PD8	PB15	PB14	PB13	
L	VREF+	PA0	PA3	PA6	PC5	PB2	PE8	PE10	PE12	PB10	PB11	PB12	
М	VDDA	PA1	OPAMP1_ VINM	OPAMP2_ VINM	PB0	PB1	PE7	PE9	PE11	PE13	PE14	PE15	
												MSv3	88035V

Figure 12. STM32L4A6Qx, external SMPS device, UFBGA132 ballout

1 2 3 4 5 6 7 8 9 10 11 12  A PE3 PE1 PB8 PH3-BOOT0 PD7 PD5 PB4 PB3 PA15 PA14 PA13 PA12  B PE4 PE2 PB9 PB7 PB6 PD6 PD4 PD3 PD1 PC12 PC10 PA11  C PC13 PE5 PE0 VDD PB5 VDD12 PG13 PD2 PD0 PC11 VDDUSB PA10  D PC14-OSC32_N PE6 VSS PF2 PF1 PF0 PG12 PG10 PG9 PA9 PA8 PC9  E PC15-OSC32_OUT VBAT VSS PF3 PF3 VSS VSS PG3 PG4 VSS VSS  G PH0-OSC_IN VSS PF4 PF5 VSS VSS PG3 PG4 VSS VSS
B PE4 PE2 PB9 PB7 PB6 PD6 PD4 PD3 PD1 PC12 PC10 PA11  C PC13 PE5 PE0 VDD PB5 VDD12 PG13 PD2 PD0 PC11 VDDUSB PA10  D PC14- OSC32_IN PE6 VSS PF2 PF1 PF0 PG12 PG10 PG9 PA9 PA8 PC9  E PC15- OSC32_OUT VBAT VSS PF3 PG5 PC8 PC7 PC6  F PH0-OSC_IN VSS PF4 PF5 VSS VSS PG3 PG4 VSS VSS
C PC13 PE5 PE0 VDD PB5 VDD12 PG13 PD2 PD0 PC11 VDDUSB PA10 D PC14- OSC32_IN PE6 VSS PF2 PF1 PF0 PG12 PG10 PG9 PA9 PA8 PC9 E PC15- OSC32_OUT VBAT VSS PF3 F PH0-OSC_IN VSS PF4 PF5 VSS VSS PG3 PG4 VSS VSS
D
E
F PH0-OSC_IN VSS PF4 PF5 VSS VSS PG3 PG4 VSS VSS
PH1- 122 224 224 224 225 225 225 225 225 225 2
G PH1- VDD PG11 PG6 VDD VDDI02 PG1 PG2 VDD VDD
G OSC_OUT VDD PG11 PG6 VDD VDDIO2 PG1 PG2 VDD VDD
H PC0 NRST VDD PG7 PD15 PD14 PD13
J VSSA/VREF- PC1 PC2 PA4 PA7 PG8 PF12 PF14 PF15 PD12 PD11 PD10
K PG15 PC3 PA2 PA5 PC4 PF11 PF13 PD9 PD8 PB15 PB14 PB13
L VREF+ PA0 PA3 PA6 PC5 PB2 PE8 PE10 PE12 PB10 VDD12 PB12
M VDDA PA1 OPAMP1_VI OPAMP2_VI PB0 PB1 PE7 PE9 PE11 PE13 PE14 PE15
N

1. The above figure shows the package top view.



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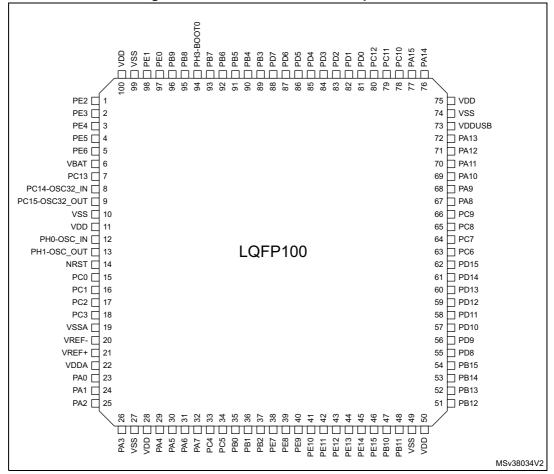


Figure 13. STM32L4A6Vx LQFP100 pinout<sup>(1)</sup>



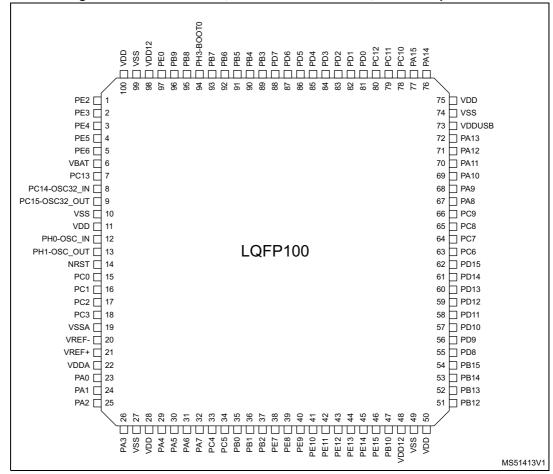


Figure 14. STM32L4A6Vx, external SMPS device, LQFP100 pinout<sup>(1)</sup>

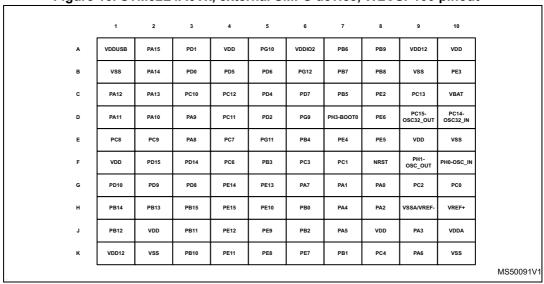


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Figure 15. STM32L4A6Vx WLCSP100 pinout<sup>(1)</sup>

			94.0			.,		. <b></b>		
	1	2	3	4	5	6	7	8	9	10
Α	VDDUSB	PA15	PD1	VDD	PG10	VDDIO2	PB6	PB9	vss	VDD
В	vss	PA14	PD0	PD4	PG9	PG12	PB5	PB8	PE2	PE3
С	PA12	PA13	PC11	PC12	PD7	PB3	PB4	PE4	PC13	VBAT
D	PA11	PA10	PA9	PC10	PD6	PG11	PB7	PE5	vss	PC14- OSC32_IN
E	PC8	PC9	PA8	PD2	PD5	РН3-ВООТ0	PE6	NRST	VDD	PC15- OSC32_OUT
F	VDD	PC6	PC7	PD15	PB2	PA4	PC3	PC1	PC0	PH0-OSC_IN
G	PD10	PD9	PD14	PE13	PE12	PA5	VREF+	VREF-	PA0	PH1- OSC_OUT
н	PB15	PB14	PD8	PE15	PE10	PC4	PA2	PA1	VSSA/VREF-	PC2
J	PB12	PB13	PB11	PE14	PE9	PB0	PA7	VDD	PA3	VDDA
к	VDD	vss	PB10	PE11	PE8	PE7	PB1	PC5	PA6	vss

Figure 16. STM32L4A6Vx, external SMPS device, WLCSP100 pinout<sup>(1)</sup>



1. The above figure shows the package top view.

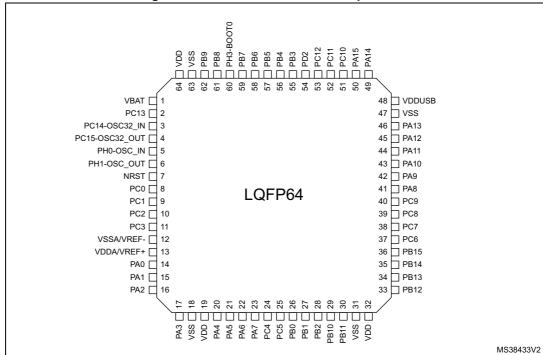


Figure 17. STM32L4A6Rx LQFP64 pinout<sup>(1)</sup>

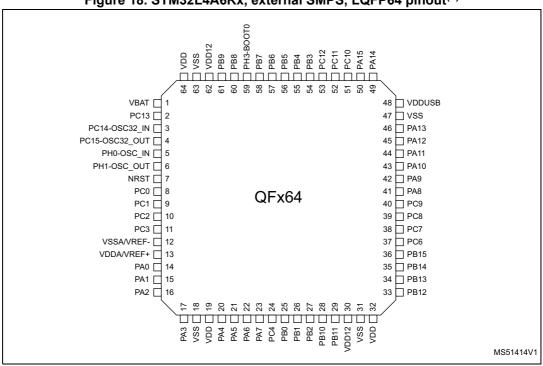


Figure 18. STM32L4A6Rx, external SMPS, LQFP64 pinout<sup>(1)</sup>

1. The above figure shows the package top view.



Table 14. Legend/abbreviations used in the pinout table

Na	me	Abbreviation	Definition								
Pin r	name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name									
		S	Supply pin								
Pin	type	I	Input only pin								
		I/O	Input / output pin								
		FT	5 V tolerant I/O								
		TT	3.6 V tolerant I/O								
		RST	Bidirectional reset pin with embedded weak pull-up resistor								
		Option for TT or FT I/Os									
I/O str	ructure	_f <sup>(1)</sup>	I/O, Fm+ capable								
		_l <sup>(2)</sup>	I/O, with LCD function supplied by V <sub>LCD</sub>								
		_u <sup>(3)</sup>	I/O, with USB function supplied by V <sub>DDUSB</sub>								
		_a <sup>(4)</sup>	I/O, with Analog switch function supplied by V <sub>DDA</sub>								
		_s <sup>(5)</sup>	I/O supplied only by V <sub>DDIO2</sub>								
Notes		Unless otherwise specified by a note, all I/Os are set as analog inputs during and after reset.									
Pin functions	Alternate functions	Leunctions selected through GPIOx AER registers									
	Additional functions	Functions directly selected/er	nabled through peripheral registers								

<sup>1.</sup> The related I/O structures in *Table 15* are: FT\_f, FT\_fa, FT\_fl, FT\_fla.

<sup>2.</sup> The related I/O structures in *Table 15* are: FT\_I, FT\_fl, FT\_lu.

<sup>3.</sup> The related I/O structures in *Table 15* are: FT\_u, FT\_lu.

<sup>4.</sup> The related I/O structures in *Table 15* are: FT\_a, FT\_la, FT\_fa, FT\_fla, TT\_a, TT\_la.

<sup>5.</sup> The related I/O structures in *Table 15* are: FT\_s, FT\_fs.



Table 15. STM32L4A6xG pin definitions

Pin Number															Pin functions		
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	-	-	-	-	-	-	СЗ	C3	PI11	I/O	FT	-	EVENTOUT	-
-	-	В9	C8	1	1	B2	B2	1	1	D3	D3	PE2	I/O	FT_I	-	TRACECK, TIM3_ETR, TSC_G7_IO1, LCD_SEG38, FMC_A23, SAI1_MCLK_A, EVENTOUT	-
-	-	B10	B10	2	2	A1	A1	2	2	D2	D2	PE3	I/O	FT_I	-	TRACED0, TIM3_CH1, TSC_G7_IO2, LCD_SEG39, FMC_A19, SAI1_SD_B, EVENTOUT	-
-	-	C8	E7	3	3	B1	B1	3	3	D1	D1	PE4	I/O	FT	-	TRACED1, TIM3_CH2, DFSDM1_DATIN3, TSC_G7_IO3, DCMI_D4, FMC_A20, SAI1_FS_A, EVENTOUT	-
-	-	D8	E8	4	4	C2	C2	4	4	E4	E4	PE5	I/O	FT	-	TRACED2, TIM3_CH3, DFSDM1_CKIN3, TSC_G7_IO4, DCMI_D6, FMC_A21, SAI1_SCK_A, EVENTOUT	-
-	-	E7	D8	5	5	D2	D2	5	5	E3	E3	PE6	I/O	FT	-	TRACED3, TIM3_CH4, DCMI_D7, FMC_A22, SAI1_SD_A, EVENTOUT	RTC_TAMP3/WKUP3
1	1	C10	C10	6	6	E2	E2	6	6	E2	E2	VBAT	S	-	-	-	-
2	2	C9	C9	7	7	C1	C1	7	7	E1	E1	PC13	I/O	FT	(1) (2)	EVENTOUT	RTC_TAMP1/RTC_TS/R TC_OUT/WKUP2

Pinouts and pin description

Table 15. STM32L4A6xG pin definitions (continued)

	Pin Number														Pin functions		
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
3	3	D10	D10	8	8	D1	D1	8	8	F1	F1	PC14- OSC32_IN (PC14)	I/O	FT	(1) (2)	EVENTOUT	OSC32_IN
4	4	E10	D9	9	9	E1	E1	9	9	G1	G1	PC15- OSC32_OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_OUT
-	-	-	-	1	-	D6	D6	10	10	F5	F5	PF0	I/O	FT_f	-	I2C2_SDA, FMC_A0, EVENTOUT	-
-	-	-	-	-	-	D5	D5	11	11	F4	F4	PF1	I/O	FT_f	-	I2C2_SCL, FMC_A1, EVENTOUT	-
-	-	-	-	-	-	D4	D4	12	12	F3	F3	PF2	I/O	FT	-	I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	-	-	-	-	E4	E4	13	13	G3	G3	PF3	I/O	FT_a	-	FMC_A3, EVENTOUT	ADC3_IN6
-	-	-	-	-	-	F3	F3	14	14	G4	G4	PF4	I/O	FT_a	-	FMC_A4, EVENTOUT	ADC3_IN7
-	-	-	-	-	-	F4	F4	15	15	G5	G5	PF5	I/O	FT_a	-	FMC_A5, EVENTOUT	ADC3_IN8
-	-	D9	E10	10	10	F2	F2	16	16	F2	F2	VSS	S	-	ı	-	-
-	-	E9	E9	11	11	G2	G2	17	17	G2	G2	VDD	S	-	1	-	-
-	-	-	-	-	-	-	-	18	18	-	-	PF6	I/O	FT_a	-	TIM5_ETR, TIM5_CH1, QUADSPI_BK1_IO3, SAI1_SD_B, EVENTOUT	ADC3_IN9





					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	-	-	-	-	19	19	-	-	PF7	I/O	FT_a	-	TIM5_CH2, QUADSPI_BK1_IO2, SAI1_MCLK_B, EVENTOUT	ADC3_IN10
-	-	-	-	-	-	-	-	20	20	-	-	PF8	I/O	FT_a	-	TIM5_CH3, QUADSPI_BK1_IO0, SAI1_SCK_B, EVENTOUT	ADC3_IN11
-	-	-	-	-	-	-	-	21	21	-	-	PF9	I/O	FT_a	1	TIM5_CH4, QUADSPI_BK1_IO1, SAI1_FS_B, TIM15_CH1, EVENTOUT	ADC3_IN12
-	-	-	-	-	-	-	-	22	22	H4	H4	PF10	I/O	FT_a	-	QUADSPI_CLK, DCMI_D11, TIM15_CH2, EVENTOUT	ADC3_IN13
5	5	F10	F10	12	12	F1	F1	23	23	H1	H1	PH0-OSC_IN (PH0)	I/O	FT	1	EVENTOUT	OSC_IN
6	6	G10	F9	13	13	G1	G1	24	24	J1	J1	PH1- OSC_OUT (PH1)	I/O	FT	1	EVENTOUT	OSC_OUT
7	7	E8	F8	14	14	H2	H2	25	25	НЗ	НЗ	NRST	I/O	RST	-	-	-
8	8	F9	G10	15	15	H1	H1	26	26	J2	J2	PC0	I/O	FT_fla	-	LPTIM1_IN1, I2C4_SCL, I2C3_SCL, DFSDM1_DATIN4, LPUART1_RX, LCD_SEG18, LPTIM2_IN1, EVENTOUT	ADC123_IN1

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
9	9	F8	F7	16	16	J2	J2	27	27	J3	J3	PC1	I/O	FT_fla	-	TRACEDO, LPTIM1_OUT, I2C4_SDA, SPI2_MOSI, I2C3_SDA, DFSDM1_CKIN4, LPUART1_TX, QUADSPI_BK2_IO0, LCD_SEG19, SAI1_SD_A, EVENTOUT	ADC123_IN2
10	10	H10	G9	17	17	J3	J3	28	28	J4	J4	PC2	I/O	FT_la	1	LPTIM1_IN2, SPI2_MISO, DFSDM1_CKOUT, QUADSPI_BK2_IO1, LCD_SEG20, EVENTOUT	ADC123_IN3
11	11	F7	F6	18	18	K2	K2	29	29	K1	K1	PC3	I/O	FT_la	1	LPTIM1_ETR, SPI2_MOSI, QUADSPI_BK2_IO2, LCD_VLCD, SAI1_SD_A, LPTIM2_ETR, EVENTOUT	ADC123_IN4
12	12	Н9	Н9	19	19	J1	J1	30	30	K2	K2	VSSA/VREF-	S	-	-	-	-
-	-	G8	-	20	20	-	-	31	31	-	-	VREF-	S	-	1	-	-
_	-	G7	H10	21	21	L1	L1	32	32	L1	L1	VREF+	S	-	- 1	-	VREFBUF_OUT
-	-	J10	J10	22	22	M1	M1	33	33	L2	L2	VDDA	S	-	-	-	-



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Table 15. STM32L4A6xG pin definitions (continued)

					Pin N	lumbe						O pin dennin	Ì				nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
13	13	-	-	-	-	-	-	-	-	-	-	VDDA/VREF+	-	-	-	-	-
14	14	G9	G8	23	23	L2	L2	34	34	КЗ	K3	PA0	I/O	FT_a	-	TIM2_CH1, TIM5_CH1, TIM8_ETR, USART2_CTS, UART4_TX, SAI1_EXTCLK, TIM2_ETR, EVENTOUT	OPAMP1_VINP, ADC12_IN5, RTC_TAMP2/WKUP1
-	1	1	1	1	-	МЗ	М3	1	-	M1	M1	OPAMP1_ VINM	I	TT	-	-	-
15	15	H8	G7	24	24	M2	M2	35	35	N2	N2	PA1	I/O	FT_la	(3)	TIM2_CH2, TIM5_CH2, I2C1_SMBA, SPI1_SCK, USART2_RTS_DE, UART4_RX, LCD_SEG0, TIM15_CH1N, EVENTOUT	OPAMP1_VINM, ADC12_IN6
16	16	H7	Н8	25	25	КЗ	K3	36	36	N1	N1	PA2	I/O	FT_la	-	TIM2_CH3, TIM5_CH3, USART2_TX, LPUART1_TX, QUADSPI_BK1_NCS, LCD_SEG1, SAI2_EXTCLK, TIM15_CH1, EVENTOUT	ADC12_IN7, WKUP4/LSCO
17	17	J9	J9	26	26	L3	L3	37	37	M2	M2	PA3	I/O	TT_la	-	TIM2_CH4, TIM5_CH4, USART2_RX, LPUART1_RX, QUADSPI_CLK, LCD_SEG2, SAI1_MCLK_A, TIM15_CH2, EVENTOUT	OPAMP1_VOUT, ADC12_IN8

Table 15. STM32L4A6xG pin definitions (continued)

					Pin N	lumbe	r									Pin fu	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
18	18	K10	K10	27	27	E3	E3	38	38	H2	H2	VSS	S	-	-	-	-
19	19	J8	J8	28	28	НЗ	НЗ	39	39	G13	G13	VDD	S	-	-	-	-
20	20	F6	H7	29	29	J4	J4	40	40	L3	L3	PA4	I/O	TT_a	-	SPI1_NSS, SPI3_NSS, USART2_CK, DCMI_HSYNC, SAI1_FS_B, LPTIM2_OUT, EVENTOUT	ADC12_IN9, DAC1_OUT1
21	21	G6	J7	30	30	K4	K4	41	41	K4	K4	PA5	I/O	TT_a	-	TIM2_CH1, TIM2_ETR, TIM8_CH1N, SPI1_SCK, LPTIM2_ETR, EVENTOUT	ADC12_IN10, DAC1_OUT2
22	22	K9	K9	31	31	L4	L4	42	42	M4	M4	PA6	I/O	FT_la	-	TIM1_BKIN, TIM3_CH1, TIM8_BKIN, DCMI_PIXCLK, SPI1_MISO, USART3_CTS, LPUART1_CTS, QUADSPI_BK1_IO3, LCD_SEG3, TIM1_BKIN_COMP2, TIM8_BKIN_COMP2, TIM16_CH1, EVENTOUT	OPAMP2_VINP, ADC12_IN11
-	-	-	-	-	-	M4	M4	-	-	N4	N4	OPAMP2_VIN M	I	TT	-	-	-



					Pin N	lumbe	ŗ									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
23	23	J7	G6	32	32	J5	J5	43	43	L4	L4	PA7	I/O	FT_fla	(3)	TIM1_CH1N, TIM3_CH2, TIM8_CH1N, I2C3_SCL, SPI1_MOSI, QUADSPI_BK1_IO2, LCD_SEG4, TIM17_CH1, EVENTOUT	OPAMP2_VINM, ADC12_IN12
24	24	Н6	K8	33	33	K5	K5	44	44	H5	H5	PC4	I/O	FT_la	-	USART3_TX, QUADSPI_BK2_IO3, LCD_SEG22, EVENTOUT	COMP1_INM, ADC12_IN13
25	-	K8	-	34	34	L5	L5	45	45	J5	J5	PC5	I/O	FT_la	1	USART3_RX, LCD_SEG23, EVENTOUT	COMP1_INP, ADC12_IN14, WKUP5
26	25	J6	Н6	35	35	M5	M5	46	46	K5	K5	PB0	I/O	TT_la	-	TIM1_CH2N, TIM3_CH3, TIM8_CH2N, SPI1_NSS, USART3_CK, QUADSPI_BK1_IO1, LCD_SEG5, COMP1_OUT, SAI1_EXTCLK, EVENTOUT	OPAMP2_VOUT, ADC12_IN15
27	26	K7	K7	36	36	M6	M6	47	47	L5	L5	PB1	I/O	FT_la	-	TIM1_CH3N, TIM3_CH4, TIM8_CH3N, DFSDM1_DATIN0, USART3_RTS_DE, LPUART1_RTS_DE, QUADSPI_BK1_IO0, LCD_SEG6, LPTIM2_IN1, EVENTOUT	COMP1_INM, ADC12_IN16

78,								Т	able 1	15. ST	M32L	.4A6x	G pin definiti	ions (	continu	ıed)	)	
78/282						Pin N	lumbe	r									Pin fur	nctions
	LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
	28	27	F5	J6	37	37	L6	L6	48	48	N5	N5	PB2	I/O	FT_la	-	RTC_OUT, LPTIM1_OUT, I2C3_SMBA, DFSDM1_CKIN0, LCD_VLCD, EVENTOUT	COMP1_INP
	-	-	-	-	-	-	K6	K6	49	49	M5	M5	PF11	I/O	FT	-	DCMI_D12, EVENTOUT	-
DS115	-	-	-	-	-	-	J7	J7	50	50	N6	N6	PF12	I/O	FT	-	FMC_A6, EVENTOUT	-
DS11584 Rev 8	-	-	-	-	-	-	-	-	51	51	-	-	VSS	S	-	-	-	-
8	-	-	-	-	-	-	-	-	52	52	A8	A8	VDD	S	-	-	-	-
	-	-	-	-	-	-	K7	K7	53	53	M6	M6	PF13	I/O	FT	-	I2C4_SMBA, DFSDM1_DATIN6, FMC_A7, EVENTOUT	-
	-	-	-	-	-	-	J8	J8	54	54	L6	L6	PF14	I/O	FT_fa	-	I2C4_SCL, DFSDM1_CKIN6, TSC_G8_IO1, FMC_A8, EVENTOUT	-
	-	-	-	-	-	-	J9	J9	55	55	K6	K6	PF15	I/O	FT_fa	-	I2C4_SDA, TSC_G8_IO2, FMC_A9, EVENTOUT	-
	-	-	-	-	-	-	Н9	H9	56	56	J6	J6	PG0	I/O	FT	-	TSC_G8_IO3,FMC_A10, EVENTOUT	-

G9

G9

57

57

H6

H6

PG1

I/O

FT

TSC\_G8\_IO4, FMC\_A11, EVENTOUT





Table 15. STM32L4A6xG pin definitions (continued)

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	K6	K6	38	38	M7	M7	58	58	L7	L7	PE7	I/O	FT	1	TIM1_ETR, DFSDM1_DATIN2, FMC_D4, SAI1_SD_B, EVENTOUT	-
-	-	K5	K5	39	39	L7	L7	59	59	K7	K7	PE8	I/O	FT	-	TIM1_CH1N, DFSDM1_CKIN2, FMC_D5, SAI1_SCK_B, EVENTOUT	-
-	-	J5	J5	40	40	M8	M8	60	60	J7	J7	PE9	I/O	FT	-	TIM1_CH1, DFSDM1_CKOUT, FMC_D6, SAI1_FS_B, EVENTOUT	-
-	-	-	-	-	-	F6	F6	61	61	M7	M7	VSS	S	-	-	-	-
-	-	-	-	-	-	G6	G6	62	62	N7	N7	VDD	S	-	-	-	-
-	-	H5	H5	41	41	L8	L8	63	63	H7	H7	PE10	I/O	FT	-	TIM1_CH2N, DFSDM1_DATIN4, TSC_G5_IO1, QUADSPI_CLK, FMC_D7, SAI1_MCLK_B, EVENTOUT	-
-	-	K4	K4	42	42	М9	M9	64	64	N8	N8	PE11	I/O	FT	-	TIM1_CH2, DFSDM1_CKIN4, TSC_G5_IO2, QUADSPI_BK1_NCS, FMC_D8, EVENTOUT	-

							Т	able 1	5. ST	M32L	.4A6x	G pin definiti	ions (	continu	ued)		
					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	G5	J4	43	43	L9	L9	65	65	M8	M8	PE12	I/O	FT	-	TIM1_CH3N, SPI1_NSS, DFSDM1_DATIN5, TSC_G5_IO3, QUADSPI_BK1_IO0, FMC_D9, EVENTOUT	-
-	-	G4	G5	44	44	M10	M10	66	66	L8	L8	PE13	I/O	FT	-	TIM1_CH3, SPI1_SCK, DFSDM1_CKIN5, TSC_G5_IO4, QUADSPI_BK1_IO1, FMC_D10, EVENTOUT	-
-	-	J4	G4	45	45	M11	M11	67	67	K8	K8	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, TIM1_BKIN2_COMP2, SPI1_MISO, QUADSPI_BK1_IO2, FMC_D11, EVENTOUT	-
-	-	H4	H4	46	46	M12	M12	68	68	J8	J8	PE15	I/O	FT	-	TIM1_BKIN, TIM1_BKIN_COMP1, SPI1_MOSI, QUADSPI_BK1_IO3, FMC_D12, EVENTOUT	-
29	28	К3	КЗ	47	47	L10	L10	69	69	N9	N9	PB10	I/O	FT_fl	-	TIM2_CH3, I2C4_SCL, I2C2_SCL, SPI2_SCK, DFSDM1_DATIN7, USART3_TX, LPUART1_RX, TSC_SYNC, QUADSPI_CLK, LCD_SEG10, COMP1_OUT, SAI1_SCK_A, EVENTOUT	-



					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
30	29	J3	J3	48	-	L11	-	70	-	Н8	Н8	PB11	I/O	FT_fl	-	TIM2_CH4, I2C4_SDA, I2C2_SDA, DFSDM1_CKIN7, USART3_RX, LPUART1_TX, QUADSPI_BK1_NCS, LCD_SEG11, COMP2_OUT, EVENTOUT	-
-	30	ı	K1	1	48	-	L11	1	70	-	M10	VDD12	S	1	1	•	-
-	-	1	-	-	-	-	-	-	-	K9	K9	PH4	I/O	FT_f	-	I2C2_SCL, EVENTOUT	-
-	-	1	-	-	-	-	-	-	-	L9	L9	PH5	I/O	FT_f	-	I2C2_SDA, DCMI_PIXCLK, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	N10	N10	PH8	I/O	FT_f	-	I2C3_SDA, DCMI_HSYNC, EVENTOUT	-
-	-	1	-	-	-	-	-	-	-	М9	М9	PH10	I/O	FT	-	TIM5_CH1, DCMI_D1, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	M10	-	PH11	I/O	FT	-	TIM5_CH2, DCMI_D2, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	М3	М3	VSS	S	-	-	-	-
-	-	1	-	ı	-	-	-	-	1	N3	N3	VDD	S	-	1	-	-

Table 15. STM32L4A6xG	pin definitions	(continued)
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					Pin N	lumbe	r									Pin fui	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	-	-	-	-	-	-	M11	M11	VSS	S	-	-	-	-
31	31	K2	K2	49	49	F12	F12	71	71	L13	L13	VSS	S	-	-	-	-
32	32	K1	J2	50	50	G12	G12	72	72	L12	L12	VDD	S	-	-	-	-
-	-	-	-	-	-	-	-	-	-	N11	N11	VDD	S	-	-	-	-
33	33	J1	J1	51	51	L12	L12	73	73	N12	N12	PB12	I/O	FT_I	-	TIM1_BKIN, TIM1_BKIN_COMP2, I2C2_SMBA, SPI2_NSS, DFSDM1_DATIN1, USART3_CK, LPUART1_RTS_DE, TSC_G1_IO1, CAN2_RX, LCD_SEG12, SWPMI1_IO, SAI2_FS_A, TIM15_BKIN, EVENTOUT	-



					Pin N	lumbe						G pin dennin	(		,	Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
34	34	J2	H2	52	52	K12	K12	74	74	N13	N13	PB13	I/O	FT_fl	-	TIM1_CH1N, I2C2_SCL, SPI2_SCK, DFSDM1_CKIN1, USART3_CTS, LPUART1_CTS, TSC_G1_IO2, CAN2_TX, LCD_SEG13, SWPMI1_TX, SAI2_SCK_A, TIM15_CH1N, EVENTOUT	-
35	35	H2	H1	53	53	K11	K11	75	75	M13	M13	PB14	I/O	FT_fl	-	TIM1_CH2N, TIM8_CH2N, I2C2_SDA, SPI2_MISO, DFSDM1_DATIN2, USART3_RTS_DE, TSC_G1_IO3, LCD_SEG14, SWPMI1_RX, SAI2_MCLK_A, TIM15_CH1, EVENTOUT	-
36	36	Н1	НЗ	54	54	K10	K10	76	76	M12	M12	PB15	I/O	FT_I	-	RTC_REFIN, TIM1_CH3N, TIM8_CH3N, SPI2_MOSI, DFSDM1_CKIN2, TSC_G1_IO4, LCD_SEG15, SWPMI1_SUSPEND, SAI2_SD_A, TIM15_CH2, EVENTOUT	-

Table 15. STM32L4A6xG pin definitions (continued)

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	НЗ	G3	55	55	K9	K9	77	77	L11	L11	PD8	I/O	FT_I	-	USART3_TX, DCMI_HSYNC, LCD_SEG28, FMC_D13, EVENTOUT	-
-	-	G2	G2	56	56	K8	K8	78	78	L10	L10	PD9	I/O	FT_I	-	USART3_RX, DCMI_PIXCLK, LCD_SEG29, FMC_D14, SAI2_MCLK_A, EVENTOUT	-
-	-	G1	G1	57	57	J12	J12	79	79	J13	J13	PD10	I/O	FT_I	-	USART3_CK, TSC_G6_IO1, LCD_SEG30, FMC_D15, SAI2_SCK_A, EVENTOUT	-
-	-	-	-	58	58	J11	J11	80	80	K12	K12	PD11	I/O	FT_I	-	I2C4_SMBA, USART3_CTS, TSC_G6_IO2, LCD_SEG31, FMC_A16, SAI2_SD_A, LPTIM2_ETR, EVENTOUT	-
-	-	-	-	59	59	J10	J10	81	81	K11	K11	PD12	I/O	FT_fl	-	TIM4_CH1, I2C4_SCL, USART3_RTS_DE, TSC_G6_IO3, LCD_SEG32, FMC_A17, SAI2_FS_A, LPTIM2_IN1, EVENTOUT	-





Table 15. STM32L4A6xG pin definitions (continued)

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	60	60	H12	H12	82	82	K13	K13	PD13	I/O	FT_fl	1	TIM4_CH2, I2C4_SDA, TSC_G6_IO4, LCD_SEG33, FMC_A18, LPTIM2_OUT, EVENTOUT	-
-	-	-	-	-	-	-	-	83	83	H12	H12	VSS	S	-	-	-	-
-	-	F1	F1	-	-	-	-	84	84	H13	H13	VDD	S	-	-	-	-
-	-	G3	F3	61	61	H11	H11	85	85	K10	K10	PD14	I/O	FT_I	-	TIM4_CH3, LCD_SEG34, FMC_D0, EVENTOUT	-
-	-	F4	F2	62	62	H10	H10	86	86	H11	H11	PD15	I/O	FT_I	-	TIM4_CH4, LCD_SEG35, FMC_D1, EVENTOUT	-
-	-	-	-	-	-	G10	G10	87	87	J12	J12	PG2	I/O	FT_s	-	SPI1_SCK, FMC_A12, SAI2_SCK_B, EVENTOUT	-
-	-	-	-	-	-	F9	F9	88	88	J11	J11	PG3	I/O	FT_s	-	SPI1_MISO, FMC_A13, SAI2_FS_B, EVENTOUT	-
-	-	-	-	-	-	F10	F10	89	89	J10	J10	PG4	I/O	FT_s	-	SPI1_MOSI, FMC_A14, SAI2_MCLK_B, EVENTOUT	-
-	-	-	-	-	-	E9	E9	90	90	J9	J9	PG5	I/O	FT_s	-	SPI1_NSS, LPUART1_CTS, FMC_A15, SAI2_SD_B, EVENTOUT	-

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	-	-	G4	G4	91	91	G11	G11	PG6	I/O	FT_s	-	I2C3_SMBA, LPUART1_RTS_DE, EVENTOUT	-
-	-	-	-	-	-	H4	H4	92	92	H10	H10	PG7	I/O	FT_fs	-	I2C3_SCL, LPUART1_TX,FMC_INT, SAI1_MCLK_A, EVENTOUT	-
-	-	-	-	-	-	J6	J6	93	93	H9	Н9	PG8	I/O	FT_fs	-	I2C3_SDA, LPUART1_RX, EVENTOUT	-
-	-	-	-	-	-	-	-	94	94	F13	F13	VSS	S	-	-	-	-
-	-	-	-	-	-	-	-	95	95	F12	F12	VDDIO2	S	-	-	-	-
37	37	F2	F4	63	63	E12	E12	96	96	F11	F11	PC6	I/O	FT_I	-	TIM3_CH1, TIM8_CH1, DFSDM1_CKIN3, TSC_G4_IO1, DCMI_D0, LCD_SEG24, SDMMC1_D6, SAI2_MCLK_A, EVENTOUT	-
38	38	F3	E4	64	64	E11	E11	97	97	G12	G12	PC7	I/O	FT_I	-	TIM3_CH2, TIM8_CH2, DFSDM1_DATIN3, TSC_G4_IO2, DCMI_D1, LCD_SEG25, SDMMC1_D7, SAI2_MCLK_B, EVENTOUT	-



					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
39	39	E1	E1	65	65	E10	E10	98	98	G10	G10	PC8	I/O	FT_I	-	TIM3_CH3, TIM8_CH3, TSC_G4_IO3, DCMI_D2, LCD_SEG26, SDMMC1_D0, EVENTOUT	-
40	40	E2	E2	66	66	D12	D12	99	99	G9	G9	PC9	I/O	FT_fl	-	TIM8_BKIN2, TIM3_CH4, TIM8_CH4, DCMI_D3, I2C3_SDA, TSC_G4_IO4, OTG_FS_NOE, LCD_SEG27, SDMMC1_D1, SAI2_EXTCLK, TIM8_BKIN2_COMP1, EVENTOUT	-
41	41	E3	E3	67	67	D11	D11	100	100	G8	G8	PA8	I/O	FT_I	-	MCO, TIM1_CH1, USART1_CK, OTG_FS_SOF, LCD_COM0, SWPMI1_IO, SAI1_SCK_A, LPTIM2_OUT, EVENTOUT	-
42	42	D3	D3	68	68	D10	D10	101	101	F10	F10	PA9	I/O	FT_lu	-	TIM1_CH2, SPI2_SCK, DCMI_D0, USART1_TX, LCD_COM1, SAI1_FS_A, TIM15_BKIN, EVENTOUT	OTG_FS_VBUS

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
43	43	D2	D2	69	69	C12	C12	102	102	F9	F9	PA10	I/O	FT_lu	-	TIM1_CH3, DCMI_D1, USART1_RX, OTG_FS_ID, LCD_COM2, SAI1_SD_A, TIM17_BKIN, EVENTOUT	-
44	44	D1	D1	70	70	B12	B12	103	103	E13	E13	PA11	I/O	FT_u	-	TIM1_CH4, TIM1_BKIN2, SPI1_MISO, USART1_CTS, CAN1_RX, OTG_FS_DM, TIM1_BKIN2_COMP1, EVENTOUT	-
45	45	C1	C1	71	71	A12	A12	104	104	D13	D13	PA12	I/O	FT_u	-	TIM1_ETR, SPI1_MOSI, USART1_RTS_DE, CAN1_TX, OTG_FS_DP, EVENTOUT	-
46	46	C2	C2	72	72	A11	A11	105	105	A11	A11	PA13 (JTMS/ SWDIO)	I/O	FT	(4)	JTMS/SWDIO, IR_OUT, OTG_FS_NOE, SWPMI1_TX, SAI1_SD_B, EVENTOUT	-
47	47	B1	B1	-	-	ı	ı	ı	ı	1	ı	VSS	S	1	-	-	-
48	48	A1	A1	73	73	C11	C11	106	106	E12	E12	VDDUSB	S	-	-	-	-
-	-	-	-	74	74	F11	F11	107	107	C12	C12	VSS	S	-	-	-	-

					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	75	75	G11	G11	108	108	C13	C13	VDD	S	-	-	-	-
-	-	-	-	-	-	-	-	-	-	E11	E11	PH6	I/O	FT	-	I2C2_SMBA, DCMI_D8, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	D12	D12	PH7	I/O	FT_f	-	I2C3_SCL, DCMI_D9, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	D11	D11	PH9	I/O	FT	-	I2C3_SMBA, DCMI_D0, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B13	B13	PH12	I/O	FT	-	TIM5_CH3, DCMI_D3, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	A13	A13	PH14	I/O	FT	-	TIM8_CH2N, DCMI_D4, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B12	B12	PH15	I/O	FT	-	TIM8_CH3N, DCMI_D11, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	A12	A12	PI0	I/O	FT	-	TIM5_CH4, SPI2_NSS, DCMI_D13, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	C11	C11	PI8	I/O	FT	-	DCMI_D12, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B11	B11	PI1	I/O	FT	-	SPI2_SCK, DCMI_D8, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B10	B10	Pl2	I/O	FT	-	TIM8_CH4, SPI2_MISO, DCMI_D9, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	C10	C10	PI3	I/O	FT	-	TIM8_ETR, SPI2_MOSI, DCMI_D10, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	D10	D10	PI4	I/O	FT	-	TIM8_BKIN, DCMI_D5, EVENTOUT	-

							Т	able 1	15. ST	M32L	_4A6x	G pin definiti	ions (	continu	ued)		
					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	-	-	-	-	-	-	E10	E10	PI5	I/O	FT	-	TIM8_CH1, DCMI_VSYNC, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	С9	C9	PH13	I/O	FT	-	TIM8_CH1N, CAN1_TX, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	В9	В9	PI6	I/O	FT	-	TIM8_CH2, DCMI_D6, EVENTOUT	-
49	49	B2	B2	76	76	A10	A10	109	109	A10	A10	PA14 (JTCK/ SWCLK)	I/O	FT	(4)	JTCK/SWCLK, LPTIM1_OUT, I2C1_SMBA, I2C4_SMBA, OTG_FS_SOF, SWPMI1_RX, SAI1_FS_B, EVENTOUT	-
50	50	A2	A2	77	77	A9	А9	110	110	А9	A9	PA15 (JTDI)	I/O	FT_I	(4)	JTDI, TIM2_CH1, TIM2_ETR, USART2_RX, SPI1_NSS, SPI3_NSS, USART3_RTS_DE, UART4_RTS_DE, TSC_G3_IO1, LCD_SEG17, SWPMI1_SUSPEND, SAI2_FS_B, EVENTOUT	-





					Pin N	lumbe	r									Pin fun	ections
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
51	51	D4	С3	78	78	B11	B11	111	111	D9	D9	PC10	I/O	FT_I	-	TRACED1, SPI3_SCK, USART3_TX, UART4_TX, TSC_G3_IO2, DCMI_D8, LCD_COM4/LCD_SEG2 8/LCD_SEG40, SDMMC1_D2, SAI2_SCK_B, EVENTOUT	-
52	52	C3	D4	79	79	C10	C10	112	112	E9	E9	PC11	I/O	FT_I	-	QUADSPI_BK2_NCS, SPI3_MISO, USART3_RX, UART4_RX, TSC_G3_IO3, DCMI_D4, LCD_COM5/LCD_SEG2 9/LCD_SEG41, SDMMC1_D3, SAI2_MCLK_B, EVENTOUT	-
53	53	C4	C4	80	80	B10	B10	113	113	F8	F8	PC12	I/O	FT_I	-	TRACED3, SPI3_MOSI, USART3_CK, UART5_TX, TSC_G3_IO4, DCMI_D9, LCD_COM6/LCD_SEG3 0/LCD_SEG42, SDMMC1_CK, SAI2_SD_B, EVENTOUT	-
-	-	В3	В3	81	81	C9	C9	114	114	B8	B8	PD0	I/O	FT	-	SPI2_NSS, DFSDM1_DATIN7, CAN1_RX, FMC_D2, EVENTOUT	-

							Т	able 1	5. ST	M32L	.4A6x	G pin definit	ions (	continu	ued)		
					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	А3	А3	82	82	В9	В9	115	115	C8	C8	PD1	I/O	FT	-	SPI2_SCK, DFSDM1_CKIN7, CAN1_TX, FMC_D3, EVENTOUT	-
54	-	E4	D5	83	83	C8	C8	116	116	D8	D8	PD2	I/O	FT_I	-	TRACED2, TIM3_ETR, USART3_RTS_DE, UART5_RX, TSC_SYNC, DCMI_D11, LCD_COM7/LCD_SEG3 1/LCD_SEG43, SDMMC1_CMD, EVENTOUT	-
-	-	-	-	84	84	B8	B8	117	117	E8	E8	PD3	I/O	FT	-	SPI2_SCK, DCMI_D5, SPI2_MISO, DFSDM1_DATINO, USART2_CTS, QUADSPI_BK2_NCS, FMC_CLK, EVENTOUT	-
-	-	B4	C5	85	85	В7	В7	118	118	C7	C7	PD4	I/O	FT	-	SPI2_MOSI, DFSDM1_CKIN0, USART2_RTS_DE, QUADSPI_BK2_IO0, FMC_NOE, EVENTOUT	-
-	-	E5	B4	86	86	A6	A6	119	119	D7	D7	PD5	I/O	FT	-	USART2_TX, QUADSPI_BK2_IO1, FMC_NWE, EVENTOUT	-
-	-	-	-	-	-	-	-	120	120	-	-	VSS	S	-	-	-	-
_	_	A4	A4	-	_	-	-	121	121	-	-	VDD	S	_	_	-	-



					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	D5	B5	87	87	В6	В6	122	122	E7	E7	PD6	I/O	FT	1	DCMI_D10, QUADSPI_BK2_IO1, DFSDM1_DATIN1, USART2_RX, QUADSPI_BK2_IO2, FMC_NWAIT, SAI1_SD_A, EVENTOUT	-
-	-	C5	C6	88	88	A5	A5	123	123	F7	F7	PD7	I/O	FT	-	DFSDM1_CKIN1, USART2_CK, QUADSPI_BK2_IO3, FMC_NE1, EVENTOUT	-
-	-	B5	D6	-	-	D9	D9	124	124	В7	В7	PG9	I/O	FT_s	-	SPI3_SCK, USART1_TX, FMC_NCE/FMC_NE2, SAI2_SCK_A, TIM15_CH1N, EVENTOUT	-
-	-	A5	<b>A</b> 5	-	1	D8	D8	125	125	D6	D6	PG10	I/O	FT_s	-	LPTIM1_IN1, SPI3_MISO, USART1_RX,FMC_NE3, SAI2_FS_A, TIM15_CH1, EVENTOUT	-
-	-	D6	E5	-	-	G3	G3	126	126	E6	E6	PG11	I/O	FT_s	-	LPTIM1_IN2, SPI3_MOSI, USART1_CTS, SAI2_MCLK_A, TIM15_CH2, EVENTOUT	-

Table 15. STM32L4A6xG	pin definitions	(continued)
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					Pin N	lumbe	r									Pin fu	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	1	В6	В6	-	-	D7	D7	127	127	F6	F6	PG12	I/O	FT_s	-	LPTIM1_ETR, SPI3_NSS, USART1_RTS_DE, FMC_NE4, SAI2_SD_A, EVENTOUT	-
-	,	,	-	-	-	C7	C7	128	128	G7	G7	PG13	I/O	FT_fs	-	I2C1_SDA, USART1_CK, FMC_A24, EVENTOUT	-
-		-	1	ı	-	C6	1	129	129	G6	G6	PG14	I/O	FT_fs	-	I2C1_SCL, FMC_A25, EVENTOUT	-
-	,	,	-	-	-	F7	F7	130	130	A7	A7	VSS	S	-	-	-	-
-	,	A6	A6	-	-	G7	G7	131	131	В6	В6	VDDIO2	S	-	-	-	-
-	,	,	-	-	-	K1	K1	132	1	C6	-	PG15	I/O	FT_s	-	LPTIM1_OUT, I2C1_SMBA, DCMI_D13, EVENTOUT	-
55	54	C6	F5	89	89	A8	A8	133	132	A6	A6	PB3 (JTDO/TRACE SWO)	I/O	FT_la	(4)	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK, SPI3_SCK, USART1_RTS_DE, OTG_FS_CRS_SYNC, LCD_SEG7, SAI1_SCK_B, EVENTOUT	COMP2_INM



					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
56	55	C7	E6	90	90	A7	A7	134	133	A5	A5	PB4 (NJTRST)	I/O	FT_fla		NJTRST, TIM3_CH1, I2C3_SDA, SPI1_MISO, SPI3_MISO, USART1_CTS, UART5_RTS_DE, TSC_G2_IO1, DCMI_D12, LCD_SEG8, SAI1_MCLK_B, TIM17_BKIN, EVENTOUT	COMP2_INP
57	56	B7	C7	91	91	C5	C5	135	134	B5	B5	PB5	I/O	FT_la	ı	LPTIM1_IN1, TIM3_CH2, CAN2_RX, I2C1_SMBA, SPI1_MOSI, SPI3_MOSI, USART1_CK, UART5_CTS, TSC_G2_IO2, DCMI_D10, LCD_SEG9, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, EVENTOUT	-
58	57	A7	A7	92	92	B5	B5	136	135	C5	C5	PB6	I/O	FT_fa	-	LPTIM1_ETR, TIM4_CH1, TIM8_BKIN2, I2C1_SCL, I2C4_SCL, DFSDM1_DATIN5, USART1_TX, CAN2_TX, TSC_G2_IO3, DCMI_D5, TIM8_BKIN2_COMP2, SAI1_FS_B, TIM16_CH1N, EVENTOUT	COMP2_INP

							Т	able 1	5. ST	M32L	.4A6x	G pin definiti	ons (	continu	ıed)		
					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
59	58	D7	В7	93	93	B4	B4	137	136	D5	D5	PB7	I/O	FT_fla	-	LPTIM1_IN2, TIM4_CH2, TIM8_BKIN, I2C1_SDA, I2C4_SDA, DFSDM1_CKIN5, USART1_RX, UART4_CTS, TSC_G2_IO4, DCMI_VSYNC, LCD_SEG21, FMC_NL, TIM8_BKIN_COMP1, TIM17_CH1N, EVENTOUT	COMP2_INM, PVD_IN
60	59	E6	D7	94	94	A4	A4	138	137	E5	E5	РН3-ВООТ0	I/O	FT	-	EVENTOUT	-
61	60	B8	B8	95	95	А3	A3	139	138	C4	C4	PB8	I/O	FT_fl	-	TIM4_CH3, I2C1_SCL, DFSDM1_DATIN6, CAN1_RX, DCMI_D6, LCD_SEG16, SDMMC1_D4, SAI1_MCLK_A, TIM16_CH1, EVENTOUT	-
62	61	A8	A8	96	96	В3	В3	140	139	D4	D4	PB9	I/O	FT_fl	-	IR_OUT, TIM4_CH4, I2C1_SDA, SPI2_NSS, DFSDM1_CKIN6, CAN1_TX, DCMI_D7, LCD_COM3, SDMMC1_D5, SAI1_FS_A, TIM17_CH1, EVENTOUT	-
-	62	-	-	-	-	-	C6	-	-	-	C6	VDD12	S	-	-	-	-





					Pin N	lumbe	r									Pin fur	nctions
LQFP64	LQFP64_SMPS	WLCSP100	WLCSP100_SMPS	LQFP100	LQFP100_SMPS	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
-	-	-	-	97	97	C3	C3	141	140	A4	A4	PE0	I/O	FT_I	-	TIM4_ETR, DCMI_D2, LCD_SEG36, FMC_NBL0, TIM16_CH1, EVENTOUT	-
-	-	-	-	98	-	A2	A2	142	141	B4	B4	PE1	I/O	FT_I	-	DCMI_D3, LCD_SEG37, FMC_NBL1, TIM17_CH1, EVENTOUT	-
-	1	-	A9	-	98	-	1	1	142	-	-	VDD12	s	-	-	-	-
63	63	A9	В9	99	99	D3	D3	143	143	В3	В3	VSS	S	-	-	-	-
64	64	A10	A10	100	100	C4	C4	144	144	A3	А3	VDD	s	-	-	-	-
-	-	-	-	-	-	-	-	-	-	C2	C2	VSS	s	-	-	-	-
-	-	-	-	-	-	-	-	-	-	C1	C1	VDD	S	-	-	-	-
-	-	-	-	-	-	-	-	-	-	A2	A2	PH2	I/O	FT	-	QUADSPI_BK2_IO0, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B2	B2	PI7	I/O	FT	-	TIM8_CH3, DCMI_D7, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	B1	B1	PI9	I/O	FT	-	CAN1_RX, EVENTOUT	-
-	-	-	-	-	-	-	-	-	-	A1	A1	PI10	I/O	FT	-	EVENTOUT	-

- 1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current(3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
  - The speed should not exceed 2 MHz with a maximum load of 30 pF.
  - These GPIOs must not be used as current sources (e.g. to drive an LED).
- 2. After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the RM0351 reference manual.
- 3. OPAMPx\_VINM pins are not available as additional functions on pins PA1 and PA7 on UFBGA packages. On UFBGA packages, use the OPAMPx\_VINM dedicated pins available on M3 and M4 balls.
- 4. After reset, these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13, PB4 pins and the internal pull-down on PA14 pin are activated.



Table 16. Alternate function AF0 to AF7<sup>(1)</sup>

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PA0	-	TIM2_CH1	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS
	PA1	-	TIM2_CH2	TIM5_CH2	-	I2C1_SMBA	SPI1_SCK	-	USART2_RTS_ DE
	PA2	-	TIM2_CH3	TIM5_CH3	-	-	-	-	USART2_TX
	PA3	-	TIM2_CH4	TIM5_CH4	-	-	-	-	USART2_RX
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS	USART2_CK
	PA5	-	TIM2_CH1	TIM2_ETR	TIM8_CH1N	-	SPI1_SCK	-	-
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	DCMI_PIXCLK	SPI1_MISO	-	USART3_CTS
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	I2C3_SCL	SPI1_MOSI	-	-
Port A	PA8	MCO	TIM1_CH1	-	-	-	-	-	USART1_CK
	PA9	-	TIM1_CH2	-	SPI2_SCK	-	DCMI_D0	-	USART1_TX
	PA10	-	TIM1_CH3	-	-	-	DCMI_D1	-	USART1_RX
	PA11	-	TIM1_CH4	TIM1_BKIN2	-	-	SPI1_MISO	-	USART1_CTS
	PA12	-	TIM1_ETR	-	-	-	SPI1_MOSI	-	USART1_RTS_ DE
	PA13	JTMS/SWDIO	IR_OUT	-	-	-	-	-	-
	PA14	JTCK/SWCLK	LPTIM1_OUT	-	-	I2C1_SMBA	I2C4_SMBA	•	-
	PA15	JTDI	TIM2_CH1	TIM2_ETR	USART2_RX	-	SPI1_NSS	SPI3_NSS	USART3_RTS_ DE

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Table 16. Alternate function AF0 to AF7 <sup>(1)</sup> (continue	Table 16	6. Alternate	function	AF0 to	AF7 <sup>(1)</sup>	(continued
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		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	12C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PB0	-	TIM1_CH2N	TIM3_CH3	TIM8_CH2N	-	SPI1_NSS	-	USART3_CK
	PB1	-	TIM1_CH3N	TIM3_CH4	TIM8_CH3N	-	-	DFSDM1_ DATIN0	USART3_RTS_ DE
	PB2	RTC_OUT	LPTIM1_OUT	-	-	I2C3_SMBA	-	DFSDM1_CKIN0	-
	PB3	JTDO/ TRACESWO	TIM2_CH2	-	-	-	SPI1_SCK	SPI3_SCK	USART1_RTS_ DE
	PB4	NJTRST	-	TIM3_CH1	-	I2C3_SDA	SPI1_MISO	SPI3_MISO	USART1_CTS
	PB5	-	LPTIM1_IN1	TIM3_CH2	CAN2_RX	I2C1_SMBA	SPI1_MOSI	SPI3_MOSI	USART1_CK
	PB6	-	LPTIM1_ETR	TIM4_CH1	TIM8_BKIN2	I2C1_SCL	I2C4_SCL	DFSDM1_ DATIN5	USART1_TX
	PB7	-	LPTIM1_IN2	TIM4_CH2	TIM8_BKIN	I2C1_SDA	I2C4_SDA	DFSDM1_CKIN5	USART1_RX
Port B	PB8	-	-	TIM4_CH3	-	I2C1_SCL	-	DFSDM1_ DATIN6	-
	PB9	-	IR_OUT	TIM4_CH4	-	I2C1_SDA	SPI2_NSS	DFSDM1_CKIN6	-
	PB10	-	TIM2_CH3	-	I2C4_SCL	I2C2_SCL	SPI2_SCK	DFSDM1_ DATIN7	USART3_TX
	PB11	-	TIM2_CH4	-	I2C4_SDA	I2C2_SDA	-	DFSDM1_CKIN7	USART3_RX
	PB12	-	TIM1_BKIN	-	TIM1_BKIN_ COMP2	I2C2_SMBA	SPI2_NSS	DFSDM1_ DATIN1	USART3_CK
	PB13	-	TIM1_CH1N	-	-	I2C2_SCL	SPI2_SCK	DFSDM1_CKIN1	USART3_CTS
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	I2C2_SDA	SPI2_MISO	DFSDM1_ DATIN2	USART3_RTS_ DE
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI	DFSDM1_CKIN2	-





Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
P	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PC0	-	LPTIM1_IN1	I2C4_SCL	-	I2C3_SCL	-	DFSDM1_ DATIN4	-
	PC1	TRACED0	LPTIM1_OUT	I2C4_SDA	SPI2_MOSI	I2C3_SDA	-	DFSDM1_CKIN4	-
	PC2	-	LPTIM1_IN2	-	-	-	SPI2_MISO	DFSDM1_ CKOUT	-
	PC3	-	LPTIM1_ETR	-	-	-	SPI2_MOSI	-	-
	PC4	-	-	-	-	-	-	-	USART3_TX
	PC5	-	-	-	-	-	-	-	USART3_RX
	PC6	-	-	TIM3_CH1	TIM8_CH1	-	-	DFSDM1_CKIN3	-
	PC7	-	-	TIM3_CH2	TIM8_CH2	-	-	DFSDM1_ DATIN3	-
Port C	PC8	-	-	TIM3_CH3	TIM8_CH3	-	-	-	-
	PC9	-	TIM8_BKIN2	TIM3_CH4	TIM8_CH4	DCMI_D3	-	I2C3_SDA	-
	PC10	TRACED1	-	-	-	-	-	SPI3_SCK	USART3_TX
	PC11	-	-	-	-	-	QUADSPI_BK 2_NCS	SPI3_MISO	USART3_RX
	PC12	TRACED3	-	-	-	-	-	SPI3_MOSI	USART3_CK
	PC13	-	-	-	-	-	-	-	-
	PC14	-	-	-	-	-	-	-	-
	PC15	-	-	-	-	-	-	-	-

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Table 16	<b>Alternate</b>	function	ΔF0 to	$\Delta F7^{(1)}$	(continued)
Table 10.	Alternate	IUIICUOII	$\Delta I \cup I \cup I$	$\Delta I I $	(COIILIIIU <del>C</del> U

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PD0	-	-	-	-	-	SPI2_NSS	DFSDM1_ DATIN7	-
	PD1	-	-	-	-	-	SPI2_SCK	DFSDM1_CKIN7	-
	PD2	TRACED2	-	TIM3_ETR	-	-	-	-	USART3_RTS_ DE
	PD3	-	-	-	SPI2_SCK	DCMI_D5	SPI2_MISO	DFSDM1_ DATIN0	USART2_CTS
	PD4	-	-	-	-	-	SPI2_MOSI	DFSDM1_CKIN0	USART2_RTS_ DE
	PD5	-	-	-	-	-	-	-	USART2_TX
Port D	PD6	-	-	-	-	DCMI_D10	QUADSPI_ BK2_IO1	DFSDM1_ DATIN1	USART2_RX
	PD7	-	-	-	-	-	-	DFSDM1_CKIN1	USART2_CK
	PD8	-	-	-	-	-	-	-	USART3_TX
	PD9	-	-	-	-	-	-	-	USART3_RX
	PD10	-	-	-	-	-	-	-	USART3_CK
	PD11	-	-	-	-	I2C4_SMBA	-	-	USART3_CTS
	PD12	-	-	TIM4_CH1	-	I2C4_SCL	-	-	USART3_RTS_ DE
	PD13	-	-	TIM4_CH2	-	I2C4_SDA	-	-	-
	PD14	-	-	TIM4_CH3	-	-	-	-	-
	PD15	-	-	TIM4_CH4	-	-	-	-	-



Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
P	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PE0	-	-	TIM4_ETR	-	-	-	-	-
	PE1	-	-	-	-	-	-	-	-
	PE2	TRACECK	-	TIM3_ETR	-	-	-	-	-
	PE3	TRACED0	-	TIM3_CH1	-	-	-	-	-
	PE4	TRACED1	-	TIM3_CH2	-	-	-	DFSDM1_ DATIN3	-
	PE5	TRACED2	-	TIM3_CH3	-	-	-	DFSDM1_CKIN3	-
	PE6	TRACED3	-	TIM3_CH4	-	-	-	-	-
	PE7	-	TIM1_ETR	-	-	-	-	DFSDM1_ DATIN2	-
Port E	PE8	-	TIM1_CH1N	-	-	-	-	DFSDM1_CKIN2	-
	PE9	-	TIM1_CH1	-	-	-	-	DFSDM1_ CKOUT	-
	PE10	-	TIM1_CH2N	-	-	-	-	DFSDM1_ DATIN4	-
	PE11	-	TIM1_CH2	-	-	-	-	DFSDM1_CKIN4	-
	PE12	-	TIM1_CH3N	-	-	-	SPI1_NSS	DFSDM1_ DATIN5	-
	PE13	-	TIM1_CH3	-	-	-	SPI1_SCK	DFSDM1_CKIN5	-
	PE14	-	TIM1_CH4	TIM1_BKIN2	TIM1_BKIN2_ COMP2	-	SPI1_MISO	-	-
	PE15	-	TIM1_BKIN	-	TIM1_BKIN_ COMP1	-	SPI1_MOSI	-	-

Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Pe	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PF0	-	-	-	-	I2C2_SDA	-	-	-
	PF1	-	-	-	-	I2C2_SCL	-	-	-
	PF2	-	-	-	-	I2C2_SMBA	-	-	-
	PF3	-	-	-	-	-	-	-	-
	PF4	-	-	-	-	-	-	-	-
	PF5	-	-	-	-	-	-	-	-
	PF6	-	TIM5_ETR	TIM5_CH1	-	-	-	-	-
	PF7	-	-	TIM5_CH2	-	-	-	-	-
Port F	PF8	-	-	TIM5_CH3	-	-	-	-	-
	PF9	-	-	TIM5_CH4	-	-	-	-	-
	PF10	-	-	-	QUADSPI_CLK	-	-	-	-
	PF11	-	-	-	-	-	-	-	-
	PF12	-	-	-	-	-	-	-	-
	PF13	-	-	-	-	I2C4_SMBA	-	DFSDM1_ DATIN6	-
	PF14	-	-	-	-	I2C4_SCL	-	DFSDM1_CKIN6	-
	PF15	-	-	-	-	I2C4_SDA	-	-	-





Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Pe	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PG0	-	-	-	-	-	-	-	-
	PG1	-	-	-	-	-	-	-	-
	PG2	-	-	-	-	-	SPI1_SCK	-	-
	PG3	-	-	-	-	-	SPI1_MISO	-	-
	PG4	-	-	-	-	-	SPI1_MOSI	-	-
	PG5	-	-	-	-	-	SPI1_NSS	-	-
	PG6	-	-	-	-	I2C3_SMBA	-	-	-
	PG7	-	-	-	-	I2C3_SCL	-	-	-
Port G	PG8	-	-	-	-	I2C3_SDA	-	-	-
	PG9	-	-	-	-	-	-	SPI3_SCK	USART1_TX
	PG10	-	LPTIM1_IN1	-	-	-	-	SPI3_MISO	USART1_RX
	PG11	-	LPTIM1_IN2	-	-	-	-	SPI3_MOSI	USART1_CTS
	PG12	-	LPTIM1_ETR	-	-	-	-	SPI3_NSS	USART1_RTS_ DE
	PG13	-	-	-	-	I2C1_SDA	-	-	USART1_CK
	PG14	-	-	-	-	I2C1_SCL	-	-	-
	PG15	-	LPTIM1_OUT	-	-	I2C1_SMBA	-	-	-

Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PH0	-	-	-	-	-	-	-	-
	PH1	-	-	-	-	-	-	-	-
	PH2	-	-	-	QUADSPI_ BK2_IO0	-	-	-	-
	PH3	-	-	-	-	-	-	-	-
	PH4	-	-	-	-	I2C2_SCL	-	-	-
	PH5	-	-	-	-	I2C2_SDA	-	-	-
	PH6	-	-	-	-	I2C2_SMBA	-	-	-
Port H	PH7	-	-	-	-	I2C3_SCL	-	-	-
	PH8	-	-	-	-	I2C3_SDA	-	-	-
	PH9	-	-	-	-	I2C3_SMBA	-	-	-
	PH10	-	-	TIM5_CH1	-	-	-	-	-
	PH11	-	-	TIM5_CH2	-	-	-	-	-
	PH12	-	-	TIM5_CH3	-	-	-	-	-
	PH13	-	-	-	TIM8_CH1N	-	-	-	-
	PH14	-	-	-	TIM8_CH2N	-	-	-	-
	PH15	-	-	-	TIM8_CH3N	-	-	-	-



Table 16. Alternate function AF0 to AF7<sup>(1)</sup> (continued)

		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
Po	ort	SYS_AF	TIM1/2/5/8/ LPTIM1	TIM1/2/3/4/5	SPI2/USART2/ CAN2/TIM8/ QUADSPI	I2C1/2/3/4/ DCMI	SPI1/2/DCMI/ QUADSPI	SPI3/I2C3/ DFSDM/ COMP1/ QUADSPI	USART1/2/3
	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS	-	-
	PI1	-	-	-	-	-	SPI2_SCK	-	-
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	-	-
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI	-	-
	PI4	-	-	-	TIM8_BKIN	-	-	-	-
Dowt	PI5	-	-	-	TIM8_CH1	-	-	-	-
Port I	PI6	-	-	-	TIM8_CH2	-	-	-	-
	PI7	-	-	-	TIM8_CH3	-	-	-	-
	PI8	-	-	-	-	-	-	-	-
	PI9	-	-	-	-	-	-	-	-
	PI10	-	-	-	-	-	-	-	-
	PI11	-	-	-	-	-	-	-	-

<sup>1.</sup> Please refer to *Table 17* for AF8 to AF15.

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Table 17. Alternate function AF8 to AF15<sup>(1)</sup>

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
Pe	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PA0	UART4_TX	-	-	-	-	SAI1_EXTCLK	TIM2_ETR	EVENTOUT
	PA1	UART4_RX	-	-	LCD_SEG0	-	-	TIM15_CH1N	EVENTOUT
	PA2	LPUART1_TX	-	QUADSPI_BK1_NCS	LCD_SEG1	-	SAI2_EXTCLK	TIM15_CH1	EVENTOUT
	PA3	LPUART1_RX	-	QUADSPI_CLK	LCD_SEG2	-	SAI1_MCLK_A	TIM15_CH2	EVENTOUT
	PA4	-	-	DCMI_HSYNC	-	-	SAI1_FS_B	LPTIM2_OUT	EVENTOUT
	PA5	-	-	-	-	-	-	LPTIM2_ETR	EVENTOUT
	PA6	LPUART1_CT S	-	QUADSPI_BK1_IO3	LCD_SEG3	TIM1_BKIN_C OMP2	TIM8_BKIN_C OMP2	TIM16_CH1	EVENTOUT
	PA7	-	-	QUADSPI_BK1_IO2	LCD_SEG4	-	-	TIM17_CH1	EVENTOUT
Port A	PA8	-	-	OTG_FS_SOF	LCD_COM0	SWPMI1_IO	SAI1_SCK_A	LPTIM2_OUT	EVENTOUT
	PA9	-	-	-	LCD_COM1	-	SAI1_FS_A	TIM15_BKIN	EVENTOUT
	PA10	-	-	OTG_FS_ID	LCD_COM2	-	SAI1_SD_A	TIM17_BKIN	EVENTOUT
	PA11	-	CAN1_RX	OTG_FS_DM	-	TIM1_BKIN2_ COMP1	-	-	EVENTOUT
	PA12	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	-	-	OTG_FS_NOE	-	SWPMI1_TX	SAI1_SD_B	-	EVENTOUT
	PA14	-	-	OTG_FS_SOF	-	SWPMI1_RX	SAI1_FS_B	-	EVENTOUT
	PA15	UART4_RTS_ DE	TSC_G3_IO1	-	LCD_SEG17	SWPMI1_SUS PEND	SAI2_FS_B	-	EVENTOUT





Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
Pe	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PB0	-	-	QUADSPI_BK1_IO1	LCD_SEG5	COMP1_OUT	SAI1_EXTCLK	-	EVENTOUT
	PB1	LPUART1_RT S_DE	-	QUADSPI_BK1_IO0	LCD_SEG6	-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	-	LCD_VLCD	-	-	-	EVENTOUT
	PB3	-	-	OTG_FS_CRS_SYNC	LCD_SEG7	-	SAI1_SCK_B	-	EVENTOUT
	PB4	UART5_RTS_ DE	TSC_G2_IO1	DCMI_D12	LCD_SEG8	1	SAI1_MCLK_B	TIM17_BKIN	EVENTOUT
	PB5	UART5_CTS	TSC_G2_IO2	DCMI_D10	LCD_SEG9	COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	CAN2_TX	TSC_G2_IO3	DCMI_D5	-	TIM8_BKIN2_ COMP2	SAI1_FS_B	TIM16_CH1N	EVENTOUT
Port B	PB7	UART4_CTS	TSC_G2_IO4	DCMI_VSYNC	LCD_SEG21	FMC_NL	TIM8_BKIN_C OMP1	TIM17_CH1N	EVENTOUT
	PB8	-	CAN1_RX	DCMI_D6	LCD_SEG16	SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	-	CAN1_TX	DCMI_D7	LCD_COM3	SDMMC1_D5	SAI1_FS_A	TIM17_CH1	EVENTOUT
	PB10	LPUART1_RX	TSC_SYNC	QUADSPI_CLK	LCD_SEG10	COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	QUADSPI_BK1_NCS	LCD_SEG11	COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RT S_DE	TSC_G1_IO1	CAN2_RX	LCD_SEG12	SWPMI1_IO	SAI2_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CT S	TSC_G1_IO2	CAN2_TX	LCD_SEG13	SWPMI1_TX	SAI2_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-	LCD_SEG14	SWPMI1_RX	SAI2_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-	LCD_SEG15	SWPMI1_SUS PEND	SAI2_SD_A	TIM15_CH2	EVENTOUT

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Table 17 Alternate	function AF8 to AF15 <sup>(1)</sup>	(continued)
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		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
Po	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PC0	LPUART1_RX	-	-	LCD_SEG18	-	-	LPTIM2_IN1	EVENTOUT
	PC1	LPUART1_TX	-	QUADSPI_BK2_IO0	LCD_SEG19	-	SAI1_SD_A	-	EVENTOUT
	PC2	-	-	QUADSPI_BK2_IO1	LCD_SEG20	-	-	-	EVENTOUT
	PC3	-	-	QUADSPI_BK2_IO2	LCD_VLCD	-	SAI1_SD_A	LPTIM2_ETR	EVENTOUT
	PC4	-	-	QUADSPI_BK2_IO3	LCD_SEG22	-	-	-	EVENTOUT
	PC5	-	-	-	LCD_SEG23	-	-	-	EVENTOUT
	PC6	-	TSC_G4_IO1	DCMI_D0	LCD_SEG24	SDMMC1_D6	SAI2_MCLK_A	-	EVENTOUT
	PC7	-	TSC_G4_IO2	DCMI_D1	LCD_SEG25	SDMMC1_D7	SAI2_MCLK_B	-	EVENTOUT
	PC8	-	TSC_G4_IO3	DCMI_D2	LCD_SEG26	SDMMC1_D0	-	-	EVENTOUT
Port C	PC9	-	TSC_G4_IO4	OTG_FS_NOE	LCD_SEG27	SDMMC1_D1	SAI2_EXTCLK	TIM8_BKIN2_C OMP1	EVENTOUT
	PC10	UART4_TX	TSC_G3_IO2	DCMI_D8	LCD_COM4/L CD_SEG28/L CD_SEG40	SDMMC1_D2	SAI2_SCK_B	-	EVENTOUT
	PC11	UART4_RX	TSC_G3_IO3	DCMI_D4	LCD_COM5/L CD_SEG29/L CD_SEG41	SDMMC1_D3	SAI2_MCLK_B	-	EVENTOUT
	PC12	UART5_TX	TSC_G3_IO4	DCMI_D9	LCD_COM6/L CD_SEG30/L CD_SEG42	SDMMC1_CK	SAI2_SD_B	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	EVENTOUT
	PC15	-		-	-	-	-	-	EVENTOUT





Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
Po	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PD0	-	CAN1_RX	-	-	FMC_D2	-	-	EVENTOUT
	PD1	-	CAN1_TX	-	-	FMC_D3	-	-	EVENTOUT
	PD2	UART5_RX	TSC_SYNC	DCMI_D11	LCD_COM7/L CD_SEG31/L CD_SEG43	SDMMC1_CM D	-	-	EVENTOUT
	PD3	-	-	QUADSPI_BK2_NCS	-	FMC_CLK	-	-	EVENTOUT
	PD4	-	-	QUADSPI_BK2_IO0	-	FMC_NOE	-	-	EVENTOUT
	PD5	-	-	QUADSPI_BK2_IO1	-	FMC_NWE	-	-	EVENTOUT
	PD6	-	-	QUADSPI_BK2_IO2	-	FMC_NWAIT	SAI1_SD_A	-	EVENTOUT
Port D	PD7	-	-	QUADSPI_BK2_IO3	-	FMC_NE1	-	-	EVENTOUT
	PD8	-	-	DCMI_HSYNC	LCD_SEG28	FMC_D13	-	-	EVENTOUT
	PD9	-	-	DCMI_PIXCLK	LCD_SEG29	FMC_D14	SAI2_MCLK_A	-	EVENTOUT
	PD10	-	TSC_G6_IO1	-	LCD_SEG30	FMC_D15	SAI2_SCK_A	-	EVENTOUT
	PD11	-	TSC_G6_IO2	-	LCD_SEG31	FMC_A16	SAI2_SD_A	LPTIM2_ETR	EVENTOUT
	PD12	-	TSC_G6_IO3	-	LCD_SEG32	FMC_A17	SAI2_FS_A	LPTIM2_IN1	EVENTOUT
	PD13	-	TSC_G6_IO4	-	LCD_SEG33	FMC_A18	-	LPTIM2_OUT	EVENTOUT
	PD14	-	-	-	LCD_SEG34	FMC_D0	-	-	EVENTOUT
	PD15	-	-	-	LCD_SEG35	FMC_D1	-	-	EVENTOUT

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Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
			Alv		ALII		Ai io	A1 14	ALIV
P	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PE0	-	-	DCMI_D2	LCD_SEG36	FMC_NBL0	-	TIM16_CH1	EVENTOUT
	PE1	-	-	DCMI_D3	LCD_SEG37	FMC_NBL1	-	TIM17_CH1	EVENTOUT
	PE2	-	TSC_G7_IO1	-	LCD_SEG38	FMC_A23	SAI1_MCLK_A	-	EVENTOUT
	PE3	-	TSC_G7_IO2	-	LCD_SEG39	FMC_A19	SAI1_SD_B	-	EVENTOUT
	PE4	-	TSC_G7_IO3	DCMI_D4	-	FMC_A20	SAI1_FS_A	-	EVENTOUT
	PE5	-	TSC_G7_IO4	DCMI_D6	-	FMC_A21	SAI1_SCK_A	-	EVENTOUT
	PE6	-	-	DCMI_D7	-	FMC_A22	SAI1_SD_A	-	EVENTOUT
Port E	PE7	-	-	-	-	FMC_D4	SAI1_SD_B	-	EVENTOUT
FOILE	PE8	-	-	-	-	FMC_D5	SAI1_SCK_B	-	EVENTOUT
	PE9	-	-	-	-	FMC_D6	SAI1_FS_B	-	EVENTOUT
	PE10	-	TSC_G5_IO1	QUADSPI_CLK	-	FMC_D7	SAI1_MCLK_B	-	EVENTOUT
	PE11	-	TSC_G5_IO2	QUADSPI_BK1_NCS	-	FMC_D8	-	-	EVENTOUT
	PE12	-	TSC_G5_IO3	QUADSPI_BK1_IO0	-	FMC_D9	-	-	EVENTOUT
	PE13	-	TSC_G5_IO4	QUADSPI_BK1_IO1	-	FMC_D10	-	-	EVENTOUT
	PE14	-	-	QUADSPI_BK1_IO2	-	FMC_D11	-	-	EVENTOUT
	PE15	-	-	QUADSPI_BK1_IO3	-	FMC_D12	-	-	EVENTOUT



Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

				able 17. Alternate lui		`	, 		
		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
P	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PF0	-	-	-	-	FMC_A0	-	-	EVENTOUT
	PF1	-	-	-	-	FMC_A1	-	-	EVENTOUT
	PF2	-	-	-	-	FMC_A2	-	-	EVENTOUT
	PF3	-	-	-	-	FMC_A3	-	-	EVENTOUT
	PF4	-	-	-	-	FMC_A4	-	-	EVENTOUT
	PF5	-	-	-	-	FMC_A5	-	-	EVENTOUT
	PF6	-	-	QUADSPI_BK1_IO3	-	-	SAI1_SD_B	-	EVENTOUT
Port F	PF7	-	-	QUADSPI_BK1_IO2	-	-	SAI1_MCLK_B	-	EVENTOUT
FUILE	PF8	-	-	QUADSPI_BK1_IO0	-	-	SAI1_SCK_B	-	EVENTOUT
	PF9	-	-	QUADSPI_BK1_IO1	-	-	SAI1_FS_B	TIM15_CH1	EVENTOUT
	PF10	-	-	DCMI_D11	-	-	-	TIM15_CH2	EVENTOUT
	PF11	-	-	DCMI_D12	-	-	-	-	EVENTOUT
	PF12	-	-	-	-	FMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	FMC_A7	-	-	EVENTOUT
	PF14	-	TSC_G8_IO1	-	-	FMC_A8	-	-	EVENTOUT
	PF15	-	TSC_G8_IO2	-	-	FMC_A9	-	-	EVENTOUT

Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
P	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PG0	-	TSC_G8_IO3	-	-	FMC_A10	-	-	EVENTOUT
	PG1	-	TSC_G8_IO4	-	-	FMC_A11	-	-	EVENTOUT
	PG2	-	-	-	-	FMC_A12	SAI2_SCK_B	-	EVENTOUT
	PG3	-	-	-	-	FMC_A13	SAI2_FS_B	-	EVENTOUT
	PG4	-	-	-	-	FMC_A14	SAI2_MCLK_B	-	EVENTOUT
	PG5	LPUART1_CT S	-	-	-	FMC_A15	SAI2_SD_B	-	EVENTOUT
	PG6	LPUART1_RT S_DE	-	-	-	-	-	-	EVENTOUT
Port G	PG7	LPUART1_TX	-	-	-	FMC_INT	SAI1_MCLK_A	-	EVENTOUT
1 011 0	PG8	LPUART1_RX	-	-	-	-	-	-	EVENTOUT
	PG9	-	-	-	-	FMC_NCE/FM C_NE2	SAI2_SCK_A	TIM15_CH1N	EVENTOUT
	PG10	-	-	-	-	FMC_NE3	SAI2_FS_A	TIM15_CH1	EVENTOUT
	PG11	-	-	-	-	-	SAI2_MCLK_A	TIM15_CH2	EVENTOUT
	PG12	-	-	-	-	FMC_NE4	SAI2_SD_A	-	EVENTOUT
	PG13	-	-	-	-	FMC_A24	-	-	EVENTOUT
	PG14	-	-	-	-	FMC_A25	-	-	EVENTOUT
	PG15	-		DCMI_D13	-	-	-	-	EVENTOUT





Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
P	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PH0	-	-	-	-	-	-	-	EVENTOUT
	PH1	-	-	-	-	-	-	-	EVENTOUT
	PH2	-	-	-	-	-	-	-	EVENTOUT
	PH3	-	-	-	-	-	-	-	EVENTOUT
	PH4	-	-	-	-	-	-	-	EVENTOUT
	PH5	-	-	DCMI_PIXCLK	-	-	-	-	EVENTOUT
	PH6	-	-	DCMI_D8	-	-	-	-	EVENTOUT
Port H	PH7	-	-	DCMI_D9	-	-	-	-	EVENTOUT
Port n	PH8	-	-	DCMI_HSYNC	-	-	-	-	EVENTOUT
	PH9	-	-	DCMI_D0	-	-	-	-	EVENTOUT
	PH10	-	-	DCMI_D1	-	-	-	-	EVENTOUT
	PH11	-	-	DCMI_D2	-	-	-	-	EVENTOUT
	PH12	-	-	DCMI_D3	-	-	-	-	EVENTOUT
	PH13	-	CAN1_TX	-	-	-	-	-	EVENTOUT
	PH14	-	-	DCMI_D4	-	-	-	-	EVENTOUT
	PH15	-	-	DCMI_D11	-	-	-	-	EVENTOUT

Table 17. Alternate function AF8 to AF15<sup>(1)</sup> (continued)

		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
P	ort	UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FM C/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
	PI0	-	-	DCMI_D13	-	-	-	-	EVENTOUT
	PI1	-	-	DCMI_D8	-	-	-	-	EVENTOUT
	PI2	-	-	DCMI_D9	-	-	-	-	EVENTOUT
	PI3	-	-	DCMI_D10	-	-	-	-	EVENTOUT
	PI4	-	-	DCMI_D5	-	-	-	-	EVENTOUT
Port I	PI5	-	-	DCMI_VSYNC	-	-	-	-	EVENTOUT
POILI	PI6	-	-	DCMI_D6	-	-	-	-	EVENTOUT
	PI7	-	-	DCMI_D7	-	-	-	-	EVENTOUT
	PI8	-	-	DCMI_D12	-	-	-	-	EVENTOUT
	PI9	-	CAN1_RX	-	-	-	-	-	EVENTOUT
	PI10	-	-	-	-	-	-	-	EVENTOUT
	PI11	-	-	-	-	-	-	-	EVENTOUT

<sup>1.</sup> Please refer to *Table 16* for AF0 to AF7.



STM32L4A6xG Memory mapping

# 5 Memory mapping

Figure 19. STM32L4A6xG memory map 0xFFFF FFFF 0xBFFF FFFF Reserved Cortex™-M4 0xA000 1400 with FPU 7 QUADSPI registers Internal 0xA000 1000 Peripherals FMC registers 0xA000 0000 0xE000 0000 0x5FFF FFFF Reserved 6 0x5006 0C00 AHB2 0x4800 0000 0xC000 0000 Reserved 0x4002 4400 AHB1 FMC and 5 QUADSPI 0x4002 0000 Reserved registers 0x4001 6400 APB2 0xA000 0000 0x4001 0000 QUADSPI Flash Reserved bank 0x4000 9800 4 0x9000 0000 APB1 0x4000 0000 FMC bank3 0x1FFF FFFF 0x8000 0000 Reserved 0x1FFF F810 Option Bytes 3 0x1FFF F800 Reserved FMC bank1 0x1FFF F000 System memory 0x6000 0000 0x1FFF 8000 Reserved 0x1FFF 7810 Options Bytes 2 0x1FFF 7800 Reserved 0x1FFF 7400 Peripherals OTP area 0x4000 0000 0x1FFF 7000 System memory 1 0x1FFF 0000 SRAM2 Reserved 0x2004 0000 0x1001 0000 SRAM1 SRAM2 0x2000 0000 0x1000 0000 Reserved 0 0x0810 0000 CODE Flash memory 0x0800 0000 Reserved 0x0000 0000 0x0010 0000 Flash, system memory or SRAM, depending on **BOOT** configuration 0x0000 0000 Reserved

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Memory mapping STM32L4A6xG

Table 18. STM32L4A6xG memory map and peripheral register boundary addresses<sup>(1)</sup>

Bus	Boundary address	Size (bytes)	Peripheral
AHB4	0xA000 1000 - 0xA000 13FF	1 KB	QUADSPI
AHB3	0xA000 0400 - 0xA000 0FFF	3 KB	Reserve d
ALIDO	0xA000 0000 - 0xA000 03FF	1 KB	FMC
-	0x5006 0C00 - 0x5FFF FFFF	~260 MB	Reserved
	0x5006 0800 - 0x5006 0BFF	1 KB	RNG
	0x5006 0400 - 0x5006 07FF	1 KB	HASH
	0x5006 0000 - 0x5006 03FF	1 KB	AES
	0x5005 0400 - 0x5005 FFFF	62 KB	Reserved
	0x5005 0000 - 0x5005 03FF	1 KB	DCMI
	0x5004 0400 - 0x5004 FFFF	62 KB	Reserved
	0x5004 0000 - 0x5004 03FF	1 KB	ADC
	0x5000 0000 - 0x5003 FFFF	16 KB	OTG_FS
AHB2	0x4800 2400 - 0x4FFF FFFF	~127 MB	Reserved
ALIDZ	0x4800 2000 - 0x4800 23FF	1 KB	GPIOI
	0x4800 1C00 - 0x4800 1FFF	1 KB	GPIOH
	0x4800 1800 - 0x4800 1BFF	1 KB	GPIOG
	0x4800 1400 - 0x4800 17FF	1 KB	GPIOF
	0x4800 1000 - 0x4800 13FF	1 KB	GPIOE
	0x4800 0C00 - 0x4800 0FFF	1 KB	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 KB	GPIOC
	0x4800 0400 - 0x4800 07FF	1 KB	GPIOB
	0x4800 0000 - 0x4800 03FF	1 KB	GPIOA
-	0x4002 BC00 - 0x47FF FFFF	~127 MB	Reserved

STM32L4A6xG Memory mapping

Table 18. STM32L4A6xG memory map and peripheral register boundary addresses<sup>(1)</sup> (continued)

Bus	Boundary address	Size (bytes)	Peripheral
	0x4002 B000 - 0x4002 BBFF	3 KB	DMA2D
	0x4002 4400 - 0x4002 AFFF	26 KB	Reserved
	0x4002 4000 - 0x4002 43FF	1 KB	TSC
	0x4002 3400 - 0x4002 3FFF	1 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
AHB1	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
ALIDI	0x4002 2000 - 0x4002 23FF	1 KB	FLASH registers
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0800 - 0x4002 0FFF	2 KB	Reserved
	0x4002 0400 - 0x4002 07FF	1 KB	DMA2
	0x4002 0000 - 0x4002 03FF	1 KB	DMA1
	0x4001 6400 - 0x4001 FFFF	39 KB	Reserved
	0x4001 6000 - 0x4001 63FF	1 KB	DFSDM1
	0x4001 5C00 - 0x4001 5FFF	1 KB	Reserved
	0x4001 5800 - 0x4001 5BFF	1 KB	SAI2
	0x4001 5400 - 0x4001 57FF	1 KB	SAI1
	0x4001 4C00 - 0x4001 53FF	2 KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16
	0x4001 4000 - 0x4001 43FF	1 KB	TIM15
APB2	0x4001 3C00 - 0x4001 3FFF	1 KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1 KB	USART1
	0x4001 3400 - 0x4001 37FF	1 KB	TIM8
	0x4001 3000 - 0x4001 33FF	1 KB	SPI1
	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1
	0x4001 2800 - 0x4001 2BFF	1 KB	SDMMC1
	0x4001 2000 - 0x4001 27FF	2 KB	Reserved
	0x4001 1C00 - 0x4001 1FFF	1 KB	FIREWALL
	0x4001 0800- 0x4001 1BFF	5 KB	Reserved
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI

Memory mapping STM32L4A6xG

Table 18. STM32L4A6xG memory map and peripheral register boundary addresses<sup>(1)</sup> (continued)

Bus	Boundary address	Size (bytes)	Peripheral
	0x4001 0200 - 0x4001 03FF		COMP
APB2	0x4001 0030 - 0x4001 01FF	1 KB	VREFBUF
	0x4001 0000 - 0x4001 002F		SYSCFG
	0x4000 9800 - 0x4000 FFFF	26 KB	Reserved
	0x4000 9400 - 0x4000 97FF	1 KB	LPTIM2
	0x4000 8C00 - 0x4000 93FF	2 KB	Reserved
	0x4000 8800 - 0x4000 8BFF	1 KB	SWPMI1
	0x4000 8400 - 0x4000 87FF	1 KB	I2C4
	0x4000 8000 - 0x4000 83FF	1 KB	LPUART1
	0x4000 7C00 - 0x4000 7FFF	1 KB	LPTIM1
	0x4000 7800 - 0x4000 7BFF	1 KB	OPAMP
	0x4000 7400 - 0x4000 77FF	1 KB	DAC1
APB1	0x4000 7000 - 0x4000 73FF	1 KB	PWR
	0x4000 6800 - 0x4000 6FFF	1 KB	Reserved
	0x4000 6800 - 0x4000 6BFF	1 KB	CAN2
	0x4000 6400 - 0x4000 67FF	1 KB	CAN1
	0x4000 6000 - 0x4000 63FF	1 KB	CRS
	0x4000 5C00- 0x4000 5FFF	1 KB	I2C3
	0x4000 5800 - 0x4000 5BFF	1 KB	I2C2
	0x4000 5400 - 0x4000 57FF	1 KB	I2C1
	0x4000 5000 - 0x4000 53FF	1 KB	UART5
	0x4000 4C00 - 0x4000 4FFF	1 KB	UART4

STM32L4A6xG Memory mapping

Table 18. STM32L4A6xG memory map and peripheral register boundary addresses<sup>(1)</sup> (continued)

Bus	Boundary address	Size (bytes)	Peripheral
	0x4000 4800 - 0x4000 4BFF	1 KB	USART3
	0x4000 4400 - 0x4000 47FF	1 KB	USART2
	0x4000 4000 - 0x4000 43FF	1 KB	Reserved
	0x4000 3C00 - 0x4000 3FFF	1 KB	SPI3
	0x4000 3800 - 0x4000 3BFF	1 KB	SPI2
	0x4000 3400 - 0x4000 37FF	1 KB	Reserved
	0x4000 3000 - 0x4000 33FF	1 KB	IWDG
	0x4000 2C00 - 0x4000 2FFF	1 KB	WWDG
APB1	0x4000 2800 - 0x4000 2BFF	1 KB	RTC
	0x4000 2400 - 0x4000 27FF	1 KB	LCD
	0x4000 1800 - 0x4000 23FF	3 KB	Reserved
	0x4000 1400 - 0x4000 17FF	1 KB	TIM7
	0x4000 1000 - 0x4000 13FF	1 KB	TIM6
	0x4000 0C00- 0x4000 0FFF	1 KB	TIM5
	0x4000 0800 - 0x4000 0BFF	1 KB	TIM4
	0x4000 0400 - 0x4000 07FF	1 KB	TIM3
	0x4000 0000 - 0x4000 03FF	1 KB	TIM2

<sup>1.</sup> The gray color is used for reserved boundary addresses.

# 6 Electrical characteristics

### 6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V<sub>SS</sub>.

### 6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A = 25$  °C and  $T_A = T_A$ max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean  $\pm 3\sigma$ ).

### 6.1.2 Typical values

Unless otherwise specified, typical data are based on  $T_A = 25$  °C,  $V_{DD} = V_{DDA} = 3$  V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean  $\pm 2\sigma$ ).

# 6.1.3 Typical curves

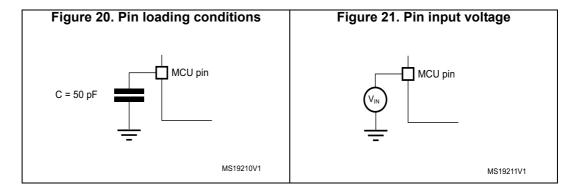
Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

### 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in Figure 20.

### 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in Figure 21.



### 6.1.6 Power supply scheme

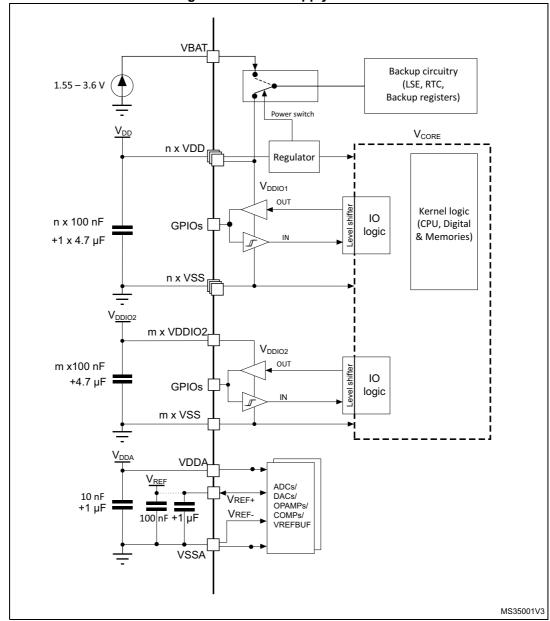


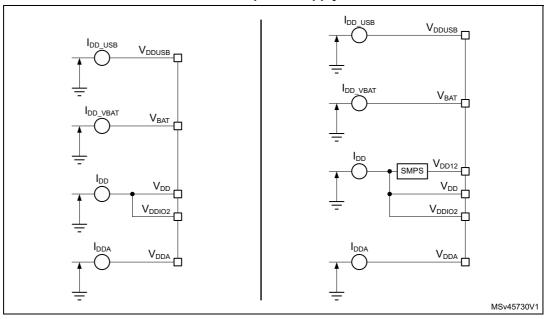
Figure 22. Power supply scheme

Caution:

Each power supply pair  $(V_{DD}/V_{SS}, V_{DDA}/V_{SSA})$  etc.) must be decoupled with filtering ceramic capacitors as shown above. These capacitors must be placed as close as possible to, or below, the appropriate pins on the underside of the PCB to ensure the good functionality of the device.

#### 6.1.7 **Current consumption measurement**

Figure 23. Current consumption measurement scheme with and without external **SMPS** power supply



The I<sub>DD ALL</sub> parameters given in *Table 26* to *Table 48* represent the total MCU consumption including the current supplying  $V_{DD}$ ,  $V_{DDIO2}$ ,  $V_{DDA}$ ,  $V_{DDUSB}$  and  $V_{BAT}$ .

#### 6.2 **Absolute maximum ratings**

Stresses above the absolute maximum ratings listed in *Table 19: Voltage characteristics*, Table 20: Current characteristics and Table 21: Thermal characteristics may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. Exposure to maximum rating conditions for extended periods may affect device reliability. Device mission profile (application conditions) is compliant with JEDEC JESD47 qualification standard, extended mission profiles are available on demand.

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Table 19. Voltage characteristics<sup>(1)</sup>

Symbol	Ratings		Min	Max	Unit
V <sub>DDX</sub> - V <sub>SS</sub>	External main supply voltage (including VDDA, VDDIO2, VDDUSB, VLCD, VBAT)		-0.3	4.0	
\/ \/	External SMPS supply voltage	Range 1	-0.3	1.4	
$V_{\rm DD12}$ - $V_{\rm SS}$	VSS External Own O supply voltage	Range 2	-0.3	1.4	
	Input voltage on FT_xxx pins		V <sub>SS</sub> -0.3	$\begin{array}{c} \text{min } (V_{DD}, V_{DDA}, V_{DDIO2}, \\ V_{DDUSB}, V_{LCD}) + 4.0^{(3)(4)} \end{array}$	٧
$V_{IN}^{(2)}$	Input voltage on TT_xx pins		V <sub>SS</sub> -0.3	' <sub>SS</sub> -0.3 4.0	
	Input voltage on TT_xx pins Input voltage on BOOT0 pin		V <sub>SS</sub>	9.0	
	Input voltage on any other pins		V <sub>SS</sub> -0.3	4.0	
$ \Delta V_{DDx} $	Variations between different V <sub>DDX</sub> power pins of the same domain		-	50	mV
V <sub>SSx</sub> -V <sub>SS</sub>	Variations between all the different ground pins <sup>(5)</sup>		-	50	mV

All main power (V<sub>DD</sub>, V<sub>DDA</sub>, V<sub>DDIO2</sub>, V<sub>DDUSB</sub>, V<sub>LCD</sub>, V<sub>BAT</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supply, in the permitted range.

Table 20. Current characteristics

Symbol	Ratings	Max	Unit
ΣIV <sub>DD</sub>	Total current into sum of all V <sub>DD</sub> power lines (source) <sup>(1) (2)</sup>	150	
ΣIV <sub>SS</sub>	Total current out of sum of all V <sub>SS</sub> ground lines (sink) <sup>(1)</sup>	150	
IV <sub>DD(PIN)</sub>	Maximum current into each V <sub>DD</sub> power pin (source) <sup>(1)(2)</sup>	100	
IV <sub>SS(PIN)</sub>	Maximum current out of each V <sub>SS</sub> ground pin (sink) <sup>(1)</sup>	100	
	Output current sunk by any I/O and control pin except FT_f	20	
I <sub>IO(PIN)</sub>	Output current sunk by any FT_f pin	20	
	Output current sourced by any I/O and control pin	20	mA
ΣΙ	Total output current sunk by sum of all I/Os and control pins <sup>(3)</sup>	100	
$\Sigma I_{IO(PIN)}$	Total output current sourced by sum of all I/Os and control pins <sup>(3)</sup>	100	
I <sub>INJ(PIN)</sub> <sup>(4)</sup>	Injected current on FT_xxx, TT_xx, RST and B pins, except PA4, PA5	-5/+0 <sup>(5)</sup>	
	Injected current on PA4, PA5	-5/0	
$\sum  I_{\text{INJ(PIN)}} $	Total injected current (sum of all I/Os and control pins) <sup>(6)</sup>	25	

All main power (V<sub>DD</sub>, V<sub>DDA</sub>, V<sub>DDIO2</sub>, V<sub>DDUSB</sub>, V<sub>LCD</sub>, V<sub>BAT</sub>) and ground (V<sub>SS</sub>, V<sub>SSA</sub>) pins must always be connected to the external power supplies, in the permitted range.

<sup>2.</sup> Valid also for  $V_{DD12}$  on SMPS Package



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<sup>2.</sup> V<sub>IN</sub> maximum must always be respected. Refer to *Table 20: Current characteristics* for the maximum allowed injected current values.

<sup>3.</sup> This formula has to be applied only on the power supplies related to the IO structure described in the pin definition table.

<sup>4.</sup> To sustain a voltage higher than 4 V the internal pull-up/pull-down resistors must be disabled.

<sup>5.</sup> Include VREF- pin.

This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.

- Positive injection (when V<sub>IN</sub> > V<sub>DDIOx</sub>) is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
- A negative injection is induced by V<sub>IN</sub> < V<sub>SS</sub>. I<sub>INJ(PIN)</sub> must never be exceeded. Refer also to *Table 19: Voltage characteristics* for the minimum allowed input voltage values.
- When several inputs are submitted to a current injection, the maximum ∑|I<sub>INJ(PIN)</sub>| is the absolute sum of the negative injected currents (instantaneous values).

**Table 21. Thermal characteristics** 

Symbol	Ratings	Value	Unit
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C
T <sub>J</sub>	Maximum junction temperature	150	°C

# 6.3 Operating conditions

# 6.3.1 General operating conditions

Table 22. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>HCLK</sub>	Internal AHB clock frequency	-	0	80	
f <sub>PCLK1</sub>	Internal APB1 clock frequency	-	0	80	MHz
f <sub>PCLK2</sub>	Internal APB2 clock frequency	-	0	80	
$V_{DD}$	Standard operating voltage	-	1.71 (1)	3.6	V
M	Ctandard enerating valtage	full frequency range	1.08	4 22	V
V <sub>DD12</sub>	Standard operating voltage	up to 26MHz	1.05	- 1.32	V
V	DCI15:21 I/Os supply voltago	At least one I/O in PG[15:2] used	1.08	3.6	V
$V_{\rm DDIO2}$	PG[15:2] I/Os supply voltage	PG[15:2] not used	0	3.6	V
		ADC or COMP used	1.62		
		DAC or OPAMP used	1.8		
$V_{DDA}$	Analog supply voltage	VREFBUF used	2.4	3.6	V
		ADC, DAC, OPAMP, COMP, VREFBUF not used	0		

Table 22. General operating conditions (continued)

Symbol	Parameter	С	onditions	Min	Max	Unit
V <sub>BAT</sub>	Backup operating voltage		-	1.55	3.6	
\ <u></u>	USB supply voltage	USB used		3.0	3.6	
V <sub>DDUSB</sub>	USB supply voltage	USB not used		0	3.6	
		TT_xx I/O		-0.3	V <sub>DDIOx</sub> +0.3	V
		воото		0	9	]
V <sub>IN</sub>	I/O input voltage	All I/O except	BOOT0 and TT_xx	-0.3	$\begin{array}{c} {\rm Min(Min(V_{DD},V_{DDA},}\\ {\rm V_{DDIO2},V_{DDUSB},}\\ {\rm V_{LCD})+3.6V,}\\ {\rm 5.5V)^{(2)(3)}} \end{array}$	
		LQFP144	-	-	625	
		LQFP100	-	-	476	
_	Power dissipation at	LQFP64	-	-	444	\
$P_{D}$	$T_A = 85  ^{\circ}\text{C}$ for suffix $6^{(4)}$	UFBGA169		-	385	mW
		UFBGA132	-	-	364	
		WLCSP100	-	-	559	
		LQFP144	-	-	156	
		LQFP100	-	-	119	
P <sub>D</sub>	Power dissipation at	LQFP64	-	-	111	mW
r <sub>D</sub>	$T_A = 125 ^{\circ}\text{C}$ for suffix $3^{(4)}$	UFBGA169		-	96	] ''''
		UFBGA132	-	-	91	
		WLCSP100	-	-	140	
	Ambient temperature for the	Maximum pov	ver dissipation	-40	85	
TA	suffix 6 version	Low-power dis	ssipation <sup>(5)</sup>	-40	105	°C
14	Ambient temperature for the	Maximum pov	ver dissipation	-40	125	
	suffix 3 version	Low-power dis	ssipation <sup>(5)</sup>	-40	130	
TJ	Junction temperature range	Suffix 6 version	n	<del>-4</del> 0	105	- °C
1 J		Suffix 3 version	on	-40	130	

<sup>1.</sup> When RESET is released functionality is guaranteed down to  $\rm V_{BOR0}\,Min.$ 

This formula has to be applied only on the power supplies related to the IO structure described by the pin definition table. Maximum I/O input voltage is the smallest value between Min(V<sub>DD</sub>, V<sub>DDA</sub>, V<sub>DDIO2</sub>, V<sub>DDUSB</sub>, V<sub>LCD</sub>)+3.6 V and 5.5V.

<sup>3.</sup> For operation with voltage higher than Min ( $V_{DD}$ ,  $V_{DDA}$ ,  $V_{DDIO2}$ ,  $V_{DDUSB}$ ,  $V_{LCD}$ ) +0.3 V, the internal Pull-up and Pull-Down resistors must be disabled.

 $<sup>4. \</sup>quad \text{If $T_A$ is lower, higher $P_D$ values are allowed as long as $T_J$ does not exceed $T_{Jmax}$ (see $Section 7.7: Thermal characteristics).} \\$ 

In low-power dissipation state, T<sub>A</sub> can be extended to this range as long as T<sub>J</sub> does not exceed T<sub>Jmax</sub> (see Section 7.7: Thermal characteristics).

# 6.3.2 Operating conditions at power-up / power-down

The parameters given in *Table 23* are derived from tests performed under the ambient temperature condition summarized in *Table 22*.

Table 23. Operating conditions at power-up / power-down<sup>(1)</sup>

Symbol	Parameter	Parameter Conditions Min		Max	Unit	
+	V <sub>DD</sub> rise time rate		0	∞	ue/\/	
t <sub>VDD</sub>	V <sub>DD</sub> fall time rate	-	10	∞	μs/V	
4	V <sub>DDA</sub> rise time rate		0	∞		
t <sub>VDDA</sub>	V <sub>DDA</sub> fall time rate	-	10	∞	μs/V	
+	V <sub>DDUSB</sub> rise time rate		0	∞	μs/V	
<sup>t</sup> VDDUSB	V <sub>DDUSB</sub> fall time rate	-	10	∞	μ5/ ν	
+	V <sub>DDIO2</sub> rise time rate		0	∞	ue/\/	
t <sub>VDDIO2</sub>	V <sub>DDIO2</sub> fall time rate	-	10	∞	µs/V	

<sup>1.</sup> At Power up, the  $V_{DD12}$  voltage should not be forced externally

The requirements for power-up/down sequence specified in *Section 3.10.1: Power supply schemes* must be respected.

# 6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 24* are derived from tests performed under the ambient temperature conditions summarized in *Table 22: General operating conditions*.

Table 24. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions <sup>(1)</sup>	Min	Тур	Max	Unit
t <sub>RSTTEMPO</sub> <sup>(2)</sup>	Reset temporization after BOR0 is detected	V <sub>DD</sub> rising	-	250	400	μs
V <sub>BOR0</sub> (2)	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.7	V
VBOR0	Brown-out reset timeshold o	Falling edge	1.6	1.64	1.69	V
V	Brown-out reset threshold 1	Rising edge	2.06	2.1	2.14	V
V <sub>BOR1</sub>	Brown-out reset timeshold i	Falling edge	1.96	2	2.04	V
V	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	V
V <sub>BOR2</sub>	Brown-out reset timeshold 2	Falling edge	2.16	2.20	2.24	V
V	Brown-out reset threshold 3	Rising edge	2.56	2.61	2.66	V
V <sub>BOR3</sub>	Brown-out reset timeshold 3	Falling edge	2.47	2.52	2.57	V
V	Drown out road throshold 4	Rising edge	2.85	2.90	2.95	\/
$V_{BOR4}$	Brown-out reset threshold 4	Falling edge	2.76	2.81	2.86	V
V	Programmable voltage	Rising edge	2.1	2.15	2.19	V
V <sub>PVD0</sub>	detector threshold 0	Falling edge	2	2.05	2.1	V



Table 24. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions <sup>(1)</sup>	Min	Тур	Max	Unit	
V	DVD throubold 1	Rising edge	2.26	2.31	2.36	V	
V <sub>PVD1</sub>	PVD threshold 1	Falling edge	2.15	2.20	2.25	V	
V	PVD threshold 2	Rising edge	2.41	2.46	2.51	V	
V <sub>PVD2</sub>	FVD tillesiloid 2	Falling edge	2.31	2.36	2.41	V	
V	PVD threshold 3	Rising edge	2.56	2.61	2.66	V	
V <sub>PVD3</sub>	1 VD tillesiloid 5	Falling edge	2.47	2.52	2.57	V	
V	PVD threshold 4	Rising edge	2.69	2.74	2.79	V	
V <sub>PVD4</sub>	1 VD tillesiloid 4	Falling edge	2.59	2.64	2.69	V	
V	PVD threshold 5	Rising edge	2.85	2.91	2.96	\/	
V <sub>PVD5</sub>	FVD tillesiloid 5	Falling edge	2.75	2.81	2.86	V	
V	PVD threshold 6	Rising edge	2.92	2.98	3.04	\/	
V <sub>PVD6</sub>	FVD tillesiloid 6	Falling edge	2.84	2.90	2.96	V	
V <sub>hyst_BORH0</sub>	Hysteresis voltage of BORH0	Hysteresis in continuous mode	-	20	-	mV	
		Hysteresis in other mode	ı	30	-		
V <sub>hyst_BOR_PVD</sub>	Hysteresis voltage of BORH (except BORH0) and PVD	-	-	100	-	mV	
I <sub>DD</sub> (BOR_PVD) <sup>(2)</sup>	BOR <sup>(3)</sup> (except BOR0) and PVD consumption from V <sub>DD</sub>	-	-	1.1	1.6	μΑ	
V <sub>PVM1</sub>	V <sub>DDUSB</sub> peripheral voltage monitoring	-	1.18	1.22	1.26	٧	
V	V <sub>DDA</sub> peripheral voltage	Rising edge	1.61	1.65	1.69	V	
V <sub>PVM3</sub>	monitoring	Falling edge	1.6	1.64	1.68	V V V mV mV	
V	V <sub>DDA</sub> peripheral voltage	Rising edge	1.78	1.82	1.86	\/	
$V_{PVM4}$	monitoring	Falling edge	1.77	1.81	1.85	V	
V <sub>hyst_PVM3</sub>	PVM3 hysteresis	-	-	10	-	mV	
V <sub>hyst_PVM4</sub>	PVM4 hysteresis	-	-	10	-	mV	
I <sub>DD</sub> (PVM1/PVM2)	PVM1 and PVM2 consumption from V <sub>DD</sub>	-	-	0.2	-	μΑ	
I <sub>DD</sub> (PVM3/PVM4)	PVM3 and PVM4 consumption from V <sub>DD</sub>	-	-	2	-	μΑ	

Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

<sup>3.</sup> BOR0 is enabled in all modes (except shutdown) and its consumption is therefore included in the supply current characteristics tables.



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<sup>2.</sup> Guaranteed by design.

# 6.3.4 Embedded voltage reference

The parameters given in *Table 25* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.

Table 25. Embedded internal voltage reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>REFINT</sub>	Internal reference voltage	-40 °C < T <sub>A</sub> < +130 °C	1.182	1.212	1.232	V
t <sub>S_vrefint</sub> (1)	ADC sampling time when reading the internal reference voltage	-	4 <sup>(2)</sup>	-	-	μs
t <sub>start_vrefint</sub>	Start time of reference voltage buffer when ADC is enable	-	-	8	12 <sup>(2)</sup>	μs
I <sub>DD</sub> (V <sub>REFINTBUF</sub> )	V <sub>REFINT</sub> buffer consumption from V <sub>DD</sub> when converted by ADC	-	-	12.5	20 <sup>(2)</sup>	μΑ
$\Delta V_{REFINT}$	Internal reference voltage spread over the temperature range	V <sub>DD</sub> = 3 V	-	5	7.5 <sup>(2)</sup>	mV
T <sub>Coeff</sub>	Average temperature coefficient	-40°C < T <sub>A</sub> < +130°C	-	30	50 <sup>(2)</sup>	ppm/°C
A <sub>Coeff</sub>	Long term stability	1000 hours, T = 25°C	ı	300	1000 <sup>(2)</sup>	ppm
V <sub>DDCoeff</sub>	Average voltage coefficient	3.0 V < V <sub>DD</sub> < 3.6 V	-	250	1200 <sup>(2)</sup>	ppm/V
V <sub>REFINT_DIV1</sub>	1/4 reference voltage		24	25	26	-
V <sub>REFINT_DIV2</sub>	1/2 reference voltage	_	49	50	51	% V <sub>REFINT</sub>
V <sub>REFINT_DIV3</sub>	3/4 reference voltage		74	75	76	INET IIVI

<sup>1.</sup> The shortest sampling time can be determined in the application by multiple iterations.



<sup>2.</sup> Guaranteed by design.

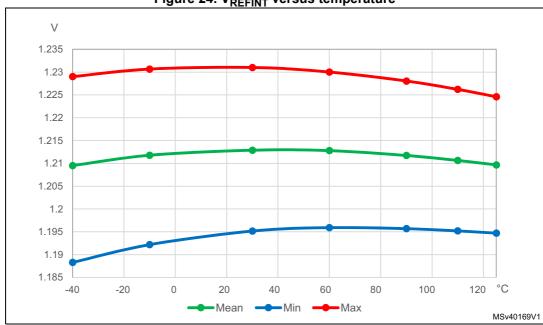


Figure 24. V<sub>REFINT</sub> versus temperature

### 6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 23: Current consumption* measurement scheme with and without external SMPS power supply.

### Typical and maximum current consumption

The MCU is placed under the following conditions:

- · All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted with the minimum wait states number, depending on the f<sub>HCLK</sub> frequency (refer to the table "Number of wait states according to CPU clock (HCLK) frequency" available in the RM0351 reference manual).
- When the peripherals are enabled f<sub>PCLK</sub> = f<sub>HCLK</sub>

The parameters given in *Table 26* to *Table 49* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.



Table 26. Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART enable (Cache ON Prefetch OFF)

		Cond	ditions				TYP					MAX <sup>(1)</sup>			
Symbol	Parameter	-	Voltage scaling	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
				26 MHz	2.65	2.69	2.82	3.05	3.51	2.9	3.0	3.3	3.8	4.7	
				16 MHz	1.68	1.72	1.85	2.07	2.53	1.9	2.0	2.2	2.7	3.7	
				8 MHz	0.91	0.94	1.07	1.29	1.74	1.0	1.1	1.4	1.8	2.8	
			Range 2	4 MHz	0.52	0.55	0.68	0.9	1.35	0.6	0.7	0.9	1.4	2.4	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up		2 MHz	0.33	0.36	0.48	0.7	1.15	0.4	0.5	0.7	1.2	2.2	
Supply current in Run mode		to 48MHz		1 MHz	0.23	0.26	0.38	0.6	1.06	0.3	0.4	0.6	1.1	2.0	
		included, bypass mode		100 kHz	0.14	0.17	0.3	0.52	0.97	0.2	0.3	0.5	1.0	2.0	m A
	Run mode	PLL ON above 48 MHz all		80 MHz	9.44	9.5	9.67	9.93	10.4	10.3	10.4	10.7	11.3	12.4	IIIA
		peripherals		72 MHz	8.52	8.59	8.75	9.01	9.53	9.3	9.4	9.7	10.3	11.4	
		disable		64 MHz	7.61	7.67	7.83	8.09	8.61	8.3	8.4	8.7	9.3	10.4	
			Range 1	48 MHz	5.72	5.78	5.94	6.2	6.72	6.3	6.4	6.7	7.3	8.4	
				32 MHz	3.87	3.92	4.07	4.33	4.84	4.2	4.4	4.7	5.2	6.3	
				24 MHz	2.94	2.99	3.14	3.39	3.9	3.2	3.4	3.6	4.2	5.3	
				16 MHz	2.01	2.06	2.2	2.45	2.95	2.2	2.3	2.6	3.2	4.2	
	Cumple			2 MHz	274	307	444	678	1150	318	425	656	1167	2197	
I <sub>DD_ALL</sub>	Supply current in	f <sub>HCLK</sub> = f <sub>MSI</sub>		1 MHz	158	195	328	564	1040	195	309	558	1047	2084	Ι.Δ
(LPR un)	Low-power run mode	all peripherals dis	able	400 kHz	88.2	123	256	490	969	116	232	485	973	2012	μΑ
	. 3.1 111000			100 kHz	63	90.6	223	457	934	79	195	447	942	1975	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.

Table 27. Current consumption in Run modes, code with data processing running from Flash, (ART enable Cache ON Prefetch OFF) and power supplied (by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

Symbol	Doromotor	Conditions <sup>(1)</sup>				TYP			Unit
Symbol	Parameter	-	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	Ullit
			80 MHz	3.39	3.42	3.48	3.57	3.74	
			72 MHz	3.06	3.09	3.15	3.24	3.43	
			64 MHz	2.74	2.76	2.81	2.91	3.10	
			48 MHz	2.06	2.08	2.14	2.23	2.42	
			32 MHz	1.39	1.41	1.46	1.56	1.74	
I (Bun)	Supply current in Run	f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48MHz included, bypass mode PLL ON above	24 MHz	1.06	1.07	1.13	1.22	1.40	- mA
I <sub>DD_ALL</sub> (Run)	mode	48 MHz all peripherals disable	16 MHz	0.72	0.74	0.79	0.88	1.06	IIIA
			8 MHz	0.39	0.41	0.46	0.56	0.75	
			4 MHz	0.22	0.24	0.29	0.39	0.58	
			2 MHz	0.14	0.16	0.21	0.30	0.50	
			1 MHz	0.10	0.11	0.16	0.26	0.46	
			100 kHz	0.06	0.07	0.13	0.22	0.42	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V





Table 28. Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART disable

		Cond	ditions				TYP					MAX <sup>(1)</sup>			
Symbol	Parameter	-	Voltage scaling	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C		125 °C	Unit
				26 MHz	3.1	3.14	3.28	3.51	3.98	3.5	3.6	3.8	4.3	5.3	
				16 MHz	2.19	2.23	2.36	2.59	3.05	2.5	2.6	2.8	3.3	4.3	
				8 MHz	1.22	1.26	1.39	1.61	2.07	1.4	1.5	1.7	2.2	3.2	
		_	Range 2	4 MHz	0.69	0.73	0.85	1.08	1.53	8.0	0.9	1.1	1.6	2.6	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48MHz		2 MHz	0.41	0.44	0.57	0.79	1.24	0.5	0.6	0.8	1.3	2.3	
	0	included, bypass		1 MHz	0.27	0.3	0.43	0.65	1.1	0.3	0.4	0.6	1.1	2.1	
I <sub>DD_ALL</sub> (Run)	Supply current in	mode		100 kHz	0.14	0.18	0.3	0.52	0.97	0.2	0.3	0.5	1.0	2.0	mA.
IDD_ALL(I (air)	Run mode	PLL ON above		80 MHz	10	10.1	10.3	10.5	11.1	11.1	11.2	11.6	12.2	13.31	] '''' \
		48 MHz all peripherals		72 MHz	9.02	9.1	9.29	9.59	10.1	10	10.1	10.5	11.0	12.2	
		disable		64 MHz	8.94	9.02	9.2	9.48	10	9.9	10.1	10.4	11.0	12.1	
			Range 1	48 MHz	7.51	7.59	7.77	8.05	8.59	8.4	8.6	8.9	9.5	10.6	
				32 MHz	5.38	5.45	5.62	5.88	6.41	6.0	6.2	6.5	7.0	8.2	
				24 MHz	4.07	4.12	4.28	4.54	5.06	4.5	4.7	5.0	5.5	6.6	
				16 MHz	2.86	2.92	3.07	3.33	3.84	3.2	3.3	3.6	4.2	5.3	
	Cupply			2 MHz	378	412	549	782	1260	436	538	761	1287	2317	
I <sub>DD ALL</sub>	Supply current in	f <sub>HCLK</sub> = f <sub>MSI</sub>		1 MHz	213	246	381	618	1100	255	367	609.	1105	2138	μA
(LPRun)	Low-power run	all peripherals disable	able	400 kHz	101	144	277	514	989	141	256	507	995	2033	μΑ
	Tull			100 kHz	62	95.8	228	463	939	85	201	454	947	1982	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.

Electrical characteristics

Table 29. Current consumption in Run modes, code with data processing running from Flash, ART disable and power supplied by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

		Conditions <sup>(1)</sup>	ייייייייייייייייייייייייייייייייייייייי			TYP			Uni
Symbol	Parameter	-	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	3.77 3.45 3.41 2.89 2.11 1.63 1.20 0.69 0.47 0.34 0.28 0.22	125 °C	t
			80 MHz	3.59	3.63	3.70	3.77	3.99	
			72 MHz	3.24	3.27	3.34	3.45	3.63	
			64 MHz	3.21	3.24	3.31	3.41	3.59	
			48 MHz	2.70	2.73	2.79	2.89	3.09	
			32 MHz	1.93	1.96	2.02	2.11	2.30	
I (Pun)	Supply current in Run	f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48MHz included, bypass mode PLL ON above	24 MHz	1.46	1.48	1.54	1.63	1.82	mA
I <sub>DD_ALL</sub> (Run)	mode	48 MHz all peripherals disable	16 MHz	1.03	1.05	1.10	1.20	1.38	111/7
			8 MHz	0.53	0.54	0.60	0.69	0.89	
			4 MHz	0.30	0.31	0.37	0.47	0.66	
			2 MHz	0.18	0.19	0.25	0.34	0.53	
			1 MHz	0.12	0.13	0.19	0.28	0.47	
			100 kHz	0.06	0.08	0.13	0.22	0.42	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V





Table 30. Current consumption in Run and Low-power run modes, code with data processing running from SRAM1

		Con	ditions				TYP					MAX <sup>(1)</sup>			
Symbol	Parameter	-	Voltage scaling	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C 3.8 2.7 1.8 1.4 1.2 1.1 1.0 11.6 10.6 9.5 7.4 5.3 4.3 3.2 1154 1034 958	125 °C	Unit
				26 MHz	2.72	2.76	2.89	3.12	3.58	3.0	3.1	3.4	3.8	4.8	
				16 MHz	1.73	1.76	1.89	2.12	2.58	1.9	2.0	2.3	2.7	3.7	
				8 MHz	0.93	0.96	1.09	1.31	1.77	1.0	1.1	1.42	1.8	2.8	
			Range 2	4 MHz	0.53	0.57	0.69	0.91	1.36	0.6	0.7	0.9	1.4	2.4	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48MHz		2 MHz	0.33	0.36	0.49	0.71	1.16	0.4	0.5	0.7	1.2	2.2	
	0	included, bypass		1 MHz	0.23	0.26	0.39	0.61	1.06	0.2	0.4	0.6	1.1	2.1	
I <sub>DD_ALL</sub> (Run)	Supply current in	mode		100 kHz	0.14	0.17	0.3	0.52	0.97	0.2	0.3	0.5	1.0	2.0	mA
IDD_ALL(TOTT)	Run mode	PLL ON above 48 MHz all		80 MHz	9.71	9.78	9.95	10.2	10.8	10.6	10.7	11.1	11.6	12.7	] ''" `
		peripherals		72 MHz	8.77	8.84	9	9.27	9.8	9.6	9.7	10.0	10.6	11.7	
		disable		64 MHz	7.82	7.89	8.05	8.32	8.84	8.5	8.7	9.0	9.5	10.6	
			Range 1	48 MHz	5.87	5.93	6.1	6.36	6.88	6.4	6.6	6.9	7.4	8.5	
				32 MHz	3.97	4.03	4.18	4.44	4.95	4.4	4.5	4.8	5.3	6.4	
				24 MHz	3.02	3.07	3.22	3.47	3.99	3.3	3.5	3.7	4.3	5.4	
				16 MHz	2.07	2.11	2.26	2.51	3.02	2.3	2.4	2.7	3.2	4.3	
	Cupply			2 MHz	258	296	430	665	1140	295	402	634	1154	2180	
I <sub>DD_ALL</sub>	Supply current in	f <sub>HCLK</sub> = f <sub>MSI</sub> all peripherals dis	ahle	1 MHz	136	180	314	550	1020	170	283	530	1034	2065	μΑ
(LPRun)	low-power run mode	FLASH in power-		400 kHz	78.5	109	241	475	951	90	206	458	958	1991	μπ
				100 kHz	37.4	78.1	208	440	918	53	171	429	925	1957	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.

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Table 31. Current consumption in Run, code with data processing running from SRAM1 and power supplied by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

Cumbal	Dovomotov	Conditions <sup>(1)</sup>		ТҮР					Unit
Symbol	Parameter	-	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	
			80 MHz	3.49	3.52	3.58	3.67	3.88	
			72 MHz	3.15	3.18	3.24	3.33	3.52	
			64 MHz	2.81	2.84	2.89	2.99	3.18	
			48 MHz	2.11	2.13	2.19	2.29	2.47	
			32 MHz	1.43	1.45	1.50	1.60	1.78	
(Dun)	Cumply ourrent in Dun made	f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48MHz included, bypass mode PLL ON above	24 MHz	1.09	1.10	1.16	1.25	1.43	- A
I <sub>DD_ALL</sub> (Run)	Supply current in Run mode	48 MHz all peripherals disable	16 MHz	0.74	0.76	0.81	0.90	1.09	mA
			8 MHz	0.40	0.41	0.47	0.57	0.76	
			4 MHz	0.23	0.25	0.30	0.39	0.59	
			2 MHz	0.14	0.16	0.21	0.31	0.50	
			1 MHz	0.10	0.11	0.17	0.26	0.46	
			100 kHz	0.06	0.07	0.13	0.22	0.42	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V



Table 32. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART enable (Cache ON Prefetch OFF)

			Condition	ons	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
			Z	Reduced code <sup>(1)</sup>	2.65		102	
			2 3 MHz	Coremark	2.97		114	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up	Range : ∟k = 26	Dhrystone 2.1	3.1	mA	119	μΑ/MHz
		to 48 MHz	Ra fHCLK	Fibonacci	2.9		112	
I <sub>DD_ALL</sub>	Supply current in	included, bypass mode PLL ON	f.	While(1)	2.43		93	
(Run)	Run mode	above 48 MHz	1z	Reduced code <sup>(1)</sup>	9.44		118	
		all peripherals	ange 1 = 80 MHz	Coremark	10.6		133	
		disable	Range ∟k = 80	Dhrystone 2.1	10.9	mA	136	μΑ/MHz
			Ra fHCLK	Fibonacci	10.3		129	
			f.	While(1)	8.66		108	
				Reduced code <sup>(1)</sup>	274		137	
	Supply			Coremark	307		154	
I <sub>DD_ALL</sub> (LPRun)	current in Low-power	f <sub>HCLK</sub> = f <sub>MSI</sub> = 2 M all peripherals dis		Dhrystone 2.1	308	μΑ	154	μΑ/MHz
(=: : (air)	run	a pep.101410 410		Fibonacci	273		137	
				While(1)	258		129	

<sup>1.</sup> Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 33. Typical current consumption in Run, with different codes running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied (by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

		Co	onditions <sup>(</sup>	1)	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
			Zł	Reduced code <sup>(2)</sup>	1.14		44	
			26 MHz	Coremark	1.28		49	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to	= 26	Dhrystone 2.1	1.34		51	
		48 MHz included,	<sup>f</sup> нсск <sup>:</sup>	Fibonacci	1.25		48	
I <sub>DD_ALL</sub>	Supply current in	bypass mode PLL ON above	fнс	While(1)	1.05	mA	40	μΑ/MHz
(Run)	Run mode	48 MHz	ZŁ	Reduced code <sup>(2)</sup>	3.39	ША	42	μΑνινιπΖ
		all peripherals	80 MHz	Coremark	3.81		48	
		disable	98 =	Dhrystone 2.1	3.92		49	
			fнсск <sup>:</sup>	Fibonacci	3.70		46	
			fπ	While(1)	3.11		39	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%,  $V_{DD12}$  = 1.10 V

<sup>2.</sup> Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.



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Table 34. Typical current consumption in Run, with different codes running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied (by external SMPS ( $V_{DD12} = 1.05 \text{ V}$ )

		C	onditions <sup>(</sup>	1)	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
		$f_{HCLK} = f_{HSE}$ up to	Z	Reduced code <sup>(2)</sup>	1.04		40	
	Supply	48 MHz included, bypass mode PLL	MHz	Coremark	1.17		45	
I <sub>DD_ALL</sub>	current in	ON above	26	Dhrystone 2.1	1.22	mA	47	μΑ/MHz
(Run)	Run mode	48 MHz	되 II	Fibonacci	1.14		44	
		all peripherals disable	fнсск	While(1)	0.96		37	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%,  $V_{DD12} = 1.05 \text{ V}$ 

Table 35. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART disable

			Conditio	ns	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
			¥	Reduced code <sup>(1)</sup>	3.1		119	
			Z =	Coremark	2.85		110	
		$f_{HCLK} = f_{HSE}$ up to	Range 2 <sub>LK</sub> = 26 MHz	Dhrystone 2.1	2.86	mA	110	μΑ/MHz
		48 MHz included,	Ra fHCLK	Fibonacci	2.63		101	
I <sub>DD_ALL</sub>	Supply current in	bypass mode PLL ON above	<b>ੰ</b> ਜ਼	While(1)	2.42		93.1	
(Run)	Run mode	48 MHz	1 MHz	Reduced code <sup>(1)</sup>	10		125	
		all peripherals		Coremark	9.33		117	
		disable	Range LK = 80	Dhrystone 2.1	9.4	mA	118	μΑ/MHz
			Ra fHCLK	Fibonacci	8.66		108	
			ੂੰ ਮੁ	While(1)	8.61		108	
				Reduced code <sup>(1)</sup>	378		189	
	Supply	£ £ 0.MI		Coremark	412		206	
I <sub>DD_ALL</sub> (LPRun)	current in Low-power	f <sub>HCLK</sub> = f <sub>MSI</sub> = 2 MI  all peripherals disa		Dhrystone 2.1	418	μΑ	209	μΑ/MHz
(=: / (arr)	run	a pap. rorato atos		Fibonacci	392		196	
				While(1)	266		133	

<sup>1.</sup> Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

<sup>2.</sup> Reduced code used for characterization results provided in Table 26, Table 28, Table 30.

Table 36. Typical current consumption in Run modes, with different codes running from Flash, ART disable and power supplied by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

		C	onditions <sup>(</sup>	1)	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
			42	Reduced code <sup>(2)</sup>	1.34		51	
			26 MHz	Coremark	1.23		47	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to	= 26	Dhrystone 2.1	1.23		47	
		48 MHz included,	fHCLK =	Fibonacci	1.13		44	
$I_{DD\_ALL}$	Supply current in	bypass mode PLL ON above	f.	While(1)	1.04	mA	40	μΑ/MHz
(Run)	Run mode	48 MHz	77	Reduced code <sup>(1)</sup>	3.59	ША	45	μΑνίνιι ιΖ
		all peripherals	) MHz	Coremark	3.35		42	
		disable	= 80	Dhrystone 2.1	3.38		42	
			fHCLK :	Fibonacci	3.11		39	
			Į.	While(1)	3.10		39	

All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V

Table 37. Typical current consumption in Run modes, with different codes running from Flash, ART disable and power supplied by external SMPS ( $V_{DD12} = 1.05 \text{ V}$ )

		C	onditions <sup>(</sup>	1)	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to	MHz	Reduced code <sup>(2)</sup>	1.22		47	
	Supply	48 MHz included,		Coremark	1.12		43	
I <sub>DD_ALL</sub> (Run)	current in	bypass mode PLL ON above	= 26	Dhrystone 2.1	1.12	mA	43	μΑ/MHz
(1.101.)	Run mode	48 MHz		Fibonacci	1.03		40	
		all peripherals	<sup>f</sup> нсск	While(1)	0.95		37	

All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.05 V



<sup>2.</sup> Reduced code used for characterization results provided in Table 26, Table 28, Table 30.

<sup>2.</sup> Reduced code used for characterization results provided in Table 26, Table 28, Table 30.

Table 38. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1

			Conditio	ons	TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C  105  105  102  95  91  121  119  110  106  129  134	Unit
			2 MHz	Reduced code <sup>(1)</sup>	2.72		105	
			Z =	Coremark	2.72		105	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to	Range 2 ∟k = 26	Dhrystone 2.1	2.65	mA	102	μA/MHz
		48 MHz included,	Ra fHCLK	Fibonacci	2.47		95	
I <sub>DD_ALL</sub>	Supply current in	bypass mode PLL ON above	ĨĘ.	While(1)	2.37		91	
(Run)	Run mode	48 MHz all	1 MHz	Reduced code <sup>(1)</sup>	9.71		121	
		peripherals	<b>-</b> ₹	Coremark	9.7		121	
		disable	Range ` LK = 80	Dhrystone 2.1	9.48	mA	119	μΑ/MHz
			Ra fHCLK	Fibonacci	8.79		110	
			ᅸ	While(1)	8.45		106	
				Reduced code <sup>(1)</sup>	258		129	
	Supply	f -f -0.MI	ı_	Coremark	268		134	
I <sub>DD_ALL</sub> (LPRun)	current in Low-power	f <sub>HCLK</sub> = f <sub>MSI</sub> = 2 MH all peripherals disa		Dhrystone 2.1	240	μΑ	120	μΑ/MHz
(=: / tan)	run	a popordio diod		Fibonacci	230		115	
				While(1)	255		128	

<sup>1.</sup> Reduced code used for characterization results provided in Table 26, Table 28, Table 30.

Table 39. Typical current consumption in Run, with different codes running from SRAM1 and power supplied by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

		Co	nditions <sup>(1)</sup>		TYP		TYP	
Symbol	Parameter	-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit
			Z	Reduced code <sup>(2)</sup>	1.17		45	
			3 MHz	Coremark	1.17		45	
		f -f un to	= 26	Dhrystone 2.1	1.14		44	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48 MHz included,	fHCLK :	Fibonacci	1.07		41	
I <sub>DD_ALL</sub>	Supply current in	bypass mode	f,	While(1)	1.02	mA	39	μΑ/MHz
(Run)	Run mode	PLL ON above	Z	Reduced code <sup>(1)</sup>	3.49	ША	44	μΑΛΙΝΙΙΊΖ
		48 MHz all peripherals disable	80 MHz	Coremark	3.49		44	
		peripricials disable	98	Dhrystone 2.1	3.41		43	
			fHCLK :	Fibonacci	3.16		39	
			fHC	While(1)	3.04		38	

All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V

<sup>2.</sup> Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 40. Typical current consumption in Run, with different codes running from SRAM1 and power supplied by external SMPS ( $V_{DD12} = 1.05 \text{ V}$ )

Symbol	Parameter	Co	TYP		TYP				
		-	Voltage scaling	Code	25 °C	Unit	25 °C	Unit	
I <sub>DD_</sub> ALL (Run)	Supply current in Run mode	f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	OLK = 26 MH	Reduced code <sup>(2)</sup>	1.07		41		
				Coremark	1.07		41		
				Dhrystone 2.1	1.04	mA	40	μΑ/MHz	
				Fibonacci	0.97		37		
				While(1)	0.93		36		

All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.05 V



<sup>2.</sup> Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

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Table 41. Current consumption in Sleep and Low-power sleep modes, Flash ON

Symbol	Parameter	Conditions			ТҮР					MAX <sup>(1)</sup>					
		-	Voltage scaling	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
I <sub>DD_ALL</sub> (Sleep)	Supply current in sleep mode,	f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48 MHz included, bypass mode pll ON above 48 MHz all peripherals disable	Range 2	26 MHz	0.79	0.82	0.95	1.17	1.63	0.9	1.0	1.2	1.7	2.7	
				16 MHz	0.54	0.57	0.7	0.92	1.38	0.6	0.7	1.0	1.4	2.4	
				8 MHz	0.33	0.37	0.49	0.71	1.17	0.4	0.5	0.7	1.2	2.2	- mA
				4 MHz	0.23	0.26	0.39	0.61	1.06	0.3	0.4	0.6	1.1	2.1	
				2 MHz	0.18	0.21	0.34	0.56	1.01	0.2	0.3	0.5	1.0	1.0	
				1 MHz	0.16	0.19	0.31	0.53	0.99	0.2	0.3	0.5	1.0	1.0	
				100 kHz	0.13	0.17	0.29	0.51	0.96	0.1	0.3	0.5	1.0	1.9	
			Range 1	80 MHz	2.57	2.62	2.76	3.01	3.53	2.8	2.9	3.2	3.8	4.9	
				72 MHz	2.34	2.38	2.53	2.78	3.29	2.6	2.7	3.0	3.5	4.6	
				64 MHz	2.1	2.15	2.29	2.54	3.05	2.3	2.4	2.7	3.3	4.4	
				48 MHz	1.58	1.63	1.78	2.03	2.54	1.8	1.9	2.2	2.7	3.8	
				32 MHz	1.11	1.15	1.3	1.54	2.05	1.2	1.4	1.7	2.2	3.3	
				24 MHz	0.87	0.91	1.06	1.3	1.81	1.0	1.1	1.4	1.9	3.0	
				16 MHz	0.63	0.67	0.82	1.06	1.56	0.7	8.0	1.1	1.6	2.7	
I <sub>DD_ALL</sub> (LPSleep)	Supply current in low-power sleep	f <sub>HCLK</sub> = f <sub>MSI</sub>		2 MHz	103	140	270	506	985	130	247	500	990	2025	μA
				1 MHz	74.2	111	245	476	955	100	215	467	963	1999	
		all peripherals dis	able	400 kHz	60	89.8	224	457	937	79	194	444	941	1975	μΑ
	mode			100 kHz	53.7	84.1	216	448	928	70	185	434	933	1967	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.





Table 42. Current consumption in Sleep, Flash ON and power supplied by external SMPS ( $V_{DD12} = 1.10 \text{ V}$ )

Symbol	Parameter	Conditions <sup>(1)</sup>				TYP			Unit
Symbol	raiailletei	-	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	Ullit
			80 MHz	0.92	0.94	0.99	1.08	1.27	
			72 MHz	0.84	0.86	0.91	1.00	1.18	
			64 MHz	0.75	0.77	0.82	0.91	1.10	
			48 MHz	0.57	0.59	0.64	0.73	0.91	
		f <sub>HCLK</sub> = f <sub>HSE</sub> up to 48 MHz included, bypass	32 MHz	0.40	0.41	0.47	0.55	0.74	
I <sub>DD_ALL</sub> (Sleep)	Supply current in sleep mode,	mode	24 MHz	0.31	0.33	0.38	0.47	0.65	mA
IDD_ALL(Gleep)	Supply current in sleep mode,	pll ON above	16 MHz	0.23	0.24	0.29	0.38	0.56	ША
		48 MHz all peripherals disable	8 MHz	0.14	0.16	0.21	0.31	0.50	
			4 MHz	0.10	0.11	0.17	0.26	0.46	
			2 MHz	0.08	0.09	0.15	0.24	0.44	
			1 MHz	0.07	0.08	0.13	0.23	0.43	
			100 kHz	0.06	0.07	0.13	0.22	0.41	

<sup>1.</sup> All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V<sub>DD12</sub> = 1.10 V

Table 43. Current consumption in Low-power sleep modes, Flash in power-down

		Co	nditions				TYP					MAX <sup>(1)</sup>			
Symbol	Parameter	-	Voltage scaling	f <sub>HCLK</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
				2 MHz	92.7	124	258	487	968	105	224	474	969	2006	
I <sub>DD_ALL</sub>	Supply current in low-power	f <sub>HCLK</sub> = f <sub>MSI</sub>		1 MHz	63.5	97.5	223	460	951	75	193	446	942	1975	uА
I <sub>DD_ALL</sub> (LPSleep)	sleep mode	all peripherals	s disable	400 kHz	42.6	75.6	207	443	947	54	171	426	923	1955	μΛ
				100 kHz	31.2	67.6	199	437	905	44	162	420	916	1947	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.

Table 44. Current consumption in Stop 2 mode

Comple ed	Downwater	Conditions				TYP					MAX <sup>(1)</sup>			11
Symbol	Parameter	-	$V_{DD}$	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
			1.8 V	2.57	6.86	25.2	60.1	135	5.3	16.4	64	154.6	353	
		LCD disabled	2.4 V	2.62	6.91	25.5	60.6	137	5.3	16.6	64.9	156.7	359	
		LCD disabled	3 V	2.69	6.93	25.7	61.5	140	5.4	16.9	66.3	159.7	366	
I <sub>DD_ALL</sub>	Supply current in		3.6 V	2.7	7.08	26.3	62.9	143	5.4	17.4	67.8	163.8	375	
(Stop 2)	Stop 2 mode, RTC disabled		1.8 V	2.92	7.19	25.3	59.5	135	5.3	16.6	64.8	155.6	355	μA
		LCD enabled <sup>(2)</sup>	2.4 V	2.99	7.3	25.6	60.3	136	5.5	16.8	65.9	157.9	360	
		clocked by LSI	3 V	3.04	7.41	26.1	61.7	140	5.9	17.3	67.1	160.8	367	
			3.6 V	3.31	7.7	26.8	63.2	143	6.2	17.9	69.1	165.0	376	





Table 44. Current consumption in Stop 2 mode (continued)

		Conditions				TYP		<u>.                                      </u>			MAX <sup>(1)</sup>			
Symbol	Parameter	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
			1.8 V	2.97	7.46	26.2	61.4	139	6.1	17.2	64.8	155.4	354	
		RTC clocked by LSI,	2.4 V	3.09	7.61	26.5	62.3	140	6.2	17.5	65.7	157.6	360	
		LCD disabled	3 V	3.15	7.81	27	63.5	144	6.5	17.9	67.2	160.6	367	
			3.6 V	3.4	8.05	27.7	65.2	147	7.1	18.7	69.0	164.9	376	
			1.8 V	2.98	7.31	25.5	60	135	5.5	16.8	65.1	155.8	355	
		RTC clocked by LSI,	2.4 V	3.10	7.46	25.8	60.7	137	5.8	17.1	66.3	158.2	360	
		LCD enabled <sup>(3)</sup>	3 V	3.23	7.63	26.4	62.1	141	6.2	17.5	67.6	161.4	367	
I <sub>DD_ALL</sub> (Stop 2	Supply current in Stop 2 mode,		3.6 V	3.47	7.95	27.1	63.6	144	6.58	18.3	69.5	165.5	376	
with RTC)	RTC enabled		1.8 V	2.93	7.52	26.2	61.4	139	-	-	-	-	-	μA
		RTC clocked by LSE bypassed at	2.4 V	3.1	7.68	26.6	62.1	140	-	-	-	-	-	
		32768Hz,LCD disabled	3 V	3.3	7.81	26.9	63.4	143	-	-	-	-	-	
			3.6 V	3.48	8.07	27.6	65.0	146	-	-	-	-	-	
		DTC algebrad by LCE	1.8 V	2.86	7.48	26.2	61.4	-	-	-	-	-	-	
		RTC clocked by LSE quartz <sup>(3)</sup>	2.4 V	3.01	7.56	26.5	62.2	-	-	-	-	-	-	
		in low drive mode, LCD disabled	3 V	3.18	7.65	26.8	63.5	-	-	-	-	-	-	
		LOD disabled	3.6 V	3.31	7.94	27.5	65.1	-	-	-	-	-	-	

Table 44. Current consumption in Stop 2 mode (continued)

Symbol	Parameter	Conditions				TYP					MAX <sup>(1)</sup>			Unit
Symbol	raiailletei	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Ullit
		Wakeup clock is MSI = 48 MHz, voltage Range 1. See <sup>(4)</sup> .	3 V	1.69	1	-	-	-	-	-	-	-	-	
I <sub>DD_ALL</sub> (wake up from Stop 2)	Supply current during wakeup from Stop 2 mode	Wakeup clock is MSI = 4 MHz, voltage Range 2. See <sup>(4)</sup> .	3 V	1.35	-	-	-	-	-	-	-	-	-	mA
		Wakeup clock is HSI16 = 16 MHz, voltage Range 1. See <sup>(4)</sup> .	3 V	1.7	1	-	-	-	-	-	-	-	-	

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. LCD enabled with external voltage source. Consumption from VLCD excluded. Refer to LCD controller characteristics for I<sub>VLCD</sub>.
- 3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 4. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.



Table 45. Current consumption in Stop 1 mode

		Cor	nditions				TYP	-				MAX <sup>(1)</sup>	)		
Symbol	Parameter	-	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
				1.8 V	11.2	30.7	107	243	523	25.4	79.6	287	651	1395	
		_	LCD	2.4 V	11.3	30.8	108	244	526	25.5	79.8	288	655	1403	
	Supply current		disabled	3 V	11.6	31	108	245	530	25.9	80.5	290	659	1413	
I <sub>DD_ALL</sub>	in Stop 1			3.6 V	11.9	31.5	109	248	536	28.6	81.4	293	665	1428	μA
(Stop 1)	mode, RTC disabled		LCD	1.8 V	11.7	29.7	102	234	504	27.1	81.1	288.5	653	1397	μ, τ
	RTC disabled	_	enabled <sup>(2)</sup>	2.4 V	11.7	29.9	102	234	506	27.2	81.0	289	656	1405	
			clocked by	3 V	12.1	29.9	103	234	508	27.4	81.6	291	660	1415	
			LSI	3.6 V	12.2	30.1	103	235	510	28.8	82.4	294	667	1429	
				1.8 V	11.9	31.1	108	244	524	26.6	80.5	288	652	1396	
			LCD	2.4 V	12.1	31.4	109	245	528	26.7	80.9	289	656	1404	
			disabled	3 V	12.4	31.7	109	246	531	27.7	81.6	291	660	1415	
		RTC clocked by		3.6 V	12.6	32.3	110	249	537	28.9	82.8	295	667	1429	
		LSI		1.8 V	11.7	30.1	104	235	510	26.7	80.6	288	653	1397	
			LCD	2.4 V	11.8	30.2	104	238	511	26.7	81.1	290	657	1406	
	Supply current		enabled <sup>(2)</sup>	3 V	11.8	30.5	104	238	515	28.3	81.8	2912	661	1416	
I <sub>DD_ALL</sub> (Stop 1 with	in stop 1			3.6 V	12.3	31	105	239	519	30.9	83.0	295	668	1430	μA
RTC)	mode,			1.8 V	11.6	31.3	108	244	524	-	-	ı	-	-	μΛ
	RTC enabled	RTC clocked by LSE bypassed	LCD	2.4 V	11.8	31.6	109	245	527	-	-	ı	-	-	
		at 32768 Hz	disabled	3 V	12.3	31.9	109	246	531	-	-	1	-	-	
				3.6 V	12.7	32.5	111	249	537	-	-	-	-	-	
				1.8 V	11.5	31.1	108	244	-	-	-	-	-	-	
		RTC clocked by LSE quartz <sup>(3)</sup> in	LCD	2.4 V	11.5	31.4	109	246	-	-	-	-	-	-	
		low drive mode	disabled	3 V	12	31.7	109	247	-	-	-	-	-	-	
				3.6 V	12.4	32.3	110	250	-	-	-	-	-	-	

Table 45. Current consumption in Stop 1 mode (continued)

0	D	Con	ditions				TYP					MAX <sup>(1)</sup>	)		11!4
Symbol	Parameter	-		$V_{DD}$	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
		Wakeup clock MS voltage Range 1. See <sup>(4)</sup> .	I = 48 MHz,	3 V	0.99	-	-	-	-	-	-	-	-	-	
I <sub>DD_ALL</sub> (wakeup from Stop1)	during wakeup from	Wakeup clock MS voltage Range 2. See <sup>(4)</sup> .	I = 4 MHz,	3 V	1.1	-	-	-	-	1	-	-	-	-	mA
	Stop 1	Wakeup clock HSI16 = 16 MHz, voltage Range 1. See <sup>(4)</sup> .		3 V	0.95	-	-	-	-	-	-	-	-	-	

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. LCD enabled with external voltage source. Consumption from VLCD excluded. Refer to LCD controller characteristics for I<sub>VLCD</sub>.
- 3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 4. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.

Table 46. Current consumption in Stop 0 mode

		Conditions			TYP					MAX <sup>(1</sup>	)		
Symbol	Parameter	$V_{DD}$	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
		1.8 V	127	153	244	404	734	148	218	471	905	1795	
I <sub>DD_ALL</sub>	Supply current in Stop 0 mode.	2.4 V	129	155	247	407	737	151	221	474	910	1803	]
(Stop 0)	RTC disabled	3 V	131	156	249	409	741	154	224	478	915	1813	μA
		3.6 V	133	158	251	412	744	157	228	482	921	1822 <sup>(2)</sup>	

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Guaranteed by test in production.





Table 47. Current consumption in Standby mode

		1			<u> </u>	•	n Stand	oy mou						1
Symbol	Parameter	Conditions				TYP					MAX <sup>(1</sup>	)		Unit
Symbol	raiailletei	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Oiiit
			1.8 V	108	299	1343	3822	10353	227	899	4159	13059	36572	
		no independent	2.4 V	118	348	1562	4447	12012	252	1009	4846	15026	41366	
	Supply current	watchdog	3 V	133	404	1777	5071	13589	318	1211	6082	17245	46714	
I <sub>DD ALL</sub>	in Standby mode (backup		3.6 V	171	501	2115	5898	15539	435	1508	7230	19850	52888 <sup>(2)</sup>	nA
(Standby)	registers		1.8 V	296	-	-	-	-	-	-	-	-	-	
		with independent	2.4 V	349	-	-	-	-	-	-	-	-	-	
	RTC disabled	watchdog	3 V	411	-	-	-	-	-	-	-	-	-	
			3.6 V	506	-	-	-	-	-	-	-	-	-	
			1.8 V	377	581	1700	4270	11100	763	1422	5182	13585	36564	
		RTC clocked by LSI, no	2.4 V	461	700	2020	5030	12900	942	1704	5992	15473	41383	
	Supply current	independent watchdog	3 V	559	843	2390	5990	15500	1166	2032	6938	17889	46728	
I <sub>DD_ALL</sub>	in Standby mode (backup		3.6 V	689	1050	2920	7130	18100	1454	2511	7754	20714	53018	nA
with RTC)	Standby registers		1.8 V	422	-	-	-	-	-	-	-	-	-	IIA
	retained),	RTC clocked by LSI, with independent	2.4 V	518	-	-	-	-	-	-	-	-	-	
		watchdog	3 V	560	-	-	-	-	-	-	-	-	-	
			3.6 V	780	-	-	-	-	-	-	-	-	-	

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Table 47. Current consumption in Standby mode (continued)

	ı	14510 47. 00					,			<u> </u>				1
Symbol	Parameter	Conditions				TYP					MAX <sup>(1</sup>	)		Unit
Symbol	Farameter	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Onne
			1.8 V	308	504	1683	4193	10783	-	-	-	-	-	
		RTC clocked by LSE	2.4 V	400	633	1963	4957	12583	-	-	-	-	-	
	Supply current	bypassed at 32768Hz	3 V	508	779	2319	5925	15130	-	-	-	-	-	
I <sub>DD_ALL</sub>	in Standby mode (backup		3.6 V	661	1009	2825	7027	17540	-	-	-	-	-	- A
(Standby with RTC)	registers		1.8 V	426	624	1679	4244	10884	-	-	-	-	-	nA
	retained), RTC enabled	RTC clocked by LSE quartz <sup>(3)</sup> in low drive	2.4 V	521	751	1985	4952	12619	-	-	-	-	-	
		mode	3 V	643	914	2371	5931	15121	-	-	-	-	-	
			3.6 V	819	1162	2914	7019	17551	-	-	-	-	-	
	Supply current		1.8 V	371	1111	4297	10153	22747	806	2640	10537	24695	54376	
I <sub>DD_ALL</sub>	to be added in		2.4 V	372	1112	4328	10154	22888	809	2661	10545	24767	54505	nA
(SRAM2) <sup>(4)</sup>	Standby mode when SRAM2	_	3 V	374	1116	4403	10429	23711	811	2683	10553	24840	54634	11/
	is retained		3.6 V	378	1149	4545	10702	24361	814	2704	10561	24913	54763	
I <sub>DD_ALL</sub> (wakeup from Standby)	Supply current during wakeup from Standby mode	Wakeup clock is MSI = 4 MHz. See <sup>(5)</sup> .	3 V	1.4	-	-	-	-	-	-	-	-	-	mA

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Guaranteed by test in production.
- 3. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 4. The supply current in Standby with SRAM2 mode is:  $I_{DD\_ALL}(Standby) + I_{DD\_ALL}(SRAM2)$ . The supply current in Standby with RTC with SRAM2 mode is:  $II_{DD\_ALL}(Standby + RTC) + I_{DD\_ALL}(SRAM2)$ .
- 5. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in *Table 51: Low-power mode wakeup timings*.





Table 48. Current consumption in Shutdown mode

	T	Table 40.	Garro		Jampa	<u> </u>	- Idiao III							
Symbol	Parameter	Conditions				TYP					MAX <sup>(1)</sup>			Unit
Symbol	Parameter	-	V <sub>DD</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
	Supply current		1.8 V	24	161	983	3020	8970	85	556	3314	10498	31391	
	in Shutdown mode		2.4 V	31	193	1150	3530	10300	111	648	3844	11897	35017	
I <sub>DD_ALL</sub> (Shutdown)	(backup	-	3 V	44	242	1400	4260	12500	154	780	4447	13473	39297	nA
(	registers retained) RTC disabled		3.6 V	76	338	1790	5220	14700	236	1009	5354	15679	44571	
			1.8 V	225	363	1190	3230	9180	-	-	-	-	-	
		RTC clocked by LSE	2.4 V	314	478	1440	3820	10700	-	-	-	-	-	
	Supply current in Shutdown	bypassed at 32768 Hz	3 V	421	621	1790	4660	12900	-	-	-	-	-	
I <sub>DD_ALL</sub>	mode		3.6 V	561	831	2280	5730	15300	-	-	-	-	-	^
(Shutdown with RTC)	(backup registers		1.8 V	341	472	1303	3459	-	-	-	-	-	-	nA
	retained) RTC enabled	RTC clocked by LSE quartz <sup>(2)</sup> in low drive	2.4 V	435	586	1572	4041	-	-	-	-	-	-	
	enabled	mode	3 V	553	732	1982	5145	-	-	-	-	-	-	
			3.6 V	716	948	2520	6325	-	-	-	-	-	-	
I <sub>DD_ALL</sub> (wakeup from Shutdown)	Supply current during wakeup from Shutdown mode	Wakeup clock is MSI = 4 MHz. See <sup>(3)</sup> .	3 V	0.6	-	-	-	-	-	-	1	-	-	mA

- 1. Guaranteed by characterization results, unless otherwise specified.
- 2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
- 3. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in Table 51: Low-power mode wakeup timings.

Electrical characteristics

Table 49. Current consumption in VBAT mode

Cumbal	Davamatav	Conditions	s			TYP					MAX <sup>(1)</sup>			11:4
Symbol	Parameter	-	V <sub>BAT</sub>	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	Unit
			1.8 V	2	18	110	329	908	-	-	-	-	-	
		DTC disabled	2.4 V	2	20	125	371	1016	-	-	-	-	-	
		RTC disabled	3 V	3	25	154	546	1965	-	-	-	-	-	
			3.6 V	10	57	324	963	2688	-	-	-	-	-	
		DTC analysis and	1.8 V	198	216	312	535	-	-	-	-	-	-	
(// )	Backup domain	RTC enabled and clocked by LSE	2.4 V	280	300	411	664	-	-	-	-	-	-	nA
$I_{VDD\_VBAT}(V_{BAT})$	supply current	bypassed at 32768 Hz	3 V	375	402	544	943	-	-	-	-	-	-	I IIA
		32700112	3.6 V	488	529	791	1459	-	-	-	-	-	-	
			1.8 V	320	347	448	856	1432	-	-	-	-	-	
		RTC enabled and	2.4 V	405	436	550	921	1567	-	-	-	-	-	
		clocked by LSE quartz <sup>(2)</sup>	3 V	512	545	686	1128	2529	-	-	-	-	-	
			3.6 V	648	705	976	1588	3293	-	-	-	-	-	

<sup>1.</sup> Guaranteed by characterization results, unless otherwise specified.



<sup>2.</sup> Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

#### I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

#### I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 70: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

#### Caution:

Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

#### I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 50: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

 $I_{\mbox{SW}}$  is the current sunk by a switching I/O to charge/discharge the capacitive load

V<sub>DDIOx</sub> is the I/O supply voltage

 $f_{\mbox{SW}}$  is the I/O switching frequency

C is the total capacitance seen by the I/O pin:  $C = C_{INT} + C_{EXT} + C_{S}$ 

C<sub>S</sub> is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.



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#### On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 50*. The MCU is placed under the following conditions:

- All I/O pins are in Analog mode
- The given value is calculated by measuring the difference of the current consumptions:
  - when the peripheral is clocked on
  - when the peripheral is clocked off
- Ambient operating temperature and supply voltage conditions summarized in *Table 19: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in *Table 50*. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Table 50. Peripheral current consumption

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
	Bus Matrix <sup>(1)</sup>	4.44	3.75	4.00	
	ADC independent clock domain	0.40	0.08	0.30	
	ADC AHB clock domain	5.55	4.63	5.00	
	AES	1.70	1.50	1.60	
	CRC	0.48	0.42	0.50	
	DMA1	2.00	1.60	2.00	
	DMA2	1.76	1.50	1.50	
	DMA2D	24.33	20.21	24.50	
	FLASH	8.50	7.10	8.00	
	FMC	7.58	6.29	7.00	
	GPIOA <sup>(2)</sup>	1.59	1.25	1.50	
AHB	GPIOB <sup>(2)</sup>	1.56	1.25	1.50	
AHB	GPIOC <sup>(2)</sup>	1.58	1.29	1.50	µA/MHz
	GPIOD <sup>(2)</sup>	1.40	1.17	1.40	
	GPIOE <sup>(2)</sup>	1.36	1.13	1.40	
	GPIOF <sup>(2)</sup>	1.70	1.40	1.50	
	GPIOG <sup>(2)</sup>	1.80	1.50	1.80	
	GPIOH <sup>(2)</sup>	1.50	1.30	1.50	
	GPIOI <sup>(2)</sup>	1.18	0.96	1.00	
	HASH	2.18	1.79	2.00	
	DCMI	1.6	1.3	1.2	
	OTG_FS independent clock domain	23.20	NA	NA	
	OTG_FS AHB clock domain	14.30	NA	NA	
	QUADSPI	6.84	5.67	6.50	
	RNG independent clock domain	2.20	NA	NA	
	RNG AHB clock domain	0.51	NA	NA	
AHB	SRAM1	2.80	2.29	2.50	Λ/ΝΛ⊔⇒
AUR	SRAM2	1.20	1.00	1.00	μΑ/MHz
	TSC	1.50	1.17	1.00	
	All AHB Peripherals	121.00	79.10	87.20	

Table 50. Peripheral current consumption (continued)

Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
	AHB to APB1 bridge <sup>(3)</sup>	0.90	0.70	0.90	
	CAN1	3.68	3.04	3.50	
	DAC1	3.20	2.70	3.00	
	I2C1 independent clock domain	3.80	3.20	3.30	
	I2C1 APB clock domain	1.00	0.79	1.00	
	I2C2 independent clock domain	3.41	2.83	3.00	
	I2C2 APB clock domain	0.98	0.79	1.00	
	I2C3 independent clock domain	2.89	2.38	2.50	
	I2C3 APB clock domain	0.98	0.83	1.00	
	I2C4 independent clock domain	3.41	2.83	3.00	
	I2C4 APB clock domain	0.98	0.79	1.00	
APB1	LCD	1.03	0.80	1.03	μΑ/MHz
AFDI	LPUART1 independent clock domain	2.40	2.00	2.20	μΑνίνιι iz
	LPUART1 APB clock domain	0.98	0.83	0.80	
	LPTIM1 independent clock domain	3.10	2.54	2.54	
	LPTIM1 APB clock domain	0.88	0.75	0.90	
	LPTIM2 independent clock domain	2.86	2.42	2.25	
	LPTIM2 APB clock domain	0.90	0.67	0.75	
	OPAMP	0.29	0.20	0.30	
	PWR	0.80	0.63	0.60	
	SPI2	1.78	1.50	1.50	
	SPI3	1.76	1.50	1.50	
	SWPMI1 independent clock domain	2.10	1.50	2.00	
	SWPMI1 APB clock domain	1.00	0.79	0.75	

Table 50. Peripheral current consumption (continued)

	Peripheral	Range 1	Range 2	Low-power run and sleep	Unit
	TIM2	5.85	4.88	5.70	
	TIM3	5.20	4.25	5.00	
	TIM4	4.50	3.67	4.20	
	TIM5	5.60	4.58	5.10	
	TIM6	0.85	0.70	0.90	
	TIM7	0.86	0.71	0.90	
	USART2 independent clock domain	4.06	3.40	4.00	
APB1	USART2 APB clock domain	1.38	1.17	1.40	μΑ/MHz
AFDI	USART3 independent clock domain	4.80	3.92	4.60	μΑνίνιπΖ
	USART3 APB clock domain	1.80	1.50	1.80	
	UART4 independent clock domain	3.80	3.10	3.00	
	UART4 APB clock domain	1.30	1.13	1.30	
	UART5 independent clock domain	3.83	3.17	3.50	
	UART5 APB clock domain	1.60	1.25	1.50	
	WWDG	0.39	0.33	0.40	
	All APB1 on	84.20	74.96	82.70	
	AHB to APB2 bridge <sup>(4)</sup>	1.00	0.90	0.90	
	DFSDM1	6.00	5.00	5.50	
	FW	0.28	0.30	0.30	
	SAI1 independent clock domain	2.60	2.10	2.30	
	SAI1 APB clock domain	2.09	1.80	2.00	
	SAI2 independent clock domain	3.30	2.70	3.00	
	SAI2 APB clock domain	2.50	2.00	2.50	
	SDMMC1 independent clock domain	4.20	3.90	4.20	
APB2	SDMMC1 APB clock domain	2.10	1.80	2.00	μΑ/MHz
AFDZ	SPI1	1.71	1.42	1.50	μΑνίνιι iz
	SYSCFG/VREFBUF/COMP	0.55	0.50	0.50	
	TIM1	8.41	6.96	7.50	
	TIM8	8.83	7.33	8.00	
	TIM15	3.96	3.29	3.50	
	TIM16	3.24	2.67	3.00	
	TIM17	2.94	2.46	2.50	
	USART1 independent clock domain	5.20	4.29	5.50	
	USART1 APB clock domain	1.70	1.50	1.60	



Peripheral		Range 1	Range 2	Low-power run and sleep	Unit
APB2	All APB2 on	55.40	41.33	46.00	uA/MHz
	ALL	234.98	195.83	235.70	μ-ν ΙΝΙΙ ΙΖ

Table 50. Peripheral current consumption (continued)

- 1. The BusMatrix is automatically active when at least one master is ON (CPU, DMA).
- 2. The GPIOx (x= A...I) dynamic current consumption is approximately divided by a factor two versus this table values when the GPIO port is locked thanks to LCKK and LCKy bits in the GPIOx\_LCKR register. In order to save the full GPIOx current consumption, the GPIOx clock should be disabled in the RCC when all port I/Os are used in alternate function or analog mode (clock is only required to read or write into GPIO registers, and is not used in AF or analog modes).
- 3. The AHB to APB1 Bridge is automatically active when at least one peripheral is ON on the APB1.
- 4. The AHB to APB2 Bridge is automatically active when at least one peripheral is ON on the APB2.

# 6.3.6 Wakeup time from low-power modes and voltage scaling transition times

The wakeup times given in *Table 51* are the latency between the event and the execution of the first user instruction.

The device goes in low-power mode after the WFE (Wait For Event) instruction.

Table 51. Low-power mode wakeup timings<sup>(1)</sup>

Symbol	Parameter	Conditions			Max	Unit
t <sub>WUSLEEP</sub>	Wakeup time from Sleep mode to Run mode	-			6	Nb of
t <sub>WULPSLEEP</sub>	Wakeup time from Low- power sleep mode to Low- power run mode	Wakeup in Flash with Flash in power-down during low-power sleep mode (SLEEP_PD=1 in FLASH_ACR) and with clock MSI = 2 MHz			9	CPU cycles
		Range 1	Wakeup clock MSI = 48 MHz	7.0	11.6	
	Wake up time from Stop 0 mode to Run mode in Flash	Trange 1	Wakeup clock HSI16 = 16 MHz	6.2	10.7	
		Range 2	Wakeup clock MSI = 24 MHz	7.3	11.7	
			Wakeup clock HSI16 = 16 MHz	6.2	10.7	
			Wakeup clock MSI = 4 MHz	7.6	13.2	
twustop0		Panga 1	Wakeup clock MSI = 48 MHz	2.5	2.9	μs
	Wake up time from Stop 0	Range 1	Wakeup clock HSI16 = 16 MHz	2.7	2.9	
	mode to Run mode in		Wakeup clock MSI = 24 MHz	3.2	3.6	
	SRAM1	Range 2	Wakeup clock HSI16 = 16 MHz	2.7	2.9	
		Wakeup clock MSI = 4 MHz		5.7	13.2	



Table 51. Low-power mode wakeup timings<sup>(1)</sup> (continued)

Symbol	Parameter		Conditions	Тур	Max	Unit
		Dange 1	Wakeup clock MSI = 48 MHz	8.4	9.4	
		Range 1	Wakeup clock HSI16 = 16 MHz	7.8	8.4	
	Wake up time from Stop 1 mode to Run mode in Flash		Wakeup clock MSI = 24 MHz	8.7	9.6	
		Range 2	Wakeup clock HSI16 = 16 MHz	7.8	8.3	
			Wakeup clock MSI = 4 MHz	8.0	12.9	
		Dance 4	Wakeup clock MSI = 48 MHz	5.5	5.9	
	Wake up time from Stop 1	Range 1	Wakeup clock HSI16 = 16 MHz	6.6	7.0	
t <sub>WUSTOP1</sub>	mode to Run mode in		Wakeup clock MSI = 24 MHz	6.1	6.5	μs
	SRAM1	Range 2	Wakeup clock HSI16 = 16 MHz	6.6	7.0	
			Wakeup clock MSI = 4 MHz	8.5	12.8	
	Wake up time from Stop 1 mode to Low-power run mode in Flash	Regulator in low-power	Makaun alaak MCL - 2 MLL	13.8	20.0	
	Wake up time from Stop 1 mode to Low-power run mode in SRAM1	mode (LPR=1 in PWR_CR1)	Wakeup clock MSI = 2 MHz	11.8	22.0	
	Wake up time from Stop 2 mode to Run mode in Flash	Dance 4	Wakeup clock MSI = 48 MHz	8.9	9.8	
		Range 1	Wakeup clock HSI16 = 16 MHz	8.3	9.2	
		Range 2	Wakeup clock MSI = 24 MHz	9.3	10.2	
			Wakeup clock HSI16 = 16 MHz	8.2	9.2	
+			Wakeup clock MSI = 4 MHz	14.2	16.1	
t <sub>WUSTOP2</sub>		Range 1	Wakeup clock MSI = 48 MHz	6.1	7.1	μs
	Wake up time from Stop 2	Range	Wakeup clock HSI16 = 16 MHz	7.2	8.1	
	mode to Run mode in		Wakeup clock MSI = 24 MHz	6.8	7.8	
	SRAM1	Range 2	Wakeup clock HSI16 = 16 MHz	7.2	8.2	
			Wakeup clock MSI = 4 MHz	8.4	16.7	
t	Wakeup time from Standby	Range 1	Wakeup clock MSI = 8 MHz	15.3	23.2	μs
twustby	mode to Run mode	Trange 1	Wakeup clock MSI = 4 MHz	21.3	30.5	μδ
t <sub>wustby</sub>	Wakeup time from Standby	Range 1	Wakeup clock MSI = 8 MHz	15.3	23.1	116
SRAM2	with SRAM2 to Run mode	Trange 1	Wakeup clock MSI = 4 MHz	21.3	30.6	μs
t <sub>WUSHDN</sub>	Wakeup time from Shutdown mode to Run mode	Range 1	Wakeup clock MSI = 4 MHz	305.9	322.3	μs

<sup>1.</sup> Guaranteed by characterization results.



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Symbol	Parameter	Conditions	Тур	Max	Unit
t <sub>WULPRUN</sub>	Wakeup time from Low-power run mode to Run mode <sup>(2)</sup>	Code run with MSI 2 MHz	5	7	us
t <sub>VOST</sub>	Regulator transition time from Range 2 to Range 1 or Range 1 to Range 2 <sup>(3)</sup>	Code run with MSI 24 MHz	20	40	μδ

- 1. Guaranteed by characterization results.
- 2. Time until REGLPF flag is cleared in PWR\_SR2.
- 3. Time until VOSF flag is cleared in PWR\_SR2.

Table 53. Wakeup time using USART/LPUART<sup>(1)</sup>

Symbol	Parameter	Conditions	Тур	Max	Unit
	<u> </u>	Stop 0 mode	-	1.7	
t <sub>WUUSART</sub> t <sub>WULPUART</sub>	maximum USART/LPUART baudrate allowing to wakeup up from stop mode when USART/LPUART clock source is HSI16	Stop 1 mode and Stop 2 mode	-	8.5	μs

<sup>1.</sup> Guaranteed by design.

#### 6.3.7 External clock source characteristics

#### High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 25: High-speed external clock source AC timing diagram*.

Table 54. High-speed external user clock characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSE_ext</sub>	User external clock source frequency	Voltage scaling Range 1	-	8	48	MHz
		Voltage scaling Range 2	-	8	26	IVII IZ
V <sub>HSEH</sub>	OSC_IN input pin high level voltage	- 0.7 V <sub>DDIOx</sub> -		-	$V_{DDIOx}$	V
V <sub>HSEL</sub>	OSC_IN input pin low level voltage	-	V <sub>SS</sub>	-	0.3 V <sub>DDIOx</sub>	V
t <sub>w(HSEH)</sub>	OSC_IN high or low time	Voltage scaling Range 1	7	-	-	nc
t <sub>w(HSEL)</sub>		Voltage scaling Range 2	18	-	-	ns

<sup>1.</sup> Guaranteed by design.

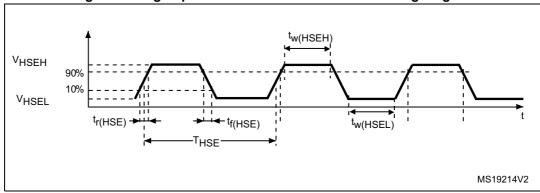


Figure 25. High-speed external clock source AC timing diagram

#### Low-speed external user clock generated from an external source

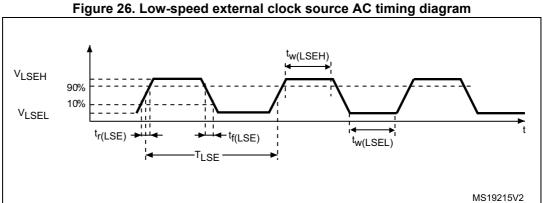
In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in Section 6.3.14. However, the recommended clock input waveform is shown in Figure 26.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
f <sub>LSE_ext</sub>	User external clock source frequency	-	-	32.768	1000	kHz				
V <sub>LSEH</sub>	OSC32_IN input pin high level voltage	-	0.7 V <sub>DDIOx</sub>	-	$V_{DDIOx}$	V				
V <sub>LSEL</sub>	OSC32_IN input pin low level voltage	-	$V_{SS}$	-	0.3 V <sub>DDIOx</sub>					
t <sub>w(LSEH)</sub>	OSC32_IN high or low time	-	250	-	-	ns				

Table 55. Low-speed external user clock characteristics<sup>(1)</sup>

<sup>1.</sup> Guaranteed by design.



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#### High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 48 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 56*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Cyllibol	i didilietei	Conditions	IVIIII	ıур	IVIAA	Offic
f <sub>OSC_IN</sub>	Oscillator frequency	-	4	8	48	MHz
R <sub>F</sub>	Feedback resistor	-	-	200	-	kΩ
		During startup <sup>(3)</sup>	-	-	5.5	
		$V_{DD}$ = 3 V, Rm = 30 $\Omega$ , CL = 10 pF@8 MHz	-	0.44	-	
		$V_{DD} = 3 \text{ V},$ $Rm = 45 \Omega,$ CL = 10  pF@8 MHz	-	0.45	-	
I <sub>DD(HSE)</sub>	HSE current consumption	$V_{DD} = 3 \text{ V},$ $Rm = 30 \Omega,$ CL = 5  pF@48 MHz	-	0.68	-	mA
		V <sub>DD</sub> = 3 V, Rm = 30 Ω.	_	0.94	_	

Table 56. HSE oscillator characteristics<sup>(1)</sup>

Conditions (2)

CL = 10 pF@48 MHz  $V_{DD} = 3 V$ ,
Rm = 30  $\Omega$ ,

CL = 20 pF@48 MHz

Startup

V<sub>DD</sub> is stabilized

Min

Tvn

1.77

2

Max

1. Guaranteed by design.

 $\mathsf{G}_{\mathsf{m}}$ 

t<sub>SU(HSE)</sub><sup>(4)</sup>

Symbol

Parameter

- 2. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 3. This consumption level occurs during the first 2/3 of the t<sub>SU(HSE)</sub> startup time

Maximum critical crystal

transconductance

Startup time

4. t<sub>SU(HSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For  $C_{L1}$  and  $C_{L2}$ , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 27*).  $C_{L1}$  and  $C_{L2}$  are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of  $C_{L1}$  and  $C_{L2}$ . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing  $C_{L1}$  and  $C_{L2}$ .

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mA/V

ms

1.5

Note:

For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

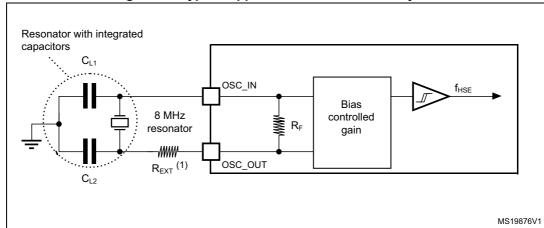


Figure 27. Typical application with an 8 MHz crystal

1. R<sub>EXT</sub> value depends on the crystal characteristics.

#### Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in Table 57. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

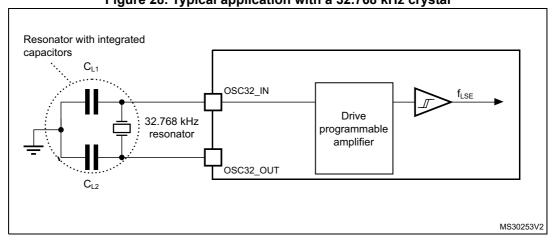
Table 57. LSE oscillator characteristics (f<sub>LSE</sub> = 32.768 kHz)<sup>(1)</sup>

Symbol	Parameter	Conditions <sup>(2)</sup>	Min	Тур	Max	Unit
		LSEDRV[1:0] = 00 Low drive capability	-	250	-	
I <sub>DD(LSE)</sub> LSE c	LSE ourrent consumption	LSEDRV[1:0] = 01 Medium low drive capability	-	315	-	nA
	LSE current consumption	LSEDRV[1:0] = 10 Medium high drive capability	-	500	-	IIA
		LSEDRV[1:0] = 11 High drive capability	-	630	-	
	Maximum critical crystal gm	LSEDRV[1:0] = 00 Low drive capability	-	-	0.5	
Gm		LSEDRV[1:0] = 01 Medium low drive capability	-	-	0.75	
Gm <sub>critmax</sub>		LSEDRV[1:0] = 10 Medium high drive capability	-	-	1.7	μA/V
		LSEDRV[1:0] = 11 High drive capability	-	_	2.7	
t <sub>SU(LSE)</sub> (3)	Startup time	V <sub>DD</sub> is stabilized	-	2	-	S

- 1. Guaranteed by design.
- Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
- t<sub>SU(LSE)</sub> is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 28. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between OSC32\_IN and OSC32\_OUT and it is forbidden to add one.

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#### 6.3.8 Internal clock source characteristics

The parameters given in *Table 58* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*. The provided curves are characterization results, not tested in production.

#### High-speed internal (HSI16) RC oscillator

Table 58. HSI16 oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI16</sub>	HSI16 Frequency	V <sub>DD</sub> =3.0 V, T <sub>A</sub> =30 °C	15.88	-	16.08	MHz
TRIM	HSI16 user trimming step	Trimming code is not a multiple of 64	0.2	0.3	0.4	%
TAIIVI		Trimming code is a multiple of 64	-4	-6	-8	70
DuCy(HSI16) <sup>(2)</sup>	Duty Cycle	-	45	-	55	%
A (LICIAC)	HSI16 oscillator frequency drift over temperature	T <sub>A</sub> = 0 to 85 °C	-1	-	1	%
$\Delta_{Temp}(HSI16)$		T <sub>A</sub> = -40 to 125 °C	-2	-	1.5	%
Δ <sub>VDD</sub> (HSI16)	HSI16 oscillator frequency drift over V <sub>DD</sub>	V <sub>DD</sub> =1.62 V to 3.6 V	-0.1	-	0.05	%
t <sub>su</sub> (HSI16) <sup>(2)</sup>	HSI16 oscillator start-up time	-	-	0.8	1.2	μs
t <sub>stab</sub> (HSI16) <sup>(2)</sup>	HSI16 oscillator stabilization time	-	-	3	5	μs
I <sub>DD</sub> (HSI16) <sup>(2)</sup>	HSI16 oscillator power consumption	-	-	155	190	μΑ

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> Guaranteed by design.

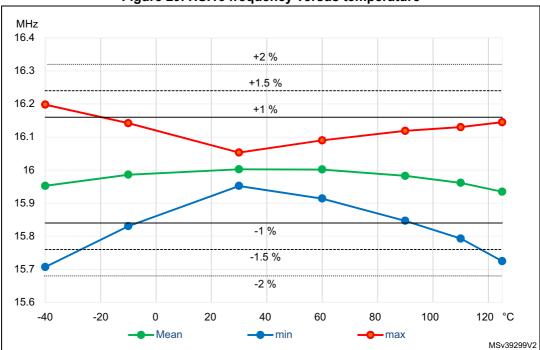


Figure 29. HSI16 frequency versus temperature

## Multi-speed internal (MSI) RC oscillator

Table 59. MSI oscillator characteristics<sup>(1)</sup>

Symbol	Parameter		Conditions	Min	Тур	Max	Unit
			Range 0	98.7	100	101.3	
			Range 1	197.4	200	202.6	kHz
			Range 2	394.8	400	405.2	KIIZ
			Range 3	7896	800	810.4	
			Range 4	0.987	1	1.013	
		MOL	Range 5	1.974	2	2.026	
		MSI mode	Range 6	3.948	4	4.052	
f <sub>MSI</sub>			Range 7	7.896	8	8.104	NAL 1-
			Range 8	15.79	16	16.21	MHz
			Range 9	23.69	24	24.31	
	MSI frequency after factory calibration, done at V <sub>DD</sub> =3 V and		Range 10	31.58	32	32.42	-
			Range 11	47.38	48	48.62	
			Range 0	-	98.304	-	- kHz
	T <sub>A</sub> =30 °C		Range 1	-	196.608	-	
			Range 2	-	393.216	-	
			Range 3	-	786.432	-	
			Range 4	-	1.016	-	
		PLL mode XTAL=	Range 5	-	1.999	-	
		32.768 kHz	Range 6	-	3.998	-	
			Range 7	-	7.995	-	NAL 1-
			Range 8	-	15.991	-	MHz
			Range 9	-	23.986	-	
			Range 10	-	32.014	-	-
			Range 11	-	48.005	-	
	MSI oscillator		T <sub>A</sub> = -0 to 85 °C	-3.5	-	3	
$\Delta_{TEMP}(MSI)^{(2)}$	frequency drift over temperature	MSI mode	T <sub>A</sub> = -40 to 125 °C	-8	-	6	%

Table 59. MSI oscillator characteristics<sup>(1)</sup> (continued)

Symbol	Parameter		Conditions		Min	Тур	Max	Unit
			Dange 0 to 0	V <sub>DD</sub> =1.62 V to 3.6 V	-1.2	-	0.5	
	MSI oscillator frequency drift		Range 0 to 3	V <sub>DD</sub> =2.4 V to 3.6 V	-0.5	-	0.5	
$\Delta_{\text{VDD}}(\text{MSI})^{(2)}$		MSI mode	Range 4 to 7	V <sub>DD</sub> =1.62 V to 3.6 V	-2.5	-	0.7	%
ΔVDD(MOI)	over V <sub>DD</sub> (reference is 3 V)	WSI mode	Nange 4 to 7	V <sub>DD</sub> =2.4 V to 3.6 V	-0.8	1	0.7	70
			Range 8 to 11	V <sub>DD</sub> =1.62 V to 3.6 V	-5	-	_ 1	
			range o to 11	V <sub>DD</sub> =2.4 V to 3.6 V	-1.6	-		
A.E.	Frequency		$T_A = -40 \text{ to } 85^\circ$	°C	-	1	2	
ΔF <sub>SAMPLING</sub> (MSI) <sup>(2)(6)</sup>	variation in sampling mode <sup>(3)</sup>	MSI mode	T <sub>A</sub> = -40 to 125	°C	-	2	4	%
P_USB Jitter(MSI) <sup>(6)</sup>	Period jitter for USB clock <sup>(4)</sup>	PLL mode Range 11	for next transition	-	ı	-	3.458	ns
			for paired transition	-	-	ı	3.916	113
MT_USB	Medium term jitter for USB clock <sup>(5)</sup>	IDII MAAA	for next transition	-	-	ı	2	ns
Jitter(MSI) <sup>(6)</sup>			for paired transition	-	-	ı	1	115
CC jitter(MSI) <sup>(6)</sup>	RMS cycle-to- cycle jitter	PLL mode R	ange 11	-	-	60	-	ps
P jitter(MSI) <sup>(6)</sup>	RMS Period jitter	PLL mode R	ange 11	-	-	50	-	ps
		Range 0		-	-	10	20	
		Range 1		-	-	5	10	
t <sub>SU</sub> (MSI) <sup>(6)</sup>	MSI oscillator	Range 2		-	-	4	8	us
isu(mon)	start-up time	Range 3		-	-	3	7	
		Range 4 to 7	7	-	-	3	6	
		Range 8 to 1	11	-	-	2.5	6	
			10 % of final frequency	-	-	0.25	0.5	
t <sub>STAB</sub> (MSI) <sup>(6)</sup>	MSI oscillator stabilization time		5 % of final frequency	-	-	0.5	1.25	ms
			1 % of final frequency	-	-	-	2.5	

Symbol	Parameter		Conditions			Тур	Max	Unit
			Range 0	-	-	0.6	1	
			Range 1	-	-	8.0	1.2	
			Range 2	-	-	1.2	1.7	
	MSI oscillator power consumption	MSI and PLL mode	Range 3	-	-	1.9	2.5	
			Range 4	-	-	4.7	6	
I <sub>DD</sub> (MSI) <sup>(6)</sup>			Range 5	-	-	6.5	9	μA
IDD(INIQI)			Range 6	-	-	11	15	
			Range 7	-	-	18.5	25	
			Range 8	-	-	62	80	
			Range 9	-	-	85	110	
			Range 10	-	-	110	130	
			Range 11	-	-	155	190	

Table 59. MSI oscillator characteristics<sup>(1)</sup> (continued)

6. Guaranteed by design.

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> This is a deviation for an individual part once the initial frequency has been measured.

<sup>3.</sup> Sampling mode means Low-power run/Low-power sleep modes with Temperature sensor disable.

Average period of MSI @48 MHz is compared to a real 48 MHz clock over 28 cycles. It includes frequency tolerance + jitter
of MSI @48 MHz clock.

Only accumulated jitter of MSI @48 MHz is extracted over 28 cycles.
 For next transition: min. and max. jitter of 2 consecutive frame of 28 cycles of the MSI @48 MHz, for 1000 captures over 28 cycles.
 For paired transitions: min. and max. jitter of 2 consecutive frame of 56 cycles of the MSI @48 MHz, for 1000 captures over 56 cycles.

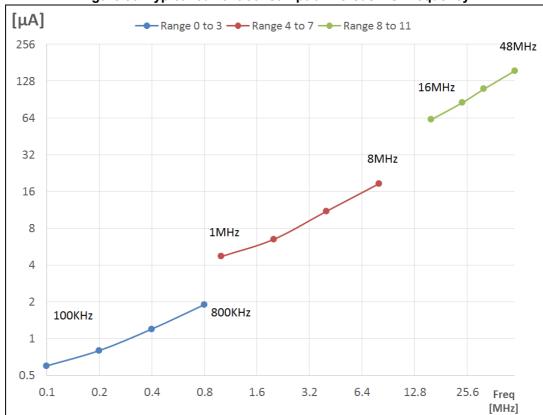


Figure 30. Typical current consumption versus MSI frequency

High-speed internal 48 MHz (HSI48) RC oscillator

Table 60. HSI48 oscillator characteristics<sup>(1)</sup>

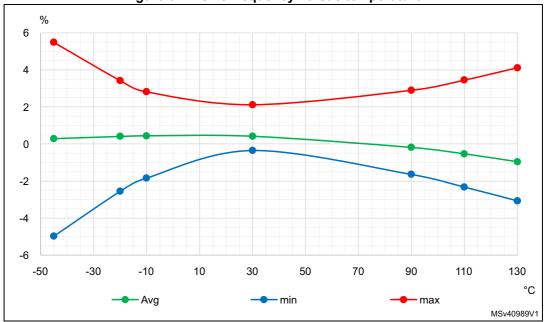
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>HSI48</sub>	HSI48 Frequency	V <sub>DD</sub> =3.0V, T <sub>A</sub> =30°C	-	48	-	MHz
TRIM	HSI48 user trimming step	-	-	0.11 <sup>(2)</sup>	0.18 <sup>(2)</sup>	%
USER TRIM COVERAGE	HSI48 user trimming coverage	±32 steps	±3 <sup>(3)</sup>	±3.5 <sup>(3)</sup>	-	%
DuCy(HSI48)	Duty Cycle	-	45 <sup>(2)</sup>	-	55 <sup>(2)</sup>	%
100	Accuracy of the HSI48 oscillator over temperature (factory calibrated)	V <sub>DD</sub> = 3.0 V to 3.6 V, T <sub>A</sub> = -15 to 85 °C	-	-	±3 <sup>(3)</sup>	%
ACC <sub>HSI48_REL</sub>		$V_{DD}$ = 1.65 V to 3.6 V, $T_A$ = -40 to 125 °C	-	-	±4.5 <sup>(3)</sup>	/0
D (HCI40)	HSI48 oscillator frequency drift	V <sub>DD</sub> = 3 V to 3.6 V	-	0.025 <sup>(3)</sup>	0.05 <sup>(3)</sup>	%
D <sub>VDD</sub> (HSI48)	with V <sub>DD</sub>	V <sub>DD</sub> = 1.65 V to 3.6 V	-	0.05 <sup>(3)</sup>	0.1 <sup>(3)</sup>	70
t <sub>su</sub> (HSI48)	HSI48 oscillator start-up time	-	-	2.5 <sup>(2)</sup>	6 <sup>(2)</sup>	μs
I <sub>DD</sub> (HSI48)	HSI48 oscillator power consumption	-	-	340 <sup>(2)</sup>	380 <sup>(2)</sup>	μA

Table 60. HSI48	3 oscillator	characteristics <sup>(1)</sup>	(continued)
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
N <sub>T</sub> jitter	Next transition jitter Accumulated jitter on 28 cycles <sup>(4)</sup>	-	-	+/-0.15 <sup>(2)</sup>	-	ns
P <sub>T</sub> jitter	Paired transition jitter Accumulated jitter on 56 cycles <sup>(4)</sup>	-	-	+/-0.25 <sup>(2)</sup>	-	ns

- 1.  $V_{DD}$  = 3 V, TA = -40 to 125°C unless otherwise specified.
- 2. Guaranteed by design.
- 3. Guaranteed by characterization results.
- 4. Jitter measurement are performed without clock source activated in parallel.

Figure 31. HSI48 frequency versus temperature



Low-speed internal (LSI) RC oscillator

Table 61. LSI oscillator characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>LSI</sub>	I SI Fraguency	V <sub>DD</sub> = 3.0 V, T <sub>A</sub> = 30 °C	31.04	-	32.96	kHz
	LSI Frequency	$V_{DD}$ = 1.62 to 3.6 V, $T_A$ = -40 to 125 °C	29.5	-	34	KI IZ
t <sub>SU</sub> (LSI) <sup>(2)</sup>	LSI oscillator start- up time	-	-	80	130	μs
t <sub>STAB</sub> (LSI) <sup>(2)</sup>	LSI oscillator stabilization time	5% of final frequency	-	125	180	μs
I <sub>DD</sub> (LSI) <sup>(2)</sup>	LSI oscillator power consumption	-	-	110	180	nA

- 1. Guaranteed by characterization results.
- 2. Guaranteed by design.



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#### 6.3.9 PLL characteristics

The parameters given in *Table 62* are derived from tests performed under temperature and  $V_{DD}$  supply voltage conditions summarized in *Table 22: General operating conditions*.

Table 62. PLL, PLLSAI1, PLLSAI2 characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f	PLL input clock <sup>(2)</sup>	-	4	-	16	MHz
f <sub>PLL_IN</sub>	PLL input clock duty cycle	-	45	-	55	%
f <sub>PLL_P_OUT</sub>	PLL multiplier output clock P	Voltage scaling Range 1	2.0645	-	80	MHz
		Voltage scaling Range 2	2.0645	-	26	IVIMZ
f <sub>PLL_Q_OUT</sub>	PLL multiplier output clock Q	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	IVIMZ
f <sub>PLL_R_OUT</sub>	PLL multiplier output clock R	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	IVIMZ
	PLL VCO output	Voltage scaling Range 1	64	-	344	N41.1-
f <sub>VCO_OUT</sub>		Voltage scaling Range 2	64	-	128	MHz
t <sub>LOCK</sub>	PLL lock time	-	-	15	40	μs
1:440.0	RMS cycle-to-cycle jitter	Custom sleek 90 MHz	-	40	-	
Jitter	RMS period jitter	System clock 80 MHz	-	30	-	±ps
		VCO freq = 64 MHz	-	150	200	
I (DII)	PLL power consumption on $V_{DD}^{(1)}$	VCO freq = 96 MHz	-	200	260	μA
I <sub>DD</sub> (PLL)		VCO freq = 192 MHz	-	300	380	
		VCO freq = 344 MHz	-	520	650	

<sup>1.</sup> Guaranteed by design.

#### 6.3.10 Flash memory characteristics

Table 63. Flash memory characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Тур	Max	Unit
t <sub>prog</sub>	64-bit programming time	-	81.69	90.76	μs
+	one row (32 double	normal programming	2.61	2.90	
Lprog_row	word) programming time	fast programming	1.91	2.12	
+	one page (2 Kbyte)	normal programming	20.91	23.24	ms
<sup>L</sup> prog_page	programming time	fast programming	15.29	16.98	
t <sub>ERASE</sub>	Page (2 KB) erase time	-	22.02	24.47	
+	one bank (512 Kbyte)	normal programming	5.35	5.95	
<sup>T</sup> prog_bank	programming time	fast programming	3.91	4.35	S



Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the 3 PLLs.

Table 63. Flash memory characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Тур	Max	Unit
t <sub>ME</sub>	Mass erase time (one or two banks)	-	22.13	24.59	ms
	Average consumption from V <sub>DD</sub>	Write mode	3.4	-	
		Erase mode	3.4	-	mA
I <sub>DD</sub>	Maximum current (peak)	Write mode	7 (for 2 µs)	-	IIIA
		Erase mode	7 (for 41 µs)	-	

<sup>1.</sup> Guaranteed by design.

Table 64. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Unit
N <sub>END</sub>	Endurance	T <sub>A</sub> = -40 to +105 °C	10	kcycles
t <sub>RET</sub>	Data retention	1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 85 °C	30	Years
		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 105 °C	15	
		1 kcycle <sup>(2)</sup> at T <sub>A</sub> = 125 °C	7	
		10 kcycles <sup>(2)</sup> at T <sub>A</sub> = 55 °C	30	
		10 kcycles <sup>(2)</sup> at T <sub>A</sub> = 85 °C	15	
		10 kcycles <sup>(2)</sup> at T <sub>A</sub> = 105 °C	10	

<sup>1.</sup> Guaranteed by characterization results.

<sup>2.</sup> Cycling performed over the whole temperature range.

#### 6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

#### Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- Electrostatic discharge (ESD) (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 65*. They are based on the EMS levels and classes defined in application note AN1709.

Symbol	Parameter	Conditions	Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}$ = 3.3 V, $T_{A}$ = +25 °C, $f_{HCLK}$ = 80 MHz, conforming to IEC 61000-4-2	2B
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100 pF on V <sub>DD</sub> and V <sub>SS</sub> pins to induce a functional disturbance	V <sub>DD</sub> = 3.3 V, T <sub>A</sub> = +25 °C, f <sub>HCLK</sub> = 80 MHz, conforming to IEC 61000-4-4	5A

**Table 65. EMS characteristics** 

#### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

#### Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

#### **Prequalification trials**

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

#### **Electromagnetic Interference (EMI)**

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Sumbol	Parameter	Conditions	Monitored	Max vs. [f <sub>HSE</sub> /f <sub>HCLK</sub> ]	l lm!4	
Symbol			frequency band	8 MHz / 80 MHz	Unit	
S <sub>EMI</sub>	Peak level	V <sub>DD</sub> = 3.6 V, T <sub>A</sub> = 25 °C, BGA169 package compliant with IEC 61967-2	0.1 MHz to 30 MHz	3		
			30 MHz to 130 MHz	-2	dBuV	
			130 MHz to 1 GHz	0	иБμν	
			1 GHz to 2 GHz	8		
			EMI Level	1.5	-	

Table 66. EMI characteristics

#### 6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

#### Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Maximum **Symbol** Conditions Class Unit **Ratings** value<sup>(1)</sup>  $T_A = +25$  °C, conforming Electrostatic discharge to ANSI/ESDA/JEDEC 2 2000  $V_{ESD(HBM)}$ voltage (human body model) JS-001 ٧ Electrostatic discharge  $T_A = +25 \,^{\circ}C$ C3 voltage (charge device conforming to ANSI/ESD 250  $V_{ESD(CDM)}$ STM5.3.1 model)

Table 67. ESD absolute maximum ratings

1. Guaranteed by characterization results.



#### Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 68. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T <sub>A</sub> = +105 °C conforming to JESD78A	II level A <sup>(1)</sup>

<sup>1.</sup> Negative injection is limited to -30 mA for PF0, PF1, PG6, PG7, PG8, PG12, PG13, PG14.

#### 6.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below  $V_{SS}$  or above  $V_{DDIOx}$  (for standard, 3.3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

#### Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of the -5  $\mu$ A/+0  $\mu$ A range) or other functional failure (for example reset occurrence or oscillator frequency deviation).

The characterization results are given in *Table 69*.

Negative induced leakage current is caused by negative injection and positive induced leakage current is caused by positive injection.

Table 69. I/O current injection susceptibility<sup>(1)</sup>

Symbol	Description	Functional susceptibility		Unit
	Description	Negative injection	Positive injection	Oille
	Injected current on all pins except PA4, PA5, PB0, PF12, PF13, OPAMP1_V1NM, OPAMP2_V1NM	-5	NA <sup>(2)</sup>	mA
I <sub>INJ</sub>	Injected current on pins PB0, PF12, PF13	0	NA <sup>(2)</sup>	
	Injected current on OPAMP1_V1NM, OPAMP2_V1NM	0	0	
	Injected current on PA4, PA5 pins	-5	0	

- 1. Guaranteed by characterization.
- 2. Injection is not possible

### 6.3.14 I/O port characteristics

#### General input/output characteristics

Unless otherwise specified, the parameters given in *Table 70* are derived from tests performed under the conditions summarized in *Table 22: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant (except BOOT0).

Table 70. I/O static characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL</sub> <sup>(1)</sup>	I/O input low level voltage except BOOT0	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	-	-	0.3xV <sub>DDIOx</sub> (2)	
	I/O input low level voltage except BOOT0	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	-	-	0.39xV <sub>DDIOx</sub> - 0.06 <sup>(3)</sup>	V
	I/O input low level voltage except BOOT0	1.08 V <v<sub>DDIOX&lt;1.62 V</v<sub>	-	-	0.43xV <sub>DDIOx</sub> - 0.1 <sup>(3)</sup>	
	BOOT0 I/O input low level voltage	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	-	-	0.17xV <sub>DDIOx</sub> (3)	
V <sub>IH</sub> <sup>(1)</sup>	I/O input high level voltage except BOOT0	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	0.7xV <sub>DDIOx</sub> <sup>(2)</sup>	-	-	V
	I/O input high level voltage except BOOT0	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	0.49xV <sub>DDIOX</sub> + 0.26 <sup>(3)</sup>	-	-	
	I/O input high level voltage except BOOT0	1.08 V <v<sub>DDIOx&lt;1.62 V</v<sub>	0.61xV <sub>DDIOX</sub> + 0.05 <sup>(3)</sup>	-	-	
	BOOT0 I/O input high level voltage	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	0.77xV <sub>DDIOX</sub> (3)	-	-	
	TT_xx, FT_xxx and NRST I/O input hysteresis	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	-	200	-	
V <sub>hys</sub> <sup>(3)</sup>	FT_sx	1.08 V <v<sub>DDIOx&lt;1.62 V</v<sub>	-	150	-	mV
	BOOT0 I/O input hysteresis	1.62 V <v<sub>DDIOx&lt;3.6 V</v<sub>	-	200	-	

Table 70. I/O static characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	FT_xx input leakage current <sup>(3)(5)</sup>	$V_{IN} \le Max(V_{DDXXX})^{(6)(7)}$	-	-	±100	
		$\begin{aligned} &\text{Max}(\text{V}_{\text{DDXXX}}) \leq \text{V}_{\text{IN}} \leq \\ &\text{Max}(\text{V}_{\text{DDXXX}}) + 1 \text{ V}^{(6)(7)} \end{aligned}$	-	-	650	
		$Max(V_{DDXXX})+1 V < V_{IN} ≤ 5.5 V^{(6)(7)}$	-	-	200	nA
		$V_{IN} \le Max(V_{DDXXX})^{(6)(7)}$	-	-	±150	
I <sub>lkg</sub> <sup>(4)</sup>	FT_lu, FT_u, PB2 and PC3 IO	$\begin{aligned} &\text{Max}(\text{V}_{\text{DDXXX}}) \leq \text{V}_{\text{IN}} \leq \\ &\text{Max}(\text{V}_{\text{DDXXX}}) + 1 \text{ V}^{(6)(7)} \end{aligned}$	-	_	2500 <sup>(3)</sup>	
		$Max(V_{DDXXX})+1 V < V_{IN} \le 5.5 V^{(6)(7)}$	-	-	250	
	TT_xx input leakage current	$V_{IN} \le Max(V_{DDXXX})^{(6)}$	-	-	±150	
		$Max(V_{DDXXX}) \le V_{IN} < 3.6 V^{(6)}$	-	-	2000 <sup>(3)</sup>	
	OPAMPx_VINM (x=1,2) dedicated input leakage current (UFBGA132 only)	-	-	-	(8)	
R <sub>PU</sub>	Weak pull-up equivalent resistor (9)	V <sub>IN</sub> = V <sub>SS</sub>	25	40	55	kΩ
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(9)</sup>	V <sub>IN</sub> = V <sub>DDIOx</sub>	25	40	55	kΩ
C <sub>IO</sub>	I/O pin capacitance	-	-	5	-	pF

- 1. Refer to Figure 32: I/O input characteristics.
- 2. Guaranteed by test production.
- 3. Guaranteed by design.
- 4. This value represents the pad leakage of the IO itself. The total product pad leakage is provided by this formula:  $I_{Total\_Ileak\_max} = 10 \ \mu A + [number of IOs where V_{IN} is applied on the pad] \times I_{lkg}(Max)$ .
- 5. All FT\_xx GPIOs except FT\_lu, FT\_u, PB2 and PC3.
- 6.  $Max(V_{DDXXX})$  is the maximum value of all the I/O supplies.
- To sustain a voltage higher than Min(V<sub>DD</sub>, V<sub>DDA</sub>, V<sub>DDIO2</sub>, V<sub>DDUSB</sub>, V<sub>LCD</sub>) +0.3 V, the internal Pull-up and Pull-Down resistors must be disabled.
- 8. Refer to I<sub>bias</sub> in *Table 86: OPAMP characteristics* for the values of the OPAMP dedicated input leakage current.
- Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimal (~10% order).

All I/Os are CMOS- and TTL-compliant (no software configuration required). Their characteristics cover more than the strict CMOS-technology or TTL parameters. The coverage of these requirements is shown in *Figure 32* for standard I/Os, and in *Figure 32* for 5 V tolerant I/Os.

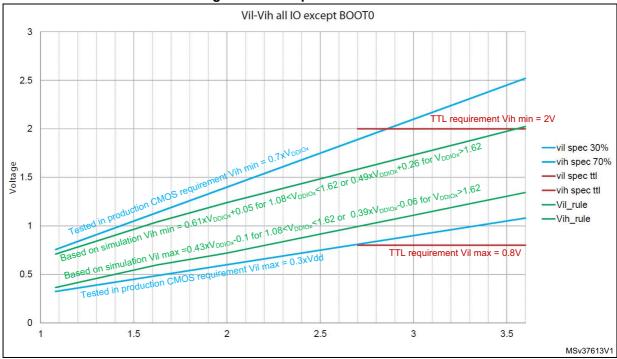


Figure 32. I/O input characteristics

### **Output driving current**

The GPIOs (general purpose input/outputs) can sink or source up to  $\pm 8$  mA, and sink or source up to  $\pm 20$  mA (with a relaxed  $V_{OL}/V_{OH}$ ).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on V<sub>DDIOX</sub>, plus the maximum consumption of the MCU sourced on V<sub>DD</sub>, cannot exceed the absolute maximum rating ΣI<sub>VDD</sub> (see *Table 19: Voltage characteristics*).
- The sum of the currents sunk by all the I/Os on V<sub>SS</sub>, plus the maximum consumption of the MCU sunk on V<sub>SS</sub>, cannot exceed the absolute maximum rating ΣI<sub>VSS</sub> (see Table 19: Voltage characteristics).

### **Output voltage levels**

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*. All I/Os are CMOS- and TTL-compliant (FT OR TT unless otherwise specified).

Table 71. Output voltage characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>OL</sub>	Output low level voltage for an I/O pin	CMOS port <sup>(2)</sup>	-	0.4	
V <sub>OH</sub>	Output high level voltage for an I/O pin	$ I_{IO}  = 8 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	V <sub>DDIOx</sub> -0.4	-	
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	TTL port <sup>(2)</sup>	-	0.4	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	$ I_{IO}  = 8 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	2.4	-	
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub>   = 20 mA	-	1.3	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	V <sub>DDIOx</sub> ≥ 2.7 V	V <sub>DDIOx</sub> -1.3	-	
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub>   = 4 mA	-	0.45	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	V <sub>DDIOx</sub> ≥ 1.62 V	V <sub>DDIOx</sub> -0.45	-	V
V <sub>OL</sub> <sup>(3)</sup>	Output low level voltage for an I/O pin	I <sub>IO</sub>   = 2 mA	-	$0.35_xV_{DDIOx}$	
V <sub>OH</sub> <sup>(3)</sup>	Output high level voltage for an I/O pin	1.62 V ≥ V <sub>DDIOx</sub> ≥ 1.08 V	0.65 <sub>x</sub> V <sub>DDIOx</sub>	-	
		$ I_{IO}  = 20 \text{ mA}$ $V_{DDIOx} \ge 2.7 \text{ V}$	-	0.4	
V <sub>OLFM+</sub>	Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with "f" option)	$ I_{IO}  = 10 \text{ mA}$ $V_{DDIOx} \ge 1.62 \text{ V}$	-	0.4	
	opaon)	I <sub>IO</sub>   = 2 mA 1.62 V ≥ V <sub>DDIOx</sub> ≥ 1.08 V	-	0.4	

The I<sub>IO</sub> current sourced or sunk by the device must always respect the absolute maximum rating specified in Table 19: Voltage characteristics, and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI<sub>IO</sub>.

### Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 33* and *Table 72*, respectively.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.



<sup>2.</sup> TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.

<sup>3.</sup> Guaranteed by design.

Table 72. I/O AC characteristics<sup>(1)(2)</sup>

Speed	Symbol	Parameter	Conditions	Min	Max	Unit	
			C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	5		
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	1		
	Fmax	Maximum fraguancy	C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	0.1	MHz	
	rillax	Maximum frequency	C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	10	IVITZ	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	1.5		
00			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	0.1		
00			C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	25		
		Tr/Tf Output rise and fall time	C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	52		
	Tr/Tf		C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	140	200	
	11/11		C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	17	ns	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	37		
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	110		
		Maximum frequency	C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	25		
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	10	1	
	Fmax		C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	1	MHz	
	FIIIdX		C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	50	IVITIZ	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	15		
01			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	1		
01			C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	9		
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	16		
	Tr/Tf	Output rise and fall time	C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	40	ne	
	11/11	Output rise and fall time	C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	4.5	ns	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	9		
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	21		

Table 72. I/O AC characteristics<sup>(1)(2)</sup> (continued)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
			C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	50	
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	25	
		Mariana francisco	C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	5	
	Fmax	max Maximum frequency	C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	100 <sup>(3)</sup>	MHz
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	37.5	
40			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	5	
10			C=50 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	5.8	
			C=50 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	11	
	T-/Tf	Outside and fall times	C=50 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	28	ns
	Tr/Tf	Output rise and fall time	C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	2.5	
			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	5	
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	12	
			C=30 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	120 <sup>(3)</sup>	
			C=30 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	50	
		Marian market	C=30 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	10	
	Fmax	Maximum frequency	C=10 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	180 <sup>(3)</sup>	MHz
11			C=10 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	75	
			C=10 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	10	
			C=30 pF, 2.7 V≤V <sub>DDIOx</sub> ≤3.6 V	-	3.3	
	Tr/Tf	Output rise and fall time	C=30 pF, 1.62 V≤V <sub>DDIOx</sub> ≤2.7 V	-	6	ns
			C=30 pF, 1.08 V≤V <sub>DDIOx</sub> ≤1.62 V	-	16	
	Fmax	Maximum frequency	C-50 = 5 4 C \ / 2 / 2 / 2 C \ /	-	1	MHz
Fm+	Tf	Output fall time <sup>(4)</sup>	- C=50 pF, 1.6 V≤V <sub>DDIOx</sub> ≤3.6 V	-	5	ns

The I/O speed is configured using the OSPEEDRy[1:0] bits. The Fm+ mode is configured in the SYSCFG\_CFGR1 register. Refer to the RM0351 reference manual for a description of GPIO Port configuration register.

<sup>2.</sup> Guaranteed by design.

<sup>3.</sup> This value represents the I/O capability but the maximum system frequency is limited to 80 MHz.

<sup>4.</sup> The fall time is defined between 70% and 30% of the output waveform accordingly to I<sup>2</sup>C specification.

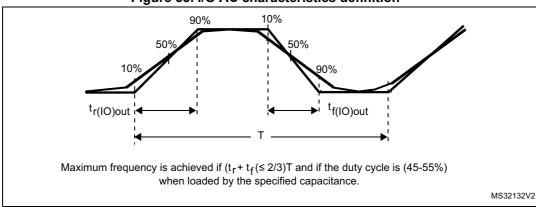


Figure 33. I/O AC characteristics definition<sup>(1)</sup>

1. Refer to Table 72: I/O AC characteristics.

# 6.3.15 NRST pin characteristics

The NRST pin input driver uses the CMOS technology. It is connected to a permanent pull-up resistor,  $R_{\text{PU}}$ .

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 22: General operating conditions*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub>	NRST input low level voltage	-	-	-	0.3 <sub>x</sub> V <sub>DDIOx</sub>	V
V <sub>IH(NRST)</sub>	NRST input high level voltage	-	0.7 <sub>x</sub> V <sub>DDIOx</sub>	-	-	
V <sub>hys(NRST)</sub>	NRST Schmitt trigger voltage hysteresis	-	-	200	-	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(2)</sup>	$V_{IN} = V_{SS}$	25	40	55	kΩ
V <sub>F(NRST)</sub>	NRST input filtered pulse	-	-	-	70	ns
V <sub>NF(NRST)</sub>	NRST input not filtered pulse	1.71 V ≤ V <sub>DD</sub> ≤ 3.6 V	350	-	-	ns

Table 73. NRST pin characteristics<sup>(1)</sup>

<sup>1.</sup> Guaranteed by design.

<sup>2.</sup> The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimal (~10% order).

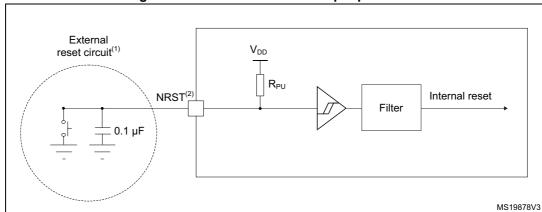


Figure 34. Recommended NRST pin protection

- 1. The reset network protects the device against parasitic resets.
- 2. The user must ensure that the level on the NRST pin can go below the V<sub>IL(NRST)</sub> max level specified in *Table 73: NRST pin characteristics*. Otherwise the reset will not be taken into account by the device.
- 3. The external capacitor on NRST must be placed as close as possible to the device.

### 6.3.16 Extended interrupt and event controller input (EXTI) characteristics

The pulse on the interrupt input must have a minimal length in order to guarantee that it is detected by the event controller.

Table 74. EXTI Input Characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PLEC	Pulse length to event controller	-	20	-	-	ns

<sup>1.</sup> Guaranteed by design.

### 6.3.17 Analog switches booster

Table 75. Analog switches booster characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Тур	Max	Unit
$V_{DD}$	Supply voltage	1.62	-	3.6	V
t <sub>SU(BOOST)</sub>	Booster startup time	-	-	240	μs
I <sub>DD(BOOST)</sub>	Booster consumption for $1.62 \text{ V} \le \text{V}_{DD} \le 2.0 \text{ V}$	-	-	250	
	Booster consumption for $2.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 2.7 \text{ V}$	-	-	500	μΑ
	Booster consumption for $2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 3.6 \text{ V}$	-	-	900	

<sup>1.</sup> Guaranteed by design.

# 6.3.18 Analog-to-Digital converter characteristics

Unless otherwise specified, the parameters given in *Table 76* are preliminary values derived from tests performed under ambient temperature,  $f_{PCLK}$  frequency and  $V_{DDA}$  supply voltage conditions summarized in *Table 22: General operating conditions*.

Note: It is recommended to perform a calibration after each power-up.

Table 76. ADC characteristics<sup>(1) (2)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DDA</sub>	Analog supply voltage	-	1.62	-	3.6	V
V	Positive reference voltage	V <sub>DDA</sub> ≥ 2 V	2	-	$V_{DDA}$	V
V <sub>REF+</sub>	Positive reference voltage	V <sub>DDA</sub> < 2 V		$V_{DDA}$		V
V <sub>REF-</sub>	Negative reference voltage	-		$V_{SSA}$		V
f.	ADC aloak froguency	Range 1	0.14	-	80	MHz
f <sub>ADC</sub>	ADC clock frequency	Range 2	0.14	-	26	IVITZ
		Resolution = 12 bits	-	-	5.33	
	Sampling rate for FAST	Resolution = 10 bits	-	-	6.15	1
	channels	Resolution = 8 bits	-	-	7.27	1
		Resolution = 6 bits	-	-	8.88	Mone
f <sub>s</sub>		Resolution = 12 bits	-	-	4.21	- Msps
	Sampling rate for SLOW channels	Resolution = 10 bits	-	-	4.71	
		Resolution = 8 bits	-	-	5.33	
		Resolution = 6 bits	-	-	6.15	
f <sub>TRIG</sub>	External trigger frequency	f <sub>ADC</sub> = 80 MHz Resolution = 12 bits	-	-	5.33	MHz
		Resolution = 12 bits	-	-	15	1/f <sub>ADC</sub>
V <sub>AIN</sub> <sup>(3)</sup>	Conversion voltage range(2)	-	0	-	V <sub>REF+</sub>	V
R <sub>AIN</sub>	External input impedance	-	-	-	50	kΩ
C <sub>ADC</sub>	Internal sample and hold capacitor	-	-	5	-	pF
t <sub>STAB</sub>	Power-up time	-		1		conversion cycle
	Calibration time	f <sub>ADC</sub> = 80 MHz		1.45		μs
t <sub>CAL</sub>	Calibration time	-		116		1/f <sub>ADC</sub>
	Trigger conversion	CKMODE = 00	1.5	2	2.5	
	Trigger conversion latency Regular and	CKMODE = 01	-	-	2.0	1 /4
t <sub>LATR</sub>	injected channels without	CKMODE = 10	-	-	2.25	1/f <sub>ADC</sub>
	conversion abort	CKMODE = 11	-	-	2.125	]



Table 76. ADC characteristics<sup>(1)</sup> (continued)

	1	1	(0011611141	/	1		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
	Triananaan	CKMODE = 00	2.5	3	3.5		
	Trigger conversion latency Injected channels	CKMODE = 01	-	-	3.0	1 /F	
<sup>t</sup> LATRINJ	aborting a regular conversion	CKMODE = 10	-	-	3.25	1/f <sub>ADC</sub>	
	Conversion	CKMODE = 11	-	-	3.125		
4	Sampling time	f <sub>ADC</sub> = 80 MHz	0.03125	-	8.00625	μs	
t <sub>s</sub>		-	2.5	-	640.5	1/f <sub>ADC</sub>	
t <sub>ADCVREG_STUP</sub>	ADC voltage regulator start-up time	-	-	-	20	μs	
	Total conversion time	f <sub>ADC</sub> = 80 MHz Resolution = 12 bits	0.1875	-	8.1625	μs	
t <sub>CONV</sub>	Total conversion time (including sampling time)	Resolution = 12 bits	ts + 12.5 cycles for successive approximation = 15 to 653			1/f <sub>ADC</sub>	
		fs = 5 Msps	-	730	830		
I <sub>DDA</sub> (ADC)	ADC consumption from the V <sub>DDA</sub> supply	fs = 1 Msps	-	160	220	μΑ	
	THE TODA COPPEN	fs = 10 ksps	-	16	50		
	ADC consumption from	fs = 5 Msps	-	130	160		
I <sub>DDV_S</sub> (ADC)	the V <sub>REF+</sub> single ended	fs = 1 Msps	-	30	40	μΑ	
	mode	fs = 10 ksps	-	0.6	2		
	ADC consumption from	fs = 5 Msps	-	260	310	μA	
I <sub>DDV_D</sub> (ADC)	the V <sub>REF+</sub> differential	fs = 1 Msps	-	60	70		
_	mode	fs = 10 ksps	-	1.3	3		

<sup>1.</sup> Guaranteed by design

The maximum value of R<sub>AIN</sub> can be found in *Table 77: Maximum ADC RAIN*.

<sup>2.</sup> The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4V). It is disable when  $V_{DDA} \ge 2.4$  V.

V<sub>REF+</sub> can be internally connected to V<sub>DDA</sub> and V<sub>REF-</sub> can be internally connected to V<sub>SSA</sub>, depending on the package. Refer to Section 4: Pinouts and pin description for further details.

Table 77. Maximum ADC R<sub>AIN</sub><sup>(1)(2)</sup>

Docalution	Sampling cycle	Sampling time [ns]	R <sub>AIN</sub> r	max (Ω)
Resolution	@80 MHz	@80 MHz	Fast channels <sup>(3)</sup>	Slow channels <sup>(4)</sup>
	2.5	31.25	100	N/A
	6.5	81.25	330	100
	12.5	156.25	680	470
40 hita	24.5	306.25	1500	1200
12 bits	47.5	593.75	2200	1800
	92.5	1156.25	4700	3900
	247.5	3093.75	12000	10000
	640.5	8006.75	39000	33000
	2.5	31.25	120	N/A
	6.5	81.25	390	180
	12.5	156.25	820	560
40.1:11	24.5	306.25	1500	1200
10 bits	47.5	593.75	2200	1800
	92.5	1156.25	5600	4700
	247.5	3093.75	12000	10000
	640.5	8006.75	47000	39000
	2.5	31.25	180	N/A
	6.5	81.25	470	270
	12.5	156.25	1000	680
0 6:4-	24.5	306.25	1800	1500
8 bits	47.5	593.75	2700	2200
	92.5	1156.25	6800	5600
	247.5	3093.75	15000	12000
	640.5	8006.75	50000	50000
	2.5	31.25	220	N/A
	6.5	81.25	560	330
	12.5	156.25	1200	1000
6 hita	24.5	306.25	2700	2200
6 bits	47.5	593.75	3900	3300
	92.5	1156.25	8200	6800
	247.5	3093.75	18000	15000
	640.5	8006.75	50000	50000

<sup>1.</sup> Guaranteed by design.



2. The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4V). It is disable when  $V_{DDA} \ge 2.4$  V.

- 3. Fast channels are: PC0, PC1, PC2, PC3, PA0.
- 4. Slow channels are: all ADC inputs except the fast channels.

Table 78. ADC accuracy - limited test conditions 1<sup>(1)(2)(3)</sup>

Sym- bol	Parameter	(	Conditions <sup>(4</sup>	)	Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	4	5	
	Total		ended	Slow channel (max speed)	-	4	5	
ET	unadjusted error		Differential	Fast channel (max speed)	-	3.5	4.5	
			Differential	Slow channel (max speed)	-	3.5	4.5	
			Single	Fast channel (max speed)	-	1	2.5	
EO	Offset		ended	Slow channel (max speed)	-	1	2.5	
	error		Differential	Fast channel (max speed)	-	1.5	2.5	
			Dillerential	Slow channel (max speed)	-	1.5	2.5	
			Single	Fast channel (max speed)	-	2.5	4.5	
EG	Gain error		ended	Slow channel (max speed)	-	2.5	4.5	LSB
EG	Gain enoi		Differential	Fast channel (max speed)	-	2.5	3.5	LOB
			Dillerential	Slow channel (max speed)	-	2.5	3.5	
			Single	Fast channel (max speed)	-	1	1.5	
ED	Differential		ended	Slow channel (max speed)	-	1	1.5	
ED linearity error	_	ADC clock frequency ≤	Differential	Fast channel (max speed)	-	1	1.2	
		80 MHz, Sampling rate ≤ 5.33 Msps,	2010111101	Slow channel (max speed)	-	1	1.2	
		$V_{DDA} = VREF + = 3 V$ , TA = 25 °C	Single ended	Fast channel (max speed)	-	1.5	2.5	
EL	Integral			Slow channel (max speed)	-	1.5	2.5	
	linearity error		D:##:-I	Fast channel (max speed)	-	1	2	
			Differential	Slow channel (max speed)	-	1	2	
			Single	Fast channel (max speed)	10.4	10.5	-	
ENOB	Effective number of		ended	Slow channel (max speed)	10.4	10.5	-	bits
LINOB	bits		Differential	Fast channel (max speed)	10.8	10.9	-	טונס
			Dillerential	Slow channel (max speed)	10.8	10.9	-	
	Cianal to		Single	Fast channel (max speed)	64.4	65	-	
SINAD	Signal-to- noise and		ended	Slow channel (max speed)	64.4	65	-	
SINAD	distortion		Differential	Fast channel (max speed)	66.8	67.4	-	
	ratio		Dillerential	Slow channel (max speed)	66.8	67.4	-	4D
			Single ended	Fast channel (max speed)	65	66	-	dB
SNR	Signal-to-			Slow channel (max speed)	65	66	-	1
SINK	noise ratio		Difforential	Fast channel (max speed)	67	68	-	
			Differential	Slow channel (max speed)	67	68	-	



Table 78. ADC accuracy - limited test conditions  $1^{(1)(2)(3)}$  (continued)

Sym- bol	Parameter	C	Min	Тур	Max	Unit		
Total THD harmonion distortion	Total	onic Sampling rate ≤ 5.33 Msps,	Single	Fast channel (max speed)	-	-74	-73	
			ended	Slow channel (max speed)	-	-74	-73	dB
	distortion		Differential	Fast channel (max speed)	-	-79	-76	uВ
		TA = 25 °C	Dillerential	Slow channel (max speed)	-	-79	-76	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
  significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
  Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4 V). It is disable when  $V_{DDA} \ge 2.4$  V. No oversampling.



Table 79. ADC accuracy - limited test conditions  $2^{(1)(2)(3)}$ 

Sym- bol	Parameter	(	Conditions <sup>(4</sup>	)	Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	4	6.5	
	Total		ended	Slow channel (max speed)	-	4	6.5	
ET	unadjusted error		Differential	Fast channel (max speed)	-	3.5	5.5	
			Differential	Slow channel (max speed)	-	3.5	5.5	
			Single	Fast channel (max speed)	-	1	4.5	
EO	Offset		ended	Slow channel (max speed)	-	1	5	
E0	error		Differential	Fast channel (max speed)	-	1.5	3	
			Differential	Slow channel (max speed)	-	1.5	3	
			Single	Fast channel (max speed)	-	2.5	6	
EG	Cain arrar		ended	Slow channel (max speed)	-	2.5	6	LOD
EG	Gain error		Differential -	Fast channel (max speed)	-	2.5	3.5	LSB
			Dillerential	Slow channel (max speed)	-	2.5	3.5	-
			Single	Fast channel (max speed)	-	1	1.5	
ED	Differential		ended	Slow channel (max speed)	-	1	1.5	
ED lineari		ADC clock frequency ≤	Differential	Fast channel (max speed)	-	1	1.2	
		80 MHz,	Differential	Slow channel (max speed)	-	1	1.2	
		Sampling rate ≤ 5.33 Msps,	Single ended	Fast channel (max speed)	-	1.5	3.5	
	Integral	2 V ≤ V <sub>DDA</sub>		Slow channel (max speed)	-	1.5	3.5	
EL	linearity error		D:#	Fast channel (max speed)	-	1	3	
			Differential	Slow channel (max speed)	-	1	2.5	
			Single	Fast channel (max speed)	10	10.5	-	
ENOB	Effective number of		ended	Slow channel (max speed)	10	10.5	-	bits
ENOB	bits		Differential	Fast channel (max speed)	10.7	10.9	-	DILS
			Dillerential	Slow channel (max speed)	10.7	10.9	-	
	Ciamal to		Single	Fast channel (max speed)	62	65	-	
SINAD	Signal-to- noise and		ended	Slow channel (max speed)	62	65	-	
SINAD	distortion ratio		Differential	Fast channel (max speed)	66	67.4	-	
	Tallo		Differential	Slow channel (max speed)	66	67.4	-	٩D
			Single ended	Fast channel (max speed)	64	66	-	dB
CVID	Signal-to-			Slow channel (max speed)	64	66	-	
SNR	noise ratio		Differential	Fast channel (max speed)	66.5	68	-	
			Differential	Slow channel (max speed)	66.5	68	-	



Table 79. ADC accuracy - limited test conditions  $2^{(1)(2)(3)}$  (continued)

Sym- bol	Parameter	C	Conditions <sup>(4)</sup>					Unit
		ADC clock frequency ≤	Single	Fast channel (max speed)	-	-74	-65	
THD	Total harmonic	80 MHz,	ended	Slow channel (max speed)	1	-74	-67	dB
וחט	distortion	Sampling rate ≤ 5.33 Msps,	Differential	Fast channel (max speed)	-	-79	-70	uБ
		2 V ≤ V <sub>DDA</sub>	Dillerential	Slow channel (max speed)	-	-79	-71	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
  significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
  Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4 V). It is disable when  $V_{DDA} \ge 2.4$  V. No oversampling.

Table 80. ADC accuracy - limited test conditions 3<sup>(1)(2)(3)</sup>

Sym- bol	Parameter	(	Conditions <sup>(4</sup>	)	Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	5.5	7.5	
ET	Total		ended	Slow channel (max speed)	-	4.5	6.5	
E1	unadjusted error		Differential	Fast channel (max speed)	-	4.5	7.5	
			Dillerential	Slow channel (max speed)	-	4.5	5.5	
			Single	Fast channel (max speed)	-	2	5	
EO	Offset		ended	Slow channel (max speed)	-	2.5	5	
	error		Differential	Fast channel (max speed)	-	2	3.5	
			Dillerential	Slow channel (max speed)	-	2.5	3	
			Single	Fast channel (max speed)	-	4.5	7	
EG	Gain error		ended	Slow channel (max speed)	-	3.5	6	LSB
EG	Gain enoi		Differential	Fast channel (max speed)	-	3.5	4	LSB
			Dillerential	Slow channel (max speed)	-	3.5	5	
			Single	Fast channel (max speed)	-	1.2	1.5	
ED	Differential		ended	Slow channel (max speed)	-	1.2	1.5	
	ED linearity error	ADC clock frequency ≤ 80 MHz, Sampling rate ≤ 5.33 Msps,	Differential	Fast channel (max speed)	-	1	1.2	
			Dillerential	Slow channel (max speed)	-	1	1.2	
		$1.65 \text{ V} \le \text{V}_{DDA} = \text{V}_{REF+} \le$ 3.6 V,	Single	Fast channel (max speed)	-	3	3.5	
EL	Integral linearity	Voltage scaling Range 1	ended	Slow channel (max speed)	-	2.5	3.5	
EL	error		Differential	Fast channel (max speed)	-	2	2.5	
			Dillerential	Slow channel (max speed)	-	2	2.5	
			Single	Fast channel (max speed)	10	10.4	-	
ENOB	Effective number of		ended	Slow channel (max speed)	10	10.4	-	bits
LINOB	bits		Differential	Fast channel (max speed)	10.6	10.7	-	טונס
			Dillerential	Slow channel (max speed)	10.6	10.7	-	
	Cianal to		Single	Fast channel (max speed)	62	64	-	
SINAD	Signal-to- noise and		ended	Slow channel (max speed)	62	64	-	
SINAD	distortion		Differential	Fast channel (max speed)	65	66	-	
	ratio		Dillerential	Slow channel (max speed)	65	66	-	ЧD
			Single	Fast channel (max speed)	63	65	-	dB
SNR	Signal-to-		ended	Slow channel (max speed)	63	65	-	
SINK	noise ratio		Difforential	Fast channel (max speed)	66	67	-	
		Differential -		Slow channel (max speed)	66	67	-	



Table 80. ADC accuracy - limited test conditions  $3^{(1)(2)(3)}$  (continued)

Sym- bol	Parameter	C	Conditions <sup>(4)</sup>					Unit
		ADC clock frequency ≤	Single	Fast channel (max speed)	-	-69	-67	
	Total	80 MHz, Sampling rate ≤ 5.33 Msps,	ended	Slow channel (max speed)	-	-71	-67	
THD	harmonic distortion	$1.65 \text{ V} \le \text{V}_{\text{DDA}} = \text{V}_{\text{REF+}} \le$		Fast channel (max speed)	-	-72	-71	dB
	distortion	3.6 V, Voltage scaling Range 1	Differential	Slow channel (max speed)	-	-72	-71	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
  significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
  Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4 V). It is disable when  $V_{DDA} \ge 2.4$  V. No oversampling.

Table 81. ADC accuracy - limited test conditions 4<sup>(1)(2)(3)</sup>

Sym- bol	Parameter	(	Conditions <sup>(4</sup>	)	Min	Тур	Max	Unit
			Single	Fast channel (max speed)	-	5	5.4	
	Total		ended	Slow channel (max speed)	-	4	5	
ET	unadjusted error		Differential	Fast channel (max speed)	-	4	5	
			Differential	Slow channel (max speed)	-	3.5	4.5	
			Single	Fast channel (max speed)	-	2	4	
EO	Offset		ended	Slow channel (max speed)	-	2	4	
	error		Differential	Fast channel (max speed)	-	2	3.5	
			Dillerential	Slow channel (max speed)	-	2	3.5	
			Single	Fast channel (max speed)	-	4	4.5	
EG	Gain error		ended	Slow channel (max speed)	-	4	4.5	LSB
EG	Gain enoi		Differential	Fast channel (max speed)	-	3	4	LOB
			Dillerential	Slow channel (max speed)	-	3	4	
			Single	Fast channel (max speed)	-	1	1.5	
ED	Differential		ended	Slow channel (max speed)	-	1	1.5	
	ED linearity error	ADC clock frequency ≤ 26 MHz,  1.65 V ≤ V <sub>DDA</sub> = VREF+ ≤	Differential	Fast channel (max speed)	-	1	1.2	
	61101		Dillerential	Slow channel (max speed)	-	1	1.2	
		3.6  V,	Single	Fast channel (max speed)	-	2.5	3	
EL	Integral	Voltage scaling Range 2	ended	Slow channel (max speed)	-	2.5	3	
	linearity error		Differential	Fast channel (max speed)	-	2	2.5	
			Dillerential	Slow channel (max speed)	-	2	2.5	
			Single	Fast channel (max speed)	10.2	10.5	-	
ENOB	Effective number of		ended	Slow channel (max speed)	10.2	10.5	-	bits
LINOB	bits		Differential	Fast channel (max speed)	10.6	10.7	-	טונס
			Dillerential	Slow channel (max speed)	10.6	10.7	-	
	Signal-to-		Single	Fast channel (max speed)	63	65	-	
SINAD	noise and		ended	Slow channel (max speed)	63	65	-	
SINAD	distortion		Differential	Fast channel (max speed)	65	66	-	
	ratio		Dillerential	Slow channel (max speed)	65	66	-	ЧD
			Single	Fast channel (max speed)	64	65	-	dB
SNR	Signal-to-		ended	Slow channel (max speed)	64	65	-	
SINK	noise ratio		Differential	Fast channel (max speed)	66	67	-	
	Differential		Slow channel (max speed)	66	67	-		



Table 81. ADC accuracy - limited test conditions  $4^{(1)(2)(3)}$  (continued)

Sym- bol	Parameter	C	Conditions <sup>(4)</sup>					Unit
		ADC clock frequency ≤	Single	Fast channel (max speed)	-	-71	-69	
THD	Total harmonic	26 MHz, 1.65 V ≤ V <sub>DDA</sub> = VREF+ ≤	ended	Slow channel (max speed)	1	-71	-69	dB
טווו	distortion	3.6 V,	Differential	Fast channel (max speed)	1	-73	-72	uБ
		Voltage scaling Range 2	Dilleterillar	Slow channel (max speed)	-	-73	-72	

- 1. Guaranteed by design.
- 2. ADC DC accuracy values are measured after internal calibration.
- ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this
  significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a
  Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
- 4. The I/O analog switch voltage booster is enable when  $V_{DDA}$  < 2.4 V (BOOSTEN = 1 in the SYSCFG\_CFGR1 when  $V_{DDA}$  < 2.4 V). It is disable when  $V_{DDA} \ge 2.4$  V. No oversampling.



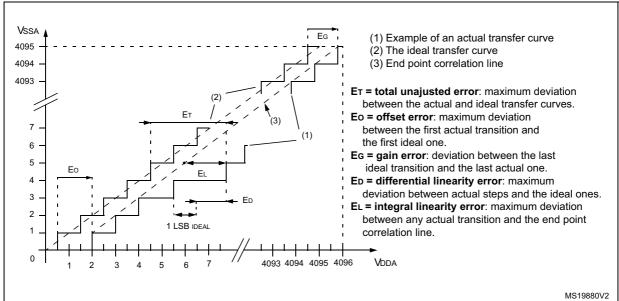


Figure 35. ADC accuracy characteristics





- Refer to Table 76: ADC characteristics for the values of R<sub>AIN</sub> and C<sub>ADC</sub>.
- 2. C<sub>parasitic</sub> represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (refer to *Table 70: I/O static characteristics* for the value of the pad capacitance). A high C<sub>parasitic</sub> value will downgrade conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced.
- 3. Refer to Table 70: I/O static characteristics for the values of I<sub>lka</sub>.

#### General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 22: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

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# 6.3.19 Digital-to-Analog converter characteristics

Table 82. DAC characteristics<sup>(1)</sup>

Symbol	Parameter	Co	Conditions M		Тур	Max	Unit
$V_{DDA}$	Analog supply voltage for DAC ON		ffer OFF (no resistive OUTx pin or internal	1.71	-	3.6	
	Site on	Other modes		1.80	-		
V <sub>REF+</sub>	Positive reference voltage	DAC output buffer OFF (no resistive load on DAC1_OUTx pin or internal connection)		1.71	-	V <sub>DDA</sub>	V
		Other modes		1.80	-		
V <sub>REF-</sub>	Negative reference voltage		-		V <sub>SSA</sub>		
	Decistive lead	DAC output	connected to V <sub>SSA</sub>	5	-	-	1.0
$R_L$	Resistive load	buffer ON	B) to output		-	-	kΩ
R <sub>O</sub>	Output Impedance	DAC output bu	ffer OFF	9.6	11.7	13.8	kΩ
Б	Output impedance sample	V <sub>DD</sub> = 2.7 V		-	-	2	1.0
$R_{BON}$	and hold mode, output buffer ON	V <sub>DD</sub> = 2.0 V	V <sub>DD</sub> = 2.0 V			3.5	kΩ
_	Output impedance sample	V <sub>DD</sub> = 2.7 V		-	-	16.5	
$R_{BOFF}$	and hold mode, output buffer OFF	V <sub>DD</sub> = 2.0 V			-	18.0	kΩ
C <sub>L</sub>	Consolting look	DAC output bu	ffer ON	-	-	50	pF
C <sub>SH</sub>	Capacitive load	Sample and ho	old mode	-	0.1	1	μF
V <sub>DAC_OUT</sub>	Voltage on DAC1_OUTx output	DAC output bu	ffer ON	0.2	ı	V <sub>REF+</sub> - 0.2	V
_	σαιραί	DAC output bu	ffer OFF	0	-	$V_{REF}$	
		<b>N</b> 111.	±0.5 LSB	-	1.7	3	
	Settling time (full scale: for a 12-bit code transition	Normal mode DAC output	±1 LSB	-	1.6	2.9	
	between the lowest and the	buffer ON CL ≤ 50 pF,	±2 LSB	-	1.55	2.85	
t <sub>SETTLING</sub>	highest input codes when DAC1 OUTx reaches final	RL ≥ 5 kΩ	±4 LSB	-	1.48	2.8	μs
	value ±0.5LSB, ±1 LSB,	±8 LSB		-	1.4	2.75	
	±2 LSB, ±4 LSB, ±8 LSB)	Normal mode DAC output buffer OFF, ±1LSB, CL = 10 pF		-	2	2.5	
. (2)	Wakeup time from off state (setting the ENx bit in the	Normal mode DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	4.2	7.5	
t <sub>WAKEUP</sub> <sup>(2)</sup>	DAC Control register) until final value ±1 LSB	Normal mode [ OFF, CL ≤ 10 p	DAC output buffer bF	-	2	5	μs
PSRR	V <sub>DDA</sub> supply rejection ratio	Normal mode [ CL ≤ 50 pF, RL	DAC output buffer ON . = 5 kΩ, DC	-	-80	-28	dB

Table 82. DAC characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Co	onditions	Min	Тур	Max	Unit
T <sub>W_to_W</sub>	Minimal time between two consecutive writes into the DAC_DORx register to guarantee a correct DAC1_OUTx for a small variation of the input code (1 LSB) DAC_MCR:MODEx[2:0] = 000 or 001 DAC_MCR:MODEx[2:0] = 010 or 011	CL ≤ 50 pF, RL ≥ 5 kΩ CL ≤ 10 pF		1	-	-	μs
		DAC1_OUTx	DAC output buffer ON, C <sub>SH</sub> = 100 nF	-	0.7	3.5	ms
	Sampling time in sample and hold mode (code transition between the	pin connected	DAC output buffer OFF, C <sub>SH</sub> = 100 nF	-	10.5	18	1115
<sup>t</sup> SAMP	lowest input code and the highest input code when DAC1_OUTx reaches final value ±1LSB)	DAC1_OUTx pin not connected (internal connection only)	DAC output buffer OFF	-	2	3.5	μs
I <sub>leak</sub>	Output leakage current	Sample and ho DAC1_OUTx p		-	-	_(3)	nA
Cl <sub>int</sub>	Internal sample and hold capacitor		-	5.2	7	8.8	pF
t <sub>TRIM</sub>	Middle code offset trim time	DAC output bu	ffer ON	50	-	-	μs
V	Middle code offset for 1 trim	V <sub>REF+</sub> = 3.6 V		-	1500	-	\/
V <sub>offset</sub>	code step	V <sub>REF+</sub> = 1.8 V		-	750	-	μV
		DAC output	No load, middle code (0x800)	-	315	500	
		buffer ON	No load, worst code (0xF1C)	-	450	670	
I <sub>DDA</sub> (DAC)	DAC consumption from $V_{DDA}$	DAC output buffer OFF	No load, middle code (0x800)	-	-	0.2	μΑ
			old mode, C <sub>SH</sub> =	-	315 x Ton/(Ton +Toff) (4)	670 x Ton/(Ton +Toff) (4)	



Symbol	Parameter	C	onditions	Min	Тур	Max	Unit
		DAC output	No load, middle code (0x800)	-	185	240	
		buffer ON	No load, worst code (0xF1C)	-	340	400	
		DAC output buffer OFF	No load, middle code (0x800)	-	155	205	
I <sub>DDV</sub> (DAC)	DAC consumption from V <sub>REF+</sub>	Sample and h C <sub>SH</sub> = 100 nF,	old mode, buffer ON, worst case	-	185 x Ton/(Ton +Toff) (4)	400 x Ton/(Ton +Toff) (4)	μA
		Sample and h C <sub>SH</sub> = 100 nF,	old mode, buffer OFF, worst case	-	155 x Ton/(Ton +Toff) (4)	205 x Ton/(Ton +Toff) (4)	

Table 82. DAC characteristics<sup>(1)</sup> (continued)

- Guaranteed by design.
- 2. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).
- 3. Refer to Table 70: I/O static characteristics.
- 4. Ton is the Refresh phase duration. Toff is the Hold phase duration. Refer to RM0351 reference manual for more details.

Figure 37. 12-bit buffered / non-buffered DAC

The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly
without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the
DAC\_CR register.

# Table 83. DAC accuracy<sup>(1)</sup>

Symbol	Parameter	Conditio	ns	Min	Тур	Max	Unit
DAII	Differential non	DAC output buffer ON		-	-	±2	
DNL	linearity (2)	DAC output buffer OFF		-	-	±2	
-	monotonicity	10 bits		9	guarantee	d	
INL	Integral non	DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	-	±4	
INC	linearity <sup>(3)</sup>	DAC output buffer OFF CL ≤ 50 pF, no RL	_	-	-	±4	
		DAC output buffer ON	V <sub>REF+</sub> = 3.6 V	-	-	±12	LCD
Offset	Offset error at code 0x800 <sup>(3)</sup>	CL ≤ 50 pF, RL ≥ 5 kΩ	V <sub>REF+</sub> = 1.8 V	-	-	±25	LSB
		DAC output buffer OFF CL ≤ 50 pF, no RL		-	-	±8	
Offset1	Offset error at code 0x001 <sup>(4)</sup>	DAC output buffer OFF CL ≤ 50 pF, no RL	_	-	-	±5	
OffsetCal	Offset Error at code 0x800	DAC output buffer ON	V <sub>REF+</sub> = 3.6 V	-	-	±5	
OlisetGal	after calibration	CL ≤ 50 pF, RL ≥ 5 kΩ	V <sub>REF+</sub> = 1.8 V	-	-	±7	
Coin	Gain error <sup>(5)</sup>	DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	-	±0.5	%
Gain	Gain enois?	DAC output buffer OFF CL ≤ 50 pF, no RL		-	-	±0.5	70
TUE	Total	DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	-	±30	LSB
TOE	unadjusted error	DAC output buffer OFF CL ≤ 50 pF, no RL		-	-	±12	LOD
TUECal	Total unadjusted error after calibration	DAC output buffer ON CL ≤ 50 pF, RL ≥ 5 kΩ		-	-	±23	LSB
SNR	Signal-to-noise	DAC output buffer ON CL $\leq$ 50 pF, RL $\geq$ 5 k $\Omega$ 1 kHz, BW 500 kHz		-	71.2	-	dВ
SINK	ratio	DAC output buffer OFF CL ≤ 50 pF, no RL, 1 kHz BW 500 kHz		-	71.6	-	dB
THD	Total harmonic	DAC output buffer ON CL $\leq$ 50 pF, RL $\geq$ 5 k $\Omega$ , 1	kHz	-	-78	-	4D
וחט	distortion	DAC output buffer OFF CL ≤ 50 pF, no RL, 1 kHz		-	-79	-	dB



Table 83. DAC accuracy<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
SINAD	Signal-to-noise and distortion	DAC output buffer ON CL $\leq$ 50 pF, RL $\geq$ 5 k $\Omega$ , 1 kHz	-	70.4	-	dB
	ratio	DAC output buffer OFF CL ≤ 50 pF, no RL, 1 kHz	-	71	-	uБ
ENOD	Effective	DAC output buffer ON CL $\leq$ 50 pF, RL $\geq$ 5 k $\Omega$ , 1 kHz	-	11.4	-	hita
ENOB	number of bits	DAC output buffer OFF CL ≤ 50 pF, no RL, 1 kHz	-	11.5	-	bits

- 1. Guaranteed by design.
- 2. Difference between two consecutive codes 1 LSB.
- 3. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
- 4. Difference between the value measured at Code (0x001) and the ideal value.
- Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V<sub>REF+</sub> – 0.2) V when buffer is ON.

# 6.3.20 Voltage reference buffer characteristics

Table 84. VREFBUF characteristics<sup>(1)</sup>

Symbol	Parameter	Conditio	ons	Min	Тур	Max	Unit
		Normal made	V <sub>RS</sub> = 0	2.4	-	3.6	
	Analog supply	Normal mode	V <sub>RS</sub> = 1	2.8	-	3.6	
$V_{DDA}$	voltage	Degraded mode <sup>(2)</sup>	V <sub>RS</sub> = 0	1.65	-	2.4	
		Degraded mode.	V <sub>RS</sub> = 1	1.65	-	2.8	V
		Normal mode	V <sub>RS</sub> = 0	2.046 <sup>(3)</sup>	2.048	2.049 <sup>(3)</sup>	V
V <sub>REFBUF</sub> _	Voltage reference	Normal mode	V <sub>RS</sub> = 1	2.498 <sup>(3)</sup>	2.5	2.502 <sup>(3)</sup>	
OUT	output	Degraded mode <sup>(2)</sup>	V <sub>RS</sub> = 0	V <sub>DDA</sub> -150 mV	-	$V_{DDA}$	
		Degraded mode	V <sub>RS</sub> = 1	V <sub>DDA</sub> -150 mV	-	$V_{DDA}$	
TRIM	Trim step resolution	-	-	-	±0.05	±0.1	%
CL	Load capacitor	-	-	0.5	1	1.5	μF
esr	Equivalent Serial Resistor of Cload	-	-	-	-	2	Ω
I <sub>load</sub>	Static load current	-	-	-	-	4	mA
1	Line regulation	2.8 V ≤ V <sub>DDA</sub> ≤ 3.6 V	I <sub>load</sub> = 500 μA	-	200	1000	nnm/\/
I <sub>line_reg</sub>	Line regulation	2.6 V \( \times \text{V}_{\text{DDA}} \( \times \text{3.0 V} \)	I <sub>load</sub> = 4 mA	-	100	500	ppm/V
I <sub>load_reg</sub>	Load regulation	500 μA ≤ I <sub>load</sub> ≤4 mA	Normal mode	-	50	500	ppm/mA
Т	Temperature	-40 °C < TJ < +125 °C	;	-	-	T <sub>coeff</sub> _ vrefint + 50	ppm/ °C
T <sub>Coeff</sub>	coefficient	0 °C < TJ < +50 °C		-	-	T <sub>coeff</sub> _ vrefint + 50	ррпи С
PSRR	Power supply	DC		40	60	-	dB
1 OKK	rejection	100 kHz		25	40	-	uБ
		$CL = 0.5  \mu F^{(4)}$		-	300	350	
t <sub>START</sub>	Start-up time	$CL = 1.1  \mu F^{(4)}$		-	500	650	μs
		$CL = 1.5  \mu F^{(4)}$		-	650	800	
I <sub>INRUSH</sub>	Control of maximum DC current drive on VREFBUF_ OUT during start-up phase (5)	-	-	-	8	-	mA

# Table 84. VREFBUF characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	VREFBUF	I <sub>load</sub> = 0 μA	-	16	25	
I <sub>DDA</sub> (VREF BUF)	consumption	I <sub>load</sub> = 500 μA	-	18	30	μΑ
,	from V <sub>DDA</sub>	I <sub>load</sub> = 4 mA	-	35	50	

- 1. Guaranteed by design, unless otherwise specified.
- In degraded mode, the voltage reference buffer can not maintain accurately the output voltage which will follow (V<sub>DDA</sub> drop voltage).
- 3. Guaranteed by test in production.
- 4. The capacitive load must include a 100 nF capacitor in order to cut-off the high frequency noise.
- To correctly control the VREFBUF inrush current during start-up phase and scaling change, the V<sub>DDA</sub> voltage should be in the range [2.4 V to 3.6 V] and [2.8 V to 3.6 V] respectively for V<sub>RS</sub> = 0 and V<sub>RS</sub> = 1.

# 6.3.21 Comparator characteristics

Table 85. COMP characteristics<sup>(1)</sup>

Symbol	Parameter	Co	onditions	Min	Тур	Max	Unit
V <sub>DDA</sub>	Analog supply voltage		-	1.62	-	3.6	
V <sub>IN</sub>	Comparator input voltage range		-	0	-	$V_{DDA}$	V
V <sub>BG</sub> <sup>(2)</sup>	Scaler input voltage	-			V <sub>REFINT</sub>	-	
V <sub>SC</sub>	Scaler offset voltage		-	-	±5	±10	mV
I <sub>DDA</sub> (SCALER)	Scaler static consumption	BRG_EN=0 (bi	ridge disable)	-	200	300	nA
IDDA(SCALER)	from V <sub>DDA</sub>	BRG_EN=1 (bridge enable)		-	0.8	1	μA
t <sub>START_SCALER</sub>	Scaler startup time		-	-	100	200	μs
		High-speed	V <sub>DDA</sub> ≥ 2.7 V	-	-	5	
	Comparator startup time to reach propagation delay	mode	V <sub>DDA</sub> < 2.7 V	-	-	7	μs
t <sub>START</sub>		Medium mode	V <sub>DDA</sub> ≥ 2.7 V	-	-	15	
	specification		V <sub>DDA</sub> < 2.7 V	-	-	25	
		Ultra-low-powe	r mode	-	-	80	
		High-speed mode	V <sub>DDA</sub> ≥ 2.7 V	-	55	80	ns µs
	Propagation delay for		V <sub>DDA</sub> < 2.7 V	-	65	100	
t <sub>D</sub> <sup>(3)</sup>	200 mV step	Mandiana na ada	V <sub>DDA</sub> ≥ 2.7 V	-	0.55	0.9	
	with 100 mV overdrive	Medium mode	V <sub>DDA</sub> < 2.7 V	-	0.65	1	
		Ultra-low-powe	r mode	-	5	12	
V <sub>offset</sub>	Comparator offset error	Full common mode range	-	-	±5	±20	mV
		No hysteresis		-	0	-	
	O	Low hysteresis		-	8	-	>/
$V_{hys}$	Comparator hysteresis	Medium hysteresis		-	15	-	mV
		High hysteresis		-	27	-	

Table 85. COMP characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Co	onditions	Min	Тур	Max	Unit
			Static	-	400	600	
I <sub>DDA</sub> (COMP)  Comparator consumpt from V <sub>DDA</sub>		Ultra-low- power mode	With 50 kHz ±100 mV overdrive square signal	-	1200	1	nA
			Static	-	5	7	- μA
	from V <sub>DDA</sub>	Medium mode	With 50 kHz ±100 mV overdrive square signal	-	6	-	
			Static	-	70	100	
		High-speed mode	With 50 kHz ±100 mV overdrive square signal	ı	75	ı	
l <sub>bias</sub>	Comparator input bias current	-		-	-	_(4)	nA

- 1. Guaranteed by design, unless otherwise specified.
- 2. Refer to Table 25: Embedded internal voltage reference.
- 3. Guaranteed by characterization results.
- 4. Mostly I/O leakage when used in analog mode. Refer to I<sub>lkg</sub> parameter in Table 70: I/O static characteristics.

# 6.3.22 Operational amplifiers characteristics

Table 86. OPAMP characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V <sub>DDA</sub>	Analog supply voltage	-	1.8	-	3.6	V	
CMIR	Common mode input range	-	0	-	$V_{DDA}$	V	
VI	Input offset	25 °C, No Load on output.		-	±1.5	mV	
VI <sub>OFFSET</sub> "v	voltage	All voltage/Temp.	-	-	±3	IIIV	
AV/I	Input offset voltage drift	Normal mode	-	±5	-	μV/°C	
ΔVI <sub>OFFSET</sub>		Low-power mode	-	±10	-	μν/ Ο	
TRIMOFFSETP TRIMLPOFFSETP	Offset trim step at low common input voltage (0.1 x V <sub>DDA</sub> )	-	-	0.8	1.1	m\/	
TRIMOFFSETN TRIMLPOFFSETN	Offset trim step at high common input voltage (0.9 x V <sub>DDA</sub> )	-	-	1	1.35	- mV	

Table 86. OPAMP characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Cor	nditions	Min	Тур	Max	Unit
	Di	Normal mode	V > 0.V	-	-	500	
I <sub>LOAD</sub>	Drive current	Low-power mode	- V <sub>DDA</sub> ≥ 2 V	-	-	100	
	Drive current in	Normal mode	V > 0.V	-	-	450	μA
I <sub>LOAD_PGA</sub>	PGA mode	Low-power mode	- V <sub>DDA</sub> ≥ 2 V	-	-	50	
В.	Resistive load (connected to	Normal mode	V <2V	4	-	-	
$R_LOAD$	VSSA or to VDDA)	Low-power mode	- V <sub>DDA</sub> < 2 V	20	-	-	
D	Resistive load in PGA mode	Normal mode	V	4.5	-	-	kΩ
R <sub>LOAD_PGA</sub>	(connected to VSSA or to V <sub>DDA</sub> )	Low-power mode	- V <sub>DDA</sub> < 2 V	40	-	-	
C <sub>LOAD</sub>	Capacitive load	-		-	-	50	pF
CMRR	Common mode	Normal mode		-	-85	-	dB
OWINI	rejection ratio	Low-power mode		-	-90	-	ub
PSRR	Power supply	Normal mode	$C_{LOAD} \le 50 \text{ pf},$ $R_{LOAD} \ge 4 \text{ k}\Omega \text{ DC}$	70	85	-	dB
1 SIXIX	rejection ratio	Low-power mode	-power mode $C_{LOAD} \le 50 \text{ pf},$ $R_{LOAD} \ge 20 \text{ k}\Omega \text{ DC}$	72	90	-	u.b
		Normal mode	V <sub>DDA</sub> ≥ 2.4 V	550	1600	2200	- kHz
GBW	Gain Bandwidth	Low-power mode	(OPA_RANGE = 1)	100	420	600	
GBW	Product	Normal mode	V <sub>DDA</sub> < 2.4 V	250	700	950	
		Low-power mode	(OPA_RANGE = 0)	40	180	280	
	Slew rate	Normal mode	- V <sub>DDA</sub> ≥ 2.4 V	-	700	-	
SR <sup>(2)</sup>	(from 10 and	Low-power mode	VDDA = 2.4 V	-	180	-	V/ms
SIX.	90% of output voltage)	Normal mode	V <24V	-	300	-	V/IIIS
	voitage)	Low-power mode	- V <sub>DDA</sub> < 2.4 V	-	80	-	
AO	Open loop gain	Normal mode		55	110	-	dB
AO	Open loop gain	Low-power mode		45	110	-	ub
V <sub>OHSAT</sub> <sup>(2)</sup>	High saturation	Normal mode	I <sub>load</sub> = max or R <sub>load</sub> =	V <sub>DDA</sub> - 100	-	-	
VOHSAT` /	voltage	Low-power mode	min Input at V <sub>DDA</sub> .	V <sub>DDA</sub> - 50	-	-	mV
V <sub>OLSAT</sub> <sup>(2)</sup>	Low saturation	Normal mode	I <sub>load</sub> = max or R <sub>load</sub> =	-	-	100	
VOLSAT` ′	voltage	Low-power mode	min Input at 0.	-	-	50	
	Phase margin	Normal mode		-	74	_	0
$\Phi_{m}$	Phase margin	Low-power mode		-	66	-	



Table 86. OPAMP characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	l	ditions	Min	Тур	Max	Unit
011		Normal mode		-	13	-	
GM	Gain margin	Low-power mode		-	20	-	- dB
	Wake up time	Normal mode	$C_{LOAD} \le 50 \text{ pf},$ $R_{LOAD} \ge 4 \text{ k}\Omega$ follower configuration	-	5	10	
t <sub>WAKEUP</sub>	from OFF state.	Low-power mode	$C_{LOAD} \le 50 \text{ pf},$ $R_{LOAD} \ge 20 \text{ k}\Omega$ follower configuration	-	10	30	- μs
		General purpose input (all packages except UFBGA132 and UFBGA169 only)		-	-	(3)	
	OPAMP input		T <sub>J</sub> ≤ 75 °C	-	-	1	
l <sub>bias</sub>	bias current	Dedicated input (UFBGA132 and	T <sub>J</sub> ≤ 85 °C	-	-	3	nA
		UFBGA169 only)	T <sub>J</sub> ≤ 105 °C	-	-	8	
			T <sub>J</sub> ≤ 125 °C	-	-	15	
				ı	2	-	
	Non inverting		_	-	4	-	
r c/ (gain	gain value			-	8	-	
				-	16	-	
		PGA Gain = 2		-	80/80	-	
	R2/R1 internal resistance	PGA Gain = 4		ı	120/ 40	-	kΩ/kΩ -
R <sub>network</sub>	values in PGA mode <sup>(4)</sup>	PGA Gain = 8		-	140/ 20	-	
		PGA Gain = 16		-	150/ 10	-	
Delta R	Resistance variation (R1 or R2)		-	-15	-	15	%
PGA gain error	PGA gain error		-	-1	-	1	%
		Gain = 2	-	-	GBW/ 2	-	
DO4 514	PGA bandwidth	Gain = 4	-	-	GBW/	-	— MHz
PGA BW	for different non inverting gain	Gain = 8	-	-	GBW/	-	
		Gain = 16	-	-	GBW/ 16	-	



Table 86. OPAMP characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Con	ditions	Min	Тур	Max	Unit
en Voltage nois density		Normal mode	at 1 kHz, Output loaded with 4 kΩ	-	500	-	
	Voltage noise	Low-power mode	at 1 kHz, Output loaded with 20 kΩ	-	600	-	nV/√Hz
	density	Normal mode	at 10 kHz, Output loaded with 4 kΩ	-	180	-	1107 1112
		Low-power mode	at 10 kHz, Output loaded with 20 kΩ	-	290	-	
I <sub>DDA</sub> (OPAMP) <sup>(2)</sup> OPAMP consumptio from V <sub>DDA</sub>		Normal mode	no Load, quiescent mode	-	120	260	
	· ·	Low-power mode		-	45	100	μΑ

- 1. Guaranteed by design, unless otherwise specified.
- 2. Guaranteed by characterization results.
- 3. Mostly I/O leakage, when used in analog mode. Refer to  $I_{lkg}$  parameter in Table 70: I/O static characteristics.
- 4. R2 is the internal resistance between OPAMP output and OPAMP inverting input. R1 is the internal resistance between OPAMP inverting input and ground. The PGA gain =1+R2/R1



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### 6.3.23 Temperature sensor characteristics

Table 87. TS characteristics

Symbol	Parameter	Min	Тур	Max	Unit
T <sub>L</sub> <sup>(1)</sup>	V <sub>TS</sub> linearity with temperature	-	±1	±2	°C
Avg_Slope <sup>(2)</sup>	Average slope	2.3	2.5	2.7	mV/°C
V <sub>30</sub>	Voltage at 30°C (±5 °C) <sup>(3)</sup>	0.742	0.76	0.785	V
t <sub>START</sub> (TS_BUF) <sup>(1)</sup>	Sensor Buffer Start-up time in continuous mode <sup>(4)</sup>	-	8	15	μs
t <sub>START</sub> (1)	Start-up time when entering in continuous mode <sup>(4)</sup>	-	70	120	μs
t <sub>S_temp</sub> <sup>(1)</sup>	ADC sampling time when reading the temperature	5	-	-	μs
I <sub>DD</sub> (TS) <sup>(1)</sup>	Temperature sensor consumption from $V_{DD}$ , when selected by ADC	-	4.7	7	μΑ

<sup>1.</sup> Guaranteed by design.

# 6.3.24 V<sub>BAT</sub> monitoring characteristics

Table 88. V<sub>BAT</sub> monitoring characteristics

Symbol	Parameter	Min	Тур	Max	Unit
R	Resistor bridge for V <sub>BAT</sub>	-	39	-	kΩ
Q	Ratio on V <sub>BAT</sub> measurement	-	3	-	-
Er <sup>(1)</sup>	Error on Q	-10	-	10	%
t <sub>S_vbat</sub> <sup>(1)</sup>	ADC sampling time when reading the VBAT	12	-	-	μs

<sup>1.</sup> Guaranteed by design.

Table 89. V<sub>BAT</sub> charging characteristics

DAI 0 0									
Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
R <sub>BC</sub> Battery charging resistor	,	VBRS = 0	-	5	-				
		VBRS = 1	-	1.5	-	kΩ			

<sup>2.</sup> Guaranteed by characterization results.

<sup>3.</sup> Measured at  $V_{DDA}$  = 3.0 V ±10 mV. The  $V_{30}$  ADC conversion result is stored in the TS\_CAL1 byte. Refer to *Table 8: Temperature sensor calibration values*.

<sup>4.</sup> Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

### 6.3.25 LCD controller characteristics

The devices embed a built-in step-up converter to provide a constant LCD reference voltage independently from the  $V_{DD}$  voltage. An external capacitor  $C_{\text{ext}}$  must be connected to the VLCD pin to decouple this converter.

Table 90. LCD controller characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{LCD}$	LCD external voltage		-	-	3.6	
V <sub>LCD0</sub>	LCD internal reference volta	ge 0	-	2.62	-	
V <sub>LCD1</sub>	LCD internal reference volta	ge 1	-	2.76	-	
V <sub>LCD2</sub>	LCD internal reference volta	ge 2	-	2.89	-	
V <sub>LCD3</sub>	LCD internal reference volta	ge 3	-	3.04	-	V
V <sub>LCD4</sub>	LCD internal reference volta	ge 4	-	3.19	-	
V <sub>LCD5</sub>	LCD internal reference volta	ge 5	-	3.32	-	
V <sub>LCD6</sub>	LCD internal reference volta	oltage 6		3.46	-	
V <sub>LCD7</sub>	LCD internal reference volta	internal reference voltage 7		3.62	-	
	C <sub>ext</sub> V <sub>LCD</sub> external capacitance	Buffer OFF (BUFEN=0 is LCD_CR register)	0.2	-	2	
Cext		Buffer ON (BUFEN=1 is LCD_CR register)	1	-	2	μF
(2)	Supply current from V <sub>DD</sub> at V <sub>DD</sub> = 2.2 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	3	-	
I <sub>LCD</sub> <sup>(2)</sup>	Supply current from V <sub>DD</sub> at V <sub>DD</sub> = 3.0 V	Buffer OFF (BUFEN=0 is LCD_CR register)	-	1.5	-	μA
		Buffer OFF (BUFFEN = 0, PON = 0)	-	0.5	-	
	Supply current from V <sub>LCD</sub>	Buffer ON (BUFFEN = 1, 1/2 Bias)	-	0.6	-	
I <sub>VLCD</sub>	(V <sub>LCD</sub> = 3 V)	Buffer ON (BUFFEN = 1, 1/3 Bias)	-	0.8	-	- μΑ
		Buffer ON (BUFFEN = 1, 1/4 Bias)	ī	1	-	
R <sub>HN</sub>	Total High Resistor value for Low drive resistive network			5.5	-	МΩ
R <sub>LN</sub>	Total Low Resistor value for	High drive resistive network	-	240	-	kΩ



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>44</sub>	Segment/Common highest level voltage		-	$V_{LCD}$	-	
V <sub>34</sub>	Segment/Common 3/4 level voltage		-	3/4 V <sub>LCD</sub>	-	
V <sub>23</sub>	Segment/Common 2/3 level voltage			2/3 V <sub>LCD</sub>	-	
V <sub>12</sub>	Segment/Common 1/2 level voltage			1/2 V <sub>LCD</sub>	ï	V
V <sub>13</sub>	Segment/Common 1/3 level voltage		-	1/3 V <sub>LCD</sub>	-	
V <sub>14</sub>	Segment/Common 1/4 level voltage		-	1/4 V <sub>LCD</sub>	ï	
V <sub>0</sub>	Segment/Common lowest le	vel voltage	-	0	-	

Table 90. LCD controller characteristics<sup>(1)</sup> (continued)

#### 6.3.26 DFSDM characteristics

Unless otherwise specified, the parameters given in *Table 91* for DFSDM are derived from tests performed under the ambient temperature, f<sub>APB2</sub> frequency and V<sub>DD</sub> supply voltage conditions summarized in *Table 22: General operating conditions*.

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x VDD

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (DFSDM1\_CKINy, DFSDM1\_DATINy, DFSDM1\_CKOUT for DFSDM).

Table 91.	DFSDM	characteristics <sup>(1)</sup>	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>DFSDMCLK</sub>	DFSDM clock	-	-	-	f <sub>SYSCLK</sub>	MHz
f <sub>CKIN</sub> (1/T <sub>CKIN</sub> )	Input clock frequency	SPI mode (SITP[1:0] = 01)	-	-	20 (f <sub>DFSDMCLK</sub> /4)	
f <sub>CKOUT</sub>	Output clock frequency	-	-	-	20	MHz
DuCy <sub>CKOUT</sub>	Output clock frequency duty cycle	-	45	50	55	%

<sup>1.</sup> Guaranteed by design.

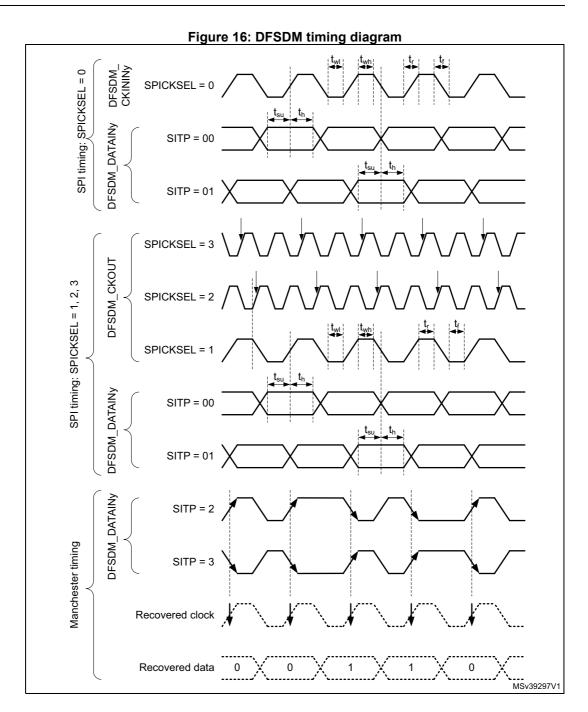
<sup>2.</sup> LCD enabled with 3 V internal step-up active, 1/8 duty, 1/4 bias, division ratio= 64, all pixels active, no LCD connected.

Table 91. DFSDM characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>wh(CKIN)</sub> t <sub>wl(CKIN)</sub>	Input clock high and low time	SPI mode (SITP[1:0] = 01), External clock mode (SPICKSEL[1:0] = 0)	T <sub>CKIN</sub> /2-0.5	T <sub>CKIN</sub> /2	-	
t <sub>su</sub>	Data input setup time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	2	-	-	
t <sub>h</sub>	Data input hold time	SPI mode (SITP[1:0]=01), External clock mode (SPICKSEL[1:0] = 0)	0	-	-	ns
T <sub>Manchester</sub>	Manchester data period (recovered clock period)	Manchester mode (SITP[1:0] = 10 or 11), Internal clock mode (SPICKSEL[1:0] ≠ 0)	(CKOUT DIV+1) x T <sub>DFSDMCLK</sub>	-	(2 x CKOUTDIV) x T <sub>DFSDMCLK</sub>	

<sup>1.</sup> Data based on characterization results, not tested in production.





### 6.3.27 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

ameter	Conditions	Min	Max
ution time	-	1	-
ation time	f <sub>TIMxCLK</sub> = 80 MHz	12.5	-

Table 92. TIMx<sup>(1)</sup> characteristics

Table 93. IWDG min/max timeout period at 32 kHz (LSI)<sup>(1)</sup>

Prescaler divider	PR[2:0] bits	Min timeout RL[11:0]= 0x000	Max timeout RL[11:0]= 0xFFF	Unit
/4	0	0.125	512	
/8	1	0.250	1024	
/16	2	0.500	2048	
/32	3	1.0	4096	ms
/64	4	2.0	8192	
/128	5	4.0	16384	
/256	6 or 7	8.0	32768	

The exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there
is always a full RC period of uncertainty.

Table 94. WWDG min/max timeout value at 80 MHz (PCLK)

Prescaler	WDGTB	Min timeout value	Max timeout value	Unit
1	0	0.0512	3.2768	
2	1	0.1024	6.5536	mo
4	2	0.2048	13.1072	ms
8	3	0.4096	26.2144	



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**Symbol** Para Unit t<sub>TIMxCLK</sub> Timer resolu t<sub>res(TIM)</sub> 0  $f_{TIMxCLK}/2$  $\mathsf{MHz}$ Timer external clock  $f_{EXT}$ frequency on CH1 to CH4  $f_{TIMxCLK}$  = 80 MHz 0 40 MHz TIMx (except TIM2 16 and TIM5) Timer resolution bit Res<sub>TIM</sub> TIM2 and TIM5 32 1 65536 t<sub>TIMxCLK</sub> 16-bit counter clock tCOUNTER period  $f_{TIMxCLK}$  = 80 MHz μs 0.0125 819.2 65536 × 65536 t<sub>TIMxCLK</sub> Maximum possible count t<sub>MAX\_COUNT</sub> with 32-bit counter  $f_{TIMxCLK}$  = 80 MHz 53.68 s

<sup>1.</sup> TIMx is used as a general term in which x stands for 1,2,3,4,5,6,7,8,15,16 or 17.

### 6.3.28 Communication interfaces characteristics

### I<sup>2</sup>C interface characteristics

The I2C interface meets the timings requirements of the I<sup>2</sup>C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I2C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0351 reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V<sub>DDIOx</sub> is disabled, but is still present. Only FT\_f I/O pins support Fm+ low level output current maximum requirement. Refer to Section 6.3.14: I/O port characteristics for the I2C I/Os characteristics.

All I2C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 95. I2C analog filter characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>AF</sub>	Maximum pulse width of spikes that are suppressed by the analog filter	50 <sup>(2)</sup>	260 <sup>(3)</sup>	ns

- 1. Guaranteed by design.
- 2. Spikes with widths below  $t_{\text{AF}(\text{min})}$  are filtered.
- 3. Spikes with widths above  $t_{\text{AF}(\text{max})}$  are not filtered

### **SPI** characteristics

Unless otherwise specified, the parameters given in *Table 96* for SPI are derived from tests performed under the ambient temperature, f<sub>PCLKx</sub> frequency and supply voltage conditions summarized in *Table 22: General operating conditions*.

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 96. SPI characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode receiver/full duplex 2.7 V < V <sub>DD</sub> < 3.6 V Voltage Range 1			40	
		Master mode receiver/full duplex 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 1			16	
		Master mode transmitter 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 1			40	
f <sub>SCK</sub> 1/t <sub>c(SCK)</sub>	SPI clock frequency	Slave mode receiver 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 1	-	-	40	MHz
		Slave mode transmitter/full duplex 2.7 V < V <sub>DD</sub> < 3.6 V Voltage Range 1			31 <sup>(2)</sup>	
		Slave mode transmitter/full duplex 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 1			18.5 <sup>(2)</sup>	
		Voltage Range 2			13	
		1.08 V < V <sub>DDIO2</sub> < 1.32 V <sup>(3)</sup>			8	
t <sub>su(NSS)</sub>	NSS setup time	Slave mode, SPI prescaler = 2	4 <sub>x</sub> T <sub>PCLK</sub>	-	-	ns
t <sub>h(NSS)</sub>	NSS hold time	Slave mode, SPI prescaler = 2	2 <sub>x</sub> T <sub>PCLK</sub>	-	-	ns
$\begin{matrix} t_{\text{w(SCKH)}} \\ t_{\text{w(SCKL)}} \end{matrix}$	SCK high and low time	Master mode	T <sub>PCLK</sub> -2	T <sub>PCLK</sub>	T <sub>PCLK</sub> +2	ns
t <sub>su(MI)</sub>	Data input setup time	Master mode	1	ı	-	ns
t <sub>su(SI)</sub>	Data input setup time	Slave mode	1.5	-	-	115
t <sub>h(MI)</sub>	Data input hold time	Master mode	5	-	-	ns
t <sub>h(SI)</sub>	Data input noid time	Slave mode	1.5	-	-	113
t <sub>a(SO)</sub>	Data output access time	Slave mode	9	-	34	ns
t <sub>dis(SO)</sub>	Data output disable time	Slave mode	9	-	16	ns



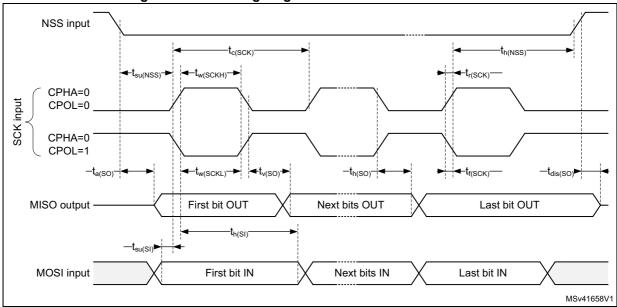
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Table 96.	SPI characteristics <sup>(1)</sup>	(continued)
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Slave mode 2.7 V < V <sub>DD</sub> < 3.6 V Voltage Range 1	-	13	15.5	
t <sub>v(SO)</sub>	Data output valid time	Slave mode 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 1	-	13	26.5	
		Slave mode 1.71 V < V <sub>DD</sub> < 3.6 V Voltage Range 2	-	13	30	ns
-		Slave mode 1.08 V < V <sub>DDIO2</sub> < 1.32 V <sup>(3)</sup>	-	26	60	
t <sub>v(MO)</sub>		Master mode	-	4.5	6	
t <sub>h(SO)</sub>	Data output hold time	Slave mode 1.71 V < V <sub>DD</sub> < 3.6 V	7	-	-	
t <sub>h(MO)</sub>	Data output Hold tillle	Master mode	0	-	-	

- 1. Guaranteed by characterization results.
- Maximum frequency in Slave transmitter mode is determined by the sum of t<sub>v(SO)</sub> and t<sub>su(MI)</sub> which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having t<sub>su(MI)</sub> = 0 while Duty(SCK) = 50 %.
- 3. SPI mapped on Port G.

Figure 38. SPI timing diagram - slave mode and CPHA = 0



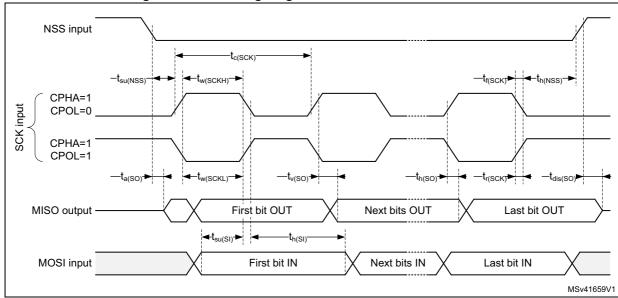


Figure 39. SPI timing diagram - slave mode and CPHA = 1

1. Measurement points are done at CMOS levels: 0.3  $\rm V_{DD}$  and 0.7  $\rm V_{DD}$ .

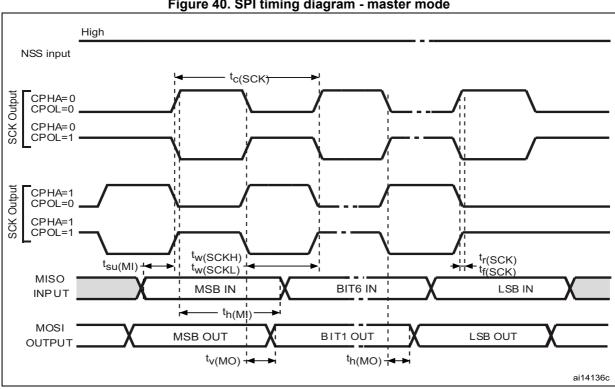


Figure 40. SPI timing diagram - master mode

1. Measurement points are done at CMOS levels: 0.3  $\rm V_{DD}$  and 0.7  $\rm V_{DD}$ .

#### **Quad SPI characteristics**

Unless otherwise specified, the parameters given in *Table 97* and *Table 98* for Quad SPI are derived from tests performed under the ambient temperature, f<sub>AHB</sub> frequency and V<sub>DD</sub> supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 15 or 20 pF
- Measurement points are done at CMOS levels: 0.5 x V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics.

Table 97. Quad SPI characteristics in SDR mode<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		1.71 V < V <sub>DD</sub> < 3.6 V, C <sub>LOAD</sub> = 20 pF Voltage Range 1	-	-	40	
F <sub>CK</sub>	Quad SPI clock	1.71 V < V <sub>DD</sub> < 3.6 V, C <sub>LOAD</sub> = 15 pF Voltage Range 1	-	-	48	MHz
1/t <sub>(CK)</sub>	frequency	2.7 V < V <sub>DD</sub> < 3.6 V, C <sub>LOAD</sub> = 15 pF Voltage Range 1	-	-	60	IVII IZ
		1.71 V < V <sub>DD</sub> < 3.6 V C <sub>LOAD</sub> = 20 pF Voltage Range 2	-	-	26	
t <sub>w(CKH)</sub>	Quad SPI clock high and	f <sub>AHBCLK</sub> = 48 MHz, presc=0	t <sub>(CK)</sub> /2 t <sub>(CK)</sub> /2-1	-	t <sub>(CK)</sub> /2+1	
t <sub>w(CKL)</sub>	low time	IAHBCLK 40 MI 12, presc-0		-	t <sub>(CK)</sub> /2	
t	Data input setup time	Voltage Range 1	1.5	-	-	
t <sub>s(IN)</sub>	Data input setup time	Voltage Range 2	3.5	-	-	
t	Data input hold time	Voltage Range 1	4	-	-	ns
t <sub>h(IN)</sub>	Data input noid time	Voltage Range 2	6.5	-	-	113
	Data output valid time	Voltage Range 1	-	1	1.5	
t <sub>v(OUT)</sub> Da	Data output valid time	Voltage Range 2	-	3	5	
+	Data output hold time	Voltage Range 1	0	-	-	
t <sub>h(OUT)</sub>	Data output hold time	Voltage Range 2	0	-	-	

<sup>1.</sup> Guaranteed by characterization results.

Table 98. QUADSPI characteristics in DDR mode<sup>(1)</sup>

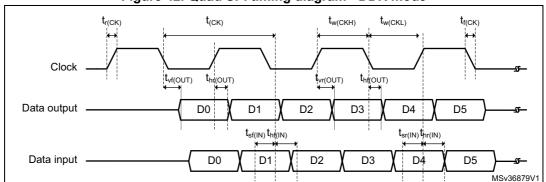
Symbol	Parameter	Conditio	ns	Min	Тур	Max	Unit	
		1.71 V < V <sub>DD</sub> < 3.6 C <sub>LOAD</sub> = 20 pF Voltage Range 1	5 <b>∨</b> ,	-	-	40		
F <sub>CK</sub>	Quad SPI clock	$2 \text{ V} < \text{V}_{\text{DD}} < 3.6 \text{ V}, \\ \text{C}_{\text{LOAD}} = 20 \text{ pF} \\ \text{Voltage Range 1}$		-	-	48	MHz	
1/t <sub>(CK)</sub>	frequency	1.71 V < V <sub>DD</sub> < 3.6 C <sub>LOAD</sub> = 15 pF Voltage Range 1	∂V,	-	-	48	IVITZ	
		1.71 V < V <sub>DD</sub> < 3.6 C <sub>LOAD</sub> = 20 pF Voltage Range 2	3 V	-	-	26		
t <sub>w(CKH)</sub>	Quad SPI clock high	f = 40 MHz	f <sub>AHBCLK</sub> = 48 MHz, presc= 1			t <sub>(CK)</sub> /2+1		
t <sub>w(CKL)</sub>	and low time	IAHBCLK = 46 IVITIZ,				t <sub>(CK)</sub> /2		
$t_{sf(IN)};t_{sr(IN)}$	Data input setup time	Voltage Dange 1 a	3.5	-	-			
t <sub>hf(IN)</sub> ; t <sub>hr(IN)</sub>	Data input hold time	Voltage Range 1 and 2		6.5	-	-		
		Voltage Range 1	DHHC = 0		4.5	5.5		
$t_{\text{vr}(\text{OUT})}$	Data output valid time on rise edge	Voltage Range 1	DHHC = 1	-	t <sub>(CK)</sub> /2+1	t <sub>(CK)</sub> /2+1.5		
	oco ougo	Voltage Range 2			9.5	14		
	_	Voltage Range 1	DHHC = 0		5	6	no	
$t_{\text{vf}(\text{OUT})}$	Data output valid time on falling edge	Voltage Range 1	DHHC = 1	-	t <sub>(CK)</sub> /2+1	t <sub>(CK)</sub> /2+1.5	ns	
	on isiming dage	Voltage Range 2			15	18		
		DHHC = 0	4	-	-			
$t_{hr(OUT)}$	Data output hold time on rise edge	Voltage Range 1	DHHC = 1	t <sub>(CK)</sub> /2+0.5	-	-		
	oco ougo	Voltage Range 2		8	-	-		
		Voltage Range 1	DHHC = 0	3.5	-	-		
$t_{hf(OUT)}$	Data output hold time on falling edge	voltage Ralige I	DHHC = 1	t <sub>(CK)</sub> /2+0.5	-	-		
		Voltage Range 2		13		-		

<sup>1.</sup> Guaranteed by characterization results.

 $t_{(\mathsf{CK})}$  $t_{\text{w}(\text{CKH})}$  $t_{\text{w}(\text{CKL})}$  $t_{\text{f(CK)}}$ Clock t<sub>v(OUT)</sub>  $\overset{t_{h(OUT)}}{\longleftrightarrow}$ Data output D0 D1 D2  $t_{\text{s}(\text{IN})}$  $t_{h(IN)} \\$ Data input D0 D1 D2 MSv36878V1

Figure 41. Quad SPI timing diagram - SDR mode





#### **SAI** characteristics

Unless otherwise specified, the parameters given in *Table 99* for SAI are derived from tests performed under the ambient temperature, f<sub>PCLKx</sub> frequency and V<sub>DD</sub> supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 99. SAI characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Max	Unit
f <sub>MCLK</sub>	SAI Main clock output	-	-	50	MHz
		Master transmitter 2.7 V ≤ V <sub>DD</sub> ≤ 3.6 V Voltage Range 1	-	21.5	
		Master transmitter 1.71 V ≤ V <sub>DD</sub> ≤ 3.6 V Voltage Range 1	-	13.5	
		Master receiver Voltage Range 1	-	25	
fск	SAI clock frequency <sup>(2)</sup>	Slave transmitter 2.7 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V Voltage Range 1	-	20	MHz
		Slave transmitter 1.71 V ≤ V <sub>DD</sub> ≤ 3.6 V Voltage Range 1	-	13.5	
		Slave receiver Voltage Range 1	-	25	
		Voltage Range 2	-	13	
		1.08 V ≤ V <sub>DD</sub> ≤ 1.32 V	-	7	
4	FS valid time	Master mode 2.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	22	ns
t <sub>v(FS)</sub>	rs valid time	Master mode 1.71 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	40	115
t <sub>h(FS)</sub>	FS hold time	Master mode	10	-	ns
t <sub>su(FS)</sub>	FS setup time	Slave mode	1	-	ns
t <sub>h(FS)</sub>	FS hold time	Slave mode	2	-	ns
t <sub>su(SD_A_MR)</sub>	Data input setup time	Master receiver	1	-	ns
t <sub>su(SD_B_SR)</sub>	Data iriput setup tillie	Slave receiver	1	-	113
t <sub>h(SD_A_MR)</sub>	Data input hold time	Master receiver	5	-	ns
t <sub>h(SD_B_SR)</sub>	Data input noid time	Slave receiver	2	-	113



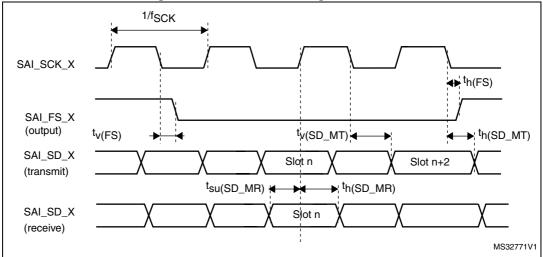
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Table 99. SAI characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
		Slave transmitter (after enable edge) 2.7 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	25	
t <sub>v(SD_B_ST)</sub>	Data output valid time	Slave transmitter (after enable edge) 1.71 V ≤ V <sub>DD</sub> ≤ 3.6 V	-	36	ns
		Slave transmitter (after enable edge) 1.8 V < V <sub>DD</sub> <1.32 V	-	68	
t <sub>h(SD_B_ST)</sub>	Data output hold time	Slave transmitter (after enable edge)	10	-	ns
4	Data output valid time	Master transmitter (after enable edge) 2.7 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	23	
<sup>t</sup> v(SD_A_MT)		Master transmitter (after enable edge) 1.71 V $\leq$ V <sub>DD</sub> $\leq$ 3.6 V	-	35	ns
		Master transmitter (after enable edge) 1.08 V $\leq$ V <sub>DD</sub> $\leq$ 1.32 V	-	70	
t <sub>h(SD_A_MT)</sub>	Data output hold time	Master transmitter (after enable edge)	10	-	ns

- 1. Guaranteed by characterization results.
- 2. APB clock frequency must be at least twice SAI clock frequency.

Figure 43. SAI master timing waveforms



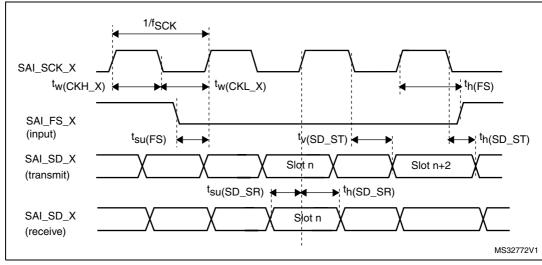


Figure 44. SAI slave timing waveforms

### **SDMMC** characteristics

Unless otherwise specified, the parameters given in *Table 100* for SDIO are derived from tests performed under the ambient temperature, f<sub>PCLKx</sub> frequency and V<sub>DD</sub> supply voltage conditions summarized in *Table 22: General operating conditions*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5 x V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output characteristics.

Table 100. SD / MMC dynamic characteristics,  $V_{DD}$ =2.7 V to 3.6  $V^{(1)}$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PP</sub>	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	4/3	-
t <sub>W(CKL)</sub>	Clock low time	f <sub>PP</sub> = 50 MHz	8	10	-	ns
t <sub>W(CKH)</sub>	Clock high time	f <sub>PP</sub> = 50 MHz	8	10	-	ns
CMD, D input	ts (referenced to CK) in MMC and SD H	S mode				
t <sub>ISU</sub>	Input setup time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns
t <sub>IH</sub>	Input hold time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns
CMD, D outp	uts (referenced to CK) in MMC and SD	HS mode				
t <sub>OV</sub>	Output valid time HS	f <sub>PP</sub> = 50 MHz	-	12	13	ns
t <sub>OH</sub>	Output hold time HS	f <sub>PP</sub> = 50 MHz	10	-	-	ns
CMD, D inpu	ts (referenced to CK) in SD default mod	de				
t <sub>ISUD</sub>	Input setup time SD	f <sub>PP</sub> = 25 MHz	3.5	-	-	ns
t <sub>IHD</sub>	Input hold time SD	f <sub>PP</sub> = 25 MHz	3.5	-	-	ns



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Table 100. SD / MMC dynamic characteristics,  $V_{DD}$ =2.7 V to 3.6  $V^{(1)}$  (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
CMD, D outputs (referenced to CK) in SD default mode						
t <sub>OVD</sub>	Output valid default time SD	f <sub>PP</sub> = 25 MHz	-	3	5	ns
t <sub>OHD</sub>	Output hold default time SD	f <sub>PP</sub> = 25 MHz	0	-	-	ns

<sup>1.</sup> Guaranteed by characterization results.

Table 101. eMMC dynamic characteristics,  $V_{DD}$  = 1.71 V to 1.9  $V^{(1)(2)}$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>PP</sub>	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/f <sub>PCLK2</sub> frequency ratio	-	-	-	4/3	-
t <sub>W(CKL)</sub>	Clock low time	f <sub>PP</sub> = 50 MHz	8	10	-	ns
t <sub>W(CKH)</sub>	Clock high time	f <sub>PP</sub> = 50 MHz	8	10	-	ns
CMD, D input	ts (referenced to CK) in eMMC mode					
t <sub>ISU</sub>	Input setup time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns
t <sub>IH</sub>	Input hold time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns
CMD, D outp	uts (referenced to CK) in eMMC mode					
t <sub>OV</sub>	Output valid time HS	f <sub>PP</sub> = 50 MHz	-	13.5	16.5	ns
t <sub>OH</sub>	Output hold time HS	f <sub>PP</sub> = 50 MHz	9	-	-	ns

<sup>1.</sup> Guaranteed by characterization results.

Figure 45. SDIO high-speed mode

CK

D, CMD
(output)

D, CMD
(input)

D, CMD
(input)

D, CMD
(input)

D, CMD
(input)

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<sup>2.</sup>  $C_{LOAD} = 20pF$ .

Figure 46. SD default mode

### **USB OTG full speed (FS) characteristics**

The STM32L4A6xG USB interface is fully compliant with the USB specification version 2.0 and is USB-IF certified (for Full-speed device operation).

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
V <sub>DDUSB</sub>	USB OTG full speed transceiver operating voltage	-	3.0 <sup>(2)</sup>	-	3.6	V
V <sub>DI</sub> <sup>(3)</sup>	Differential input sensitivity	Over VCM range	0.2	-	-	
V <sub>CM</sub> <sup>(3)</sup>	Differential input common mode range	Includes V <sub>DI</sub> range	0.8	-	2.5	V
V <sub>SE</sub> <sup>(3)</sup>	Single ended receiver input threshold	-	0.8	-	2.0	
V <sub>OL</sub>	Static output level low	$R_L$ of 1.5 k $\Omega$ to 3.6 $V^{(4)}$	-	-	0.3	V
V <sub>OH</sub>	Static output level high	$R_L$ of 15 kΩ to $V_{SS}^{(4)}$	2.8	-	3.6	V
R <sub>PD</sub> <sup>(3)</sup>	Pull down resistor on PA11, PA12 (USB_FS_DP/DM)	V <sub>IN</sub> = V <sub>DD</sub>	14.25	-	24.8	kΩ
	Pull Up Resistor on PA12 (USB_FS_DP)	V <sub>IN</sub> = V <sub>SS</sub> , during idle	0.9	1.25	1.575	kΩ
R <sub>PU</sub> <sup>(3)</sup>	Pull Up Resistor on PA12 (USB_FS_DP)	V <sub>IN</sub> = V <sub>SS</sub> during reception	1.425	2.25	3.09	kΩ
	Pull Up Resistor on PA10 (OTG_FS_ID)	-	-	-	14.5	kΩ

Table 102. USB OTG DC electrical characteristics

4.  $R_L$  is the load connected on the USB OTG full speed drivers.

Note:

When VBUS sensing feature is enabled, PA9 should be left at its default state (floating input), not as alternate function. A typical 200  $\mu$ A current consumption of the sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 when the feature is enabled.



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<sup>1.</sup> All the voltages are measured from the local ground potential.

<sup>2.</sup> The USB OTG full speed transceiver functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V  $V_{\rm DD}$  voltage range.

<sup>3.</sup> Guaranteed by design.

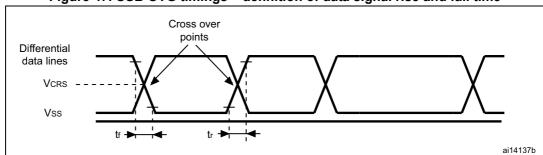


Figure 47. USB OTG timings – definition of data signal rise and fall time

Table 103. USB OTG electrical characteristics<sup>(1)</sup>

	Driver characteristics							
Symbol	Parameter	Conditions	Min	Max	Unit			
t <sub>rLS</sub>	Rise time in LS <sup>(2)</sup>	C <sub>L</sub> = 200 to 600 pF	75	300	ns			
t <sub>fLS</sub>	Fall time in LS <sup>(2)</sup>	C <sub>L</sub> = 200 to 600 pF	75	300	ns			
t <sub>rfmLS</sub>	Rise/ fall time matching in LS	t <sub>r</sub> /t <sub>f</sub>	80	125	%			
t <sub>rFS</sub>	Rise time in FS <sup>(2)</sup>	C <sub>L</sub> = 50 pF	4	20	ns			
t <sub>fFS</sub>	Fall time in FS <sup>(2)</sup>	C <sub>L</sub> = 50 pF	4	20	ns			
t <sub>rfmFS</sub>	Rise/ fall time matching in FS	t <sub>r</sub> /t <sub>f</sub>	90	111	%			
V <sub>CRS</sub>	Output signal crossover voltage (LS/FS)	-	1.3	2.0	V			
Z <sub>DRV</sub>	Output driver impedance <sup>(3)</sup>	Driving high or low	28	44	Ω			

<sup>1.</sup> Guaranteed by design.

Table 104. USB BCD DC electrical characteristics<sup>(1)</sup>

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
1	Primary detection mode consumption	-	-	-	300	μA
IDD(USBBCD)	Secondary detection mode consumption	-	-	-	300	μA
RDAT_LKG	Data line leakage resistance	-	300	-	-	kΩ
VDAT_LKG	Data line leakage voltage	-	0.0	-	3.6	V
RDCP_DAT	Dedicated charging port resistance across D+/D-	-	-	1	200	Ω
VLGC_HI	Logic high	-	2.0	-	3.6	٧
VLGC_LOW	Logic low	-	-	-	0.8	V
VLGC	Logic threshold	-	0.8		2.0	٧

Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

No external termination series resistors are required on DP (D+) and DM (D-) pins since the matching impedance is included in the embedded driver.

Table 104. USB BCD DC electrical characteristics<sup>(1)</sup> (continued)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
VDAT_REF	Data detect voltage	-	0.25	-	0.4	V
VDP_SRC	D+ source voltage	-	0.5	-	0.7	V
VDM_SRC	D- source voltage	-	0.5	-	0.7	V
IDP_SINK	D+ sink current	-	25	-	175	μA
IDM_SINK	D- sink current	-	25	-	175	μA

<sup>1.</sup> Guaranteed by design.

# CAN (controller area network) interface

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output alternate function characteristics (CAN\_TX and CAN\_RX).



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### 6.3.29 FSMC characteristics

Unless otherwise specified, the parameters given in *Table 105* to *Table 118* for the FMC interface are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 22*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output characteristics.

## Asynchronous waveforms and timings

Figure 48 through Figure 51 represent asynchronous waveforms and Table 105 through Table 112 provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode, DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0

In all timing tables, the THCLK is the HCLK clock period.



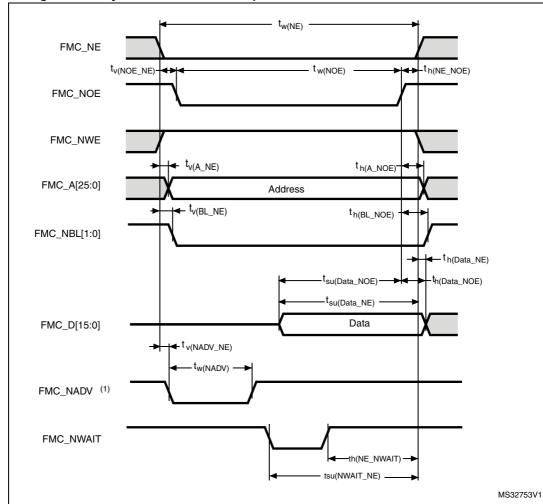


Figure 48. Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms

Table 105. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	2T <sub>HCLK</sub> -1	2T <sub>HCLK</sub> +1	
t <sub>v(NOE_NE)</sub>	FMC_NEx low to FMC_NOE low	0	0.5	
t <sub>w(NOE)</sub>	FMC_NOE low time	2T <sub>HCLK</sub> -1	2T <sub>HCLK</sub> +1	
t <sub>h(NE_NOE)</sub>	FMC_NOE high to FMC_NE high hold time	0	-	
t <sub>v(A_NE)</sub>	FMC_NEx low to FMC_A valid	-	0.5	
t <sub>h(A_NOE)</sub>	Address hold time after FMC_NOE high	0	-	
t <sub>v(BL_NE)</sub>	FMC_NEx low to FMC_BL valid	-	0.5	ns
t <sub>h(BL_NOE)</sub>	FMC_BL hold time after FMC_NOE high	0	-	115
t <sub>su(Data_NE)</sub>	Data to FMC_NEx high setup time	T <sub>HCLK</sub> -1	-	
t <sub>su(Data_NOE)</sub>	Data to FMC_NOEx high setup time	T <sub>HCLK</sub> -1	-	
t <sub>h(Data_NOE)</sub>	Data hold time after FMC_NOE high	0	-	
t <sub>h(Data_NE)</sub>	Data hold time after FMC_NEx high	0	-	
t <sub>v(NADV_NE)</sub>	FMC_NEx low to FMC_NADV low	-	0	
t <sub>w(NADV)</sub>	FMC_NADV low time	-	T <sub>HCLK</sub> +1	

<sup>1.</sup> CL = 30 pF.

Table 106. Asynchronous non-multiplexed SRAM/PSRAM/NOR read-NWAIT timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	7T <sub>HCLK</sub> -1	7T <sub>HCLK</sub> +1	
t <sub>w(NOE)</sub>	FMC_NWE low time	5T <sub>HCLK</sub> -1	5T <sub>HCLK</sub> +1	
t <sub>w(NWAIT)</sub>	FMC_NWAIT low time	T <sub>HCLK</sub> -0.5	-	ns
t <sub>su(NWAIT_NE)</sub>	FMC_NWAIT valid before FMC_NEx high	5T <sub>HCLK</sub> +1.5	-	
t <sub>h(NE_NWAIT)</sub>	FMC_NEx hold time after FMC_NWAIT invalid	4T <sub>HCLK</sub> +1	-	

<sup>1.</sup> CL = 30 pF.

<sup>2.</sup> Guaranteed by characterization results.

<sup>2.</sup> Guaranteed by characterization results.

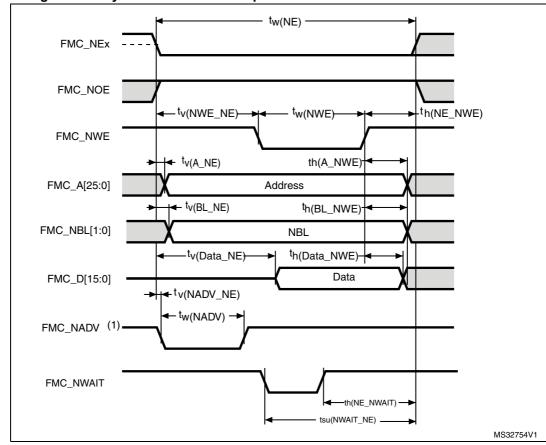


Figure 49. Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms

Table 107. Asynchronous non-multiplexed SRAM/PSRAM/NOR write timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	3T <sub>HCLK</sub> -1	3T <sub>HCLK</sub> +1	
t <sub>v(NWE_NE)</sub>	FMC_NEx low to FMC_NWE low	T <sub>HCLK</sub> -1	T <sub>HCLK</sub> +1	
t <sub>w(NWE)</sub>	FMC_NWE low time	T <sub>HCLK</sub> -1.5	T <sub>HCLK</sub> + 0.5	
t <sub>h(NE_NWE)</sub>	FMC_NWE high to FMC_NE high hold time	T <sub>HCLK</sub>	-	
t <sub>v(A_NE)</sub>	FMC_NEx low to FMC_A valid	-	0	
t <sub>h(A_NWE)</sub>	Address hold time after FMC_NWE high	T <sub>HCLK</sub> -0.5	-	ns
t <sub>v(BL_NE)</sub>	FMC_NEx low to FMC_BL valid	-	0.5	115
t <sub>h(BL_NWE)</sub>	FMC_BL hold time after FMC_NWE high	T <sub>HCLK</sub> -0.5	-	
t <sub>v(Data_NE)</sub>	Data to FMC_NEx low to Data valid	-	T <sub>HCLK</sub> +3	
t <sub>h(Data_NWE)</sub>	Data hold time after FMC_NWE high	T <sub>HCLK</sub> +0.5	-	
t <sub>v(NADV_NE)</sub>	FMC_NEx low to FMC_NADV low	-	0	
t <sub>w(NADV)</sub>	FMC_NADV low time	-	T <sub>HCLK</sub> +1	

<sup>1.</sup> CL = 30 pF.

<sup>2.</sup> Guaranteed by characterization results.

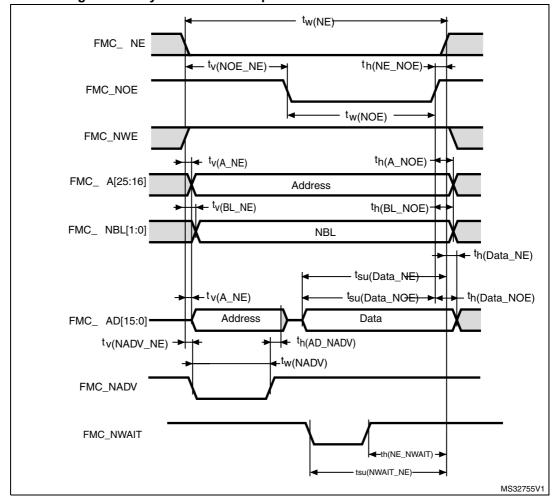


Table 108. Asynchronous non-multiplexed SRAM/PSRAM/NOR write-NWAIT timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	8T <sub>HCLK</sub> -1	8T <sub>HCLK</sub> +1	
t <sub>w(NWE)</sub>	FMC_NWE low time	6T <sub>HCLK</sub> -1.5	6T <sub>HCLK</sub> +0.5	ne
t <sub>su(NWAIT_NE)</sub>	FMC_NWAIT valid before FMC_NEx high	6T <sub>HCLK</sub> -1	-	ns
t <sub>h(NE_NWAIT)</sub>	FMC_NEx hold time after FMC_NWAIT invalid	4T <sub>HCLK</sub> +2	-	

<sup>1.</sup> CL = 30 pF.

Figure 50. Asynchronous multiplexed PSRAM/NOR read waveforms



<sup>2.</sup> Guaranteed by characterization results.

Table 109. Asynchronous multiplexed PSRAM/NOR read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	3T <sub>HCLK</sub> -1	3T <sub>HCLK</sub> +1	
t <sub>v(NOE_NE)</sub>	FMC_NEx low to FMC_NOE low	2T <sub>HCLK</sub>	2T <sub>HCLK</sub> +0.5	
t <sub>w(NOE)</sub>	FMC_NOE low time	T <sub>HCLK</sub> - 1	T <sub>HCLK</sub> +1	
t <sub>h(NE_NOE)</sub>	FMC_NOE high to FMC_NE high hold time	0	-	
t <sub>v(A_NE)</sub>	FMC_NEx low to FMC_A valid	-	0.5	
t <sub>v(NADV_NE)</sub>	FMC_NEx low to FMC_NADV low	0	0.5	
t <sub>w(NADV)</sub>	FMC_NADV low time	T <sub>HCLK</sub> - 0.5	T <sub>HCLK</sub> +1	
t <sub>h(AD_NADV)</sub>	FMC_AD(address) valid hold time after FMC_NADV high	T <sub>HCLK</sub> + 0.5	-	ns
t <sub>h(A_NOE)</sub>	Address hold time after FMC_NOE high	T <sub>HCLK</sub> - 0.5	-	
t <sub>h(BL_NOE)</sub>	FMC_BL time after FMC_NOE high	0	-	
t <sub>v(BL_NE)</sub>	FMC_NEx low to FMC_BL valid	-	0.5	
t <sub>su(Data_NE)</sub>	Data to FMC_NEx high setup time	T <sub>HCLK</sub> -1	-	
t <sub>su(Data_NOE)</sub>	Data to FMC_NOE high setup time	T <sub>HCLK</sub> -1	-	
t <sub>h(Data_NE)</sub>	Data hold time after FMC_NEx high	0	-	
t <sub>h(Data_NOE)</sub>	Data hold time after FMC_NOE high	0	-	

<sup>1.</sup> CL = 30 pF.

Table 110. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	8T <sub>HCLK</sub> + 1	8T <sub>HCLK</sub> + 1	
t <sub>w(NOE)</sub>	FMC_NWE low time	5T <sub>HCLK</sub> - 1.5	5T <sub>HCLK</sub> + 0.5	ns
t <sub>su(NWAIT_NE)</sub>	FMC_NWAIT valid before FMC_NEx high	5T <sub>HCLK</sub> +0.5	-	113
t <sub>h(NE_NWAIT)</sub>	FMC_NEx hold time after FMC_NWAIT invalid	4T <sub>HCLK</sub> +1	-	

<sup>1.</sup> CL = 30 pF.

<sup>2.</sup> Guaranteed by characterization results.

<sup>2.</sup> Guaranteed by characterization results.

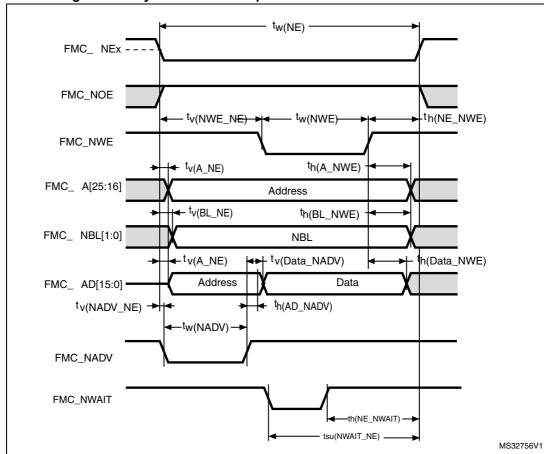


Figure 51. Asynchronous multiplexed PSRAM/NOR write waveforms

Table 111. Asynchronous multiplexed PSRAM/NOR write timings<sup>(1)(2)</sup>

			-	
Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	4T <sub>HCLK</sub> -1	4T <sub>HCLK</sub> +1	
t <sub>v(NWE_NE)</sub>	FMC_NEx low to FMC_NWE low	T <sub>HCLK</sub> -1	T <sub>HCLK</sub> +1	
t <sub>w(NWE)</sub>	FMC_NWE low time	2xT <sub>HCLK</sub> -0.5	2xT <sub>HCLK</sub> + 0.5	
t <sub>h(NE_NWE)</sub>	FMC_NWE high to FMC_NE high hold time	T <sub>HCLK</sub> -0.5	-	
t <sub>v(A_NE)</sub>	FMC_NEx low to FMC_A valid	-	0	
t <sub>v(NADV_NE)</sub>	FMC_NEx low to FMC_NADV low	0	0.5	
t <sub>w(NADV)</sub>	FMC_NADV low time	T <sub>HCLK</sub>	T <sub>HCLK</sub> +1	ns
t <sub>h(AD_NADV)</sub>	FMC_AD(adress) valid hold time after FMC_NADV high	T <sub>HCLK</sub> + 0.5	-	
t <sub>h(A_NWE)</sub>	Address hold time after FMC_NWE high	T <sub>HCLK</sub> + 0.5	-	
t <sub>h(BL_NWE)</sub>	FMC_BL hold time after FMC_NWE high	T <sub>HCLK</sub> - 0.5	-	
t <sub>v(BL_NE)</sub>	FMC_NEx low to FMC_BL valid	-	0.5	
t <sub>v(Data_NADV)</sub>	FMC_NADV high to Data valid	-	T <sub>HCLK</sub> +3	
t <sub>h(Data_NWE)</sub>	Data hold time after FMC_NWE high	T <sub>HCLK</sub> +0.5	-	

- 1. CL = 30 pF.
- 2. Guaranteed by characterization results.

Table 112. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(NE)</sub>	FMC_NE low time	9T <sub>HCLK</sub> - 1	9T <sub>HCLK</sub> + 1	
t <sub>w(NWE)</sub>	FMC_NWE low time	7T <sub>HCLK</sub> - 0.5	7T <sub>HCLK</sub> + 0.5	ns
t <sub>su(NWAIT_NE)</sub>	FMC_NWAIT valid before FMC_NEx high	6T <sub>HCLK</sub> + 2	-	
t <sub>h(NE_NWAIT)</sub>	FMC_NEx hold time after FMC_NWAIT invalid	4T <sub>HCLK</sub> - 1	-	

<sup>1.</sup> CL = 30 pF.

### Synchronous waveforms and timings

*Figure 52* through *Figure 55* represent synchronous waveforms and *Table 113* through *Table 116* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC\_BurstAccessMode\_Enable
- MemoryType = FMC\_MemoryType\_CRAM
- WriteBurst = FMC\_WriteBurst\_Enable
- CLKDivision = 1
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM In all timing tables, the T<sub>HCLK</sub> is the HCLK clock period.

<sup>2.</sup> Guaranteed by characterization results.

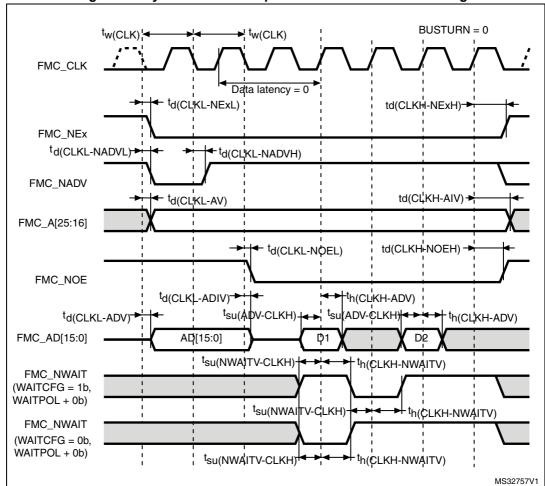


Figure 52. Synchronous multiplexed NOR/PSRAM read timings



Table 113. Synchronous multiplexed NOR/PSRAM read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FMC_CLK period	2T <sub>HCLK</sub> -0.5	-	
t <sub>d(CLKL-NExL)</sub>	FMC_CLK low to FMC_NEx low (x=02)	-	2	
t <sub>d(CLKH_NExH)</sub>	FMC_CLK high to FMC_NEx high (x= 02)	T <sub>HCLK</sub> +0.5	-	
t <sub>d(CLKL-NADVL)</sub>	FMC_CLK low to FMC_NADV low	-	1	
t <sub>d(CLKL-NADVH)</sub>	FMC_CLK low to FMC_NADV high	0	-	
t <sub>d(CLKL-AV)</sub>	FMC_CLK low to FMC_Ax valid (x=1625)	-	4.5	
t <sub>d(CLKH-AIV)</sub>	FMC_CLK high to FMC_Ax invalid (x=1625)	T <sub>HCLK</sub>	-	
t <sub>d(CLKL-NOEL)</sub>	FMC_CLK low to FMC_NOE low	-	1.5	ns
t <sub>d(CLKH-NOEH)</sub>	FMC_CLK high to FMC_NOE high	T <sub>HCLK</sub> +0.5	-	
t <sub>d(CLKL-ADV)</sub>	FMC_CLK low to FMC_AD[15:0] valid	-	3	
t <sub>d(CLKL-ADIV)</sub>	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
t <sub>su(ADV-CLKH)</sub>	FMC_A/D[15:0] valid data before FMC_CLK high	1	-	
t <sub>h(CLKH-ADV)</sub>	FMC_A/D[15:0] valid data after FMC_CLK high	3.5	-	
t <sub>su(NWAIT-CLKH)</sub>	FMC_NWAIT valid before FMC_CLK high	2	-	
t <sub>h(CLKH-NWAIT)</sub>	FMC_NWAIT valid after FMC_CLK high	3.5	-	

<sup>1.</sup> CL = 30 pF.

<sup>2.</sup> Guaranteed by characterization results.

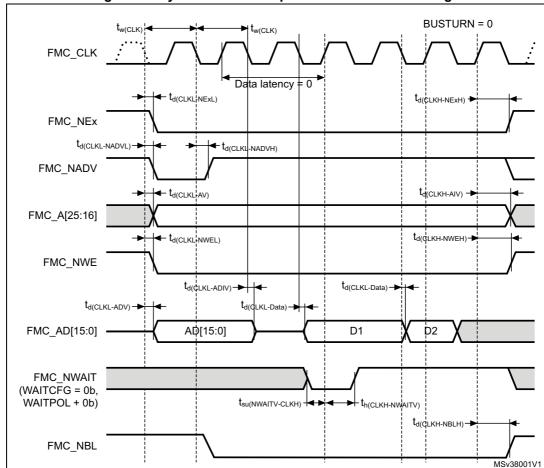


Figure 53. Synchronous multiplexed PSRAM write timings



Table 114. Synchronous multiplexed PSRAM write timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FMC_CLK period	2T <sub>HCLK</sub> - 0.5	-	
t <sub>d(CLKL-NExL)</sub>	FMC_CLK low to FMC_NEx low (x=02)	-	2	
t <sub>d(CLKH-NExH)</sub>	FMC_CLK high to FMC_NEx high (x= 02)	T <sub>HCLK</sub> + 0.5	-	
t <sub>d(CLKL-NADVL)</sub>	FMC_CLK low to FMC_NADV low	-	1	
t <sub>d(CLKL-NADVH)</sub>	FMC_CLK low to FMC_NADV high	0	-	
t <sub>d(CLKL-AV)</sub>	FMC_CLK low to FMC_Ax valid (x=1625)	-	4.5	
t <sub>d(CLKH-AIV)</sub>	FMC_CLK high to FMC_Ax invalid (x=1625)	T <sub>HCLK</sub>	-	
t <sub>d(CLKL-NWEL)</sub>	FMC_CLK low to FMC_NWE low	-	1.5	ns
t <sub>d(CLKH-NWEH)</sub>	FMC_CLK high to FMC_NWE high	T <sub>HCLK</sub> + 0.5	-	113
t <sub>d(CLKL-ADV)</sub>	FMC_CLK low to FMC_AD[15:0] valid	-	3	
t <sub>d(CLKL-ADIV)</sub>	FMC_CLK low to FMC_AD[15:0] invalid	0	-	
t <sub>d(CLKL-DATA)</sub>	FMC_A/D[15:0] valid data after FMC_CLK low	-	3.5	
t <sub>d(CLKL-NBLL)</sub>	FMC_CLK low to FMC_NBL low	-	2	
t <sub>d(CLKH-NBLH)</sub>	FMC_CLK high to FMC_NBL high	T <sub>HCLK</sub> + 0.5	-	
t <sub>su(NWAIT-CLKH)</sub>	FMC_NWAIT valid before FMC_CLK high	2	-	
t <sub>h(CLKH-NWAIT)</sub>	FMC_NWAIT valid after FMC_CLK high	3.5	-	

<sup>1.</sup> CL = 30 pF.

<sup>2.</sup> Guaranteed by characterization results.

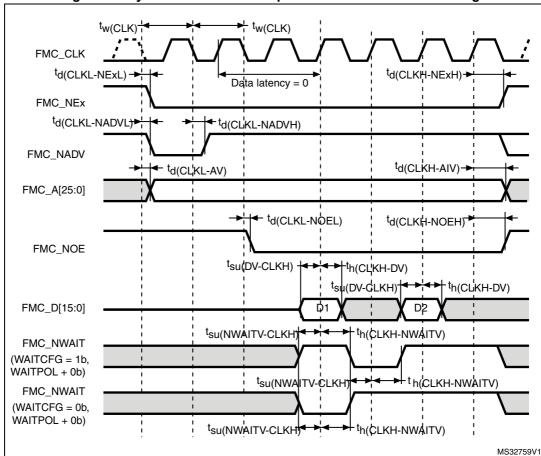


Figure 54. Synchronous non-multiplexed NOR/PSRAM read timings

Table 115. Synchronous non-multiplexed NOR/PSRAM read timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FMC_CLK period	2T <sub>HCLK</sub> - 0.5	-	
t <sub>d(CLKL-NExL)</sub>	FMC_CLK low to FMC_NEx low (x=02)	-	2	
t <sub>d(CLKH-NExH)</sub>	FMC_CLK high to FMC_NEx high (x= 02)	T <sub>HCLK</sub> +0.5	-	
t <sub>d(CLKL-NADVL)</sub>	FMC_CLK low to FMC_NADV low	-	0.5	
t <sub>d(CLKL-NADVH)</sub>	FMC_CLK low to FMC_NADV high	0	1	
t <sub>d(CLKL-AV)</sub>	FMC_CLK low to FMC_Ax valid (x=1625)	-	4	ns
t <sub>d(CLKH-AIV)</sub>	FMC_CLK high to FMC_Ax invalid (x=1625)	T <sub>HCLK</sub>	1	
t <sub>d(CLKL-NOEL)</sub>	FMC_CLK low to FMC_NOE low	-	1.5	
t <sub>d(CLKH-NOEH)</sub>	FMC_CLK high to FMC_NOE high	T <sub>HCLK</sub> -0.5	1	
t <sub>su(DV-CLKH)</sub>	FMC_D[15:0] valid data before FMC_CLK high	1	-	
t <sub>h(CLKH-DV)</sub>	FMC_D[15:0] valid data after FMC_CLK high	3.5	-	

Table 115. Synchronous non-multiplexed NOR/PSRAM read timings<sup>(1)(2)</sup> (continued)

Symbol	Parameter	Min	Max	Unit
t <sub>su(NWAIT-CLKH)</sub>	FMC_NWAIT valid before FMC_CLK high	2	-	ns
t <sub>h(CLKH-NWAIT)</sub>	FMC_NWAIT valid after FMC_CLK high	3.5	-	113

- 1. CL = 30 pF.
- 2. Guaranteed by characterization results.

Figure 55. Synchronous non-multiplexed PSRAM write timings

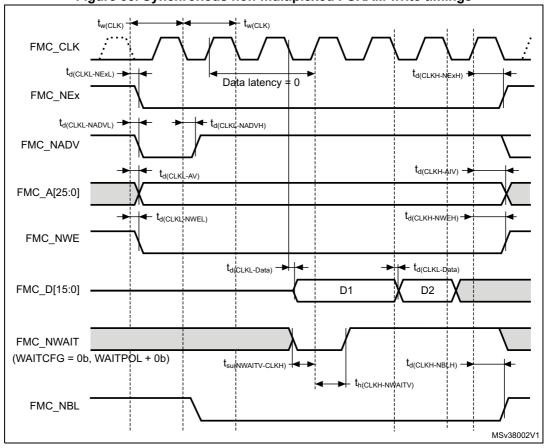


Table 116. Synchronous non-multiplexed PSRAM write timings<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
t <sub>w(CLK)</sub>	FMC_CLK period	2T <sub>HCLK</sub> -0.5	-	
t <sub>d(CLKL-NExL)</sub>	FMC_CLK low to FMC_NEx low (x=02)	-	2	
t <sub>d(CLKH-NExH)</sub>	FMC_CLK high to FMC_NEx high (x= 02)	T <sub>HCLK</sub> +0.5	ı	
t <sub>d(CLKL-NADVL)</sub>	FMC_CLK low to FMC_NADV low	-	0.5	
t <sub>d(CLKL-NADVH)</sub>	FMC_CLK low to FMC_NADV high	0	-	
t <sub>d(CLKL-AV)</sub>	FMC_CLK low to FMC_Ax valid (x=1625)	-	4	
t <sub>d(CLKH-AIV)</sub>	FMC_CLK high to FMC_Ax invalid (x=1625)	0	-	ns
t <sub>d(CLKL-NWEL)</sub>	FMC_CLK low to FMC_NWE low	-	1.5	113
t <sub>d(CLKH-NWEH)</sub>	FMC_CLK high to FMC_NWE high	T <sub>HCLK</sub> +1	-	
t <sub>d(CLKL-Data)</sub>	FMC_D[15:0] valid data after FMC_CLK low	-	3	
t <sub>d(CLKL-NBLL)</sub>	FMC_CLK low to FMC_NBL low	1.5	-	
t <sub>d(CLKH-NBLH)</sub>	FMC_CLK high to FMC_NBL high	T <sub>HCLK</sub> +0.5	-	
t <sub>su(NWAIT-CLKH)</sub>	FMC_NWAIT valid before FMC_CLK high	2	-	
t <sub>h(CLKH-NWAIT)</sub>	FMC_NWAIT valid after FMC_CLK high	3.5	-	

<sup>1.</sup> CL = 30 pF.

### NAND controller waveforms and timings

Figure 56 through Figure 59 represent synchronous waveforms, and Table 117 and Table 118 provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- COM.FMC\_SetupTime = 0x01
- COM.FMC\_WaitSetupTime = 0x03
- COM.FMC\_HoldSetupTime = 0x02
- COM.FMC\_HiZSetupTime = 0x01
- ATT.FMC\_SetupTime = 0x01
- ATT.FMC\_WaitSetupTime = 0x03
- ATT.FMC\_HoldSetupTime = 0x02
- ATT.FMC HiZSetupTime = 0x01
- Bank = FMC\_Bank\_NAND
- MemoryDataWidth = FMC\_MemoryDataWidth\_16b
- ECC = FMC ECC Enable
- ECCPageSize = FMC\_ECCPageSize\_512Bytes
- TCLRSetupTime = 0
- TARSetupTime = 0

In all timing tables, the T<sub>HCLK</sub> is the HCLK clock period.

<sup>2.</sup> Guaranteed by characterization results.

FMC\_NCEX

ALE (FMC\_A17)
CLE (FMC\_A16)

FMC\_NWE

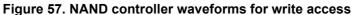
FMC\_NOE (NRE)

Th(NOE-ALE)

FMC\_D[15:0]

MSv38003V1

Figure 56. NAND controller waveforms for read access



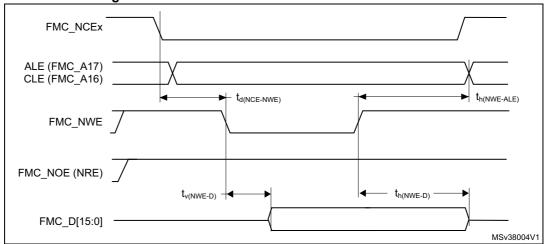


Figure 58. NAND controller waveforms for common memory read access



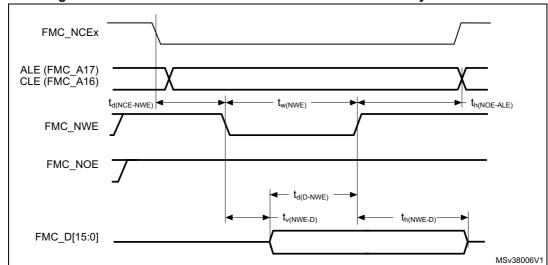


Figure 59. NAND controller waveforms for common memory write access

Table 117. Switching characteristics for NAND Flash read cycles<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
T <sub>w(N0E)</sub>	FMC_NOE low width	4T <sub>HCLK</sub> -0.5	4T <sub>HCLK</sub> +0.5	
T <sub>su(D-NOE)</sub>	FMC_D[15-0] valid data before FMC_NOE high	12	-	
T <sub>h(NOE-D)</sub>	FMC_D[15-0] valid data after FMC_NOE high	0	-	ns
T <sub>d(NCE-NOE)</sub>	FMC_NCE valid before FMC_NOE low	-	3T <sub>HCLK</sub> +1	
T <sub>h(NOE-ALE)</sub>	FMC_NOE high to FMC_ALE invalid	4T <sub>HCLK</sub> -2	-	

<sup>1.</sup> CL = 30 pF.

Table 118. Switching characteristics for NAND Flash write cycles<sup>(1)(2)</sup>

Symbol	Parameter	Min	Max	Unit
T <sub>w(NWE)</sub>	FMC_NWE low width	4T <sub>HCLK</sub> -0.5	4T <sub>HCLK</sub> +0.5	
$T_{v(NWE-D)}$	FMC_NWE low to FMC_D[15-0] valid	5	-	
T <sub>h(NWE-D)</sub>	FMC_NWE high to FMC_D[15-0] invalid	2T <sub>HCLK</sub> -1	-	ns
T <sub>d(D-NWE)</sub>	WE) FMC_D[15-0] valid before FMC_NWE high		-	115
T <sub>d(NCE_NWE)</sub>	FMC_NCE valid before FMC_NWE low	-	3T <sub>HCLK</sub> +1	
T <sub>h(NWE-ALE)</sub>	FMC_NWE high to FMC_ALE invalid	2T <sub>HCLK</sub> -2	-	

<sup>1.</sup> CL = 30 pF.

# 6.3.30 Camera interface (DCMI) timing specifications

Unless otherwise specified, the parameters given in *Table 119* for DCMI are derived from tests performed under the ambient temperature,  $f_{HCLK}$  frequency and  $V_{DD}$  supply voltage



<sup>2.</sup> Guaranteed by characterization results.

<sup>2.</sup> Guaranteed by characterization results.

summarized in *Table 21*, with the following configuration:

- DCMI\_PIXCLK polarity: falling
- DCMI\_VSYNC and DCMI\_HSYNC polarity: high
- Data format: 14 bits
- Capacitive load C=30pF

Figure 60. DCMI timing diagram

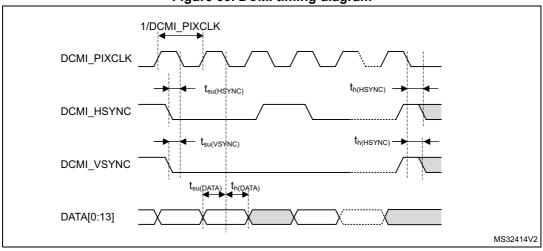


Table 119. DCMI characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
	Frequency ratio DCMI_PIXCLK/f <sub>HCLK</sub>	-	0.4	
DCMI_PIXCLK	DCMI_PIXCLK Pixel clock input		32	MHz
D <sub>pixel</sub>	Pixel clock input duty cycle	30	70	%
t <sub>su(DATA)</sub>	Data input setup time	4	-	
t <sub>h(DATA)</sub>	Data hold time	5	-	
t <sub>su(HSYNC)</sub> , t <sub>su(VSYNC)</sub>	DCMI_HSYNC/DCMI_VSYNC input setup time	3	-	ns
t <sub>h(HSYNC)</sub> , t <sub>h(VSYNC)</sub>	DCMI_HSYNC/DCMI_VSYNC input hold time	3	-	

<sup>1.</sup> Data based on characterization results, not tested in production.

### 6.3.31 SWPMI characteristics

The Single Wire Protocol Master Interface (SWPMI) and the associated SWPMI\_IO transceiver are compliant with the ETSI TS 102 613 technical specification.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>SWPSTART</sub>	SWPMI regulator startup time	SWP Class B 2.7 V ≤ V <sub>DD</sub> ≤ 3,3V	-	-	300	μs
t	SWP bit duration	V <sub>CORE</sub> voltage range 1	500	ı	ı	ns
<sup>L</sup> SWPBIT	SWP bit duration	V <sub>CORE</sub> voltage range 2	620	-	-	115

Table 120. SWPMI electrical characteristics

## 6.3.32 SD/SDIO MMC card host interface (SDIO) characteristics

Unless otherwise specified, the parameters given in *Table 121* for the SDIO/MMC interface are derived from tests performed under the ambient temperature,  $f_{PCLK2}$  frequency and  $V_{DD}$  supply voltage conditions summarized in *Table 22*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: 0.5V<sub>DD</sub>

Refer to Section 6.3.14: I/O port characteristics for more details on the input/output characteristics.

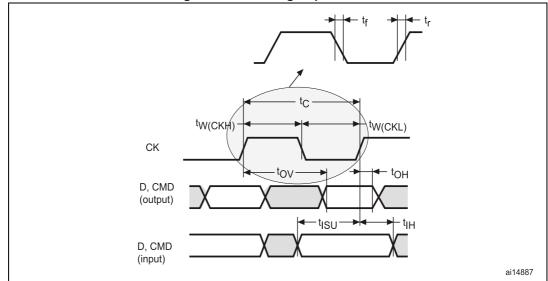


Figure 61. SDIO high-speed mode

CK +tovd **◆** tohd D, CMD (output) ai14888

Figure 62. SD default mode

Table 121. SD / MMC dynamic characteristics,  $V_{DD}$ =2.7 V to 3.6  $V^{(1)}$ 

Table 121. 3D / Willie dynamic characteristics, VDD-2.7 V to 3.6 V					
Parameter	Conditions	Min	Тур	Max	Unit
Clock frequency in data transfer mode		0		50	MHz
SDIO_CK/fPCLK2 frequency ratio		-	-	4/3	-
Clock low time	fpp =50 MHz	8	10	-	no
Clock high time	fpp =50 MHz	8	10	-	ns
outs (referenced to CK) in MMC and SI	) HS mode				
Input setup time HS	fpp =50 MHz	2.5	-	-	
Input hold time HS	fpp =50 MHz	2.5	-	-	ns
tputs (referenced to CK) in MMC and S	SD HS mode				
Output valid time HS	fpp =50 MHz	-	12	13	no
Output hold time HS	fpp =50 MHz	10	-	-	– ns
outs (referenced to CK) in SD default n	node				
Input setup time SD	fpp =25 MHz	3.5	-	-	
Input hold time SD	fpp =25 MHz	3	-	-	ns
tputs (referenced to CK) in SD default	mode	1			1
Output valid default time SD	fpp =25 MHz	-	3	5	
Output hold default time SD	fpp =25 MHz	0	-	-	ns
	Parameter  Clock frequency in data transfer mode  SDIO_CK/fPCLK2 frequency ratio  Clock low time  Clock high time  outs (referenced to CK) in MMC and SI  Input setup time HS  Input hold time HS  Output valid time HS  Output valid time HS  outs (referenced to CK) in SD default not setup time SD  Input hold time SD  Input hold time SD  Input hold time SD  Input yalid default time SD	Parameter Conditions  Clock frequency in data transfer mode  SDIO_CK/fPCLK2 frequency ratio  Clock low time fpp =50 MHz  Clock high time fpp =50 MHz  Outs (referenced to CK) in MMC and SD HS mode  Input setup time HS fpp =50 MHz  Input hold time HS fpp =50 MHz  Aputs (referenced to CK) in MMC and SD HS mode  Output valid time HS fpp =50 MHz  Output valid time HS fpp =50 MHz  Output hold time HS fpp =50 MHz  Output setup time SD fpp =25 MHz  Input hold time SD fpp =25 MHz  Aputs (referenced to CK) in SD default mode  Output valid default time SD fpp =25 MHz  Output valid default time SD fpp =25 MHz	Parameter Conditions Min  Clock frequency in data transfer mode 0  SDIO_CK/fPCLK2 frequency ratio -  Clock low time fpp =50 MHz 8  Clock high time fpp =50 MHz 8  Clock high time fpp =50 MHz 8  Input setup time HS fpp =50 MHz 2.5  Input hold time HS fpp =50 MHz 2.5  Input hold time HS fpp =50 MHz 2.5  Input hold time HS fpp =50 MHz 2.5  Input (referenced to CK) in MMC and SD HS mode  Output valid time HS fpp =50 MHz -  Output hold time HS fpp =50 MHz 10  Output hold time HS fpp =50 MHz 10  Outs (referenced to CK) in SD default mode  Input setup time SD fpp =25 MHz 3.5  Input hold time SD fpp =25 MHz 3  Input (referenced to CK) in SD default mode  Output valid default time SD fpp =25 MHz -	Parameter Conditions Min Typ  Clock frequency in data transfer mode 0  SDIO_CK/fPCLK2 frequency ratio  Clock low time fpp =50 MHz 8 10  Clock high time fpp =50 MHz 8 10  Clock high time fpp =50 MHz 8 10  Linputs (referenced to CK) in MMC and SD HS mode 10  Input setup time HS fpp =50 MHz 2.5 - 1  Input hold time HS fpp =50 MHz 2.5 - 1  Input setup time HS fpp =50 MHz 10  Cutput valid time HS fpp =50 MHz 10  Cutput valid time HS fpp =50 MHz 10  Cutput valid time HS fpp =50 MHz 10  Cutput hold time HS fpp =50 MHz 10  Cutput setup time SD fpp =25 MHz 10  Input setup time SD fpp =25 MHz 3.5 - 1  Input hold time SD fpp =25 MHz 3  Cutputs (referenced to CK) in SD default mode 10  Cutput valid default time SD fpp =25 MHz 3  Cutput valid default time SD fpp =25 MHz 3  Cutput valid default time SD fpp =25 MHz 3  Cutput valid default time SD fpp =25 MHz 3	Parameter   Conditions   Min   Typ   Max

<sup>1.</sup> Guaranteed by characterization results.

Table 122. SD / MMC dynamic characteristics,  $V_{DD}$ =1.71 V to 1.9  $V^{(1)}$ 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$f_{PP}$	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	4/3	-
t <sub>W(CKL)</sub>	Clock low time	f <sub>PP</sub> = 50 MHz	8	10	-	ns
t <sub>W(CKH)</sub>	Clock high time	f <sub>PP</sub> = 50 MHz	8	10	-	ns



Table 122. SD / MMC dynamic characteristics,  $V_{DD}$ =1.71 V to 1.9  $V^{(1)}$  (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
CMD, D inputs (referenced to CK) in MMC and SD HS mode										
t <sub>ISU</sub>	Input setup time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns				
t <sub>IH</sub>	Input hold time HS	f <sub>PP</sub> = 50 MHz	2.5	-	-	ns				
CMD, D outputs (referenced to CK) in MMC and SD HS mode										
t <sub>OV</sub>	Output valid time HS	f <sub>PP</sub> = 50 MHz	-	13.5	16.5	ns				
t <sub>OH</sub>	Output hold time HS	f <sub>PP</sub> = 50 MHz	9	-	-	ns				
CMD, D inputs (referenced to CK) in SD default mode										
t <sub>ISUD</sub>	Input setup time SD	f <sub>PP</sub> = 50 MHz	2	-	-	ns				
t <sub>IHD</sub>	Input hold time SD	f <sub>PP</sub> = 50 MHz	4.5	-	-	ns				
CMD, D outputs (referenced to CK) in SD default mode										
t <sub>OVD</sub>	Output valid default time SD	f <sub>PP</sub> = 50 MHz	-	4.5	5	ns				
t <sub>OHD</sub>	Output hold default time SD	f <sub>PP</sub> = 50 MHz	0	-	-	ns				

<sup>1.</sup> Guaranteed by characterization results.

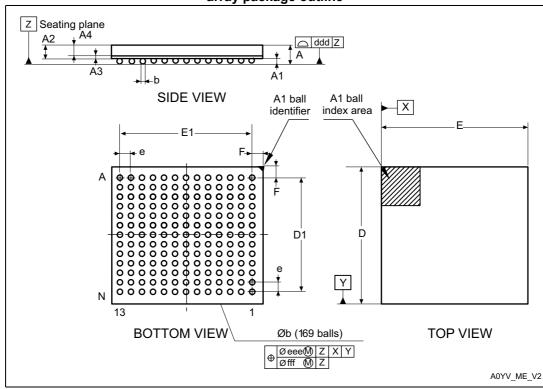
STM32L4A6xG Package information

## 7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>. ECOPACK<sup>®</sup> is an ST trademark.

### 7.1 UFBGA169 package information

Figure 63. UFBGA - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline



1. Drawing is not to scale.

Table 123. UFBGA - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
А3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146

Table 123. UFBGA - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data (continued)

	millimeters			inches <sup>(1)</sup>			
Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	
b	0.230	0.280	0.330	0.0091	0.0110	0.0130	
D	6.950	7.000	7.050	0.2736	0.2756	0.2776	
D1	5.950	6.000	6.050	0.2343	0.2362	0.2382	
E	6.950	7.000	7.050	0.2736	0.2756	0.2776	
E1	5.950	6.000	6.050	0.2343	0.2362	0.2382	
е	-	0.500	-	-	0.0197	-	
F	0.450	0.500	0.550	0.0177	0.0197	0.0217	
ddd	-	-	0.100	-	-	0.0039	
eee	-	-	0.150	-	-	0.0059	
fff		-	0.050	-	-	0.0020	

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 64. UFBGA - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array recommended footprint

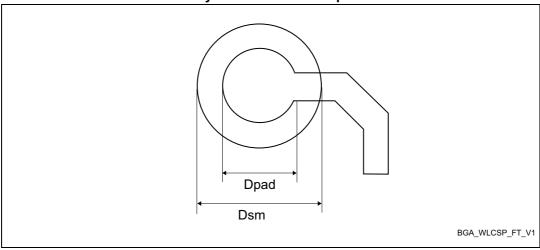


Table 124. UFBGA169 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values		
Pitch	0.5 mm		
Dpad	0.27 mm		
Dsm	0.35 mm typ. (depends on the soldermask registration tolerance)		
Solder paste	0.27 mm aperture diameter.		

Note: Non-solder mask defined (NSMD) pads are recommended.



Note: 4 to 6 mils solder paste screen printing process.

#### **Device marking**

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

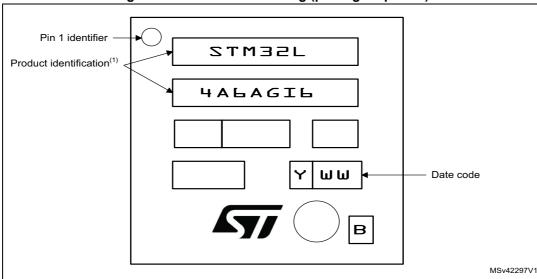


Figure 65. UFBGA169 marking (package top view)

1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

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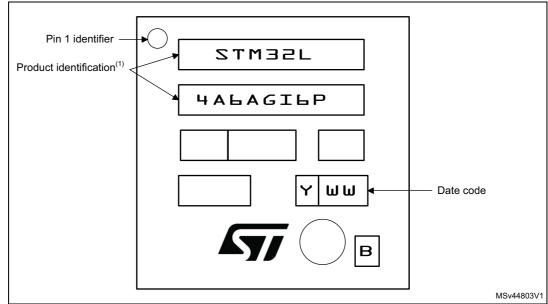


Figure 66. UFBGA169, external SMPS device, marking (package top view

1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.



## 7.2 LQFP144 package information

SEATING P<u>LAN</u>E С 0.25 mm □ ccc C GAUGE PLANE D D1 D3 109 E3 E1 37 PIN 1 **IDENTIFICATION** 1A\_ME\_V4

Figure 67. LQFP - 144-pin, 20 x 20 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 125. LQFP - 144-pin, 20 x 20 mm low-profile quad flat package mechanical data

Sumbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	21.800	22.000	22.200	0.8583	0.8661	0.8740
D1	19.800	20.000	20.200	0.7795	0.7874	0.7953
D3	-	17.500	-	-	0.6890	-
Е	21.800	22.000	22.200	0.8583	0.8661	0.8740
E1	19.800	20.000	20.200	0.7795	0.7874	0.7953
E3	-	17.500	-	-	0.6890	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

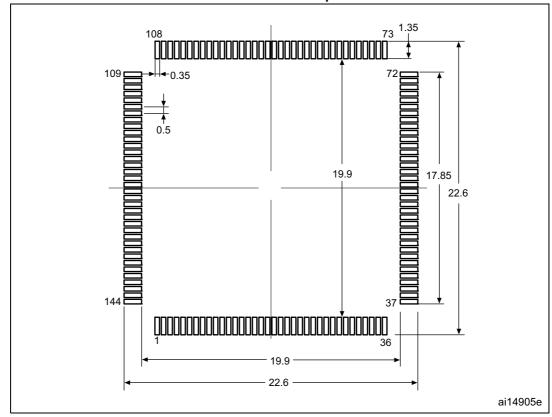


Figure 68. LQFP - 144-pin,20 x 20 mm low-profile quad flat package recommended footprint

1. Dimensions are expressed in millimeters.



#### **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

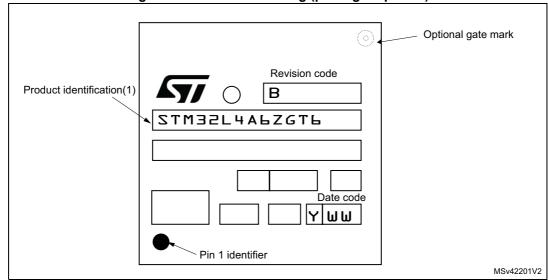


Figure 69. LQFP144 marking (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.



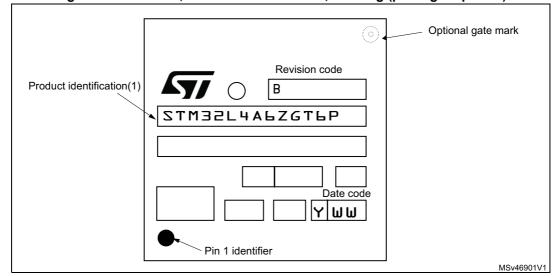


Figure 70. LQFP144, external SMPS device, marking (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.



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### 7.3 UFBGA132 package information

A1 ball identifier Ε **\$**00000000**\$** 000000000000 Ż 000000000000 000000000000 0000 0000 0,0 0000 0000 D1 D 0000 0000 0000 0000 000000000000 000000000000 <del>+</del>00000000000 <del>+</del>00000000000 . Øb (132 balls) **BOTTOM VIEW TOP VIEW** ⊕ Øeee® C A B Ø fff ® C A1 A **SEÀTING PLANE** UFBGA132\_A0G8\_ME\_V2

Figure 71. UFBGA - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package outline

1. Drawing is not to scale.

Table 126. UFBGA - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data

Cumbal	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	0.600	-	-	0.0236
A1	-	-	0.110	-	-	0.0043
A2	-	0.450	-	-	0.0177	-
A3	-	0.130	-	-	0.0051	-
A4	-	0.320	-	-	0.0126	-
b	0.240	0.290	0.340	0.0094	0.0114	0.0134
D	6.850	7.000	7.150	0.2697	0.2756	0.2815
D1	-	5.500	-	-	0.2165	-
Е	6.850	7.000	7.150	0.2697	0.2756	0.2815
E1	-	5.500	-	-	0.2165	-

STM32L4A6xG Package information

Table 126. UFBGA - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package mechanical data (continued)

Symbol	millimeters			inches <sup>(1)</sup>		
	Min	Тур	Max	Min	Тур	Max
е	-	0.500	-	-	0.0197	-
Z	-	0.750	-	-	0.0295	-
ddd	-	0.080	-	-	0.0031	-
eee	-	0.150	-	-	0.0059	-
fff	-	0.050	-	-	0.0020	-

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 72. UFBGA - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint

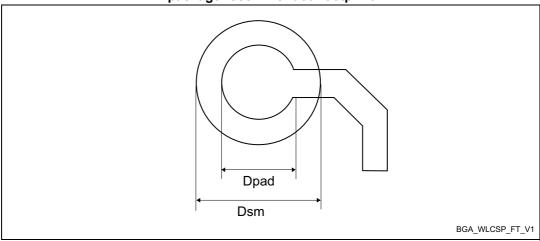


Table 127. UFBGA132 recommended PCB design rules (0.5 mm pitch BGA)

Dimension	Recommended values
Pitch	0.5 mm
Dpad	0.280 mm
Dsm	0.370 mm typ. (depends on the soldermask registration tolerance)
Stencil opening	0.280 mm
Stencil thickness	Between 0.100 mm and 0.125 mm
Pad trace width	0.100 mm
Ball diameter	0.280 mm

### **Device marking**

The following figure gives an example of topside marking orientation versus ball A1 identifier location.



> Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

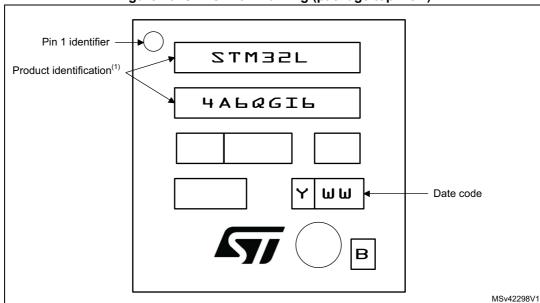


Figure 73. UFBGA132 marking (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

Pin 1 identifier STM32L Product identification<sup>(1)</sup> 4 A L Q G I L P  $\mathbf{W}$ Date code MS46970V1

Figure 74. UFBGA132, external SMPS device, marking (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.



## 7.4 LQFP100 package information

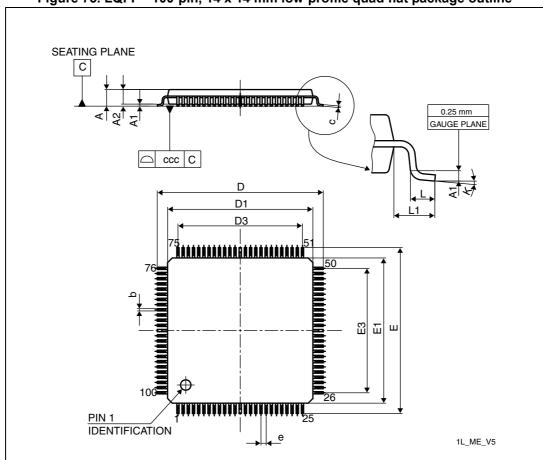


Figure 75. LQFP - 100-pin, 14 x 14 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 128. LQPF - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
Α	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
Е	15.800	16.000	16.200	0.6220	0.6299	0.6378

Symbol	millimeters			inches <sup>(1)</sup>					
	Min	Тур	Max	Min	Тур	Max			
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591			
E3	-	12.000	-	-	0.4724	-			
е	-	0.500	-	-	0.0197	-			
L	0.450	0.600	0.750	0.0177	0.0236	0.0295			
L1	-	1.000	-	-	0.0394	-			
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°			
ccc	_	-	0.080	-	-	0.0031			

Table 128. LQPF - 100-pin, 14 x 14 mm low-profile quad flat package mechanical data (continued)

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

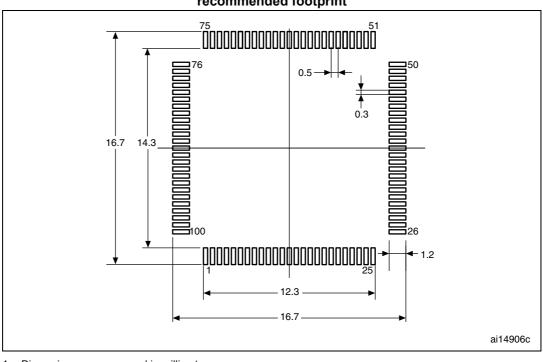


Figure 76. LQFP - 100-pin, 14 x 14 mm low-profile quad flat recommended footprint

1. Dimensions are expressed in millimeters.

#### **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

STM32L4A6xG Package information

Product identification<sup>(1)</sup>

STM32L4AL

Revision code

Pin 1
indentifier

Figure 77. LQFP100 marking (package top view)

1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.

Product identification<sup>(1)</sup>

STM32L4AL

Optional gate mark

Revision code

Yww

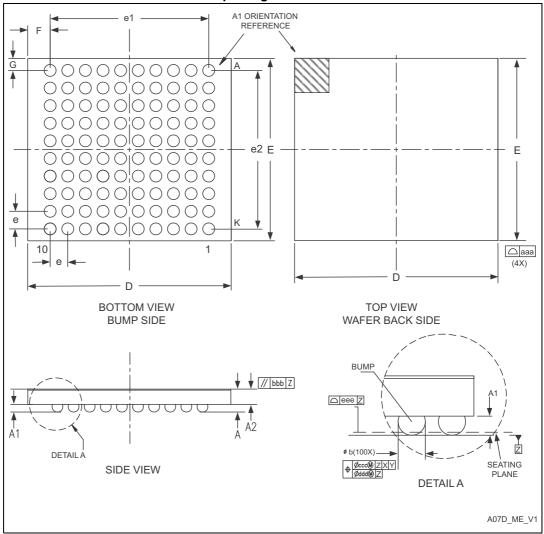
Pin 1
indentifier

Figure 78. LQFP100, external SMPS device, marking (package top view)

MS51416V1

### 7.5 WLCSP100 package information

Figure 79.WLCSP – 100 ball, 4.618 x 4.142 mm, 0.4 mm pitch wafer level chip scale package outline



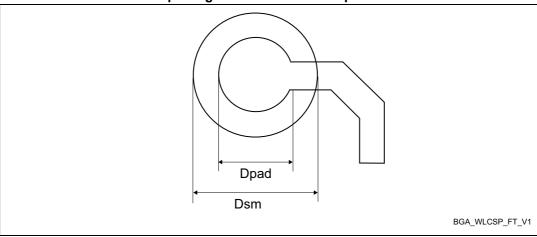
- 1. Drawing is not to scale.
- 2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.
- 3. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
- 4. Bump position designation per JESD 95-1, SPP-010.

Table 129. WLCSP – 100 ball, 4.618 x 4.142 mm, 0.4 mm pitch wafer level chip scale package mechanical data

package mechanical data								
Symbol		millimeters			inches <sup>(1)</sup>			
Symbol	Min	Тур	Max	Min	Тур	Max		
Α	0.525	0.555	0.585	0.0207	0.0219	0.0230		
A1	-	0.175	-	-	0.0069	-		
A2	-	0.380	-	-	0.0150	-		
A3 <sup>(2)</sup>	-	0.025	-	-	0.0010	-		
Ø b <sup>(3)</sup>	0.220	0.250	0.280	0.0087	0.0098	0.0110		
D	4.583	4.618	4.653	0.1804	0.1818	0.1832		
Е	4.107	4.142	4.177	0.1617	0.1631	0.1644		
е	-	0.400	-	-	0.0157	-		
e1	-	3.600	-	-	0.1417	-		
e2	-	3.600	-	-	0.1417	-		
F	-	0.509	-	-	0.0200	-		
G	-	0.271	-	-	0.0107	-		
aaa	-	0.100	-	-	0.0039	-		
bbb	-	0.100	-	-	0.0039			
ccc	-	0.100	-	-	0.0039	-		
ddd	-	0.050	-	-	0.0020	-		
eee	-	0.050	-	-	0.0020	-		

- 1. Values in inches are converted from mm and rounded to 4 decimal digits.
- 2. Back side coating.
- 3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 80. WLCSP – 100 ball, 4.166 x 4.628 mm 0.4 mm pitch wafer level chip scale package recommended footprint

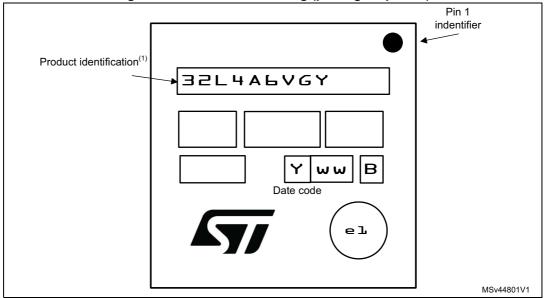


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Table 130. WLCSP100 recommended PCB design rules (0.4 mm pitch)

Dimension	Recommended values		
Pitch	0.4 mm		
Dpad	0.225 mm		
Dsm	0.290 mm		
Stencil thickness	0.1 mm		

Figure 81. WLCSP100 marking (package top view)



Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.



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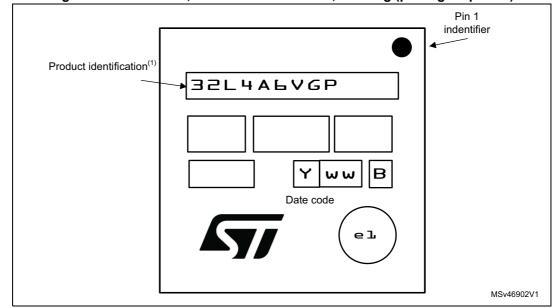


Figure 82. WLCSP100, external SMPS device, marking (package top view)

1. Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified and therefore not approved for use in production. ST is not responsible for any consequences resulting from such use. In no event will ST be liable for the customer using any of these engineering samples in production. ST's Quality department must be contacted prior to any decision to use these engineering samples to run a qualification activity.



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## 7.6 LQFP64 package information

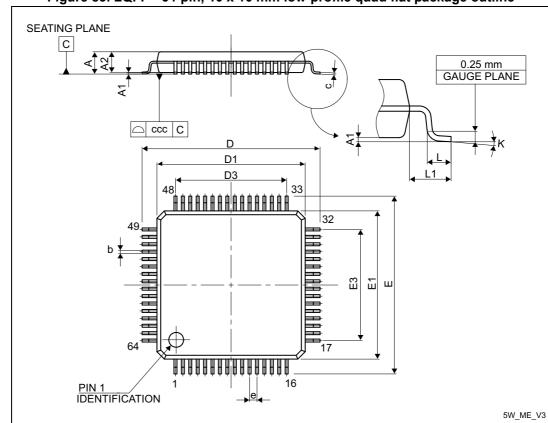


Figure 83. LQFP - 64-pin, 10 x 10 mm low-profile quad flat package outline

1. Drawing is not to scale.

Table 131. LQFP - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

Cumbal	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Max	Min	Тур	Max
А	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
С	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

parage mornamen and (common)							
Symbol	millimeters			inches <sup>(1)</sup>			
	Min	Тур	Max	Min	Тур	Max	
E3	-	7.500	-	-	0.2953	-	
е	-	0.500	-	-	0.0197	-	
K	0°	3.5°	7°	0°	3.5°	7°	
L	0.450	0.600	0.750	0.0177	0.0236	0.0295	
L1	-	1.000	-	-	0.0394	-	
CCC	-	-	0.080	-	-	0.0031	

Table 131. LQFP - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

<sup>1.</sup> Values in inches are converted from mm and rounded to 4 decimal digits.

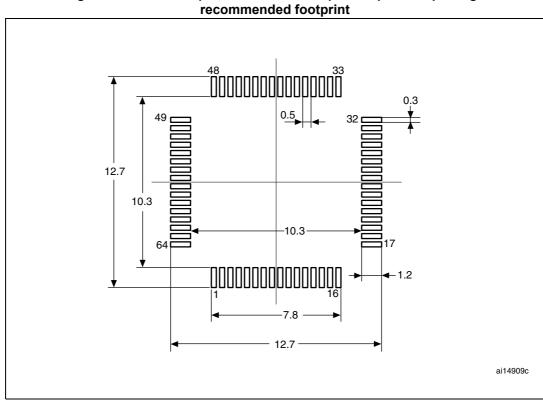


Figure 84. LQFP - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint

1. Dimensions are expressed in millimeters.

### **Device marking**

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

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Product identification(1)

Revision code

B

STM32L4AL

RGTL

Y WW Date code

Pin 1 identifier

MSv44800V1

Figure 85. LQFP64 marking (package top view)

Parts marked as ES or E or accompanied by an Engineering Sample notification letter are not yet qualified
and therefore not approved for use in production. ST is not responsible for any consequences resulting
from such use. In no event will ST be liable for the customer using any of these engineering samples in
production. ST's Quality department must be contacted prior to any decision to use these engineering
samples to run a qualification activity.

Product identification(1)

Revision code

B

STM32L4AL

RCTLP

Y W W

Date code

MS51418V1

Figure 86. LQFP64, external SMPS device, marking (package top view)

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STM32L4A6xG Package information

### 7.7 Thermal characteristics

The maximum chip-junction temperature,  $T_J$  max, in degrees Celsius, may be calculated using the following equation:

$$T_{J} \max = T_{A} \max + (P_{D} \max x \Theta_{JA})$$

#### Where:

- T<sub>A</sub> max is the maximum ambient temperature in °C,
- Θ<sub>JA</sub> is the package junction-to-ambient thermal resistance, in °C/W,
- $P_D$  max is the sum of  $P_{INT}$  max and  $P_{I/O}$  max ( $P_D$  max =  $P_{INT}$  max +  $P_{I/O}$ max),
- P<sub>INT</sub> max is the product of all I<sub>DDXXX</sub> and V<sub>DDXXX</sub>, expressed in Watts. This is the maximum chip internal power.

P<sub>I/O</sub> max represents the maximum power dissipation on output pins where:

$$P_{I/O}$$
 max =  $\Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIOx} - V_{OH}) \times I_{OH})$ ,

taking into account the actual  $V_{OL}$  /  $I_{OL}$  and  $V_{OH}$  /  $I_{OH}$  of the I/Os at low and high level in the application.

**Symbol Parameter** Value Unit Thermal resistance junction-ambient 52 UFBGA169 - 7 × 7 mm Thermal resistance junction-ambient 32 LQFP144 - 20 × 20 mm Thermal resistance junction-ambient 55 UFBGA132 - 7 × 7 mm  $\Theta_{JA}$ °C/W Thermal resistance junction-ambient 35.8 WLCSP100 Thermal resistance junction-ambient 42 LQFP100 - 14 × 14mm Thermal resistance junction-ambient 45 LQFP64

Table 132. Package thermal characteristics

#### 7.7.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

### 7.7.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Ordering information*.

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32L4A6xG at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.



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The following examples show how to calculate the temperature range needed for a given application.

#### **Example 1: High-performance application**

Assuming the following application conditions:

Maximum ambient temperature  $T_{Amax}$  = 82 °C (measured according to JESD51-2),  $I_{DDmax}$  = 50 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V and maximum 8 I/Os used at the same time in output at low level with  $I_{OL}$  = 20 mA,  $V_{OL}$ = 1.3 V

 $P_{INTmax}$  = 50 mA × 3.5 V= 175 mW

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} + 8 \times 20 \text{ mA} \times 1.3 \text{ V} = 272 \text{ mW}$ 

This gives: P<sub>INTmax</sub> = 175 mW and P<sub>IOmax</sub> = 272 mW:

 $P_{Dmax} = 175 + 272 = 447 \text{ mW}$ 

Using the values obtained in *Table 132* T<sub>Jmax</sub> is calculated as follows:

For LQFP100, 42 °C/W

$$T_{Jmax}$$
 = 82 °C + (42 °C/W × 447 mW) = 82 °C + 18.774 °C = 100.774 °C

This is within the range of the suffix 6 version parts ( $-40 < T_J < 105$  °C) see Section 8: Ordering information.

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note:

With this given  $P_{Dmax}$  we can find the  $T_{Amax}$  allowed for a given device temperature range (order code suffix 6 or 3).

Suffix 6: 
$$T_{Amax} = T_{Jmax}$$
 -  $(42^{\circ}C/W \times 447 \ mW) = 105-18.774 = 86.226 ^{\circ}C$   
Suffix 3:  $T_{Amax} = T_{Jmax}$  -  $(42^{\circ}C/W \times 447 \ mW) = 130-18.774 = 111.226 ^{\circ}C$ 

### **Example 2: High-temperature application**

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature  $T_J$  remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature  $T_{Amax}$  = 100 °C (measured according to JESD51-2),  $I_{DDmax}$  = 20 mA,  $V_{DD}$  = 3.5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V

 $P_{INTmax}$  = 20 mA × 3.5 V= 70 mW

 $P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4 \text{ V} = 64 \text{ mW}$ 

This gives:  $P_{INTmax} = 70 \text{ mW}$  and  $P_{IOmax} = 64 \text{ mW}$ :

 $P_{Dmax} = 70 + 64 = 134 \text{ mW}$ 

Thus: P<sub>Dmax</sub> = 134 mW

Using the values obtained in *Table 132* T<sub>Jmax</sub> is calculated as follows:

For LQFP100, 42 °C/W

$$T_{Jmax}$$
 = 100 °C + (42 °C/W × 134 mW) = 100 °C + 5.628 °C = 105.628 °C

This is above the range of the suffix 6 version parts ( $-40 < T_{.l} < 105$  °C).

In this case, parts must be ordered at least with the temperature range suffix 3 (see *Section 8: Ordering information*) unless we reduce the power dissipation in order to be able to use suffix 6 parts.



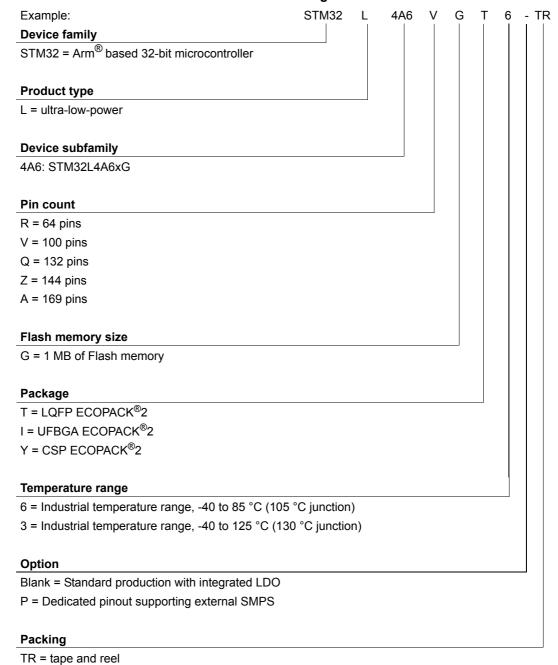
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Ordering information STM32L4A6xG

## 8 Ordering information

xxx = programmed parts

Table 133. STM32L4A6xG ordering information scheme



For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

STM32L4A6xG Revision history

# 9 Revision history

Table 134. Document revision history

Date	Revision	Changes
23-Feb-2017	1	Initial release
04-Jul-2017	2	Updated:  - Features, Section 2: Description, Section 3.10.1: Power supply schemes, Section 3.10.3: Voltage regulator, Section 3.39: Universal serial bus on-the-go full-speed (OTG_FS), Section 6.1.7: Current consumption measurement, Section 6.3.18: Analog- to-Digital converter characteristics, Section 7.7: Thermal characteristics, Section 7.7:2: Selecting the product temperature range  - Table 15: STM32L4A6xG pin definitions, Table 44: Current consumption in Stop 2 mode, Table 45: Current consumption in Stop 1 mode, Table 47: Current consumption in Standby mode, Table 48: Current consumption in Shutdown mode, Table 48: Current consumption in Shutdown mode, Table 51: Low-power mode wakeup timings, Table 70: I/O static characteristics, Table 82: DAC characteristics, Table 133: STM32L4A6xG ordering information scheme  - Figure 1: STM32L4A6xG block diagram, Figure 3: Power supply overview, Figure 19: Voltage characteristics Added:  - Note 3 on Table 2: STM32L4A6xG family device features and peripheral counts, Figure 8: STM32L4A6Ax, external SMPS device, UFBGA169 pinout <sup>(1)</sup> , Figure 10: STM32L4A6Zx, external SMPS device, LQFP144 pinout <sup>(1)</sup> , Figure 16: STM32L4A6Vx, external SMPS device, WLCSP100 pinout <sup>(1)</sup> , Figure 66: UFBGA169, external SMPS device, marking (package top view, Figure 70: LQFP144, external SMPS device, marking (package top view), Figure 82: WLCSP100, external SMPS device, marking (package top view)

Revision history STM32L4A6xG

Table 134. Document revision history (continued)

Date	Revision	nent revision history (continued)  Changes
09-Jan-2018	3	Updated Features, Section 3.12: Clocks and startup, Table 15: STM32L4A6xG pin definitions, Table 66: EMI characteristics, Table 70: I/O static characteristics, Table 76: ADC characteristics  Added Figure 12: STM32L4A6Qx, external SMPS device, UFBGA132 ballout, Table 27: Current consumption in Run modes, code with data processing running from Flash, (ART enable Cache ON Prefetch OFF) and power supplied (by external SMPS (VDD12 = 1.10 V)Table 29: Current consumption in Run modes, code with data processing running from Flash, ART disable and power supplied by external SMPS (VDD12 = 1.10 V), Table 31: Current consumption in Run, code with data processing running from SRAM1 and power supplied by external SMPS (VDD12 = 1.10 V), Table 31: Typical current consumption in Run, with different codes running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied (by external SMPS (VDD12 = 1.10 V), Table 34: Typical current consumption in Run, with different codes running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied (by external SMPS (VDD12 = 1.10 V), Table 36: Typical current consumption in Run modes, with different codesrunning from Flash, ART disable and power supplied by external SMPS (VDD12 = 1.10 V), Table 37: Typical current consumption in Run modes, with different codesrunning from Flash, ART disable and power supplied by external SMPS (VDD12 = 1.05 V), Table 39: Typical current consumption in Run modes, with different codesrunning from SRAM1 and power supplied by external SMPS (VDD12 = 1.10 V), Table 40: Typical current consumption in Run, with different codesrunning from SRAM1 and power supplied by external SMPS (VDD12 = 1.10 V), Table 40: Typical current consumption in Run, with different codesrunning from SRAM1 and power supplied by external SMPS (VDD12 = 1.10 V), Table 40: Typical current consumption in Run, with different codesrunning from SRAM1 and power supplied by external SMPS (VDD12 = 1.10 V), Table 40: Typical current consumption in Run, with different codesrunning from SRA
11-Jan-2018	4	Updated Table 15: STM32L4A6xG pin definitions
14-Feb-2018	5	Updated Table 8: Temperature sensor calibration values
17-May-2018	6	Updated: Figure 1: STM32L4A6xG block diagram, Figure 5: Clock tree, Table 5: Functionalities depending on the working mode, Table 6: STM32L4A6xG peripherals interconnect matrix, Section 3.10.1: Power supply schemes, Table 19: Voltage characteristics, Table 86: OPAMP characteristics, Section 3.17: Analog to digital converter (ADC), Table 82: DAC characteristics Added: Figure 4: Power-up/down sequence

STM32L4A6xG Revision history

Table 134. Document revision history (continued)

Date	Revision	Changes	
16-Jul-2018	7	Updated Figure 15: STM32L4A6Vx WLCSP100 pinout <sup>(1)</sup> , Figure 16: STM32L4A6Vx, external SMPS device, WLCSP100 pinout <sup>(1)</sup> , Table 15: STM32L4A6xG pin definitions, Figure 72: UFBGA - 132-ball, 7 x 7 mm ultra thin fine pitch ball grid array package recommended footprint, Figure 80: WLCSP – 100 ball, 4.166 x 4.628 mm 0.4 mm pitch wafer level chip scale package recommended footprint	
24-Sep-2018	8	Updated Section 3.41: Flexible static memory controller (FSMC), Table 15: STM32L4A6xG pin definitions, Table 16: Alternate function AF0 to AF7  Added Figure 13: STM32L4A6Vx LQFP100 pinout <sup>(1)</sup> , Figure 18: STM32L4A6Rx, external SMPS, LQFP64 pinout <sup>(1)</sup> , Figure 78: LQFP100, external SMPS device, marking (package top view), Figure 86: LQFP64, external SMPS device, marking (package top view)	

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